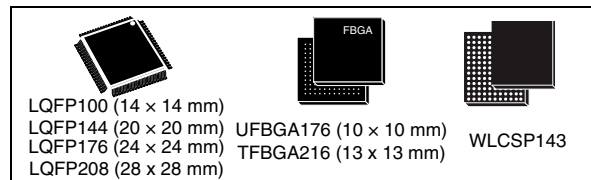


ARM Cortex-M4 32b MCU+FPU, 225DMIPS, up to 2MB Flash/256+4KB RAM, USB OTG HS/FS, Ethernet, 17 TIMs, 3 ADCs, 20 comm. interfaces, camera & LCD-TFT

Datasheet - production data

Features

- Core: ARM 32-bit Cortex™-M4 CPU with FPU, Adaptive real-time accelerator (ART Accelerator™) allowing 0-wait state execution from Flash memory, frequency up to 180 MHz, MPU, 225 DMIPS/1.25 DMIPS/MHz (Dhrystone 2.1), and DSP instructions
- Memories
 - Up to 2 MB of Flash memory organized into two banks allowing read-while-write
 - Up to 256+4 KB of SRAM including 64-KB of CCM (core coupled memory) data RAM
 - Flexible external memory controller with up to 32-bit data bus: SRAM, PSRAM, SDRAM, Compact Flash/NOR/NAND memories
- LCD parallel interface, 8080/6800 modes
- LCD-TFT controller up to SVGA resolution with dedicated Chrom-ART Accelerator™ for enhanced graphic content creation (DMA2D)
- Clock, reset and supply management
 - 1.8 V to 3.6 V application supply and I/Os
 - POR, PDR, PVD and BOR
 - 4-to-26 MHz crystal oscillator
 - Internal 16 MHz factory-trimmed RC (1% accuracy)
 - 32 kHz oscillator for RTC with calibration
 - Internal 32 kHz RC with calibration
- Low power
 - Sleep, Stop and Standby modes
 - V_{BAT} supply for RTC, 20×32 bit backup registers + optional 4 KB backup SRAM
- 3×12-bit, 2.4 MSPS ADC: up to 24 channels and 7.2 MSPS in triple interleaved mode
- 2×12-bit D/A converters
- General-purpose DMA: 16-stream DMA controller with FIFOs and burst support
- Up to 17 timers: up to twelve 16-bit and two 32-bit timers up to 180 MHz, each with up to 4 IC/OC/PWM or pulse counter and quadrature (incremental) encoder input
- Debug mode
 - SWD & JTAG interfaces
 - Cortex-M4 Embedded Trace Macrocell™



- Up to 168 I/O ports with interrupt capability
 - Up to 164 fast I/Os up to 90 MHz
 - Up to 166 5 V-tolerant I/Os
- Up to 21 communication interfaces
 - Up to 3 × I²C interfaces (SMBus/PMBus)
 - Up to 4 USARTs/4 UARTs (11.25 Mbit/s, ISO7816 interface, LIN, IrDA, modem control)
 - Up to 6 SPIs (45 Mbits/s), 2 with muxed full-duplex I²S for audio class accuracy via internal audio PLL or external clock
 - 1 × SAI (serial audio interface)
 - 2 × CAN (2.0B Active) and SDIO interface
- Advanced connectivity
 - USB 2.0 full-speed device/host/OTG controller with on-chip PHY
 - USB 2.0 high-speed/full-speed device/host/OTG controller with dedicated DMA, on-chip full-speed PHY and ULPI
 - 10/100 Ethernet MAC with dedicated DMA: supports IEEE 1588v2 hardware, MII/RMII
- 8- to 14-bit parallel camera interface up to 54 Mbytes/s
- True random number generator
- CRC calculation unit
- 96-bit unique ID
- RTC: subsecond accuracy, hardware calendar

Table 1. Device summary

Reference	Part number
STM32F427xx	STM32F427VG, STM32F427ZG, STM32F427IG, STM32F427VI, STM32F427ZI, STM32F427II
STM32F429xx	STM32F429VG, STM32F429ZG, STM32F429IG, STM32F429VI, STM32F429ZI, STM32F429II, STM32F429BG, STM32F429BI, STM32F429NI, STM32F429NG

Contents

- 1 Introduction 12**
- 2 Description 13**
 - 2.1 Full compatibility throughout the family 17
- 3 Functional overview 20**
 - 3.1 ARM® Cortex™-M4 with FPU and embedded Flash and SRAM 20
 - 3.2 Adaptive real-time memory accelerator (ART Accelerator™) 20
 - 3.3 Memory protection unit 20
 - 3.4 Embedded Flash memory 21
 - 3.5 CRC (cyclic redundancy check) calculation unit 21
 - 3.6 Embedded SRAM 21
 - 3.7 Multi-AHB bus matrix 21
 - 3.8 DMA controller (DMA) 22
 - 3.9 Flexible memory controller (FMC) 23
 - 3.10 LCD-TFT controller (available only on STM32F429xx) 23
 - 3.11 Chrom-ART Accelerator™ (DMA2D) 24
 - 3.12 Nested vectored interrupt controller (NVIC) 24
 - 3.13 External interrupt/event controller (EXTI) 24
 - 3.14 Clocks and startup 24
 - 3.15 Boot modes 25
 - 3.16 Power supply schemes 25
 - 3.17 Power supply supervisor 25
 - 3.17.1 Internal reset ON 25
 - 3.17.2 Internal reset OFF 26
 - 3.18 Voltage regulator 27
 - 3.18.1 Regulator ON 27
 - 3.18.2 Regulator OFF 28
 - 3.18.3 Regulator ON/OFF and internal reset ON/OFF availability 31
 - 3.19 Real-time clock (RTC), backup SRAM and backup registers 31
 - 3.20 Low-power modes 32
 - 3.21 V_{BAT} operation 33

3.22	Timers and watchdogs	33
3.22.1	Advanced-control timers (TIM1, TIM8)	35
3.22.2	General-purpose timers (TIMx)	35
3.22.3	Basic timers TIM6 and TIM7	35
3.22.4	Independent watchdog	36
3.22.5	Window watchdog	36
3.22.6	SysTick timer	36
3.23	Inter-integrated circuit interface (I ² C)	36
3.24	Universal synchronous/asynchronous receiver transmitters (USART)	36
3.25	Serial peripheral interface (SPI)	37
3.26	Inter-integrated sound (I ² S)	38
3.27	Serial Audio interface (SAI1)	38
3.28	Audio PLL (PLLI2S)	38
3.29	Audio and LCD PLL(PLLSAI)	38
3.30	Secure digital input/output interface (SDIO)	39
3.31	Ethernet MAC interface with dedicated DMA and IEEE 1588 support	39
3.32	Controller area network (bxCAN)	39
3.33	Universal serial bus on-the-go full-speed (OTG_FS)	40
3.34	Universal serial bus on-the-go high-speed (OTG_HS)	40
3.35	Digital camera interface (DCMI)	41
3.36	Random number generator (RNG)	41
3.37	General-purpose input/outputs (GPIOs)	41
3.38	Analog-to-digital converters (ADCs)	41
3.39	Temperature sensor	42
3.40	Digital-to-analog converter (DAC)	42
3.41	Serial wire JTAG debug port (SWJ-DP)	42
3.42	Embedded Trace Macrocell™	42
4	Pinouts and pin description	44
5	Memory mapping	82
6	Electrical characteristics	87
6.1	Parameter conditions	87
6.1.1	Minimum and maximum values	87

6.1.2	Typical values	87
6.1.3	Typical curves	87
6.1.4	Loading capacitor	87
6.1.5	Pin input voltage	87
6.1.6	Power supply scheme	88
6.1.7	Current consumption measurement	89
6.2	Absolute maximum ratings	89
6.3	Operating conditions	91
6.3.1	General operating conditions	91
6.3.2	VCAP1/VCAP2 external capacitor	94
6.3.3	Operating conditions at power-up / power-down (regulator ON)	94
6.3.4	Operating conditions at power-up / power-down (regulator OFF)	94
6.3.5	Embedded reset and power control block characteristics	95
6.3.6	Over-drive switching characteristics	96
6.3.7	Supply current characteristics	96
6.3.8	Wakeup time from low-power modes	112
6.3.9	External clock source characteristics	113
6.3.10	Internal clock source characteristics	117
6.3.11	PLL characteristics	119
6.3.12	PLL spread spectrum clock generation (SSCG) characteristics	122
6.3.13	Memory characteristics	124
6.3.14	EMC characteristics	126
6.3.15	Absolute maximum ratings (electrical sensitivity)	128
6.3.16	I/O current injection characteristics	128
6.3.17	I/O port characteristics	129
6.3.18	NRST pin characteristics	133
6.3.19	TIM timer characteristics	134
6.3.20	Communications interfaces	134
6.3.21	12-bit ADC characteristics	149
6.3.22	Temperature sensor characteristics	155
6.3.23	V _{BAT} monitoring characteristics	155
6.3.24	Embedded reference voltage	155
6.3.25	DAC electrical characteristics	156
6.3.26	FMC characteristics	158
6.3.27	Camera interface (DCMI) timing specifications	181
6.3.28	LCD-TFT controller (LTDC) characteristics	182
6.3.29	SD/SDIO MMC card host interface (SDIO) characteristics	184

6.3.30	RTC characteristics	185
7	Package characteristics	186
7.1	Package mechanical data	186
7.2	Thermal characteristics	200
8	Part numbering	201
Appendix A	Application block diagrams	202
A.1	USB OTG full speed (FS) interface solutions	202
A.2	USB OTG high speed (HS) interface solutions	204
A.3	Ethernet interface solutions	205
9	Revision history	207

List of tables

Table 1.	Device summary	1
Table 2.	STM32F427xx and STM32F429xx features and peripheral counts	14
Table 3.	Voltage regulator configuration mode versus device operating mode	28
Table 4.	Regulator ON/OFF and internal reset ON/OFF availability.	31
Table 5.	Voltage regulator modes in stop mode	32
Table 6.	Timer feature comparison.	34
Table 7.	Comparison of I2C analog and digital filters	36
Table 8.	USART feature comparison	37
Table 9.	Legend/abbreviations used in the pinout table	51
Table 10.	STM32F427xx and STM32F429xx pin and ball definitions	51
Table 11.	FMC pin definition	68
Table 12.	STM32F427xx and STM32F429xx alternate function mapping	71
Table 13.	STM32F427xx and STM32F429xx register boundary addresses.	83
Table 14.	Voltage characteristics	89
Table 15.	Current characteristics	90
Table 16.	Thermal characteristics.	90
Table 17.	General operating conditions	91
Table 18.	Limitations depending on the operating power supply range	93
Table 19.	VCAP1/VCAP2 operating conditions	94
Table 20.	Operating conditions at power-up / power-down (regulator ON)	94
Table 21.	Operating conditions at power-up / power-down (regulator OFF).	94
Table 22.	Embedded reset and power control block characteristics.	95
Table 23.	Over-drive switching characteristics	96
Table 24.	Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator enabled except prefetch) or RAM.	98
Table 25.	Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator disabled)	99
Table 26.	Typical and maximum current consumption in Sleep mode	100
Table 27.	Typical and maximum current consumptions in Stop mode	101
Table 28.	Typical and maximum current consumptions in Standby mode	101
Table 29.	Typical and maximum current consumptions in V _{BAT} mode.	102
Table 30.	Typical current consumption in Run mode, code with data processing running from Flash memory, regulator ON (ART accelerator enabled except prefetch), VDD=1.8 V	104
Table 31.	Typical current consumption in Run mode, code with data processing running from Flash memory, regulator OFF (ART accelerator enabled except prefetch).	105
Table 32.	Typical current consumption in Sleep mode, regulator ON, VDD=1.8 V	106
Table 33.	Typical current consumption in Sleep mode, regulator OFF.	107
Table 34.	Switching output I/O current consumption	108
Table 35.	Peripheral current consumption	110
Table 36.	Low-power mode wakeup timings	113
Table 37.	High-speed external user clock characteristics.	114
Table 38.	Low-speed external user clock characteristics	114
Table 39.	HSE 4-26 MHz oscillator characteristics	116
Table 40.	LSE oscillator characteristics (f _{LSE} = 32.768 kHz)	117
Table 41.	HSI oscillator characteristics	117
Table 42.	LSI oscillator characteristics	118
Table 43.	Main PLL characteristics.	119
Table 44.	PLL12S (audio PLL) characteristics	120

Table 45.	PLLISAI (audio and LCD-TFT PLL) characteristics	121
Table 46.	SSCG parameters constraint	122
Table 47.	Flash memory characteristics	124
Table 48.	Flash memory programming	124
Table 49.	Flash memory programming with V_{PP}	125
Table 50.	Flash memory endurance and data retention	126
Table 51.	EMS characteristics	126
Table 52.	EMI characteristics	127
Table 53.	ESD absolute maximum ratings	128
Table 54.	Electrical sensitivities	128
Table 55.	I/O current injection susceptibility	129
Table 56.	I/O static characteristics	129
Table 57.	Output voltage characteristics	131
Table 58.	I/O AC characteristics	132
Table 59.	NRST pin characteristics	133
Table 60.	TIMx characteristics	134
Table 61.	I ² C characteristics	135
Table 62.	SCL frequency ($f_{PCLK1} = 42$ MHz, $V_{DD} = V_{DD_I2C} = 3.3$ V)	136
Table 63.	SPI dynamic characteristics	137
Table 64.	I ² S dynamic characteristics	140
Table 65.	SAI characteristics	142
Table 66.	USB OTG FS startup time	144
Table 67.	USB OTG FS DC electrical characteristics	144
Table 68.	USB OTG FS electrical characteristics	145
Table 69.	USB HS DC electrical characteristics	145
Table 70.	USB HS clock timing parameters	145
Table 71.	Dynamic characteristics: USB ULPI	146
Table 72.	Ethernet DC electrical characteristics	147
Table 73.	Dynamics characteristics: Ethernet MAC signals for SMI	147
Table 74.	Dynamics characteristics: Ethernet MAC signals for RMII	148
Table 75.	Dynamics characteristics: Ethernet MAC signals for MII	149
Table 76.	ADC characteristics	149
Table 77.	ADC static accuracy at $f_{ADC} = 18$ MHz	151
Table 78.	ADC static accuracy at $f_{ADC} = 30$ MHz	151
Table 79.	ADC static accuracy at $f_{ADC} = 36$ MHz	151
Table 80.	ADC dynamic accuracy at $f_{ADC} = 18$ MHz - limited test conditions	152
Table 81.	ADC dynamic accuracy at $f_{ADC} = 36$ MHz - limited test conditions	152
Table 82.	Temperature sensor characteristics	155
Table 83.	Temperature sensor calibration values	155
Table 84.	V_{BAT} monitoring characteristics	155
Table 85.	Embedded internal reference voltage	155
Table 86.	Internal reference voltage calibration values	156
Table 87.	DAC characteristics	156
Table 88.	Asynchronous non-multiplexed SRAM/PSRAM/NOR - read timings	159
Table 89.	Asynchronous non-multiplexed SRAM/PSRAM/NOR read - NWAIT timings	160
Table 90.	Asynchronous non-multiplexed SRAM/PSRAM/NOR write timings	161
Table 91.	Asynchronous non-multiplexed SRAM/PSRAM/NOR write - NWAIT timings	162
Table 92.	Asynchronous multiplexed PSRAM/NOR read timings	163
Table 93.	Asynchronous multiplexed PSRAM/NOR read-NWAIT timings	163

Table 94.	Asynchronous multiplexed PSRAM/NOR write timings	164
Table 95.	Asynchronous multiplexed PSRAM/NOR write-NWAIT timings	165
Table 96.	Synchronous multiplexed NOR/PSRAM read timings	166
Table 97.	Synchronous multiplexed PSRAM write timings	167
Table 98.	Synchronous non-multiplexed NOR/PSRAM read timings	169
Table 99.	Synchronous non-multiplexed PSRAM write timings	170
Table 100.	Switching characteristics for PC Card/CF read and write cycles in attribute/common space	175
Table 101.	Switching characteristics for PC Card/CF read and write cycles in I/O space	176
Table 102.	Switching characteristics for NAND Flash read cycles	178
Table 103.	Switching characteristics for NAND Flash write cycles	179
Table 104.	SDRAM read timings	180
Table 105.	SDRAM write timings	181
Table 106.	DCMI characteristics	181
Table 107.	LTDC characteristics	182
Table 108.	Dynamic characteristics: SD / MMC characteristics	184
Table 109.	RTC characteristics	185
Table 110.	LQPF100, 14 x 14 mm 100-pin low-profile quad flat package mechanical data	187
Table 111.	WLCSP143, 0.4 mm pitch wafer level chip scale package mechanical data	190
Table 112.	LQFP144, 20 x 20 mm, 144-pin low-profile quad flat package mechanical data	191
Table 113.	LQFP176, 24 x 24 mm, 176-pin low-profile quad flat package mechanical data	193
Table 114.	LQFP208, 28 x 28 mm, 208-pin low-profile quad flat package mechanical data	196
Table 115.	UFBGA176+25 - ultra thin fine pitch ball grid array 10 × 10 × 0.6 mm mechanical data	198
Table 116.	TFBGA216 - thin fine pitch ball grid array 13 × 13 × 0.8mm package mechanical data	199
Table 117.	Package thermal characteristics	200
Table 118.	Ordering information scheme	201
Table 119.	Document revision history	207

List of figures

Figure 1.	Compatible board design STM32F10xx/STM32F2xx/STM32F4xx for LQFP100 package.	17
Figure 2.	Compatible board design between STM32F10xx/STM32F2xx/STM32F4xx for LQFP144 package.	18
Figure 3.	Compatible board design between STM32F2xx and STM32F4xx for LQFP176 and UFBGA176 packages	18
Figure 4.	STM32F427xx and STM32F429xx block diagram	19
Figure 5.	STM32F427xx and STM32F429xx Multi-AHB matrix	22
Figure 6.	Power supply supervisor interconnection with internal reset OFF	26
Figure 7.	PDR_ON control with internal reset OFF	27
Figure 8.	Regulator OFF	29
Figure 9.	Startup in regulator OFF: slow V_{DD} slope - power-down reset risen after V_{CAP_1}/V_{CAP_2} stabilization	30
Figure 10.	Startup in regulator OFF mode: fast V_{DD} slope - power-down reset risen before V_{CAP_1}/V_{CAP_2} stabilization	30
Figure 11.	STM32F42x LQFP100 pinout	44
Figure 12.	STM32F42x WLCSP143 ballout	45
Figure 13.	STM32F42x LQFP144 pinout	46
Figure 14.	STM32F42x LQFP176 pinout	47
Figure 15.	STM32F42x LQFP208 pinout	48
Figure 16.	STM32F42x UFBGA176 ballout	49
Figure 17.	STM32F42x TFBGA216 ballout	50
Figure 18.	Memory map	82
Figure 19.	Pin loading conditions	87
Figure 20.	Pin input voltage	87
Figure 21.	Power supply scheme	88
Figure 22.	Current consumption measurement scheme	89
Figure 23.	External capacitor C_{EXT}	94
Figure 24.	Typical V_{BAT} current consumption (LSE and RTC ON/backup RAM OFF)	102
Figure 25.	Typical V_{BAT} current consumption (LSE and RTC ON/backup RAM ON)	103
Figure 26.	High-speed external clock source AC timing diagram	115
Figure 27.	Low-speed external clock source AC timing diagram	115
Figure 28.	Typical application with an 8 MHz crystal	116
Figure 29.	Typical application with a 32.768 kHz crystal	117
Figure 30.	ACC_{HSI} versus temperature	118
Figure 31.	ACC_{LSI} versus temperature	119
Figure 32.	PLL output clock waveforms in center spread mode	123
Figure 33.	PLL output clock waveforms in down spread mode	123
Figure 34.	I/O AC characteristics definition	133
Figure 35.	Recommended NRST pin protection	134
Figure 36.	I ² C bus AC waveforms and measurement circuit	136
Figure 37.	SPI timing diagram - slave mode and CPHA = 0	138
Figure 38.	SPI timing diagram - slave mode and CPHA = 1 ⁽¹⁾	139
Figure 39.	SPI timing diagram - master mode ⁽¹⁾	139
Figure 40.	I ² S slave timing diagram (Philips protocol) ⁽¹⁾	141
Figure 41.	I ² S master timing diagram (Philips protocol) ⁽¹⁾	141
Figure 42.	SAI master timing waveforms	143
Figure 43.	SAI slave timing waveforms	143

Figure 44.	USB OTG FS timings: definition of data signal rise and fall time	145
Figure 45.	ULPI timing diagram	146
Figure 46.	Ethernet SMI timing diagram	147
Figure 47.	Ethernet RMII timing diagram	148
Figure 48.	Ethernet MII timing diagram	148
Figure 49.	ADC accuracy characteristics	153
Figure 50.	Typical connection diagram using the ADC	153
Figure 51.	Power supply and reference decoupling (V_{REF+} not connected to V_{DDA})	154
Figure 52.	Power supply and reference decoupling (V_{REF+} connected to V_{DDA})	154
Figure 53.	12-bit buffered /non-buffered DAC	158
Figure 54.	Asynchronous non-multiplexed SRAM/PSRAM/NOR read waveforms	159
Figure 55.	Asynchronous non-multiplexed SRAM/PSRAM/NOR write waveforms	161
Figure 56.	Asynchronous multiplexed PSRAM/NOR read waveforms	162
Figure 57.	Asynchronous multiplexed PSRAM/NOR write waveforms	164
Figure 58.	Synchronous multiplexed NOR/PSRAM read timings	166
Figure 59.	Synchronous multiplexed PSRAM write timings	167
Figure 60.	Synchronous non-multiplexed NOR/PSRAM read timings	169
Figure 61.	Synchronous non-multiplexed PSRAM write timings	170
Figure 62.	PC Card/CompactFlash controller waveforms for common memory read access	172
Figure 63.	PC Card/CompactFlash controller waveforms for common memory write access	172
Figure 64.	PC Card/CompactFlash controller waveforms for attribute memory read access	173
Figure 65.	PC Card/CompactFlash controller waveforms for attribute memory write access	174
Figure 66.	PC Card/CompactFlash controller waveforms for I/O space read access	174
Figure 67.	PC Card/CompactFlash controller waveforms for I/O space write access	175
Figure 68.	NAND controller waveforms for read access	177
Figure 69.	NAND controller waveforms for write access	177
Figure 70.	NAND controller waveforms for common memory read access	178
Figure 71.	NAND controller waveforms for common memory write access	178
Figure 72.	SDRAM read access waveforms	179
Figure 73.	SDRAM write access waveforms	180
Figure 74.	DCMI timing diagram	182
Figure 75.	LCD-TFT horizontal timing diagram	183
Figure 76.	LCD-TFT vertical timing diagram	183
Figure 77.	SDIO high-speed mode	184
Figure 78.	SD default mode	184
Figure 79.	LQFP100, 14 x 14 mm 100-pin low-profile quad flat package outline	186
Figure 80.	LQFP100 recommended footprint	188
Figure 81.	WLCSP143, 0.4 mm pitch wafer level chip scale package outline	189
Figure 82.	LQFP144, 20 x 20 mm, 144-pin low-profile quad flat package outline	191
Figure 83.	LQFP144 recommended footprint	192
Figure 84.	LQFP176 24 x 24 mm, 176-pin low-profile quad flat package outline	193
Figure 85.	LQFP176 recommended footprint	195
Figure 86.	LQFP208, 28 x 28 mm, 208-pin low-profile quad flat package outline	196
Figure 87.	LQFP208 recommended footprint	197
Figure 88.	UFBGA176+25 - ultra thin fine pitch ball grid array 10 x 10 x 0.6 mm, package outline	198
Figure 89.	TFBGA216 - thin fine pitch ball grid array 13 x 13 x 0.8mm, package outline	199
Figure 90.	USB controller configured as peripheral-only and used in Full speed mode	202

Figure 91.	USB controller configured as host-only and used in full speed mode.	202
Figure 92.	USB controller configured in dual mode and used in full speed mode	203
Figure 93.	USB controller configured as peripheral, host, or dual-mode and used in high speed mode.	204
Figure 94.	MII mode using a 25 MHz crystal	205
Figure 95.	RMII with a 50 MHz oscillator	205
Figure 96.	RMII with a 25 MHz crystal and PHY with PLL.	206

1 Introduction

This datasheet provides the description of the STM32F427xx and STM32F429xx line of microcontrollers. For more details on the whole STMicroelectronics STM32™ family, please refer to [Section 2.1: Full compatibility throughout the family](#).

The STM32F427xx and STM32F429xx datasheet should be read in conjunction with the STM32F4xx reference manual.

For information on the Cortex™-M4 core, please refer to the Cortex™-M4 programming manual (PM0214), available from the www.st.com.

2 Description

The STM32F427xx and STM32F429xx devices are based on the high-performance ARM® Cortex™-M4 32-bit RISC core operating at a frequency of up to 180 MHz. The Cortex-M4 core features a Floating point unit (FPU) single precision which supports all ARM single-precision data-processing instructions and data types. It also implements a full set of DSP instructions and a memory protection unit (MPU) which enhances application security.

The STM32F427xx and STM32F429xx devices incorporate high-speed embedded memories (Flash memory up to 2 Mbyte, up to 256 Kbytes of SRAM), up to 4 Kbytes of backup SRAM, and an extensive range of enhanced I/Os and peripherals connected to two APB buses, two AHB buses and a 32-bit multi-AHB bus matrix.

All devices offer three 12-bit ADCs, two DACs, a low-power RTC, twelve general-purpose 16-bit timers including two PWM timers for motor control, two general-purpose 32-bit timers, a true random number generator (RNG). They also feature standard and advanced communication interfaces.

- Up to three I²Cs
- Six SPIs, two I²Ss full duplex. To achieve audio class accuracy, the I²S peripherals can be clocked via a dedicated internal audio PLL or via an external clock to allow synchronization.
- Four USARTs plus four UARTs
- An USB OTG full-speed and a USB OTG high-speed with full-speed capability (with the ULPI),
- Two CANs
- One SAI serial audio interface
- An SDIO/MMC interface
- Ethernet and the camera interface
- LCD-TFT display controller
- Chrom-ART Accelerator™.

Advanced peripherals include an SDIO, a flexible memory control (FMC) interface, a camera interface for CMOS sensors. Refer to [Table 2: STM32F427xx and STM32F429xx features and peripheral counts](#) for the list of peripherals available on each part number.

The STM32F427xx and STM32F429xx devices operates in the –40 to +105 °C temperature range from a 1.8 to 3.6 V power supply.

The supply voltage can drop to 1.7 V when the device operates in the 0 to 70 °C temperature range with the use of an external power supply supervisor (refer to [Section 3.17.2: Internal reset OFF](#)). A comprehensive set of power-saving mode allows the design of low-power applications.

The STM32F427xx and STM32F429xx devices offers devices in 7 packages ranging from 100 pins to 216 pins. The set of included peripherals changes with the device chosen.

These features make the STM32F427xx and STM32F429xx microcontrollers suitable for a wide range of applications:

- Motor drive and application control
- Medical equipment
- Industrial applications: PLC, inverters, circuit breakers
- Printers, and scanners
- Alarm systems, video intercom, and HVAC
- Home audio appliances

Figure 4 show the general block diagram of the device family.

Table 2. STM32F427xx and STM32F429xx features and peripheral counts

Peripherals		STM32F427Vx		STM32F429Vx		STM32F427Zx		STM32F429Zx		STM32F427Ix		STM32F429Ix		STM32F429Bx		STM32F429Nx	
Flash memory in Kbytes		1024	2048	1024	2048	1024	2048	1024	2048	1024	2048	1024	2048	1024	2048	1024	2048
SRAM in Kbytes	System	256(112+16+64+64)															
	Backup	4															
FMC memory controller		Yes ⁽¹⁾															
Ethernet		Yes															
Timers	General-purpose	10															
	Advanced-control	2															
	Basic	2															
Random number generator		Yes															



Table 2. STM32F427xx and STM32F429xx features and peripheral counts (continued)

Peripherals		STM32F427Vx	STM32F429Vx	STM32F427Zx	STM32F429Zx	STM32F427Ix	STM32F429Ix	STM32F429Bx	STM32F429Nx
Communication interfaces	SPI / I ² S	6/2 (full duplex) ⁽²⁾							
	I ² C	3							
	USART/UART	4/4							
	USB OTG FS	Yes							
	USB OTG HS	Yes							
	CAN	2							
	SAI	1							
	SDIO	Yes							
Camera interface		Yes							
LCD-TFT (STM32F429xx only)		No	Yes	No	Yes	No	Yes		
Chrom-ART Accelerator™		Yes							
GPIOs		82		114		140		168	
12-bit ADC		3							
Number of channels		16		24					
12-bit DAC		Yes							
Number of channels		2							
Maximum CPU frequency		180 MHz							
Operating voltage		1.8 to 3.6 V ⁽³⁾							


Table 2. STM32F427xx and STM32F429xx features and peripheral counts (continued)

Peripherals	STM32F427Vx	STM32F429Vx	STM32F427Zx	STM32F429Zx	STM32F427Ix	STM32F429Ix	STM32F429Bx	STM32F429Nx
Operating temperatures	Ambient temperatures: –40 to +85 °C / –40 to +105 °C							
	Junction temperature: –40 to + 125 °C							
Packages	LQFP100		WLCSP143 LQFP144		UFBGA176 LQFP176		LQFP208	TFBGA216

1. For the LQFP100 package, only FMC Bank1 or Bank2 are available. Bank1 can only support a multiplexed NOR/PSRAM memory using the NE1 Chip Select. Bank2 can only support a 16- or 8-bit NAND Flash memory using the NCE2 Chip Select. The interrupt line cannot be used since Port G is not available in this package.
2. The SPI2 and SPI3 interfaces give the flexibility to work in an exclusive way in either the SPI mode or the I2S audio mode.
3. V_{DD}/V_{DDA} minimum value of 1.7 V is obtained when the device operates in reduced temperature range, and with the use of an external power supply supervisor (refer to [Section 3.17.2: Internal reset OFF](#)).

Figure 2. Compatible board design between STM32F10xx/STM32F2xx/STM32F4xx for LQFP144 package

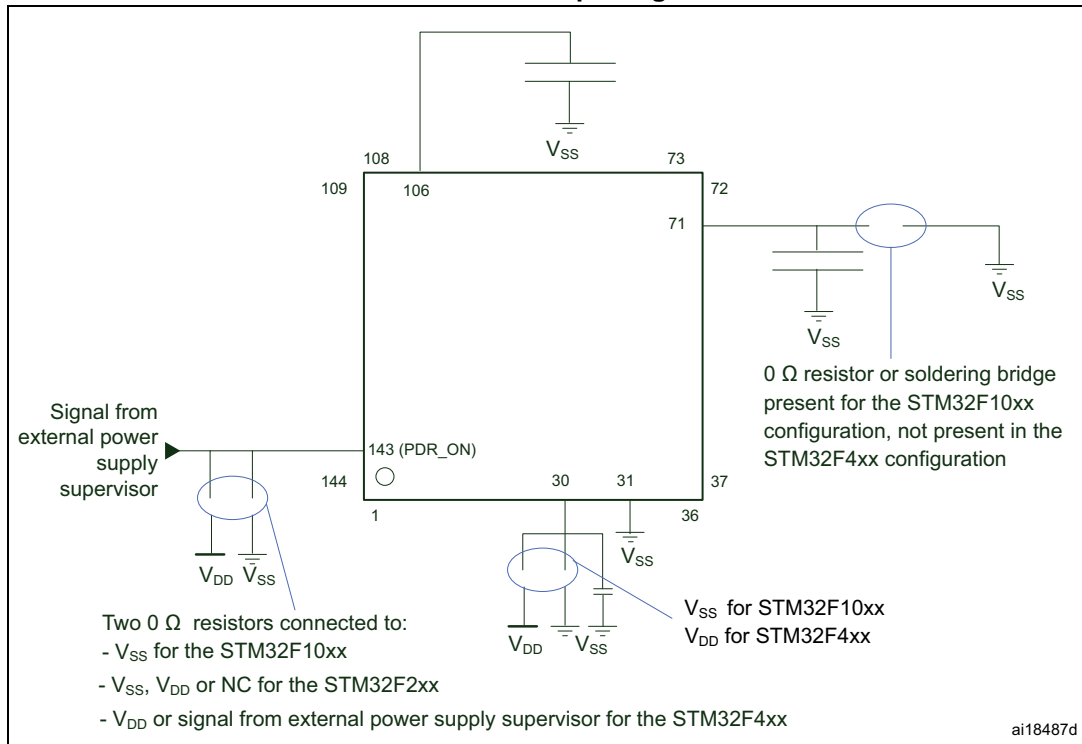


Figure 3. Compatible board design between STM32F2xx and STM32F4xx for LQFP176 and UFBGA176 packages

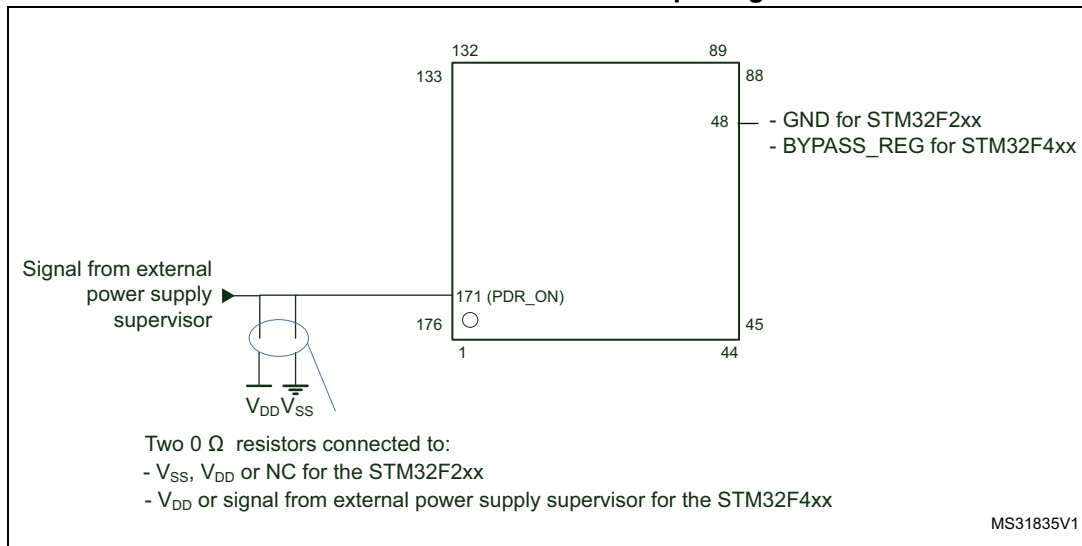
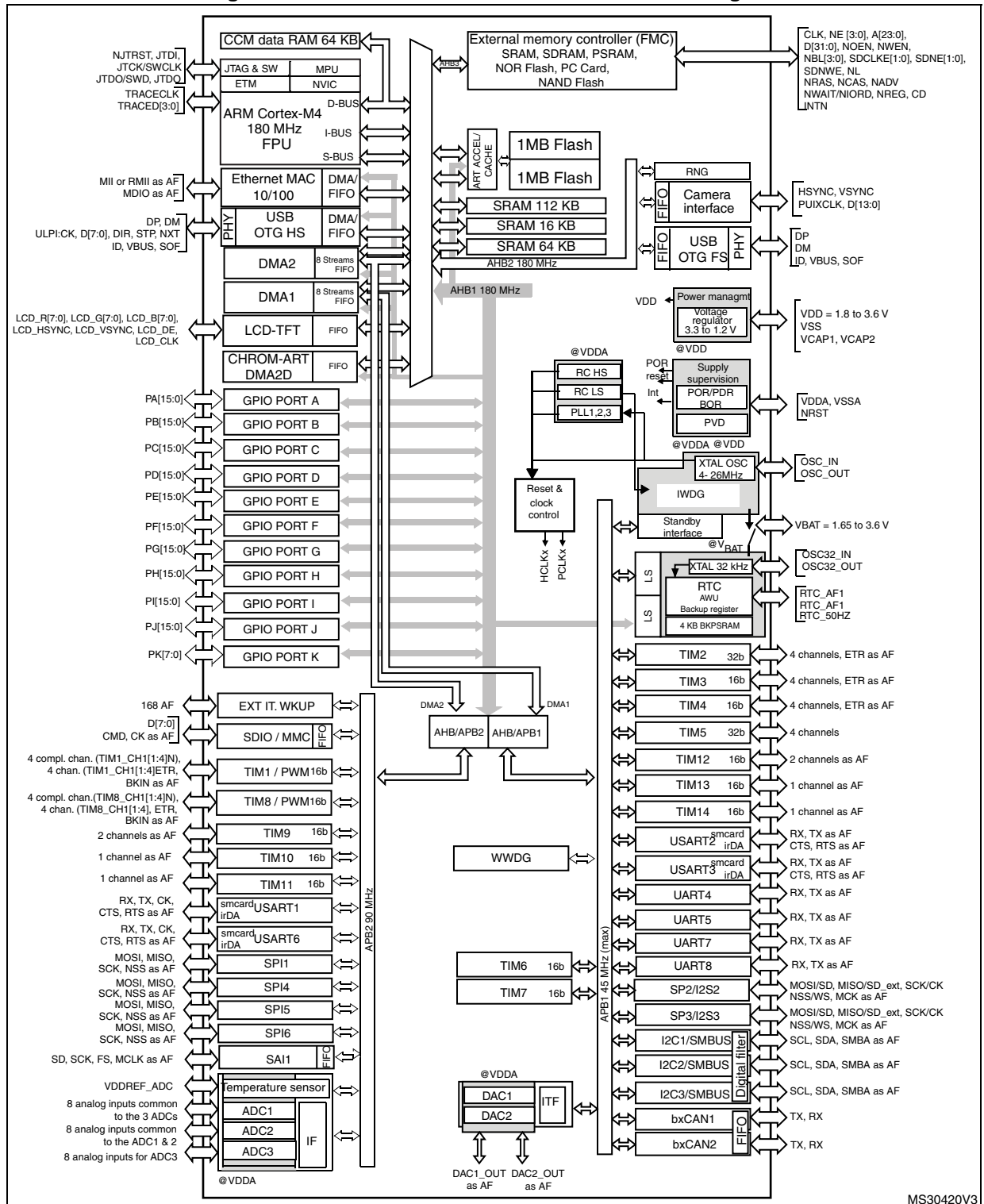


Figure 4. STM32F427xx and STM32F429xx block diagram



1. The timers connected to APB2 are clocked from TIMxCLK up to 180 MHz, while the timers connected to APB1 are clocked from TIMxCLK either up to 90 MHz or 180 MHz depending on TIMPRE bit configuration in the RCC_DCKCFGR register.
2. The LCD-TFT is available only on STM32F429xx devices.

3 Functional overview

3.1 ARM[®] Cortex[™]-M4 with FPU and embedded Flash and SRAM

The ARM Cortex-M4 with FPU processor is the latest generation of ARM processors for embedded systems. It was developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and low-power consumption, while delivering outstanding computational performance and an advanced response to interrupts.

The ARM Cortex-M4 with FPU core is a 32-bit RISC processor that features exceptional code-efficiency, delivering the high-performance expected from an ARM core in the memory size usually associated with 8- and 16-bit devices.

The processor supports a set of DSP instructions which allow efficient signal processing and complex algorithm execution.

Its single precision FPU (floating point unit) speeds up software development by using metalanguage development tools, while avoiding saturation.

The STM32F42x family is compatible with all ARM tools and software.

Figure 4: STM32F427xx and STM32F429xx block diagram shows the general block diagram of the STM32F42x family.

Note: Cortex-M4 with FPU core is binary compatible with the Cortex-M3 core.

3.2 Adaptive real-time memory accelerator (ART Accelerator[™])

The ART Accelerator[™] is a memory accelerator which is optimized for STM32 industry-standard ARM[®] Cortex[™]-M4 with FPU processors. It balances the inherent performance advantage of the ARM Cortex-M4 with FPU over Flash memory technologies, which normally requires the processor to wait for the Flash memory at higher frequencies.

To release the processor full 225 DMIPS performance at this frequency, the accelerator implements an instruction prefetch queue and branch cache, which increases program execution speed from the 128-bit Flash memory. Based on CoreMark benchmark, the performance achieved thanks to the ART Accelerator is equivalent to 0 wait state program execution from Flash memory at a CPU frequency up to 180 MHz.

3.3 Memory protection unit

The memory protection unit (MPU) is used to manage the CPU accesses to memory to prevent one task to accidentally corrupt the memory or resources used by any other active task. This memory area is organized into up to 8 protected areas that can in turn be divided up into 8 subareas. The protection area sizes are between 32 bytes and the whole 4 gigabytes of addressable memory.

The MPU is especially helpful for applications where some critical or certified code has to be protected against the misbehavior of other tasks. It is usually managed by an RTOS (real-time operating system). If a program accesses a memory location that is prohibited by the MPU, the RTOS can detect it and take action. In an RTOS environment, the kernel can dynamically update the MPU area setting, based on the process to be executed.

The MPU is optional and can be bypassed for applications that do not need it.

3.4 Embedded Flash memory

The devices embed a Flash memory of 1 Mbytes or 2 Mbytes available for storing programs and data.

3.5 CRC (cyclic redundancy check) calculation unit

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code from a 32-bit data word and a fixed generator polynomial.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a software signature during runtime, to be compared with a reference signature generated at link-time and stored at a given memory location.

3.6 Embedded SRAM

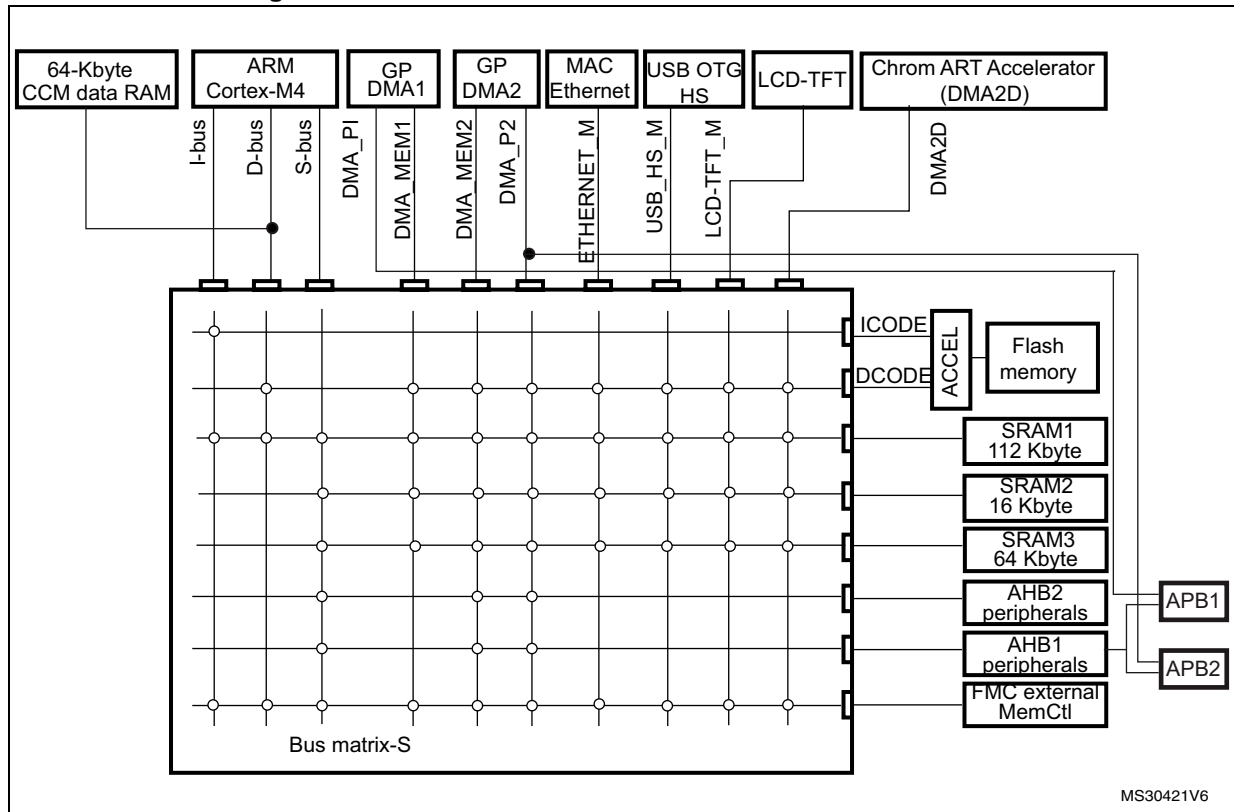
All devices embed:

- Up to 256 Kbytes of system SRAM including 64 Kbytes of CCM (core coupled memory) data RAM
RAM memory is accessed (read/write) at CPU clock speed with 0 wait states.
- 4 Kbytes of backup SRAM
This area is accessible only from the CPU. Its content is protected against possible unwanted write accesses, and is retained in Standby or VBAT mode.

3.7 Multi-AHB bus matrix

The 32-bit multi-AHB bus matrix interconnects all the masters (CPU, DMAs, Ethernet, USB HS, the LCD-TFT, and the DMA2D) and the slaves (Flash memory, RAM, FMC, AHB and APB peripherals) and ensures a seamless and efficient operation even when several high-speed peripherals work simultaneously.

Figure 5. STM32F427xx and STM32F429xx Multi-AHB matrix



3.8 DMA controller (DMA)

The devices feature two general-purpose dual-port DMAs (DMA1 and DMA2) with 8 streams each. They are able to manage memory-to-memory, peripheral-to-memory and memory-to-peripheral transfers. They feature dedicated FIFOs for APB/AHB peripherals, support burst transfer and are designed to provide the maximum peripheral bandwidth (AHB/APB).

The two DMA controllers support circular buffer management, so that no specific code is needed when the controller reaches the end of the buffer. The two DMA controllers also have a double buffering feature, which automates the use and switching of two memory buffers without requiring any special code.

Each stream is connected to dedicated hardware DMA requests, with support for software trigger on each stream. Configuration is made by software and transfer sizes between source and destination are independent.

The DMA can be used with the main peripherals:

- SPI and I²S
- I²C
- USART
- General-purpose, basic and advanced-control timers TIMx
- DAC
- SDIO
- Camera interface (DCMI)
- ADC
- SAI1.

3.9 Flexible memory controller (FMC)

All devices embed an FMC. It has four Chip Select outputs supporting the following modes: PCCard/Compact Flash, SDRAM, SRAM, PSRAM, NOR Flash and NAND Flash.

Functionality overview:

- 8-, 16-, 32-bit data bus width
- Read FIFO for SDRAM controller
- Write FIFO
- Maximum FMC_CLK/FMC_SDCLK frequency for synchronous accesses is 90 MHz.

LCD parallel interface

The FMC can be configured to interface seamlessly with most graphic LCD controllers. It supports the Intel 8080 and Motorola 6800 modes, and is flexible enough to adapt to specific LCD interfaces. This LCD parallel interface capability makes it easy to build cost-effective graphic applications using LCD modules with embedded controllers or high performance solutions using external controllers with dedicated acceleration.

3.10 LCD-TFT controller (available only on STM32F429xx)

The LCD-TFT display controller provides a 24-bit parallel digital RGB (Red, Green, Blue) and delivers all signals to interface directly to a broad range of LCD and TFT panels up to SVGA (800x600) resolution with the following features:

- 2 displays layers with dedicated FIFO (64x32-bit)
- Color Look-Up table (CLUT) up to 256 colors (256x24-bit) per layer
- Up to 8 Input color formats selectable per layer
- Flexible blending between two layers using alpha value (per pixel or constant)
- Flexible programmable parameters for each layer
- Color keying (transparency color)
- Up to 4 programmable interrupt events.

3.11 Chrom-ART Accelerator™ (DMA2D)

The Chrom-Art Accelerator™ (DMA2D) is a graphic accelerator which offers advanced bit blitting, row data copy and pixel format conversion. It supports the following functions:

- Rectangle filling with a fixed color
- Rectangle copy
- Rectangle copy with pixel format conversion
- Rectangle composition with blending and pixel format conversion.

Various image format coding are supported, from indirect 4bpp color mode up to 32bpp direct color. It embeds dedicated memory to store color lookup tables.

An interrupt can be generated when an operation is complete or at a programmed watermark.

All the operations are fully automatized and are running independently from the CPU or the DMAs.

3.12 Nested vectored interrupt controller (NVIC)

The devices embed a nested vectored interrupt controller able to manage 16 priority levels, and handle up to 91 maskable interrupt channels plus the 16 interrupt lines of the Cortex™-M4 with FPU core.

- Closely coupled NVIC gives low-latency interrupt processing
- Interrupt entry vector table address passed directly to the core
- Allows early processing of interrupts
- Processing of late arriving, higher-priority interrupts
- Support tail chaining
- Processor state automatically saved
- Interrupt entry restored on interrupt exit with no instruction overhead

This hardware block provides flexible interrupt management features with minimum interrupt latency.

3.13 External interrupt/event controller (EXTI)

The external interrupt/event controller consists of 23 edge-detector lines used to generate interrupt/event requests. Each line can be independently configured to select the trigger event (rising edge, falling edge, both) and can be masked independently. A pending register maintains the status of the interrupt requests. The EXTI can detect an external line with a pulse width shorter than the Internal APB2 clock period. Up to 168 GPIOs can be connected to the 16 external interrupt lines.

3.14 Clocks and startup

On reset the 16 MHz internal RC oscillator is selected as the default CPU clock. The 16 MHz internal RC oscillator is factory-trimmed to offer 1% accuracy over the full temperature range. The application can then select as system clock either the RC oscillator or an external 4-26 MHz clock source. This clock can be monitored for failure. If a failure is

detected, the system automatically switches back to the internal RC oscillator and a software interrupt is generated (if enabled). This clock source is input to a PLL thus allowing to increase the frequency up to 180 MHz. Similarly, full interrupt management of the PLL clock entry is available when necessary (for example if an indirectly used external oscillator fails).

Several prescalers allow the configuration of the two AHB buses, the high-speed APB (APB2) and the low-speed APB (APB1) domains. The maximum frequency of the two AHB buses is 180 MHz while the maximum frequency of the high-speed APB domains is 90 MHz. The maximum allowed frequency of the low-speed APB domain is 45 MHz.

The devices embed a dedicated PLL (PLL12S) and PLLSAI which allows to achieve audio class performance. In this case, the I²S master clock can generate all standard sampling frequencies from 8 kHz to 192 kHz.

3.15 Boot modes

At startup, boot pins are used to select one out of three boot options:

- Boot from user Flash
- Boot from system memory
- Boot from embedded SRAM

The boot loader is located in system memory. It is used to reprogram the Flash memory by using USART1 (PA9/PA10), USART3 (PC10/PC11 or PB10/PB11), I2C2 (PF0/PF1), I2C3 (PA8/PC9), CAN2 (PB5/PB13), USB OTG FS in Device mode (PA11/PA12) through DFU (device firmware upgrade).

3.16 Power supply schemes

- $V_{DD} = 1.8$ to 3.6 V: external power supply for I/Os and the internal regulator (when enabled), provided externally through V_{DD} pins.
- $V_{SSA}, V_{DDA} = 1.8$ to 3.6 V: external analog power supplies for ADC, DAC, Reset blocks, RCs and PLL. V_{DDA} and V_{SSA} must be connected to V_{DD} and V_{SS} , respectively.
- $V_{BAT} = 1.65$ to 3.6 V: power supply for RTC, external clock 32 kHz oscillator and backup registers (through power switch) when V_{DD} is not present.

Note: V_{DD}/V_{DDA} minimum value of 1.7 V is obtained when the device operates in reduced temperature range, and with the use of an external power supply supervisor (refer to [Section 3.17.2: Internal reset OFF](#)). Refer to [Table 3: Voltage regulator configuration mode versus device operating mode](#) to identify the packages supporting this option.

3.17 Power supply supervisor

3.17.1 Internal reset ON

On packages embedding the PDR_ON pin, the power supply supervisor is enabled by holding PDR_ON high. On the other package, the power supply supervisor is always enabled.

The device has an integrated power-on reset (POR)/ power-down reset (PDR) circuitry coupled with a Brownout reset (BOR) circuitry. At power-on, POR/PDR is always active and ensures proper operation starting from 1.8 V. After the 1.8 V POR threshold level is reached, the option byte loading process starts, either to confirm or modify default BOR thresholds, or to disable BOR permanently. Three BOR thresholds are available through option bytes. The device remains in reset mode when V_{DD} is below a specified threshold, $V_{POR/PDR}$ or V_{BOR} , without the need for an external reset circuit.

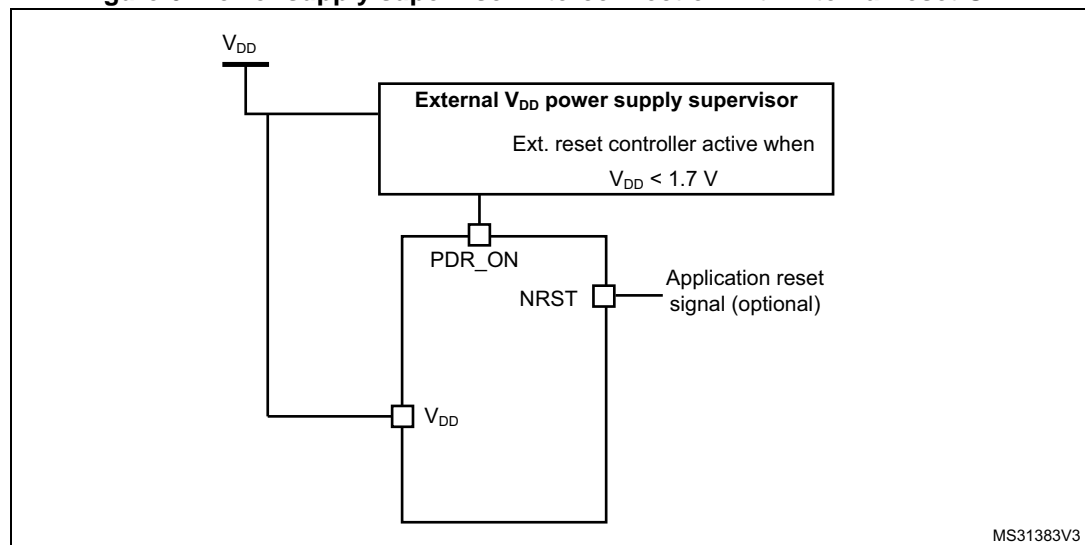
The device also features an embedded programmable voltage detector (PVD) that monitors the V_{DD}/V_{DDA} power supply and compares it to the V_{PVD} threshold. An interrupt can be generated when V_{DD}/V_{DDA} drops below the V_{PVD} threshold and/or when V_{DD}/V_{DDA} is higher than the V_{PVD} threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

3.17.2 Internal reset OFF

This feature is available only on packages featuring the PDR_ON pin. The internal power-on reset (POR) / power-down reset (PDR) circuitry is disabled through the PDR_ON pin.

An external power supply supervisor should monitor V_{DD} and should maintain the device in reset mode as long as V_{DD} is below a specified threshold. PDR_ON should be connected to this external power supply supervisor. Refer to [Figure 6: Power supply supervisor interconnection with internal reset OFF](#).

Figure 6. Power supply supervisor interconnection with internal reset OFF



1. PDR = 1.7 V for reduce temperature range; PDR = 1.8 V for all temperature range.

The V_{DD} specified threshold, below which the device must be maintained under reset, is 1.8 V (see [Figure 7](#)). This supply voltage can drop to 1.7 V when the device operates in the 0 to 70 °C temperature range.

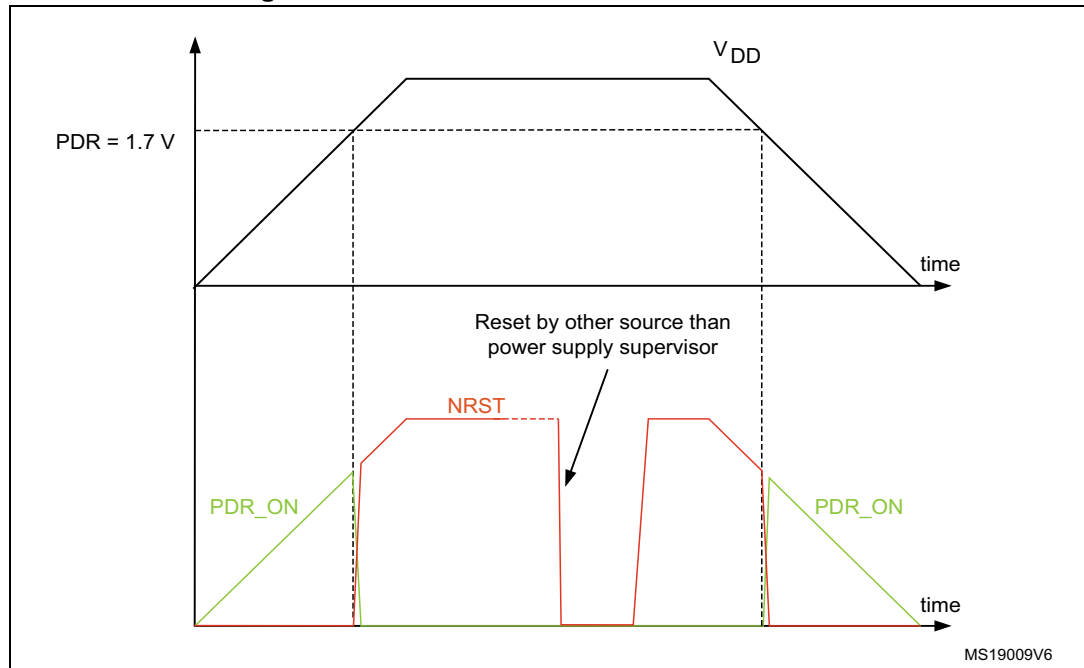
A comprehensive set of power-saving mode allows to design low-power applications.

When the internal reset is OFF, the following integrated features are no more supported:

- The integrated power-on reset (POR) / power-down reset (PDR) circuitry is disabled
- The brownout reset (BOR) circuitry must be disabled
- The embedded programmable voltage detector (PVD) is disabled
- V_{BAT} functionality is no more available and V_{BAT} pin should be connected to V_{DD} .

All packages, except for the LQFP100, allow to disable the internal reset through the PDR_ON signal.

Figure 7. PDR_ON control with internal reset OFF



1. PDR = 1.7 V for reduce temperature range; PDR = 1.8 V for all temperature range.

3.18 Voltage regulator

The regulator has four operating modes:

- Regulator ON
 - Main regulator mode (MR)
 - Low power regulator (LPR)
 - Power-down
- Regulator OFF

3.18.1 Regulator ON

On packages embedding the BYPASS_REG pin, the regulator is enabled by holding BYPASS_REG low. On all other packages, the regulator is always enabled.

There are three power modes configured by software when the regulator is ON:

- MR mode used in Run/sleep modes or in Stop modes
 - In Run/Sleep mode

The MR mode is used either in the normal mode (default mode) or the over-drive mode (enabled by software). Different voltages scaling are provided to reach the best compromise between maximum frequency and dynamic power consumption. The over-drive mode allows operating at a higher frequency than the normal mode for a given voltage scaling.
 - In Stop modes

The MR can be configured in two ways during stop mode:
 MR operates in normal mode (default mode of MR in stop mode)
 MR operates in under-drive mode (reduced leakage mode).
- LPR is used in the Stop modes:

The LP regulator mode is configured by software when entering Stop mode. Like the MR mode, the LPR can be configured in two ways during stop mode:

 - LPR operates in normal mode (default mode when LPR is ON)
 - LPR operates in under-drive mode (reduced leakage mode).
- Power-down is used in Standby mode.

The Power-down mode is activated only when entering in Standby mode. The regulator output is in high impedance and the kernel circuitry is powered down, inducing zero consumption. The contents of the registers and SRAM are lost.

Refer to [Table 3](#) for a summary of voltage regulator modes versus device operating modes.

Two external ceramic capacitors should be connected on V_{CAP_1} and V_{CAP_2} pin. Refer to [Figure 21: Power supply scheme](#) and [Table 19: VCAP1/VCAP2 operating conditions](#).

All packages have the regulator ON feature.

Table 3. Voltage regulator configuration mode versus device operating mode⁽¹⁾

Voltage regulator configuration	Run mode	Sleep mode	Stop mode	Standby mode
Normal mode	MR	MR	MR or LPR	-
Over-drive mode ⁽²⁾	MR	MR	-	-
Under-drive mode	-	-	MR or LPR	-
Power-down mode	-	-	-	Yes

1. '-' means that the corresponding configuration is not available.
 2. The over-drive mode is not available when V_{DD} = 1.8 to 2.1 V.

3.18.2 Regulator OFF

This feature is available only on packages featuring the BYPASS_REG pin. The regulator is disabled by holding BYPASS_REG high. The regulator OFF mode allows to supply externally a V₁₂ voltage source through V_{CAP_1} and V_{CAP_2} pins.

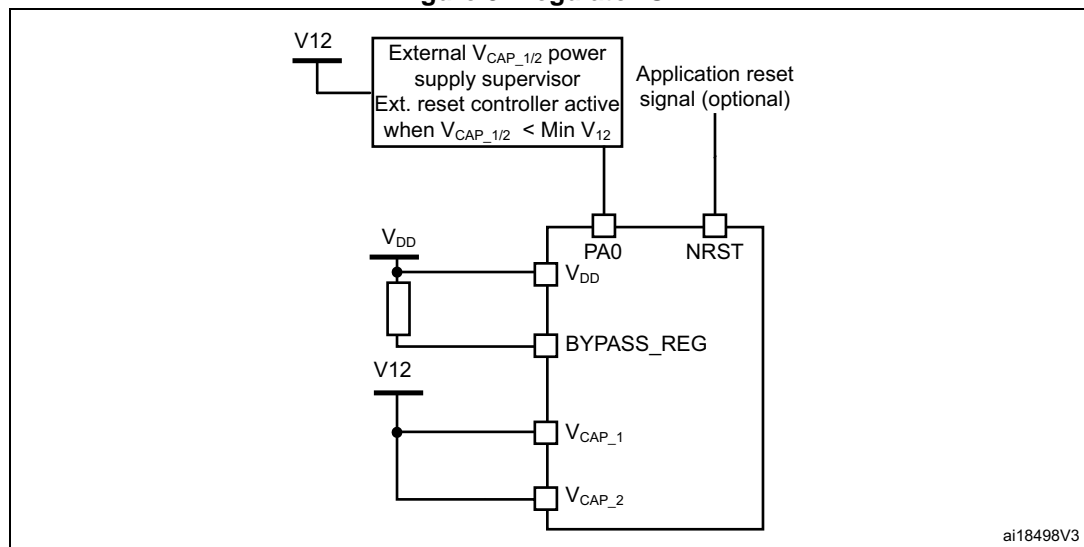
Since the internal voltage scaling is not managed internally, the external voltage value must be aligned with the targeted maximum frequency. Refer to [Table 17: General operating conditions](#). The two 2.2 μF ceramic capacitors should be replaced by two 100 nF decoupling capacitors. Refer to [Figure 21: Power supply scheme](#).

When the regulator is OFF, there is no more internal monitoring on V_{12} . An external power supply supervisor should be used to monitor the V_{12} of the logic power domain. PA0 pin should be used for this purpose, and act as power-on reset on V_{12} power domain.

In regulator OFF mode, the following features are no more supported:

- PA0 cannot be used as a GPIO pin since it allows to reset a part of the V_{12} logic power domain which is not reset by the NRST pin.
- As long as PA0 is kept low, the debug mode cannot be used under power-on reset. As a consequence, PA0 and NRST pins must be managed separately if the debug connection under reset or pre-reset is required.
- The over-drive and under-drive modes are not available.

Figure 8. Regulator OFF

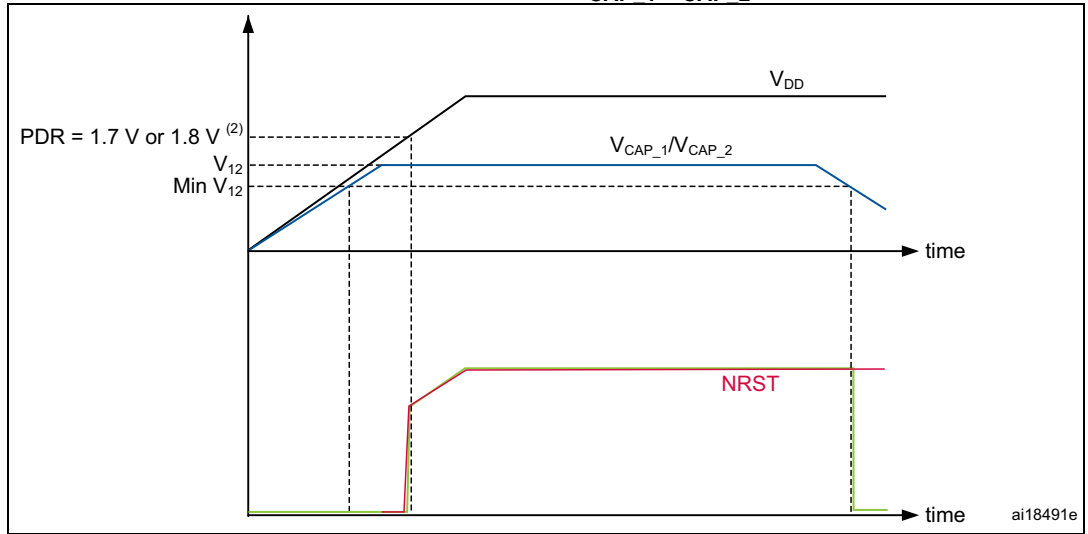


The following conditions must be respected:

- V_{DD} should always be higher than V_{CAP_1} and V_{CAP_2} to avoid current injection between power domains.
- If the time for V_{CAP_1} and V_{CAP_2} to reach V_{12} minimum value is faster than the time for V_{DD} to reach 1.8 V, then PA0 should be kept low to cover both conditions: until V_{CAP_1} and V_{CAP_2} reach V_{12} minimum value and until V_{DD} reaches 1.8 V (see [Figure 9](#)).
- Otherwise, if the time for V_{CAP_1} and V_{CAP_2} to reach V_{12} minimum value is slower than the time for V_{DD} to reach 1.8 V, then PA0 could be asserted low externally (see [Figure 10](#)).
- If V_{CAP_1} and V_{CAP_2} go below V_{12} minimum value and V_{DD} is higher than 1.8 V, then a reset must be asserted on PA0 pin.

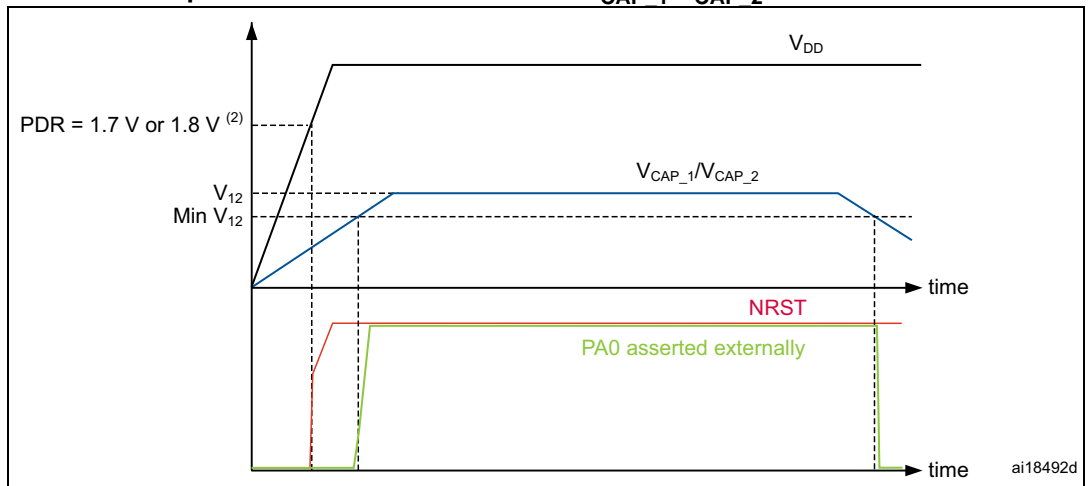
Note: The minimum value of V_{12} depends on the maximum frequency targeted in the application (see [Table 17: General operating conditions](#)).

Figure 9. Startup in regulator OFF: slow V_{DD} slope - power-down reset risen after V_{CAP_1}/V_{CAP_2} stabilization



1. This figure is valid whatever the internal reset mode (ON or OFF).
2. PDR = 1.7 V for a reduced temperature range; PDR = 1.8 V for all temperature ranges.

Figure 10. Startup in regulator OFF mode: fast V_{DD} slope - power-down reset risen before V_{CAP_1}/V_{CAP_2} stabilization



1. This figure is valid whatever the internal reset mode (ON or OFF).
2. PDR = 1.7 V for a reduced temperature range; PDR = 1.8 V for all temperature ranges.

3.18.3 Regulator ON/OFF and internal reset ON/OFF availability

Table 4. Regulator ON/OFF and internal reset ON/OFF availability

Package	Regulator ON	Regulator OFF	Internal reset ON	Internal reset OFF
LQFP100	Yes	No	Yes	No
LQFP144			Yes PDR_ON set to V _{DD}	Yes PDR_ON connected to an external power supply supervisor
WLCSP143, LQFP176, UFBGA176, LQFP208, TFBGA216	Yes BYPASS_REG set to V _{SS}	Yes BYPASS_REG set to V _{DD}		

3.19 Real-time clock (RTC), backup SRAM and backup registers

The backup domain includes:

- The real-time clock (RTC)
- 4 Kbytes of backup SRAM
- 20 backup registers

The real-time clock (RTC) is an independent BCD timer/counter. Dedicated registers contain the second, minute, hour (in 12/24 hour), week day, date, month, year, in BCD (binary-coded decimal) format. Correction for 28, 29 (leap year), 30, and 31 day of the month are performed automatically. The RTC provides a programmable alarm and programmable periodic interrupts with wakeup from Stop and Standby modes. The sub-seconds value is also available in binary format.

It is clocked by a 32.768 kHz external crystal, resonator or oscillator, the internal low-power RC oscillator or the high-speed external clock divided by 128. The internal low-speed RC has a typical frequency of 32 kHz. The RTC can be calibrated using an external 512 Hz output to compensate for any natural quartz deviation.

Two alarm registers are used to generate an alarm at a specific time and calendar fields can be independently masked for alarm comparison. To generate a periodic interrupt, a 16-bit programmable binary auto-reload downcounter with programmable resolution is available and allows automatic wakeup and periodic alarms from every 120 μs to every 36 hours.

A 20-bit prescaler is used for the time base clock. It is by default configured to generate a time base of 1 second from a clock at 32.768 kHz.

The 4-Kbyte backup SRAM is an EEPROM-like memory area. It can be used to store data which need to be retained in VBAT and standby mode. This memory area is disabled by default to minimize power consumption (see [Section 3.20: Low-power modes](#)). It can be enabled by software.

The backup registers are 32-bit registers used to store 80 bytes of user application data when V_{DD} power is not present. Backup registers are not reset by a system, a power reset, or when the device wakes up from the Standby mode (see [Section 3.20: Low-power modes](#)).

Additional 32-bit registers contain the programmable alarm subseconds, seconds, minutes, hours, day, and date.

Like backup SRAM, the RTC and backup registers are supplied through a switch that is powered either from the V_{DD} supply when present or from the V_{BAT} pin.

3.20 Low-power modes

The devices support three low-power modes to achieve the best compromise between low power consumption, short startup time and available wakeup sources:

- **Sleep mode**

In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.

- **Stop mode**

The Stop mode achieves the lowest power consumption while retaining the contents of SRAM and registers. All clocks in the 1.2 V domain are stopped, the PLL, the HSI RC and the HSE crystal oscillators are disabled.

The voltage regulator can be put either in main regulator mode (MR) or in low-power mode (LPR). Both modes can be configured as follows (see [Table 5: Voltage regulator modes in stop mode](#)):

- Normal mode (default mode when MR or LPR is enabled)
- Under-drive mode.

The device can be woken up from the Stop mode by any of the EXTI line (the EXTI line source can be one of the 16 external lines, the PVD output, the RTC alarm / wakeup / tamper / time stamp events, the USB OTG FS/HS wakeup or the Ethernet wakeup).

Table 5. Voltage regulator modes in stop mode

Voltage regulator configuration	Main regulator (MR)	Low-power regulator (LPR)
Normal mode	MR ON	LPR ON
Under-drive mode	MR in under-drive mode	LPR in under-drive mode

- **Standby mode**

The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire 1.2 V domain is powered off. The PLL, the HSI RC and the HSE crystal oscillators are also switched off. After entering Standby mode, the SRAM and register contents are lost except for registers in the backup domain and the backup SRAM when selected.

The device exits the Standby mode when an external reset (NRST pin), an IWDG reset, a rising edge on the WKUP pin, or an RTC alarm / wakeup / tamper /time stamp event occurs.

The standby mode is not supported when the embedded voltage regulator is bypassed and the 1.2 V domain is controlled by an external power.

3.21 V_{BAT} operation

The V_{BAT} pin allows to power the device V_{BAT} domain from an external battery, an external supercapacitor, or from V_{DD} when no external battery and an external supercapacitor are present.

V_{BAT} operation is activated when V_{DD} is not present.

The V_{BAT} pin supplies the RTC, the backup registers and the backup SRAM.

Note: When the microcontroller is supplied from V_{BAT} , external interrupts and RTC alarm/events do not exit it from V_{BAT} operation. When PDR_ON pin is not connected to V_{DD} (Internal Reset OFF), the V_{BAT} functionality is no more available and V_{BAT} pin should be connected to V_{DD} .

3.22 Timers and watchdogs

The devices include two advanced-control timers, eight general-purpose timers, two basic timers and two watchdog timers.

All timer counters can be frozen in debug mode.

[Table 6](#) compares the features of the advanced-control, general-purpose and basic timers.

Table 6. Timer feature comparison

Timer type	Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/compare channels	Complementary output	Max interface clock (MHz)	Max timer clock (MHz) ⁽¹⁾
Advanced -control	TIM1, TIM8	16-bit	Up, Down, Up/down	Any integer between 1 and 65536	Yes	4	Yes	90	180
General purpose	TIM2, TIM5	32-bit	Up, Down, Up/down	Any integer between 1 and 65536	Yes	4	No	45	90/180
	TIM3, TIM4	16-bit	Up, Down, Up/down	Any integer between 1 and 65536	Yes	4	No	45	90/180
	TIM9	16-bit	Up	Any integer between 1 and 65536	No	2	No	90	180
	TIM10, TIM11	16-bit	Up	Any integer between 1 and 65536	No	1	No	90	180
	TIM12	16-bit	Up	Any integer between 1 and 65536	No	2	No	45	90/180
	TIM13, TIM14	16-bit	Up	Any integer between 1 and 65536	No	1	No	45	90/180
	Basic	TIM6, TIM7	16-bit	Up	Any integer between 1 and 65536	Yes	0	No	45

1. The maximum timer clock is either 90 or 180 MHz depending on TIMPRE bit configuration in the RCC_DCKCFGR register.



3.22.1 Advanced-control timers (TIM1, TIM8)

The advanced-control timers (TIM1, TIM8) can be seen as three-phase PWM generators multiplexed on 6 channels. They have complementary PWM outputs with programmable inserted dead times. They can also be considered as complete general-purpose timers. Their 4 independent channels can be used for:

- Input capture
- Output compare
- PWM generation (edge- or center-aligned modes)
- One-pulse mode output

If configured as standard 16-bit timers, they have the same features as the general-purpose TIMx timers. If configured as 16-bit PWM generators, they have full modulation capability (0-100%).

The advanced-control timer can work together with the TIMx timers via the Timer Link feature for synchronization or event chaining.

TIM1 and TIM8 support independent DMA request generation.

3.22.2 General-purpose timers (TIMx)

There are ten synchronizable general-purpose timers embedded in the STM32F42x devices (see [Table 6](#) for differences).

- **TIM2, TIM3, TIM4, TIM5**

The STM32F42x include 4 full-featured general-purpose timers: TIM2, TIM5, TIM3, and TIM4. The TIM2 and TIM5 timers are based on a 32-bit auto-reload up/downcounter and a 16-bit prescaler. The TIM3 and TIM4 timers are based on a 16-bit auto-reload up/downcounter and a 16-bit prescaler. They all feature 4 independent channels for input capture/output compare, PWM or one-pulse mode output. This gives up to 16 input capture/output compare/PWMs on the largest packages.

The TIM2, TIM3, TIM4, TIM5 general-purpose timers can work together, or with the other general-purpose timers and the advanced-control timers TIM1 and TIM8 via the Timer Link feature for synchronization or event chaining.

Any of these general-purpose timers can be used to generate PWM outputs.

TIM2, TIM3, TIM4, TIM5 all have independent DMA request generation. They are capable of handling quadrature (incremental) encoder signals and the digital outputs from 1 to 4 hall-effect sensors.

- **TIM9, TIM10, TIM11, TIM12, TIM13, and TIM14**

These timers are based on a 16-bit auto-reload upcounter and a 16-bit prescaler. TIM10, TIM11, TIM13, and TIM14 feature one independent channel, whereas TIM9 and TIM12 have two independent channels for input capture/output compare, PWM or one-pulse mode output. They can be synchronized with the TIM2, TIM3, TIM4, TIM5 full-featured general-purpose timers. They can also be used as simple time bases.

3.22.3 Basic timers TIM6 and TIM7

These timers are mainly used for DAC trigger and waveform generation. They can also be used as a generic 16-bit time base.

TIM6 and TIM7 support independent DMA request generation.

3.22.4 Independent watchdog

The independent watchdog is based on a 12-bit downcounter and 8-bit prescaler. It is clocked from an independent 32 kHz internal RC and as it operates independently from the main clock, it can operate in Stop and Standby modes. It can be used either as a watchdog to reset the device when a problem occurs, or as a free-running timer for application timeout management. It is hardware- or software-configurable through the option bytes.

3.22.5 Window watchdog

The window watchdog is based on a 7-bit downcounter that can be set as free-running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early warning interrupt capability and the counter can be frozen in debug mode.

3.22.6 SysTick timer

This timer is dedicated to real-time operating systems, but could also be used as a standard downcounter. It features:

- A 24-bit downcounter
- Autoreload capability
- Maskable system interrupt generation when the counter reaches 0
- Programmable clock source.

3.23 Inter-integrated circuit interface (I²C)

Up to three I²C bus interfaces can operate in multimaster and slave modes. They can support the standard (up to 100 KHz) and fast (up to 400 KHz) modes. They support the 7/10-bit addressing mode and the 7-bit dual addressing mode (as slave). A hardware CRC generation/verification is embedded.

They can be served by DMA and they support SMBus 2.0/PMBus.

The devices also include programmable analog and digital noise filters (see [Table 7](#)).

Table 7. Comparison of I2C analog and digital filters

	Analog filter	Digital filter
Pulse width of suppressed spikes	≥ 50 ns	Programmable length from 1 to 15 I2C peripheral clocks

3.24 Universal synchronous/asynchronous receiver transmitters (USART)

The devices embed four universal synchronous/asynchronous receiver transmitters (USART1, USART2, USART3 and USART6) and two universal asynchronous receiver transmitters (UART4, UART5, UART7, and UART8).

These six interfaces provide asynchronous communication, IrDA SIR ENDEC support, multiprocessor communication mode, single-wire half-duplex communication mode and have LIN Master/Slave capability. The USART1 and USART6 interfaces are able to

communicate at speeds of up to 11.25 Mbit/s. The other available interfaces communicate at up to 5.62 bit/s.

USART1, USART2, USART3 and USART6 also provide hardware management of the CTS and RTS signals, Smart Card mode (ISO 7816 compliant) and SPI-like communication capability. All interfaces can be served by the DMA controller.

Table 8. USART feature comparison⁽¹⁾

USART name	Standard features	Modem (RTS/CTS)	LIN	SPI master	irDA	Smartcard (ISO 7816)	Max. baud rate in Mbit/s (oversampling by 16)	Max. baud rate in Mbit/s (oversampling by 8)	APB mapping
USART1	X	X	X	X	X	X	5.62	11.25	APB2 (max. 90 MHz)
USART2	X	X	X	X	X	X	2.81	5.62	APB1 (max. 45 MHz)
USART3	X	X	X	X	X	X	2.81	5.62	APB1 (max. 45 MHz)
UART4	X	-	X	-	X	-	2.81	5.62	APB1 (max. 45 MHz)
UART5	X	-	X	-	X	-	2.81	5.62	APB1 (max. 45 MHz)
USART6	X	X	X	X	X	X	5.62	11.25	APB2 (max. 90 MHz)
UART7	X	-	X	-	X	-	2.81	5.62	APB1 (max. 45 MHz)
UART8	X	-	X	-	X	-	2.81	5.62	APB1 (max. 45 MHz)

1. X = feature supported.

3.25 Serial peripheral interface (SPI)

The devices feature up to six SPIs in slave and master modes in full-duplex and simplex communication modes. SPI1, SPI4, SPI5, and SPI6 can communicate at up to 45 Mbits/s, SPI2 and SPI3 can communicate at up to 22.5 Mbit/s. The 3-bit prescaler gives 8 master mode frequencies and the frame is configurable to 8 bits or 16 bits. The hardware CRC generation/verification supports basic SD Card/MMC modes. All SPIs can be served by the DMA controller.

The SPI interface can be configured to operate in TI mode for communications in master mode and slave mode.

3.26 Inter-integrated sound (I²S)

Two standard I²S interfaces (multiplexed with SPI2 and SPI3) are available. They can be operated in master or slave mode, in full duplex and simplex communication modes, and can be configured to operate with a 16-/32-bit resolution as an input or output channel. Audio sampling frequencies from 8 kHz up to 192 kHz are supported. When either or both of the I²S interfaces is/are configured in master mode, the master clock can be output to the external DAC/CODEC at 256 times the sampling frequency.

All I2Sx can be served by the DMA controller.

Note: For I2S2 full-duplex mode, I2S2_CK and I2S2_WS signals can be used only on GPIO Port B and GPIO Port D.

3.27 Serial Audio interface (SAI1)

The serial audio interface (SAI1) is based on two independent audio subblocks which can operate as transmitter or receiver with their FIFO. Many audio protocols are supported by each block: I2S standards, LSB or MSB-justified, PCM/DSP, TDM, AC'97 and SPDIF output, supporting audio sampling frequencies from 8 kHz up to 192 kHz. Both subblocks can be configured in master or in slave mode.

In master mode, the master clock can be output to the external DAC/CODEC at 256 times of the sampling frequency.

The two subblocks can be configured in synchronous mode when full-duplex mode is required.

SAI1 can be served by the DMA controller.

3.28 Audio PLL (PLLI2S)

The devices feature an additional dedicated PLL for audio I²S and SAI applications. It allows to achieve error-free I²S sampling clock accuracy without compromising on the CPU performance, while using USB peripherals.

The PLLI2S configuration can be modified to manage an I²S/SAI sample rate change without disabling the main PLL (PLL) used for CPU, USB and Ethernet interfaces.

The audio PLL can be programmed with very low error to obtain sampling rates ranging from 8 KHz to 192 KHz.

In addition to the audio PLL, a master clock input pin can be used to synchronize the I²S/SAI flow with an external PLL (or Codec output).

3.29 Audio and LCD PLL(PLLSAI)

An additional PLL dedicated to audio and LCD-TFT is used for SAI1 peripheral in case the PLLI2S is programmed to achieve another audio sampling frequency (49.152 MHz or 11.2896 MHz) and the audio application requires both sampling frequencies simultaneously.

The PLLSAI is also used to generate the LCD-TFT clock.

3.30 Secure digital input/output interface (SDIO)

An SD/SDIO/MMC host interface is available, that supports MultiMediaCard System Specification Version 4.2 in three different databus modes: 1-bit (default), 4-bit and 8-bit.

The interface allows data transfer at up to 48 MHz, and is compliant with the SD Memory Card Specification Version 2.0.

The SDIO Card Specification Version 2.0 is also supported with two different databus modes: 1-bit (default) and 4-bit.

The current version supports only one SD/SDIO/MMC4.2 card at any one time and a stack of MMC4.1 or previous.

In addition to SD/SDIO/MMC, this interface is fully compliant with the CE-ATA digital protocol Rev1.1.

3.31 Ethernet MAC interface with dedicated DMA and IEEE 1588 support

The devices provide an IEEE-802.3-2002-compliant media access controller (MAC) for ethernet LAN communications through an industry-standard medium-independent interface (MII) or a reduced medium-independent interface (RMII). The microcontroller requires an external physical interface device (PHY) to connect to the physical LAN bus (twisted-pair, fiber, etc.). The PHY is connected to the device MII port using 17 signals for MII or 9 signals for RMII, and can be clocked using the 25 MHz (MII) from the microcontroller.

The devices include the following features:

- Supports 10 and 100 Mbit/s rates
- Dedicated DMA controller allowing high-speed transfers between the dedicated SRAM and the descriptors (see the STM32F4xx reference manual for details)
- Tagged MAC frame support (VLAN support)
- Half-duplex (CSMA/CD) and full-duplex operation
- MAC control sublayer (control frames) support
- 32-bit CRC generation and removal
- Several address filtering modes for physical and multicast address (multicast and group addresses)
- 32-bit status code for each transmitted or received frame
- Internal FIFOs to buffer transmit and receive frames. The transmit FIFO and the receive FIFO are both 2 Kbytes.
- Supports hardware PTP (precision time protocol) in accordance with IEEE 1588 2008 (PTP V2) with the time stamp comparator connected to the TIM2 input
- Triggers interrupt when system time becomes greater than target time

3.32 Controller area network (bxCAN)

The two CANs are compliant with the 2.0A and B (active) specifications with a bitrate up to 1 Mbit/s. They can receive and transmit standard frames with 11-bit identifiers as well as extended frames with 29-bit identifiers. Each CAN has three transmit mailboxes, two receive

FIFOS with 3 stages and 28 shared scalable filter banks (all of them can be used even if one CAN is used). 256 bytes of SRAM are allocated for each CAN.

3.33 Universal serial bus on-the-go full-speed (OTG_FS)

The devices embed an USB OTG full-speed device/host/OTG peripheral with integrated transceivers. The USB OTG FS peripheral is compliant with the USB 2.0 specification and with the OTG 1.0 specification. It has software-configurable endpoint setting and supports suspend/resume. The USB OTG full-speed controller requires a dedicated 48 MHz clock that is generated by a PLL connected to the HSE oscillator. The major features are:

- Combined Rx and Tx FIFO size of 320 × 35 bits with dynamic FIFO sizing
- Supports the session request protocol (SRP) and host negotiation protocol (HNP)
- 4 bidirectional endpoints
- 8 host channels with periodic OUT support
- HNP/SNP/IP inside (no need for any external resistor)
- For OTG/Host modes, a power switch is needed in case bus-powered devices are connected

3.34 Universal serial bus on-the-go high-speed (OTG_HS)

The devices embed a USB OTG high-speed (up to 480 Mb/s) device/host/OTG peripheral. The USB OTG HS supports both full-speed and high-speed operations. It integrates the transceivers for full-speed operation (12 MB/s) and features a UTMI low-pin interface (ULPI) for high-speed operation (480 MB/s). When using the USB OTG HS in HS mode, an external PHY device connected to the ULPI is required.

The USB OTG HS peripheral is compliant with the USB 2.0 specification and with the OTG 1.0 specification. It has software-configurable endpoint setting and supports suspend/resume. The USB OTG full-speed controller requires a dedicated 48 MHz clock that is generated by a PLL connected to the HSE oscillator.

The major features are:

- Combined Rx and Tx FIFO size of 1 Kbit × 35 with dynamic FIFO sizing
- Supports the session request protocol (SRP) and host negotiation protocol (HNP)
- 6 bidirectional endpoints
- 12 host channels with periodic OUT support
- Internal FS OTG PHY support
- External HS or HS OTG operation supporting ULPI in SDR mode. The OTG PHY is connected to the microcontroller ULPI port through 12 signals. It can be clocked using the 60 MHz output.
- Internal USB DMA
- HNP/SNP/IP inside (no need for any external resistor)
- for OTG/Host modes, a power switch is needed in case bus-powered devices are connected

3.35 Digital camera interface (DCMI)

The devices embed a camera interface that can connect with camera modules and CMOS sensors through an 8-bit to 14-bit parallel interface, to receive video data. The camera interface can sustain a data transfer rate up to 54 Mbyte/s at 54 MHz. It features:

- Programmable polarity for the input pixel clock and synchronization signals
- Parallel data communication can be 8-, 10-, 12- or 14-bit
- Supports 8-bit progressive video monochrome or raw bayer format, YCbCr 4:2:2 progressive video, RGB 565 progressive video or compressed data (like JPEG)
- Supports continuous mode or snapshot (a single frame) mode
- Capability to automatically crop the image

3.36 Random number generator (RNG)

All devices embed an RNG that delivers 32-bit random numbers generated by an integrated analog circuit.

3.37 General-purpose input/outputs (GPIOs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain, with or without pull-up or pull-down), as input (floating, with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions. All GPIOs are high-current-capable and have speed selection to better manage internal noise, power consumption and electromagnetic emission.

The I/O configuration can be locked if needed by following a specific sequence in order to avoid spurious writing to the I/Os registers.

Fast I/O handling allowing maximum I/O toggling up to 90 MHz.

3.38 Analog-to-digital converters (ADCs)

Three 12-bit analog-to-digital converters are embedded and each ADC shares up to 16 external channels, performing conversions in the single-shot or scan mode. In scan mode, automatic conversion is performed on a selected group of analog inputs.

Additional logic functions embedded in the ADC interface allow:

- Simultaneous sample and hold
- Interleaved sample and hold

The ADC can be served by the DMA controller. An analog watchdog feature allows very precise monitoring of the converted voltage of one, some or all selected channels. An interrupt is generated when the converted voltage is outside the programmed thresholds.

To synchronize A/D conversion and timers, the ADCs could be triggered by any of TIM1, TIM2, TIM3, TIM4, TIM5, or TIM8 timer.

3.39 Temperature sensor

The temperature sensor has to generate a voltage that varies linearly with temperature. The conversion range is between 1.8 V and 3.6 V. The temperature sensor is internally connected to the same input channel as V_{BAT} , ADC1_IN18, which is used to convert the sensor output voltage into a digital value. When the temperature sensor and V_{BAT} conversion are enabled at the same time, only V_{BAT} conversion is performed.

As the offset of the temperature sensor varies from chip to chip due to process variation, the internal temperature sensor is mainly suitable for applications that detect temperature changes instead of absolute temperatures. If an accurate temperature reading is needed, then an external temperature sensor part should be used.

3.40 Digital-to-analog converter (DAC)

The two 12-bit buffered DAC channels can be used to convert two digital signals into two analog voltage signal outputs.

This dual digital Interface supports the following features:

- two DAC converters: one for each output channel
- 8-bit or 10-bit monotonic output
- left or right data alignment in 12-bit mode
- synchronized update capability
- noise-wave generation
- triangular-wave generation
- dual DAC channel independent or simultaneous conversions
- DMA capability for each channel
- external triggers for conversion
- input voltage reference V_{REF+}

Eight DAC trigger inputs are used in the device. The DAC channels are triggered through the timer update outputs that are also connected to different DMA streams.

3.41 Serial wire JTAG debug port (SWJ-DP)

The ARM SWJ-DP interface is embedded, and is a combined JTAG and serial wire debug port that enables either a serial wire debug or a JTAG probe to be connected to the target.

Debug is performed using 2 pins only instead of 5 required by the JTAG (JTAG pins could be re-use as GPIO with alternate function): the JTAG TMS and TCK pins are shared with SWDIO and SWCLK, respectively, and a specific sequence on the TMS pin is used to switch between JTAG-DP and SW-DP.

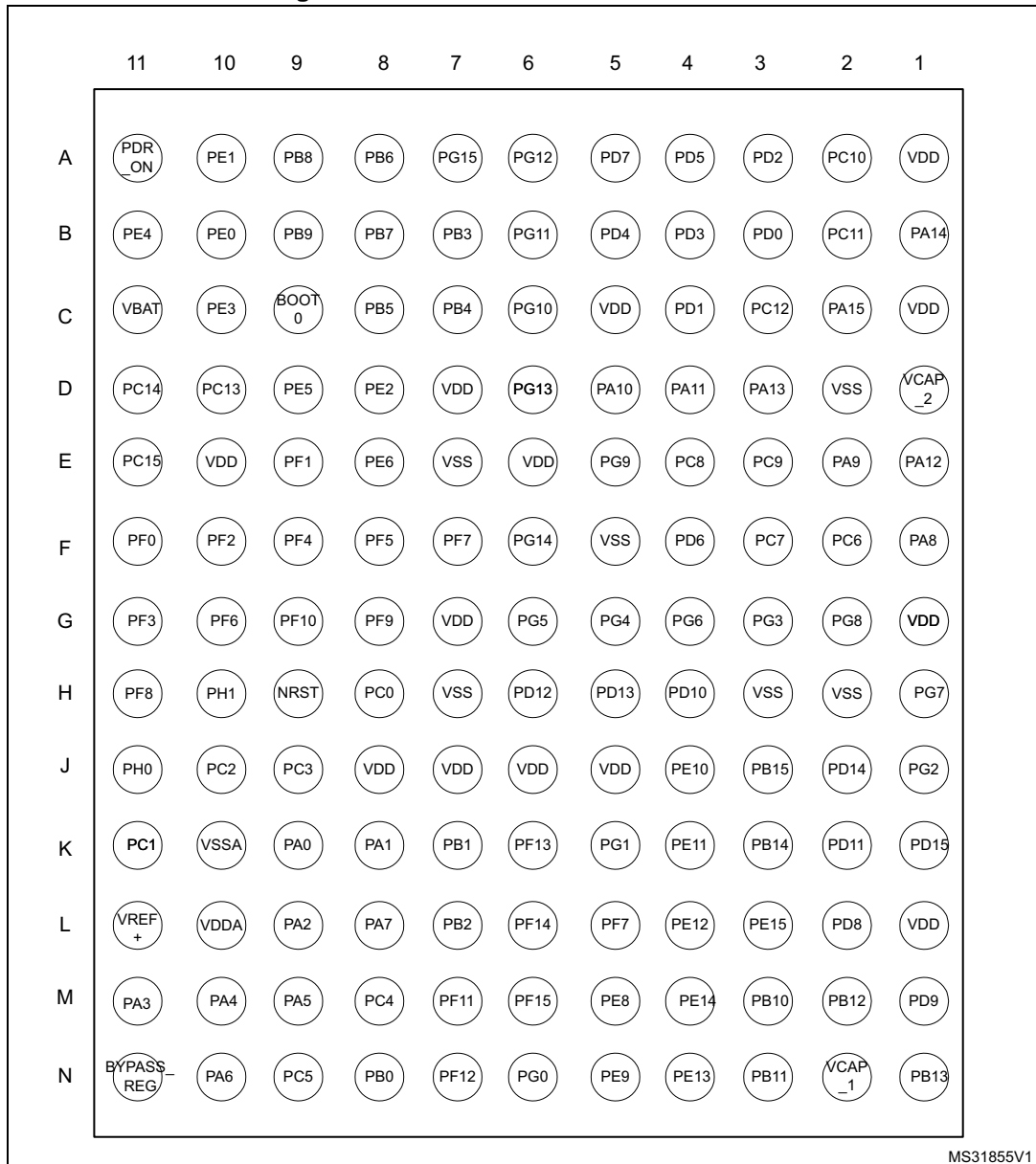
3.42 Embedded Trace Macrocell™

The ARM Embedded Trace Macrocell provides a greater visibility of the instruction and data flow inside the CPU core by streaming compressed data at a very high rate from the STM32F42x through a small number of ETM pins to an external hardware trace port analyzer (TPA) device. The TPA is connected to a host computer using USB, Ethernet, or

any other high-speed channel. Real-time instruction and data flow activity can be recorded and then formatted for display on the host computer that runs the debugger software. TPA hardware is commercially available from common development tool vendors.

The Embedded Trace Macrocell operates with third party debugger software tools.

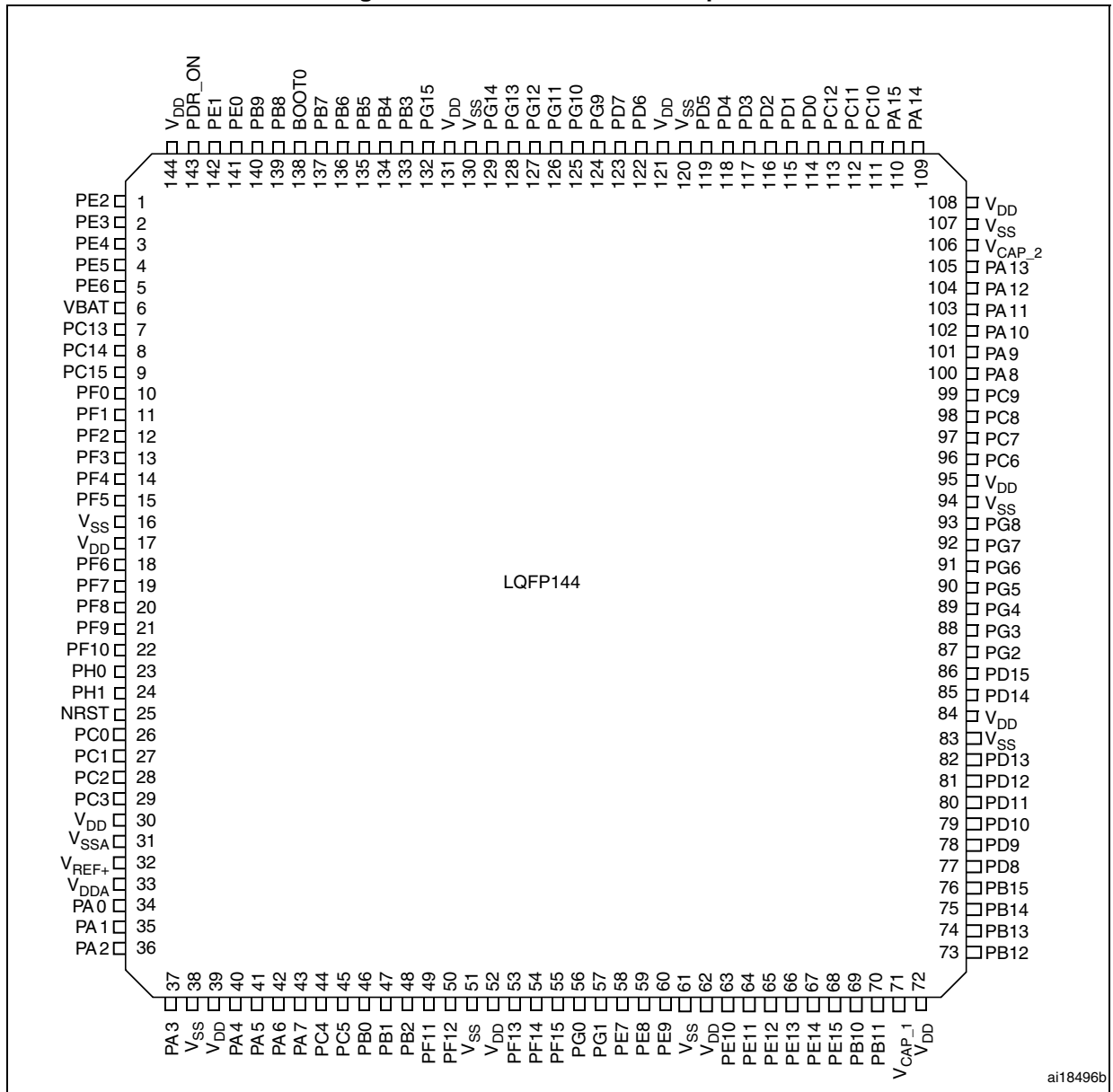
Figure 12. STM32F42x WLCSP143 ballout



MS31855V1

1. The above figure shows the package bump view.

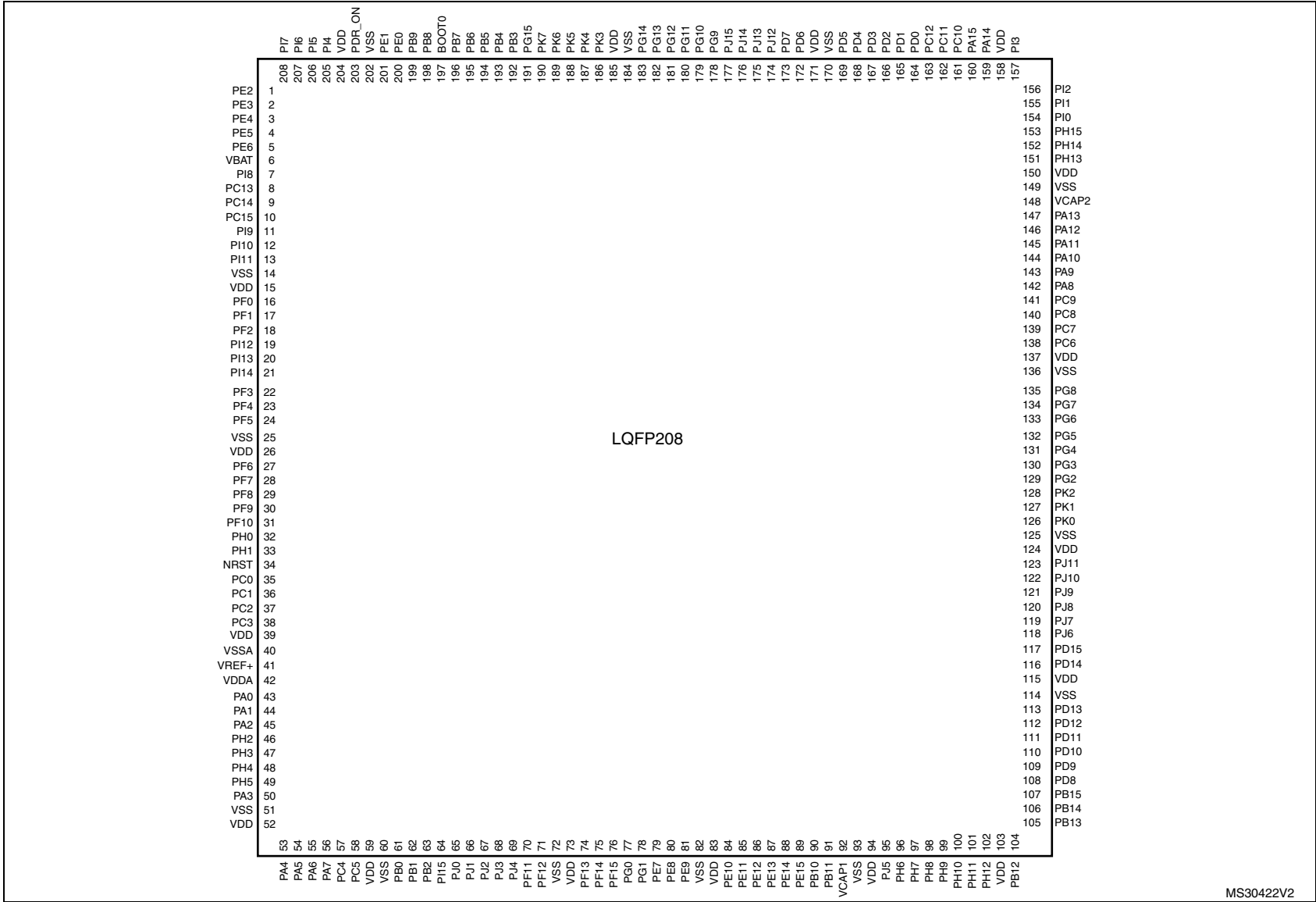
Figure 13. STM32F42x LQFP144 pinout



1. The above figure shows the package top view.



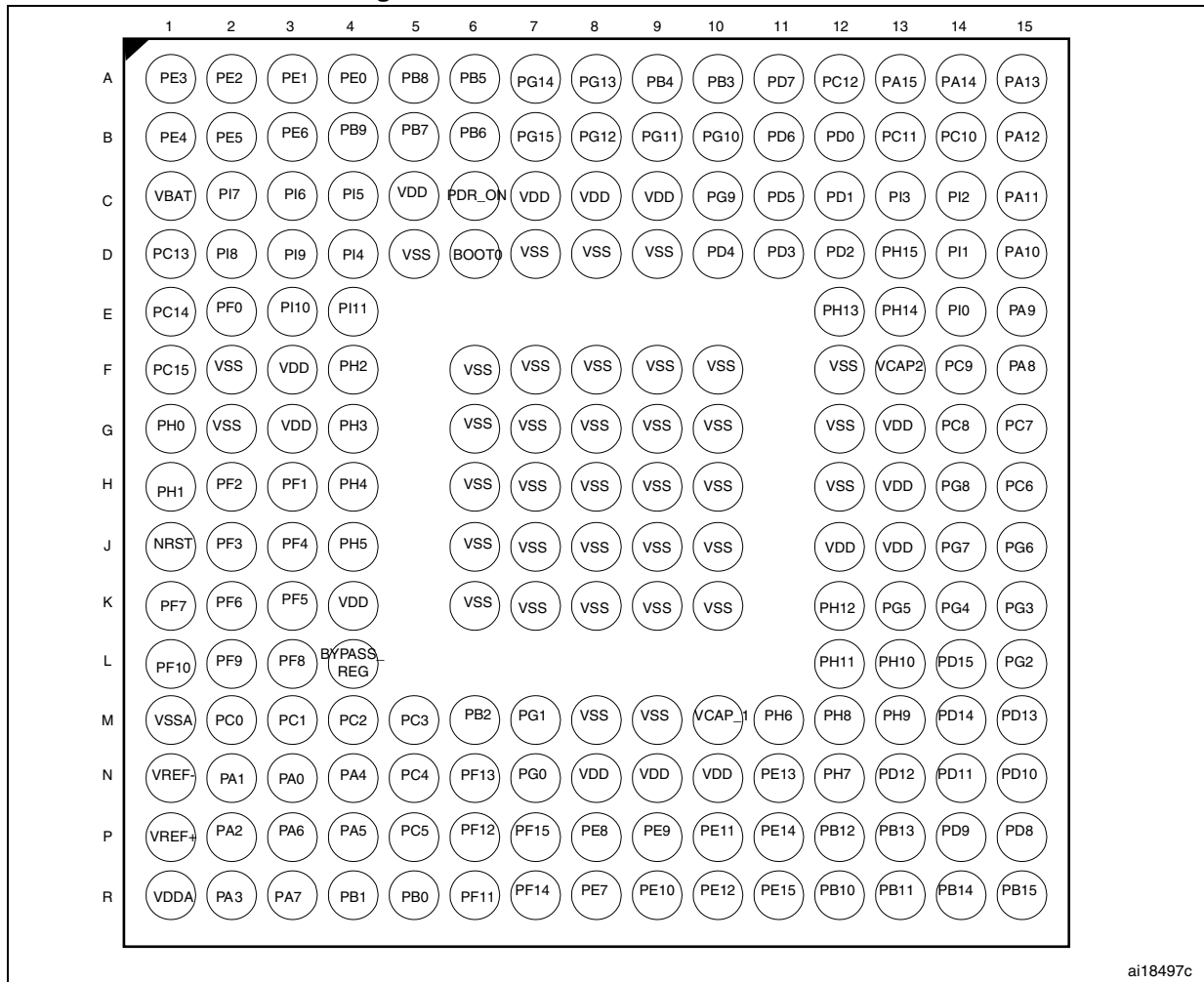
Figure 15. STM32F42x LQFP208 pinout



MS30422V2

1. The above figure shows the package top view.

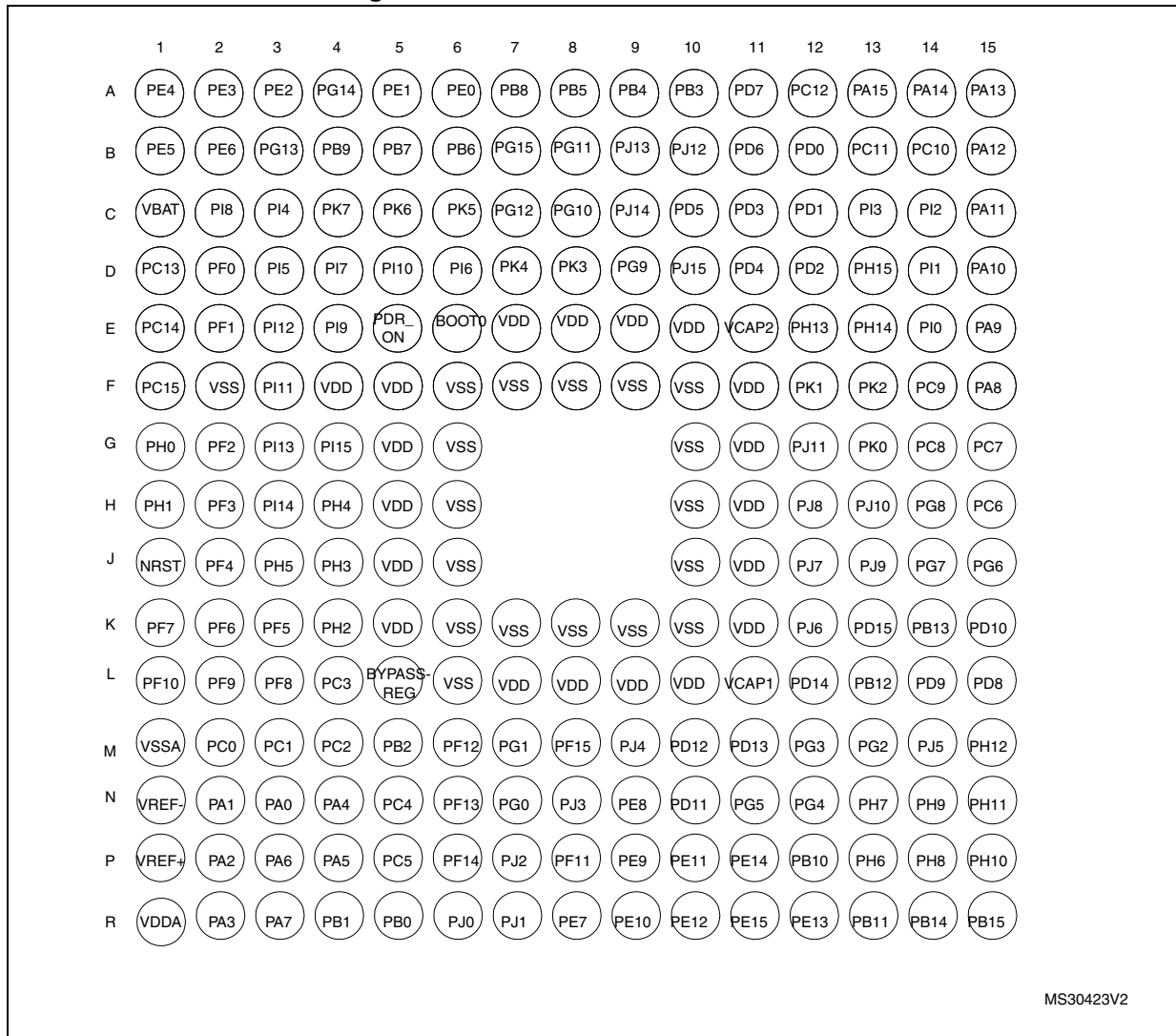
Figure 16. STM32F42x UFBGA176 ballout



ai18497c

1. The above figure shows the package top view.

Figure 17. STM32F42x TFBGA216 ballout



MS30423V2

1. The above figure shows the package top view.

Table 9. Legend/abbreviations used in the pinout table

Name	Abbreviation	Definition
Pin name	Unless otherwise specified in brackets below the pin name, the pin function during and after reset is the same as the actual pin name	
Pin type	S	Supply pin
	I	Input only pin
	I/O	Input / output pin
I/O structure	FT	5 V tolerant I/O
	TTa	3.3 V tolerant I/O directly connected to ADC
	B	Dedicated BOOT0 pin
	RST	Bidirectional reset pin with embedded weak pull-up resistor
Notes	Unless otherwise specified by a note, all I/Os are set as floating inputs during and after reset	
Alternate functions	Functions selected through GPIOx_AFR registers	
Additional functions	Functions directly selected/enabled through peripheral registers	

Table 10. STM32F427xx and STM32F429xx pin and ball definitions

Pin number							Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	UFBGA176	LQFP176	WLCSP143	LQFP208	TFBGA216						
1	1	A2	1	D8	1	A3	PE2	I/O	FT		TRACECLK, SPI4_SCK, SAI1_MCLK_A, ETH_MII_TXD3, FMC_A23, EVENTOUT	
2	2	A1	2	C10	2	A2	PE3	I/O	FT		TRACED0, SAI1_SD_B, FMC_A19, EVENTOUT	
3	3	B1	3	B11	3	A1	PE4	I/O	FT		TRACED1, SPI4_NSS, SAI1_FS_A, FMC_A20, DCMI_D4, LCD_B0, EVENTOUT	

Table 10. STM32F427xx and STM32F429xx pin and ball definitions (continued)

Pin number							Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	UFBGA176	LQFP176	WLCSP143	LQFP208	TFBGA216						
4	4	B2	4	D9	4	B1	PE5	I/O	FT		TRACED2, TIM9_CH1, SPI4_MISO, SAI1_SCK_A, FMC_A21, DCMI_D6, LCD_G0, EVENTOUT	
5	5	B3	5	E8	5	B2	PE6	I/O	FT		TRACED3, TIM9_CH2, SPI4_MOSI, SAI1_SD_A, FMC_A22, DCMI_D7, LCD_G1, EVENTOUT	
-	-	-	-	-	-	G6	V _{SS}	S				
-	-	-	-	-	-	F5	V _{DD}	S				
6	6	C1	6	C11	6	C1	V _{BAT}	S				
-	-	D2	7	-	7	C2	PI8	I/O	FT	(2) (3)	EVENTOUT	TAMP_2
7	7	D1	8	D10	8	D1	PC13	I/O	FT	(2) (3)	EVENTOUT	TAMP_1
8	8	E1	9	D11	9	E1	PC14- OSC32_IN (PC14)	I/O	FT	(2) (3)	EVENTOUT	OSC32_IN ⁽⁴⁾
9	9	F1	10	E11	10	F1	PC15- OSC32_OUT (PC15)	I/O	FT	(2) (3)	EVENTOUT	OSC32_OUT ⁽⁴⁾
-	-	-	-	-	-	G5	V _{DD}	S				
-	-	D3	11	-	11	E4	PI9	I/O	FT		CAN1_RX, FMC_D30, LCD_VSYNC, EVENTOUT	
-	-	E3	12	-	12	D5	PI10	I/O	FT		ETH_MII_RX_ER, FMC_D31, LCD_HSYNC, EVENTOUT	
-	-	E4	13	-	13	F3	PI11	I/O	FT		OTG_HS_ULPI_DIR, EVENTOUT	
-	-	F2	14	E7	14	F2	V _{SS}	S				
-	-	F3	15	E10	15	F4	V _{DD}	S				
-	10	E2	16	F11	16	D2	PF0	I/O	FT		I2C2_SDA, FMC_A0, EVENTOUT	

Table 10. STM32F427xx and STM32F429xx pin and ball definitions (continued)

Pin number							Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	UFBGA176	LQFP176	WLCSP143	LQFP208	TFBGA216						
-	11	H3	17	E9	17	E2	PF1	I/O	FT		I2C2_SCL, FMC_A1, EVENTOUT	
-	12	H2	18	F10	18	G2	PF2	I/O	FT		I2C2_SMBA, FMC_A2, EVENTOUT	
-	-	-	-	-	19	E3	PI12	I/O	FT		LCD_HSYNC, EVENTOUT	
-	-	-	-	-	20	G3	PI13	I/O	FT		LCD_VSYNC, EVENTOUT	
-	-	-	-	-	21	H3	PI14	I/O	FT		LCD_CLK, EVENTOUT	
-	13	J2	19	G11	22	H2	PF3	I/O	FT	(4)	FMC_A3, EVENTOUT	ADC3_IN9
-	14	J3	20	F9	23	J2	PF4	I/O	FT	(4)	FMC_A4, EVENTOUT	ADC3_IN14
-	15	K3	21	F8	24	K3	PF5	I/O	FT	(4)	FMC_A5, EVENTOUT	ADC3_IN15
10	16	G2	22	H7	25	H6	V _{SS}	S				
11	17	G3	23	-	26	H5	V _{DD}	S				
-	18	K2	24	G10	27	K2	PF6	I/O	FT	(4)	TIM10_CH1, SPI5_NSS, SAI1_SD_B, UART7_Rx, FMC_NIORD, EVENTOUT	ADC3_IN4
-	19	K1	25	F7	28	K1	PF7	I/O	FT	(4)	TIM11_CH1, SPI5_SCK, SAI1_MCLK_B, UART7_Tx, FMC_NREG, EVENTOUT	ADC3_IN5
-	20	L3	26	H11	29	L3	PF8	I/O	FT	(4)	SPI5_MISO, SAI1_SCK_B, TIM13_CH1, FMC_NIOWR, EVENTOUT	ADC3_IN6
-	21	L2	27	G8	30	L2	PF9	I/O	FT	(4)	SPI5_MOSI, SAI1_FS_B, TIM14_CH1, FMC_CD, EVENTOUT	ADC3_IN7
-	22	L1	28	G9	31	L1	PF10	I/O	FT	(4)	FMC_INTR, DCMI_D11, LCD_DE, EVENTOUT	ADC3_IN8
12	23	G1	29	J11	32	G1	PH0-OSC_IN (PH0)	I/O	FT		EVENTOUT	OSC_IN ⁽⁴⁾

Table 10. STM32F427xx and STM32F429xx pin and ball definitions (continued)

Pin number							Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	UFBGA176	LQFP176	WLCSP143	LQFP208	TFBGA216						
13	24	H1	30	H10	33	H1	PH1-OSC_OUT (PH1)	I/O	FT		EVENTOUT	OSC_OUT ⁽⁴⁾
14	25	J1	31	H9	34	J1	NRST	I/O	RST			
15	26	M2	32	H8	35	M2	PC0	I/O	FT	(4)	OTG_HS_ULPI_STP, FMC_SDNWE, EVENTOUT	ADC123_IN10
16	27	M3	33	K11	36	M3	PC1	I/O	FT	(4)	ETH_MDC, EVENTOUT	ADC123_IN11
17	28	M4	34	J10	37	M4	PC2	I/O	FT	(4)	SPI2_MISO, I2S2ext_SD, OTG_HS_ULPI_DIR, ETH_MII_TXD2, FMC_SDNE0, EVENTOUT	ADC123_IN12
18	29	M5	35	J9	38	L4	PC3	I/O	FT	(4)	SPI2_MOSI/I2S2_SD, OTG_HS_ULPI_NXT, ETH_MII_TX_CLK, FMC_SDCKE0, EVENTOUT	ADC123_IN13
19	30	-	36	G7	39	J5	V _{DD}	S				
-	-	-	-	-	-	J6	V _{SS}	S				
20	31	M1	37	K10	40	M1	V _{SSA}	S				
-	-	N1	-	-	-	N1	V _{REF-}	S				
21	32	P1	38	L11	41	P1	V _{REF+}	S				
22	33	R1	39	L10	42	R1	V _{DDA}	S				
23	34	N3	40	K9	43	N3	PA0-WKUP (PA0)	I/O	FT	(5)	TIM2_CH1/TIM2_ETR, TIM5_CH1, TIM8_ETR, USART2_CTS, UART4_TX, ETH_MII_CRS, EVENTOUT	ADC123_IN0/WKUP ⁽⁴⁾

Table 10. STM32F427xx and STM32F429xx pin and ball definitions (continued)

Pin number							Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	UFBGA176	LQFP176	WLCSP143	LQFP208	TFBGA216						
24	35	N2	41	K8	44	N2	PA1	I/O	FT	(4)	TIM2_CH2, TIM5_CH2, USART2_RTS, UART4_RX, ETH_MII_RX_CLK/ETH_RMII_REF_CLK, EVENTOUT	ADC123_IN1
25	36	P2	42	L9	45	P2	PA2	I/O	FT	(4)	TIM2_CH3, TIM5_CH3, TIM9_CH1, USART2_TX, ETH_MDIO, EVENTOUT	ADC123_IN2
-	-	F4	43	-	46	K4	PH2	I/O	FT		ETH_MII_CRD, FMC_SDCKE0, LCD_R0, EVENTOUT	
-	-	G4	44	-	47	J4	PH3	I/O	FT		ETH_MII_COL, FMC_SDNE0, LCD_R1, EVENTOUT	
-	-	H4	45	-	48	H4	PH4	I/O	FT		I2C2_SCL, OTG_HS_ULPI_NXT, EVENTOUT	
-	-	J4	46	-	49	J3	PH5	I/O	FT		I2C2_SDA, SPI5_NSS, FMC_SDNWE, EVENTOUT	
26	37	R2	47	M11	50	R2	PA3	I/O	FT	(4)	TIM2_CH4, TIM5_CH4, TIM9_CH2, USART2_RX, OTG_HS_ULPI_D0, ETH_MII_COL, LCD_B5, EVENTOUT	ADC123_IN3
27	38	-		-	51	K6	V _{SS}	S				
-	-	L4	48	N11	-	L5	BYPASS_REG	I	FT			
28	39	K4	49	J8	52	K5	V _{DD}	S				
29	40	N4	50	M10	53	N4	PA4	I/O	TC	(4)	SPI1_NSS, SPI3_NSS/I2S3_WS, USART2_CK, OTG_HS_SOF, DCMI_HSYNC, LCD_VSYNC, EVENTOUT	ADC12_IN4 /DAC_OUT1

Table 10. STM32F427xx and STM32F429xx pin and ball definitions (continued)

Pin number							Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	UFBGA176	LQFP176	WLCSP143	LQFP208	TFBGA216						
30	41	P4	51	M9	54	P4	PA5	I/O	TC	(4)	TIM2_CH1/TIM2_ETR, TIM8_CH1N, SPI1_SCK, OTG_HS_ULPI_CK, EVENTOUT	ADC12_IN5/ DAC_OUT2
31	42	P3	52	N10	55	P3	PA6	I/O	FT	(4)	TIM1_BKIN, TIM3_CH1, TIM8_BKIN, SPI1_MISO, TIM13_CH1, DCMI_PIXCLK, LCD_G2, EVENTOUT	ADC12_IN6
32	43	R3	53	L8	56	R3	PA7	I/O	FT	(4)	TIM1_CH1N, TIM3_CH2, TIM8_CH1N, SPI1_MOSI, TIM14_CH1, ETH_MII_RX_DV/ETH_R MII_CRS_DV, EVENTOUT	ADC12_IN7
33	44	N5	54	M8	57	N5	PC4	I/O	FT	(4)	ETH_MII_RXD0/ETH_RM II_RXD0, EVENTOUT	ADC12_IN14
34	45	P5	55	N9	58	P5	PC5	I/O	FT	(4)	ETH_MII_RXD1/ETH_RM II_RXD1, EVENTOUT	ADC12_IN15
-	-	-	-	J7	59	L7	V _{DD}	S				
-	-	-	-	-	60	L6	VSS	S				
35	46	R5	56	N8	61	R5	PB0	I/O	FT	(4)	TIM1_CH2N, TIM3_CH3, TIM8_CH2N, LCD_R3, OTG_HS_ULPI_D1, ETH_MII_RXD2, EVENTOUT	ADC12_IN8
36	47	R4	57	K7	62	R4	PB1	I/O	FT	(4)	TIM1_CH3N, TIM3_CH4, TIM8_CH3N, LCD_R6, OTG_HS_ULPI_D2, ETH_MII_RXD3, EVENTOUT	ADC12_IN9
37	48	M6	58	L7	63	M5	PB2-BOOT1 (PB2)	I/O	FT		EVENTOUT	
-	-	-	-	-	64	G4	PI15	I/O	FT		LCD_R0, EVENTOUT	
-	-	-	-	-	65	R6	PJ0	I/O	FT		LCD_R1, EVENTOUT	
-	-	-	-	-	66	R7	PJ1	I/O	FT		LCD_R2, EVENTOUT	

Table 10. STM32F427xx and STM32F429xx pin and ball definitions (continued)

Pin number							Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	UFBGA176	LQFP176	WLCSP143	LQFP208	TFBGA216						
-	-	-	-	-	67	P7	PJ2	I/O	FT		LCD_R3, EVENTOUT	
-	-	-	-	-	68	N8	PJ3	I/O	FT		LCD_R4, EVENTOUT	
-	-	-	-	-	69	M9	PJ4	I/O	FT		LCD_R5, EVENTOUT	
-	49	R6	59	M7	70	P8	PF11	I/O	FT		SPI5_MOSI, FMC_SDNRAS, DCMI_D12, EVENTOUT	
-	50	P6	60	N7	71	M6	PF12	I/O	FT		FMC_A6, EVENTOUT	
-	51	M8	61	-	72	K7	V _{SS}	S				
-	52	N8	62	-	73	L8	V _{DD}	S				
-	53	N6	63	K6	74	N6	PF13	I/O	FT		FMC_A7, EVENTOUT	
-	54	R7	64	L6	75	P6	PF14	I/O	FT		FMC_A8, EVENTOUT	
-	55	P7	65	M6	76	M8	PF15	I/O	FT		FMC_A9, EVENTOUT	
-	56	N7	66	N6	77	N7	PG0	I/O	FT		FMC_A10, EVENTOUT	
-	57	M7	67	K5	78	M7	PG1	I/O	FT		FMC_A11, EVENTOUT	
38	58	R8	68	L5	79	R8	PE7	I/O	FT		TIM1_ETR, UART7_Rx, FMC_D4, EVENTOUT	
39	59	P8	69	M5	80	N9	PE8	I/O	FT		TIM1_CH1N, UART7_Tx, FMC_D5, EVENTOUT	
40	60	P9	70	N5	81	P9	PE9	I/O	FT		TIM1_CH1, FMC_D6, EVENTOUT	
-	61	M9	71	H3	82	K8	V _{SS}	S				
-	62	N9	72	J5	83	L9	V _{DD}	S				
41	63	R9	73	J4	84	R9	PE10	I/O	FT		TIM1_CH2N, FMC_D7, EVENTOUT	
42	64	P10	74	K4	85	P10	PE11	I/O	FT		TIM1_CH2, SPI4_NSS, FMC_D8, LCD_G3, EVENTOUT	
43	65	R10	75	L4	86	R10	PE12	I/O	FT		TIM1_CH3N, SPI4_SCK, FMC_D9, LCD_B4, EVENTOUT	

Table 10. STM32F427xx and STM32F429xx pin and ball definitions (continued)

Pin number							Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	UFBGA176	LQFP176	WLCSP143	LQFP208	TFBGA216						
44	66	N11	76	N4	87	R12	PE13	I/O	FT		TIM1_CH3, SPI4_MISO, FMC_D10, LCD_DE, EVENTOUT	
45	67	P11	77	M4	88	P11	PE14	I/O	FT		TIM1_CH4, SPI4_MOSI, FMC_D11, LCD_CLK, EVENTOUT	
46	68	R11	78	L3	89	R11	PE15	I/O	FT		TIM1_BKIN, FMC_D12, LCD_R7, EVENTOUT	
47	69	R12	79	M3	90	P12	PB10	I/O	FT		TIM2_CH3, I2C2_SCL, SPI2_SCK/I2S2_CK, USART3_TX, OTG_HS_ULPI_D3, ETH_MII_RX_ER, LCD_G4, EVENTOUT	
48	70	R13	80	N3	91	R13	PB11	I/O	FT		TIM2_CH4, I2C2_SDA, USART3_RX, OTG_HS_ULPI_D4, ETH_MII_TX_EN/ETH_R MII_TX_EN, LCD_G5, EVENTOUT	
49	71	M10	81	N2	92	L11	V _{CAP_1}	S				
-	-	-	-	H2	93	K9	V _{SS}	S				
50	72	N10	82	J6	94	L10	V _{DD}	S				
-	-	-	-	-	95	M14	PJ5	I/O			LCD_R6, EVENTOUT	
-	-	M11	83	-	96	P13	PH6	I/O	FT		I2C2_SMBA, SPI5_SCK, TIM12_CH1, ETH_MII_RXD2, FMC_SDNE1, DCMI_D8, EVENTOUT	
-	-	N12	84	-	97	N13	PH7	I/O	FT		I2C3_SCL, SPI5_MISO, ETH_MII_RXD3, FMC_SDCKE1, DCMI_D9, EVENTOUT	
-	-	M12	85	-	98	P14	PH8	I/O	FT		I2C3_SDA, FMC_D16, DCMI_HSYNC, LCD_R2, EVENTOUT	

Table 10. STM32F427xx and STM32F429xx pin and ball definitions (continued)

Pin number							Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	UFBGA176	LQFP176	WLCSP143	LQFP208	TFBGA216						
-	-	M13	86	-	99	N14	PH9	I/O	FT		I2C3_SMBA, TIM12_CH2, FMC_D17, DCMI_D0, LCD_R3, EVENTOUT	
-	-	L13	87	-	100	P15	PH10	I/O	FT		TIM5_CH1, FMC_D18, DCMI_D1, LCD_R4, EVENTOUT	
-	-	L12	88	-	101	N15	PH11	I/O	FT		TIM5_CH2, FMC_D19, DCMI_D2, LCD_R5, EVENTOUT	
-	-	K12	89	-	102	M15	PH12	I/O	FT		TIM5_CH3, FMC_D20, DCMI_D3, LCD_R6, EVENTOUT	
-	-	H12	90	-	-	K10	V _{SS}	S				
-	-	J12	91	-	103	K11	V _{DD}	S				
51	73	P12	92	M2	104	L13	PB12	I/O	FT		TIM1_BKIN, I2C2_SMBA, SPI2_NSS/I2S2_WS, USART3_CK, CAN2_RX, OTG_HS_ULPI_D5, ETH_MII_TXD0/ETH_RMII_TXD0, OTG_HS_ID, EVENTOUT	
52	74	P13	93	N1	105	K14	PB13	I/O	FT		TIM1_CH1N, SPI2_SCK/I2S2_CK, USART3_CTS, CAN2_TX, OTG_HS_ULPI_D6, ETH_MII_TXD1/ETH_RMII_TXD1, EVENTOUT	OTG_HS_VBUS
53	75	R14	94	K3	106	R14	PB14	I/O	FT		TIM1_CH2N, TIM8_CH2N, SPI2_MISO, I2S2ext_SD, USART3_RTS, TIM12_CH1, OTG_HS_DM, EVENTOUT	

Table 10. STM32F427xx and STM32F429xx pin and ball definitions (continued)

Pin number							Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	UFBGA176	LQFP176	WLCSP143	LQFP208	TFBGA216						
54	76	R15	95	J3	107	R15	PB15	I/O	FT		RTC_REFIN, TIM1_CH3N, TIM8_CH3N, SPI2_MOSI/I2S2_SD, TIM12_CH2, OTG_HS_DP, EVENTOUT	
55	77	P15	96	L2	108	L15	PD8	I/O	FT		USART3_TX, FMC_D13, EVENTOUT	
56	78	P14	97	M1	109	L14	PD9	I/O	FT		USART3_RX, FMC_D14, EVENTOUT	
57	79	N15	98	H4	110	K15	PD10	I/O	FT		USART3_CK, FMC_D15, LCD_B3, EVENTOUT	
58	80	N14	99	K2	111	N10	PD11	I/O	FT		USART3_CTS, FMC_A16, EVENTOUT	
59	81	N13	100	H6	112	M10	PD12	I/O	FT		TIM4_CH1, USART3_RTS, FMC_A17, EVENTOUT	
60	82	M15	101	H5	113	M11	PD13	I/O	FT		TIM4_CH2, FMC_A18, EVENTOUT	
-	83	-	102	-	114	J10	V _{SS}	S				
-	84	J13	103	L1	115	J11	V _{DD}	S				
61	85	M14	104	J2	116	L12	PD14	I/O	FT		TIM4_CH3, FMC_D0, EVENTOUT	
62	86	L14	105	K1	117	K13	PD15	I/O	FT		TIM4_CH4, FMC_D1, EVENTOUT	
-	-	-	-	-	118	K12	PJ6	I/O	FT		LCD_R7, EVENTOUT	
-	-	-	-	-	119	J12	PJ7	I/O	FT		LCD_G0, EVENTOUT	
-	-	-	-	-	120	H12	PJ8	I/O	FT		LCD_G1, EVENTOUT	
-	-	-	-	-	121	J13	PJ9	I/O	FT		LCD_G2, EVENTOUT	
-	-	-	-	-	122	H13	PJ10	I/O	FT		LCD_G3, EVENTOUT	
-	-	-	-	-	123	G12	PJ11	I/O	FT		LCD_G4, EVENTOUT	
-	-	-	-	-	124	H11	VDD	I/O	FT			

Table 10. STM32F427xx and STM32F429xx pin and ball definitions (continued)

Pin number							Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	UFBGA176	LQFP176	WLCSP143	LQFP208	TFBGA216						
-	-	-	-	-	125	H10	VSS	I/O	FT			
-	-	-	-	-	126	G13	PK0	I/O	FT		LCD_G5, EVENTOUT	
-	-	-	-	-	127	F12	PK1	I/O	FT		LCD_G6, EVENTOUT	
-	-	-	-	-	128	F13	PK2	I/O	FT		LCD_G7, EVENTOUT	
-	87	L15	106	J1	129	M13	PG2	I/O	FT		FMC_A12, EVENTOUT	
-	88	K15	107	G3	130	M12	PG3	I/O	FT		FMC_A13, EVENTOUT	
-	89	K14	108	G5	131	N12	PG4	I/O	FT		FMC_A14/FMC_BA0, EVENTOUT	
-	90	K13	109	G6	132	N11	PG5	I/O	FT		FMC_A15/FMC_BA1, EVENTOUT	
-	91	J15	110	G4	133	J15	PG6	I/O	FT		FMC_INT2, DCMI_D12, LCD_R7, EVENTOUT	
-	92	J14	111	H1	134	J14	PG7	I/O	FT		USART6_CK, FMC_INT3, DCMI_D13, LCD_CLK, EVENTOUT	
-	93	H14	112	G2	135	H14	PG8	I/O	FT		SPI6_NSS, USART6_RTS, ETH_PPS_OUT, FMC_SDCLK, EVENTOUT	
-	94	G12	113	D2	136	G10	V _{SS}	S				
-	95	H13	114	G1	137	G11	V _{DD}	S				
63	96	H15	115	F2	138	H15	PC6	I/O	FT		TIM3_CH1, TIM8_CH1, I2S2_MCK, USART6_TX, SDIO_D6, DCMI_D0, LCD_HSYNC, EVENTOUT	
64	97	G15	116	F3	139	G15	PC7	I/O	FT		TIM3_CH2, TIM8_CH2, I2S3_MCK, USART6_RX, SDIO_D7, DCMI_D1, LCD_G6, EVENTOUT	
65	98	G14	117	E4	140	G14	PC8	I/O	FT		TIM3_CH3, TIM8_CH3, USART6_CK, SDIO_D0, DCMI_D2, EVENTOUT	

Table 10. STM32F427xx and STM32F429xx pin and ball definitions (continued)

Pin number							Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	UFBGA176	LQFP176	WLCSP143	LQFP208	TFBGA216						
66	99	F14	118	E3	141	F14	PC9	I/O	FT		MCO2, TIM3_CH4, TIM8_CH4, I2C3_SDA, I2S_CKIN, SDIO_D1, DCMI_D3, EVENTOUT	
67	100	F15	119	F1	142	F15	PA8	I/O	FT		MCO1, TIM1_CH1, I2C3_SCL, USART1_CK, OTG_FS_SOF, LCD_R6, EVENTOUT	
68	101	E15	120	E2	143	E15	PA9	I/O	FT		TIM1_CH2, I2C3_SMBA, USART1_TX, DCMI_D0, EVENTOUT	OTG_FS_VBUS
69	102	D15	121	D5	144	D15	PA10	I/O	FT		TIM1_CH3, USART1_RX, OTG_FS_ID, DCMI_D1, EVENTOUT	
70	103	C15	122	D4	145	C15	PA11	I/O	FT		TIM1_CH4, USART1_CTS, CAN1_RX, LCD_R4, OTG_FS_DM, EVENTOUT	
71	104	B15	123	E1	146	B15	PA12	I/O	FT		TIM1_ETR, USART1 RTS, CAN1_TX, LCD_R5, OTG_FS_DP, EVENTOUT	
72	105	A15	124	D3	147	A15	PA13 (JTMS-SWDIO)	I/O	FT		JTMS-SWDIO, EVENTOUT	
73	106	F13	125	D1	148	E11	V _{CAP_2}	S				
74	107	F12	126	D2	149	F10	V _{SS}	S				
75	108	G13	127	C1	150	F11	V _{DD}	S				
-	-	E12	128	-	151	E12	PH13	I/O	FT		TIM8_CH1N, CAN1_TX, FMC_D21, LCD_G2, EVENTOUT	
-	-	E13	129	-	152	E13	PH14	I/O	FT		TIM8_CH2N, FMC_D22, DCMI_D4, LCD_G3, EVENTOUT	

Table 10. STM32F427xx and STM32F429xx pin and ball definitions (continued)

Pin number							Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	UFBGA176	LQFP176	WLCSP143	LQFP208	TFBGA216						
-	-	D13	130	-	153	D13	PH15	I/O	FT		TIM8_CH3N, FMC_D23, DCMI_D11, LCD_G4, EVENTOUT	
-	-	E14	131	-	154	E14	PI0	I/O	FT		TIM5_CH4, SPI2_NSS/I2S2_WS ⁽⁶⁾ , FMC_D24, DCMI_D13, LCD_G5, EVENTOUT	
-	-	D14	132	-	155	D14	PI1	I/O	FT		SPI2_SCK/I2S2_CK ⁽⁶⁾ , FMC_D25, DCMI_D8, LCD_G6, EVENTOUT	
-	-	C14	133	-	156	C14	PI2	I/O	FT		TIM8_CH4, SPI2_MISO, I2S2ext_SD, FMC_D26, DCMI_D9, LCD_G7, EVENTOUT	
-	-	C13	134	-	157	C13	PI3	I/O	FT		TIM8_ETR, SPI2_MOSI/I2S2_SD, FMC_D27, DCMI_D10, EVENTOUT	
-	-	D9	135	F5	-	F9	V _{SS}	S				
-	-	C9	136	A1	158	E10	V _{DD}	S				
76	109	A14	137	B1	159	A14	PA14 (JTCK-SWCLK)	I/O	FT		JTCK-SWCLK/ EVENTOUT	
77	110	A13	138	C2	160	A13	PA15 (JTDI)	I/O	FT		JTDI, TIM2_CH1/TIM2_ETR, SPI1_NSS, SPI3_NSS/I2S3_WS, EVENTOUT	
78	111	B14	139	A2	161	B14	PC10	I/O	FT		SPI3_SCK/I2S3_CK, USART3_TX, UART4_TX, SDIO_D2, DCMI_D8, LCD_R2, EVENTOUT	
79	112	B13	140	B2	162	B13	PC11	I/O	FT		I2S3ext_SD, SPI3_MISO, USART3_RX, UART4_RX, SDIO_D3, DCMI_D4, EVENTOUT	

Table 10. STM32F427xx and STM32F429xx pin and ball definitions (continued)

Pin number							Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	UFBGA176	LQFP176	WLCSP143	LQFP208	TFBGA216						
80	113	A12	141	C3	163	A12	PC12	I/O	FT		SPI3_MOSI/I2S3_SD, USART3_CK, UART5_TX, SDIO_CK, DCMI_D9, EVENTOUT	
81	114	B12	142	B3	164	B12	PD0	I/O	FT		CAN1_RX, FMC_D2, EVENTOUT	
82	115	C12	143	C4	165	C12	PD1	I/O	FT		CAN1_TX, FMC_D3, EVENTOUT	
83	116	D12	144	A3	166	D12	PD2	I/O	FT		TIM3_ETR, UART5_RX, SDIO_CMD, DCMI_D11, EVENTOUT	
84	117	D11	145	B4	167	C11	PD3	I/O	FT		SPI2_SCK/I2S2_CK, USART2_CTS, FMC_CLK, DCMI_D5, LCD_G7, EVENTOUT	
85	118	D10	146	B5	168	D11	PD4	I/O	FT		USART2_RTS, FMC_NOE, EVENTOUT	
86	119	C11	147	A4	169	C10	PD5	I/O	FT		USART2_TX, FMC_NWE, EVENTOUT	
-	120	D8	148	-	170	F8	V _{SS}	S				
-	121	C8	149	C5	171	E9	V _{DD}	S				
87	122	B11	150	F4	172	B11	PD6	I/O	FT		SPI3_MOSI/I2S3_SD, SAI1_SD_A, USART2_RX, FMC_NWAIT, DCMI_D10, LCD_B2, EVENTOUT	
88	123	A11	151	A5	173	A11	PD7	I/O	FT		USART2_CK, FMC_NE1/FMC_NCE2, EVENTOUT	
-	-	-	-	-	174	B10	PJ12	I/O	FT		LCD_B0, EVENTOUT	
-	-	-	-	-	175	B9	PJ13	I/O	FT		LCD_B1, EVENTOUT	
-	-	-	-	-	176	C9	PJ14	I/O	FT		LCD_B2, EVENTOUT	
-	-	-	-	-	177	D10	PJ15	I/O	FT		LCD_B3, EVENTOUT	

Table 10. STM32F427xx and STM32F429xx pin and ball definitions (continued)

Pin number							Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	UFBGA176	LQFP176	WLCSP143	LQFP208	TFBGA216						
-	124	C10	152	E5	178	D9	PG9	I/O	FT		USART6_RX, FMC_NE2/FMC_NCE3, EVENTOUT	
-	125	B10	153	C6	179	C8	PG10	I/O	FT		LCD_G3, FMC_NCE4_1/FMC_NE3, DCMI_D2, LCD_B2, EVENTOUT	
-	126	B9	154	B6	180	B8	PG11	I/O	FT		ETH_MII_TX_EN/ETH_R MII_TX_EN, FMC_NCE4_2, DCMI_D3, LCD_B3, EVENTOUT	
-	127	B8	155	A6	181	C7	PG12	I/O	FT		SPI6_MISO, USART6_RTS, LCD_B4, FMC_NE4, LCD_B1, EVENTOUT	
-	128	A8	156	D6	182	B3	PG13	I/O	FT		SPI6_SCK, USART6_CTS, ETH_MII_TXD0/ETH_RMI I_TXD0, FMC_A24, EVENTOUT	
-	129	A7	157	F6	183	A4	PG14	I/O	FT		SPI6_MOSI, USART6_TX, ETH_MII_TXD1/ETH_RMI I_TXD1, FMC_A25, EVENTOUT	
-	130	D7	158	-	184	F7	V _{SS}	S				
-	131	C7	159	E6	185	E8	V _{DD}	S				
-	-	-	-	-	186	D8	PK3	I/O	FT		LCD_B4, EVENTOUT	
-	-	-	-	-	187	D7	PK4	I/O	FT		LCD_B5, EVENTOUT	
-	-	-	-	-	188	C6	PK5	I/O	FT		LCD_B6, EVENTOUT	
-	-	-	-	-	189	C5	PK6	I/O	FT		LCD_B7, EVENTOUT	
-	-	-	-	-	190	C4	PK7	I/O	FT		LCD_DE, EVENTOUT	
-	132	B7	160	A7	191	B7	PG15	I/O	FT		USART6_CTS, FMC_SDNCAS, DCMI_D13, EVENTOUT	

Table 10. STM32F427xx and STM32F429xx pin and ball definitions (continued)

Pin number							Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	UFBGA176	LQFP176	WLCSP143	LQFP208	TFBGA216						
89	133	A10	161	B7	192	A10	PB3 (JTDO/TRACE SWO)	I/O	FT		JTDO/TRACESWO, TIM2_CH2, SPI1_SCK, SPI3_SCK/I2S3_CK, EVENTOUT	
90	134	A9	162	C7	193	A9	PB4 (NJTRST)	I/O	FT		NJTRST, TIM3_CH1, SPI1_MISO, SPI3_MISO, I2S3ext_SD, EVENTOUT	
91	135	A6	163	C8	194	A8	PB5	I/O	FT		TIM3_CH2, I2C1_SMBA, SPI1_MOSI, SPI3_MOSI/I2S3_SD, CAN2_RX, OTG_HS_ULPI_D7, ETH_PPS_OUT, FMC_SDCKE1, DCM1_D10, EVENTOUT	
92	136	B6	164	A8	195	B6	PB6	I/O	FT		TIM4_CH1, I2C1_SCL, USART1_TX, CAN2_TX, FMC_SDNE1, DCM1_D5, EVENTOUT	
93	137	B5	165	B8	196	B5	PB7	I/O	FT		TIM4_CH2, I2C1_SDA, USART1_RX, FMC_NL, DCM1_VSYNC, EVENTOUT	
94	138	D6	166	C9	197	E6	BOOT0	I	B			V _{PP}
95	139	A5	167	A9	198	A7	PB8	I/O	FT		TIM4_CH3, TIM10_CH1, I2C1_SCL, CAN1_RX, ETH_MII_TXD3, SDIO_D4, DCM1_D6, LCD_B6, EVENTOUT	
96	140	B4	168	B9	199	B4	PB9	I/O	FT		TIM4_CH4, TIM11_CH1, I2C1_SDA, SPI2_NSS/I2S2_WS, CAN1_TX, SDIO_D5, DCM1_D7, LCD_B7, EVENTOUT	
97	141	A4	169	B10	200	A6	PE0	I/O	FT		TIM4_ETR, UART8_RX, FMC_NBL0, DCM1_D2, EVENTOUT	

Table 10. STM32F427xx and STM32F429xx pin and ball definitions (continued)

Pin number							Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	UFBGA176	LQFP176	WLCSP143	LQFP208	TFBGA216						
98	142	A3	170	A10	201	A5	PE1	I/O	FT		UART8_Tx, FMC_NBL1, DCMI_D3, EVENTOUT	
99	-	D5	-	-	202	F6	V _{SS}	S				
-	143	C6	171	A11	203	E5	PDR_ON	S				
100	144	C5	172	D7	204	E7	V _{DD}	S				
-	-	D4	173	-	205	C3	PI4	I/O	FT		TIM8_BKIN, FMC_NBL2, DCMI_D5, LCD_B4, EVENTOUT	
-	-	C4	174	-	206	D3	PI5	I/O	FT		TIM8_CH1, FMC_NBL3, DCMI_VSYNC, LCD_B5, EVENTOUT	
-	-	C3	175	-	207	D6	PI6	I/O	FT		TIM8_CH2, FMC_D28, DCMI_D6, LCD_B6, EVENTOUT	
-	-	C2	176	-	208	D4	PI7	I/O	FT		TIM8_CH3, FMC_D29, DCMI_D7, LCD_B7, EVENTOUT	

- Function availability depends on the chosen device.
- PC13, PC14, PC15 and PI8 are supplied through the power switch. Since the switch only sinks a limited amount of current (3 mA), the use of GPIOs PC13 to PC15 and PI8 in output mode is limited:
 - The speed should not exceed 2 MHz with a maximum load of 30 pF.
 - These I/Os must not be used as a current source (e.g. to drive an LED).
- Main function after the first backup domain power-up. Later on, it depends on the contents of the RTC registers even after reset (because these registers are not reset by the main reset). For details on how to manage these I/Os, refer to the RTC register description sections in the STM32F4xx reference manual, available from the STMicroelectronics website: www.st.com.
- FT = 5 V tolerant except when in analog mode or oscillator mode (for PC14, PC15, PH0 and PH1).
- If the device is delivered in an UFBGA176, LQFP176 or TFBGA216 package, and the BYPASS_REG pin is set to V_{DD} (Regulator OFF/internal reset ON mode), then PA0 is used as an internal Reset (active low).
- PI0 and PI1 cannot be used for I2S2 full-duplex mode.

Table 11. FMC pin definition

Pin name	CF	NOR/PSRAM/ SRAM	NOR/PSRAM Mux	NAND16	SDRAM
PF0	A0	A0			A0
PF1	A1	A1			A1
PF2	A2	A2			A2
PF3	A3	A3			A3
PF4	A4	A4			A4
PF5	A5	A5			A5
PF12	A6	A6			A6
PF13	A7	A7			A7
PF14	A8	A8			A8
PF15	A9	A9			A9
PG0	A10	A10			A10
PG1		A11			A11
PG2		A12			A12
PG3		A13			
PG4		A14			BA0
PG5		A15			BA1
PD11		A16	A16	CLE	
PD12		A17	A17	ALE	
PD13		A18	A18		
PE3		A19	A19		
PE4		A20	A20		
PE5		A21	A21		
PE6		A22	A22		
PE2		A23	A23		
PG13		A24	A24		
PG14		A25	A25		
PD14	D0	D0	DA0	D0	D0
PD15	D1	D1	DA1	D1	D1
PD0	D2	D2	DA2	D2	D2
PD1	D3	D3	DA3	D3	D3
PE7	D4	D4	DA4	D4	D4
PE8	D5	D5	DA5	D5	D5
PE9	D6	D6	DA6	D6	D6
PE10	D7	D7	DA7	D7	D7

Table 11. FMC pin definition (continued)

Pin name	CF	NOR/PSRAM/ SRAM	NOR/PSRAM Mux	NAND16	SDRAM
PE11	D8	D8	DA8	D8	D8
PE12	D9	D9	DA9	D9	D9
PE13	D10	D10	DA10	D10	D10
PE14	D11	D11	DA11	D11	D11
PE15	D12	D12	DA12	D12	D12
PD8	D13	D13	DA13	D13	D13
PD9	D14	D14	DA14	D14	D14
PD10	D15	D15	DA15	D15	D15
PH8		D16			D16
PH9		D17			D17
PH10		D18			D18
PH11		D19			D19
PH12		D20			D20
PH13		D21			D21
PH14		D22			D22
PH15		D23			D23
PI0		D24			D24
PI1		D25			D25
PI2		D26			D26
PI3		D27			D27
PI6		D28			D28
PI7		D29			D29
PI9		D30			D30
PI10		D31			D31
PD7		NE1	NE1	NCE2	
PG9		NE2	NE2	NCE3	
PG10	NCE4_1	NE3	NE3		
PG11	NCE4_2				
PG12		NE4	NE4		
PD3		CLK	CLK		
PD4	NOE	NOE	NOE	NOE	
PD5	NWE	NWE	NWE	NWE	
PD6	NWAIT	NWAIT	NWAIT	NWAIT	
PB7		NADV	NADV		

Table 11. FMC pin definition (continued)

Pin name	CF	NOR/PSRAM/ SRAM	NOR/PSRAM Mux	NAND16	SDRAM
PF6	NIORD				
PF7	NREG				
PF8	NIOWR				
PF9	CD				
PF10	INTR				
PG6				INT2	
PG7				INT3	
PE0		NBL0	NBL0		NBL0
PE1		NBL1	NBL1		NBL1
PI4		NBL2			NBL2
PI5		NBL3			NBL3
PG8					SDCLK
PC0					SDNWE
PF11					SDNRAS
PG15					SDNCAS
PH2					SDCKE0
PH3					SDNE0
PH6					SDNE1
PH7					SDCKE1
PH5					SDNWE
PC2					SDNE0
PC3					SDCKE0
PB5					SDCKE1
PB6					SDNE1



Table 12. STM32F427xx and STM32F429xx alternate function mapping

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15	
		SYS	TIM1/2	TIM3/4/5	TIM8/9/ 10/11	I2C1/ 2/3	SPI1/2/ 3/4/5/6	SPI2/3/S AI1	SPI3/US ART1/2/3	USART6/U ART4/5/7/8	CAN1/2/TIM 12/13/14/ LCD	OTG2_HS /OTG1_ FS	ETH	FMC/SDIO /OTG2_FS	DCMI	LCD	SYS	
Port A	PA0	-	TIM2_ CH1/TIM2_ ETR	TIM5_ CH1	TIM8_ ETR	-	-	-	USART2_ CTS	UART4_TX	-	-	ETH_MII_ CRS	-	-	-	EVEN TOUT	
	PA1	-	TIM2_ CH2	TIM5_ CH2	-	-	-	-	USART2_ RTS	UART4_RX	-	-	ETH_MII_ RX_CLK/E TH_RMII_ REF_CLK	-	-	-	EVEN TOUT	
	PA2	-	TIM2_ CH3	TIM5_ CH3	TIM9_ CH1	-	-	-	USART2_ TX	-	-	-	ETH_ MDIO	-	-	-	EVEN TOUT	
	PA3	-	TIM2_ CH4	TIM5_ CH4	TIM9_ CH2	-	-	-	USART2_ RX	-	-	OTG_HS_ ULPI_D0	ETH_MII_ COL	-	-	LCD_B5	EVEN TOUT	
	PA4	-	-	-	-	-	SPI1_ NSS	SPI3_ NSS/ I2S3_WS	USART2_ CK	-	-	-	-	OTG_HS_ SOF	DCMI_ HSYNC	LCD_ VSYNC	EVEN TOUT	
	PA5	-	TIM2_ CH1/TIM2_ ETR	-	TIM8_ CH1N	-	SPI1_ SCK	-	-	-	-	OTG_HS_ ULPI_CK	-	-	-	-	-	EVEN TOUT
	PA6	-	TIM1_ BKIN	TIM3_ CH1	TIM8_ BKIN	-	SPI1_ MISO	-	-	-	-	TIM13_CH1	-	-	DCMI_ PIXCLK	LCD_G2	EVEN TOUT	
	PA7	-	TIM1_ CH1N	TIM3_ CH2	TIM8_ CH1N	-	SPI1_ MOSI	-	-	-	-	TIM14_CH1	-	ETH_MII_ RX_DV/ ETH_RMII_ CRS_DV	-	-	-	EVEN TOUT
	PA8	MCO1	TIM1_ CH1	-	-	I2C3_ SCL	-	-	USART1_ CK	-	-	-	OTG_FS_ SOF	-	-	-	LCD_R6	EVEN TOUT
	PA9	-	TIM1_ CH2	-	-	I2C3_ SMBA	-	-	USART1_ TX	-	-	-	-	-	DCMI_ D0	-	-	EVEN TOUT
	PA10	-	TIM1_ CH3	-	-	-	-	-	USART1_ RX	-	-	-	OTG_FS_ ID	-	DCMI_ D1	-	-	EVEN TOUT
	PA11	-	TIM1_ CH4	-	-	-	-	-	USART1_ CTS	-	-	CAN1_RX	OTG_FS_ DM	-	-	-	LCD_R4	EVEN TOUT
PA12	-	TIM1_ ETR	-	-	-	-	-	USART1_ RTS	-	-	CAN1_TX	OTG_FS_ DP	-	-	-	LCD_R5	EVEN TOUT	



Table 12. STM32F427xx and STM32F429xx alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15		
		SYS	TIM1/2	TIM3/4/5	TIM8/9/ 10/11	I2C1/ 2/3	SPI1/2/ 3/4/5/6	SPI2/3/S AI1	SPI3/US ART1/2/3	USART6/U ART4/5/7/8	CAN1/2/TIM 12/13/14/ LCD	OTG2_HS /OTG1_ FS	ETH	FMC/SDIO /OTG2_FS	DCMI	LCD	SYS		
Port A	PA13	JTMS- SWDI O	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVEN TOUT	
	PA14	JTCK- SWCL K	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVEN TOUT	
	PA15	JTDI	TIM2_ CH1/TIM2 _ETR	-	-	-	SPI1_ NSS	SPI3_ NSS/ I2S3_WS	-	-	-	-	-	-	-	-	-	-	EVEN TOUT
Port B	PB0	-	TIM1_ CH2N	TIM3_ CH3	TIM8_ CH2N	-	-	-	-	-	LCD_R3	OTG_HS_ ULPI_D1	ETH_MII_ RXD2	-	-	-	-	EVEN TOUT	
	PB1	-	TIM1_ CH3N	TIM3_ CH4	TIM8_ CH3N	-	-	-	-	-	LCD_R6	OTG_HS_ ULPI_D2	ETH_MII_ RXD3	-	-	-	-	EVEN TOUT	
	PB2	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVEN TOUT	
	PB3	JTDO/ TRAC ESWO	TIM2_ CH2	-	-	-	SPI1_ SCK	SPI3_ SCK/ I2S3_CK	-	-	-	-	-	-	-	-	-	-	EVEN TOUT
	PB4	NJTR ST	-	TIM3_ CH1	-	-	SPI1_ MISO	SPI3_ MISO	I2S3ext_ SD	-	-	-	-	-	-	-	-	-	EVEN TOUT
	PB5	-	-	TIM3_ CH2	-	I2C1_ SMBA	SPI1_ MOSI	SPI3_ MOSI/ I2S3_SD	-	-	-	CAN2_RX	OTG_HS_ ULPI_D7	ETH_PPS_ OUT	FMC_ SDCKE1	DCMI_ D10	-	-	EVEN TOUT
	PB6	-	-	TIM4_ CH1	-	I2C1_ SCL	-	-	USART1_ TX	-	-	CAN2_TX	-	-	FMC_ SDNE1	DCMI_ D5	-	-	EVEN TOUT
	PB7	-	-	TIM4_ CH2	-	I2C1_ SDA	-	-	USART1_ RX	-	-	-	-	-	FMC_NL	DCMI_ VSYNC	-	-	EVEN TOUT
	PB8	-	-	TIM4_ CH3	TIM10_ CH1	I2C1_ SCL	-	-	-	-	-	CAN1_RX	-	ETH_MII_ TXD3	SDIO_D4	DCMI_ D6	LCD_B6	-	EVEN TOUT
	PB9	-	-	TIM4_ CH4	TIM11_ CH1	I2C1_ SDA	SPI2_ NSS/I2 S2_WS	-	-	-	-	CAN1_TX	-	-	SDIO_D5	DCMI_ D7	LCD_B7	-	EVEN TOUT
PB10	-	TIM2_ CH3	-	-	I2C2_ SCL	SPI2_ SCK/I2 S2_CK	-	-	USART3_ TX	-	-	OTG_HS_ ULPI_D3	ETH_MII_ RX_ER	-	-	-	LCD_G4	-	EVEN TOUT



Table 12. STM32F427xx and STM32F429xx alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/ 10/11	I2C1/ 2/3	SPI1/2/ 3/4/5/6	SPI2/3/S AI1	SPI3/US ART1/2/3	USART6/U ART4/5/7/8	CAN1/2/TIM 12/13/14/ LCD	OTG2_HS /OTG1_ FS	ETH	FMC/SDIO /OTG2_FS	DCMI	LCD	SYS
Port B	PB11	-	TIM2_ CH4	-	-	I2C2_ SDA	-	-	USART3_ RX	-	-	OTG_HS_ ULPI_D4	ETH_MII_ TX_EN/ ETH_RMII_ TX_EN	-	-	LCD_G5	EVEN TOUT
	PB12	-	TIM1_ BKIN	-	-	I2C2_ SMBA	SPI2_ NSS/I2 S2_WS	-	USART3_ CK	-	CAN2_RX	OTG_HS_ ULPI_D5	ETH_MII_ TXD0/ETH_ RMII_ TXD0	OTG_HS_ ID	-	-	EVEN TOUT
	PB13	-	TIM1_ CH1N	-	-	-	SPI2_ SCK/I2 S2_CK	-	USART3_ CTS	-	CAN2_TX	OTG_HS_ ULPI_D6	ETH_MII_ TXD1/ETH_ RMII_TX D1	-	-	-	EVEN TOUT
	PB14	-	TIM1_ CH2N	-	TIM8_ CH2N	-	SPI2_ MISO	I2S2ext_ SD	USART3_ RTS	-	TIM12_CH1	-	-	OTG_HS_ DM	-	-	EVEN TOUT
	PB15	RTC_ REFIN	TIM1_ CH3N	-	TIM8_ CH3N	-	SPI2_ MOSI/I2 S2_SD	-	-	-	TIM12_CH2	-	-	OTG_HS_ DP	-	-	EVEN TOUT
Port C	PC0	-	-	-	-	-	-	-	-	-	-	OTG_HS_ ULPI_STP	-	FMC_SDN WE	-	-	EVEN TOUT
	PC1	-	-	-	-	-	-	-	-	-	-	-	ETH_MDC	-	-	-	EVEN TOUT
	PC2	-	-	-	-	-	SPI2_ MISO	I2S2ext_ SD	-	-	-	OTG_HS_ ULPI_DIR	ETH_MII_ TXD2	FMC_ SDNE0	-	-	EVEN TOUT
	PC3	-	-	-	-	-	SPI2_ MOSI/I2 S2_SD	-	-	-	-	OTG_HS_ ULPI_NXT	ETH_MII_ TX_CLK	FMC_ SDCKE0	-	-	EVEN TOUT
	PC4	-	-	-	-	-	-	-	-	-	-	-	ETH_MII_ RXD0/ETH_ RMII_ RXD0	-	-	-	EVEN TOUT
	PC5	-	-	-	-	-	-	-	-	-	-	-	ETH_MII_ RXD1/ETH_ RMII_ RXD1	-	-	-	EVEN TOUT
	PC6	-	-	TIM3_ CH1	TIM8_ CH1	-	I2S2_ MCK	-	-	USART6_ TX	-	-	-	SDIO_D6	DCMI_ D0	LCD_ HSYNC	EVEN TOUT
	PC7	-	-	TIM3_ CH2	TIM8_ CH2	-	-	I2S3_ MCK	-	USART6_ RX	-	-	-	SDIO_D7	DCMI_ D1	LCD_G6	EVEN TOUT



Table 12. STM32F427xx and STM32F429xx alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15	
		SYS	TIM1/2	TIM3/4/5	TIM8/9/ 10/11	I2C1/ 2/3	SPI1/2/ 3/4/5/6	SPI2/3/S AI1	SPI3/US ART1/2/3	USART6/U ART4/5/7/8	CAN1/2/TIM 12/13/14/ LCD	OTG2_HS /OTG1_ FS	ETH	FMC/SDIO /OTG2_FS	DCMI	LCD	SYS	
Port C	PC8	-	-	TIM3_ CH3	TIM8_ CH3	-	-	-	-	USART6_ CK	-	-	-	SDIO_D0	DCMI_ D2	-	EVEN TOUT	
	PC9	MCO2	-	TIM3_ CH4	TIM8_ CH4	I2C3_ SDA	I2S_ CKIN	-	-	-	-	-	-	SDIO_D1	DCMI_ D3	-	EVEN TOUT	
	PC10	-	-	-	-	-	-	SPI3_ SCK/I2S 3_CK	USART3_ TX	UART4_TX	-	-	-	SDIO_D2	DCMI_ D8	LCD_R2	EVEN TOUT	
	PC11	-	-	-	-	-	I2S3ext _SD	SPI3_ MISO	USART3_ RX	UART4_RX	-	-	-	SDIO_D3	DCMI_ D4	-	EVEN TOUT	
	PC12	-	-	-	-	-	-	SPI3_ MOSI/I2 S3_SD	USART3_ CK	UART5_TX	-	-	-	SDIO_CK	DCMI_ D9	-	EVEN TOUT	
	PC13	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVEN TOUT
	PC14	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVEN TOUT
	PC15	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVEN TOUT
Port D	PD0	-	-	-	-	-	-	-	-	-	CAN1_RX	-	-	FMC_D2	-	-	EVEN TOUT	
	PD1	-	-	-	-	-	-	-	-	-	CAN1_TX	-	-	FMC_D3	-	-	EVEN TOUT	
	PD2	-	-	TIM3_ ETR	-	-	-	-	-	UART5_RX	-	-	-	SDIO_ CMD	DCMI_ D11	-	EVEN TOUT	
	PD3	-	-	-	-	-	SPI2_S CK/I 2S2_CK	-	USART2_ CTS	-	-	-	-	FMC_CLK	DCMI_ D5	LCD_G7	EVEN TOUT	
	PD4	-	-	-	-	-	-	-	USART2_ RTS	-	-	-	-	FMC_NOE	-	-	EVEN TOUT	
	PD5	-	-	-	-	-	-	-	USART2_ TX	-	-	-	-	FMC_NWE	-	-	EVEN TOUT	
	PD6	-	-	-	-	-	SPI3_ MOSI/I2 S3_SD	SAI1_ SD_A	USART2_ RX	-	-	-	-	FMC_ NWAIT	DCMI_ D10	LCD_B2	EVEN TOUT	



Table 12. STM32F427xx and STM32F429xx alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/ 10/11	I2C1/ 2/3	SPI1/2/ 3/4/5/6	SPI2/3/S AI1	SPI3/US ART1/2/3	USART6/U ART4/5/7/8	CAN1/2/TIM 12/13/14/ LCD	OTG2_HS /OTG1_ FS	ETH	FMC/SDIO /OTG2_FS	DCMI	LCD	SYS
Port D	PD7	-	-	-	-	-	-	-	USART2_ CK	-	-	-	-	FMC_NE1/ FMC NCE2	-	-	EVEN TOUT
	PD8	-	-	-	-	-	-	-	USART3_ TX	-	-	-	-	FMC_D13	-	-	EVEN TOUT
	PD9	-	-	-	-	-	-	-	USART3_ RX	-	-	-	-	FMC_D14	-	-	EVEN TOUT
	PD10	-	-	-	-	-	-	-	USART3_ CK	-	-	-	-	FMC_D15	-	LCD_B3	EVEN TOUT
	PD11	-	-	-	-	-	-	-	USART3_ CTS	-	-	-	-	FMC_A16	-	-	EVEN TOUT
	PD12	-	-	TIM4_ CH1	-	-	-	-	USART3_ RTS	-	-	-	-	FMC_A17	-	-	EVEN TOUT
	PD13	-	-	TIM4_ CH2	-	-	-	-	-	-	-	-	-	FMC_A18	-	-	EVEN TOUT
	PD14	-	-	TIM4_ CH3	-	-	-	-	-	-	-	-	-	FMC_D0	-	-	EVEN TOUT
	PD15	-	-	TIM4_ CH4	-	-	-	-	-	-	-	-	-	FMC_D1	-	-	EVEN TOUT
Port E	PE0	-	-	TIM4_ ETR	-	-	-	-	-	UART8_Rx	-	-	-	FMC_ NBL0	DCMI_ D2	-	EVEN TOUT
	PE1	-	-	-	-	-	-	-	-	UART8_Tx	-	-	-	FMC_ NBL1	DCMI_ D3	-	EVEN TOUT
	PE2	TRAC ECLK	-	-	-	-	SPI4_ SCK	SAI1_ MCLK_A	-	-	-	-	ETH_MII_ TXD3	FMC_A23	-	-	EVEN TOUT
	PE3	TRAC ED0	-	-	-	-	-	SAI1_ SD_B	-	-	-	-	-	FMC_A19	-	-	EVEN TOUT
	PE4	TRAC ED1	-	-	-	-	SPI4_ NSS	SAI1_ FS_A	-	-	-	-	-	FMC_A20	DCMI_ D4	LCD_B0	EVEN TOUT
	PE5	TRAC ED2	-	-	TIM9_ CH1	-	SPI4_M ISO	SAI1_ SCK_A	-	-	-	-	-	FMC_A21	DCMI_ D6	LCD_G0	EVEN TOUT
	PE6	TRAC ED3	-	-	TIM9_ CH2	-	SPI4_ MOSI	SAI1_ SD_A	-	-	-	-	-	FMC_A22	DCMI_ D7	LCD_G1	EVEN TOUT



Table 12. STM32F427xx and STM32F429xx alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15	
		SYS	TIM1/2	TIM3/4/5	TIM8/9/ 10/11	I2C1/ 2/3	SPI1/2/ 3/4/5/6	SPI2/3/S AI1	SPI3/US ART1/2/3	USART6/U ART4/5/7/8	CAN1/2/TIM 12/13/14/ LCD	OTG2_HS /OTG1_ FS	ETH	FMC/SDIO /OTG2_FS	DCMI	LCD	SYS	
Port E	PE7	-	TIM1_ETR	-	-	-	-	-	-	UART7_Rx	-	-	-	FMC_D4	-	-	EVEN TOUT	
	PE8	-	TIM1_CH1N	-	-	-	-	-	-	UART7_Tx	-	-	-	FMC_D5	-	-	EVEN TOUT	
	PE9	-	TIM1_CH1	-	-	-	-	-	-	-	-	-	-	FMC_D6	-	-	EVEN TOUT	
	PE10	-	TIM1_CH2N	-	-	-	-	-	-	-	-	-	-	FMC_D7	-	-	EVEN TOUT	
	PE11	-	TIM1_CH2	-	-	-	SPI4_NSS	-	-	-	-	-	-	FMC_D8	-	LCD_G3	EVEN TOUT	
	PE12	-	TIM1_CH3N	-	-	-	SPI4_SCK	-	-	-	-	-	-	FMC_D9	-	LCD_B4	EVEN TOUT	
	PE13	-	TIM1_CH3	-	-	-	SPI4_MISO	-	-	-	-	-	-	FMC_D10	-	LCD_DE	EVEN TOUT	
	PE14	-	TIM1_CH4	-	-	-	SPI4_MOSI	-	-	-	-	-	-	FMC_D11	-	LCD_CLK	EVEN TOUT	
	PE15	-	TIM1_BKIN	-	-	-	-	-	-	-	-	-	-	FMC_D12	-	LCD_R7	EVEN TOUT	
Port F	PF0	-	-	-	-	I2C2_SDA	-	-	-	-	-	-	-	FMC_A0	-	-	EVEN TOUT	
	PF1	-	-	-	-	I2C2_SCL	-	-	-	-	-	-	-	FMC_A1	-	-	EVEN TOUT	
	PF2	-	-	-	-	I2C2_SMBA	-	-	-	-	-	-	-	FMC_A2	-	-	EVEN TOUT	
	PF3	-	-	-	-	-	-	-	-	-	-	-	-	FMC_A3	-	-	EVEN TOUT	
	PF4	-	-	-	-	-	-	-	-	-	-	-	-	FMC_A4	-	-	EVEN TOUT	
	PF5	-	-	-	-	-	-	-	-	-	-	-	-	FMC_A5	-	-	EVEN TOUT	
	PF6	-	-	-	TIM10_CH1	-	SPI5_NSS	SAI1_SD_B	-	UART7_Rx	-	-	-	-	FMC_NIORD	-	-	EVEN TOUT
	PF7	-	-	-	TIM11_CH1	-	SPI5_SCK	SAI1_MCLK_B	-	UART7_Tx	-	-	-	-	FMC_NREG	-	-	EVEN TOUT



Table 12. STM32F427xx and STM32F429xx alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/ 10/11	I2C1/ 2/3	SPI1/2/ 3/4/5/6	SPI2/3/S AI1	SPI3/US ART1/2/3	USART6/U ART4/5/7/8	CAN1/2/TIM 12/13/14/ LCD	OTG2_HS /OTG1_ FS	ETH	FMC/SDIO /OTG2_FS	DCMI	LCD	SYS
Port F	PF8	-	-	-	-	-	SPI5_ MISO	SAI1_ SCK_B	-	-	TIM13_CH1	-	-	FMC_ NIOWR	-	-	EVEN TOUT
	PF9	-	-	-	-	-	SPI5_ MOSI	SAI1_ FS_B	-	-	TIM14_CH1	-	-	FMC_CD	-	-	EVEN TOUT
	PF10	-	-	-	-	-	-	-	-	-	-	-	-	FMC_INTR	DCMI_ D11	LCD_DE	EVEN TOUT
	PF11	-	-	-	-	-	SPI5_ MOSI	-	-	-	-	-	-	FMC_ SDNRAS	DCMI_ D12	-	EVEN TOUT
	PF12	-	-	-	-	-	-	-	-	-	-	-	-	FMC_A6	-	-	EVEN TOUT
	PF13	-	-	-	-	-	-	-	-	-	-	-	-	FMC_A7	-	-	EVEN TOUT
	PF14	-	-	-	-	-	-	-	-	-	-	-	-	FMC_A8	-	-	EVEN TOUT
	PF15	-	-	-	-	-	-	-	-	-	-	-	-	FMC_A9	-	-	EVEN TOUT
Port G	PG0	-	-	-	-	-	-	-	-	-	-	-	-	FMC_A10	-	-	EVEN TOUT
	PG1	-	-	-	-	-	-	-	-	-	-	-	-	FMC_A11	-	-	EVEN TOUT
	PG2	-	-	-	-	-	-	-	-	-	-	-	-	FMC_A12	-	-	EVEN TOUT
	PG3	-	-	-	-	-	-	-	-	-	-	-	-	FMC_A13	-	-	EVEN TOUT
	PG4	-	-	-	-	-	-	-	-	-	-	-	-	FMC_A14/ FMC_BA0	-	-	EVEN TOUT
	PG5	-	-	-	-	-	-	-	-	-	-	-	-	FMC_A15/ FMC_BA1	-	-	EVEN TOUT
	PG6	-	-	-	-	-	-	-	-	-	-	-	-	FMC_INT2	DCMI_ D12	LCD_R7	EVEN TOUT
	PG7	-	-	-	-	-	-	-	-	USART6_ CK	-	-	-	FMC_INT3	DCMI_ D13	LCD_ CLK	EVEN TOUT
	PG8	-	-	-	-	-	SPI6_ NSS	-	-	USART6_ RTS	-	-	-	ETH_PPS_ OUT	FMC_SDC LK	-	-



Table 12. STM32F427xx and STM32F429xx alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15	
		SYS	TIM1/2	TIM3/4/5	TIM8/9/ 10/11	I2C1/ 2/3	SPI1/2/ 3/4/5/6	SPI2/3/S AI1	SPI3/US ART1/2/3	USART6/U ART4/5/7/8	CAN1/2/TIM 12/13/14/ LCD	OTG2_HS /OTG1_ FS	ETH	FMC/SDIO /OTG2_FS	DCMI	LCD	SYS	
Port G	PG9	-	-	-	-	-	-	-	-	USART6_ RX	-	-	-	FMC_NE2/ FMC_ NCE3	-	-	EVEN TOUT	
	PG10	-	-	-	-	-	-	-	-	-	LCD_G3	-	-	FMC_ NCE4_1/ FMC_NE3	DCMI_ D2	LCD_B2	EVEN TOUT	
	PG11	-	-	-	-	-	-	-	-	-	-	-	ETH_MII_ TX_EN/ ETH_RMII_ TX_EN	FMC_ NCE4_2	DCMI_ D3	LCD_B3	EVEN TOUT	
	PG12	-	-	-	-	-	SPI6_ MISO	-	-	USART6_ RTS	LCD_B4	-	-	FMC_NE4	-	LCD_B1	EVEN TOUT	
	PG13	-	-	-	-	-	SPI6_ SCK	-	-	USART6_ CTS	-	-	-	ETH_MII_ TXD0/ ETH_RMII_ TXD0	FMC_A24	-	-	EVEN TOUT
	PG14	-	-	-	-	-	SPI6_ MOSI	-	-	USART6_ TX	-	-	-	ETH_MII_ TXD1/ ETH_RMII_ TXD1	FMC_A25	-	-	EVEN TOUT
	PG15	-	-	-	-	-	-	-	-	USART6_ CTS	-	-	-	-	FMC_ SDNCAS	DCMI_ D13	-	EVEN TOUT
Port H	PH0	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVEN TOUT	
	PH1	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVEN TOUT	
	PH2	-	-	-	-	-	-	-	-	-	-	-	ETH_MII_ CRS	FMC_ SDCKE0	-	LCD_R0	EVEN TOUT	
	PH3	-	-	-	-	-	-	-	-	-	-	-	ETH_MII_ COL	FMC_SDN E0	-	LCD_R1	EVEN TOUT	
	PH4	-	-	-	-	I2C2_ SCL	-	-	-	-	-	OTG_HS_ ULPI_NXT	-	-	-	-	EVEN TOUT	
	PH5	-	-	-	-	I2C2_ SDA	SPI5_N SS	-	-	-	-	-	-	FMC_SDN WE	-	-	EVEN TOUT	
	PH6	-	-	-	-	I2C2_ SMBA	SPI5_ SCK	-	-	-	-	TIM12_CH1	-	-	FMC_ SDNE1	DCMI_ D8	-	-



Table 12. STM32F427xx and STM32F429xx alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/ 10/11	I2C1/ 2/3	SPI1/2/ 3/4/5/6	SPI2/3/S AI1	SPI3/US ART1/2/3	USART6/U ART4/5/7/8	CAN1/2/TIM 12/13/14/ LCD	OTG2_HS /OTG1_ FS	ETH	FMC/SDIO /OTG2_FS	DCMI	LCD	SYS
Port H	PH7	-	-	-	-	I2C3_ SCL	SPI5_ MISO	-	-	-	-	-	ETH_MII_ RXD3	FMC_ SDCKE1	DCMI_ D9	-	-
	PH8	-	-	-	-	I2C3_ SDA	-	-	-	-	-	-	-	FMC_D16	DCMI_ HSYNC	LCD_R2	EVEN TOUT
	PH9	-	-	-	-	I2C3_ SMBA	-	-	-	-	TIM12_CH2	-	-	FMC_D17	DCMI_ D0	LCD_R3	EVEN TOUT
	PH10	-	-	TIM5_ CH1	-	-	-	-	-	-	-	-	-	FMC_D18	DCMI_ D1	LCD_R4	EVEN TOUT
	PH11	-	-	TIM5_ CH2	-	-	-	-	-	-	-	-	-	FMC_D19	DCMI_ D2	LCD_R5	EVEN TOUT
	PH12	-	-	TIM5_ CH3	-	-	-	-	-	-	-	-	-	FMC_D20	DCMI_ D3	LCD_R6	EVEN TOUT
	PH13	-	-	-	TIM8_ CH1N	-	-	-	-	-	CAN1_TX	-	-	FMC_D21	-	LCD_G2	EVEN TOUT
	PH14	-	-	-	TIM8_ CH2N	-	-	-	-	-	-	-	-	FMC_D22	DCMI_ D4	LCD_G3	EVEN TOUT
	PH15	-	-	-	TIM8_ CH3N	-	-	-	-	-	-	-	-	FMC_D23	DCMI_ D11	LCD_G4	EVEN TOUT
Port I	PI0	-	-	TIM5_ CH4	-	-	SPI2_ NSS/I2 S2_WS	-	-	-	-	-	-	FMC_D24	DCMI_ D13	LCD_G5	EVEN TOUT
	PI1	-	-	-	-	-	SPI2_ SCK/I2 S2_CK	-	-	-	-	-	-	FMC_D25	DCMI_ D8	LCD_G6	EVEN TOUT
	PI2	-	-	-	TIM8_ CH4	-	SPI2_ MISO	I2S2ext_ SD	-	-	-	-	-	FMC_D26	DCMI_ D9	LCD_G7	EVEN TOUT
	PI3	-	-	-	TIM8_ ETR	-	SPI2_M OSI/I2S 2_SD	-	-	-	-	-	-	FMC_D27	DCMI_D 10	-	EVEN TOUT
	PI4	-	-	-	TIM8_ BKIN	-	-	-	-	-	-	-	-	FMC_ NBL2	DCMI_D 5	LCD_B4	EVEN TOUT
	PI5	-	-	-	TIM8_ CH1	-	-	-	-	-	-	-	-	FMC_ NBL3	DCMI_ VSYNC	LCD_B5	EVEN TOUT
	PI6	-	-	-	TIM8_ CH2	-	-	-	-	-	-	-	-	FMC_D28	DCMI_ D6	LCD_B6	EVEN TOUT



Table 12. STM32F427xx and STM32F429xx alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/ 10/11	I2C1/ 2/3	SPI1/2/ 3/4/5/6	SPI2/3/S AI1	SPI3/US ART1/2/3	USART6/U ART4/5/7/8	CAN1/2/TIM 12/13/14/ LCD	OTG2_HS /OTG1_ FS	ETH	FMC/SDIO /OTG2_FS	DCMI	LCD	SYS
Port I	PI7	-	-	-	TIM8_ CH3	-	-	-	-	-	-	-	-	FMC_D29	DCMI_ D7	LCD_B7	EVEN TOUT
	PI8	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVEN TOUT
	PI9	-	-	-	-	-	-	-	-	-	CAN1_RX	-	-	FMC_D30	-	LCD_ VSYNC	EVEN TOUT
	PI10	-	-	-	-	-	-	-	-	-	-	-	ETH_MII_ RX_ER	FMC_D31	-	LCD_ HSYNC	EVEN TOUT
	PI11	-	-	-	-	-	-	-	-	-	-	OTG_HS_ ULPI_DIR	-	-	-	-	EVEN TOUT
	PI12	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_ HSYNC	EVEN TOUT
	PI13	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_ VSYNC	EVEN TOUT
	PI14	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_ CLK	EVEN TOUT
	PI15	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_R0	EVEN TOUT
Port J	PJ0	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_R1	EVEN TOUT
	PJ1	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_R2	EVEN TOUT
	PJ2	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_R3	EVEN TOUT
	PJ3	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_R4	EVEN TOUT
	PJ4	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_R5	EVEN TOUT
	PJ5	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_R6	EVEN TOUT
	PJ6	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_R7	EVEN TOUT
	PJ7	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_G0	EVEN TOUT



Table 12. STM32F427xx and STM32F429xx alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/ 10/11	I2C1/ 2/3	SPI1/2/ 3/4/5/6	SPI2/3/S AI1	SPI3/US ART1/2/3	USART6/U ART4/5/7/8	CAN1/2/TIM 12/13/14/ LCD	OTG2_HS /OTG1_ FS	ETH	FMC/SDIO /OTG2_FS	DCMI	LCD	SYS
Port J	PJ8	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_G1	EVEN TOUT
	PJ9	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_G2	EVEN TOUT
	PJ10	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_G3	EVEN TOUT
	PJ11	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_G4	EVEN TOUT
	PJ12	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_B0	EVEN TOUT
	PJ13	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_B1	EVEN TOUT
	PJ14	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_B2	EVEN TOUT
	PJ15	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_B3	EVEN TOUT
Port K	PK0	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_G5	EVEN TOUT
	PK1	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_G6	EVEN TOUT
	PK2	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_G7	EVEN TOUT
	PK3	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_B4	EVEN TOUT
	PK4	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_B5	EVEN TOUT
	PK5	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_B6	EVEN TOUT
	PK6	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_B7	EVEN TOUT
	PK7	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_DE	EVEN TOUT

5 Memory mapping

The memory map is shown in *Figure 18*.

Figure 18. Memory map

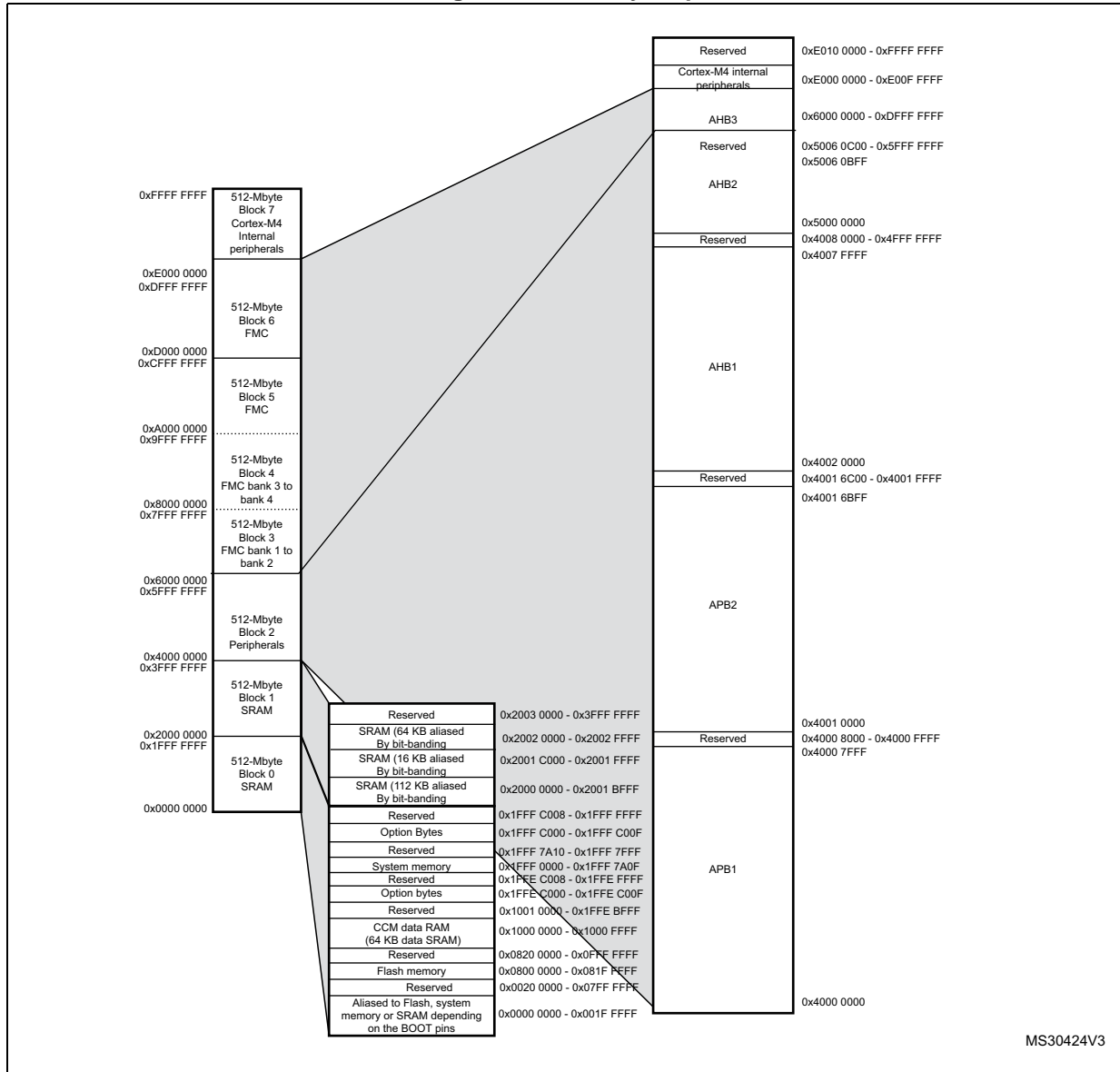


Table 13. STM32F427xx and STM32F429xx register boundary addresses

Bus	Boundary address	Peripheral
	0xE00F FFFF - 0xFFFF FFFF	Reserved
Cortex-M4	0xE000 0000 - 0xE00F FFFF	Cortex-M4 internal peripherals
AHB3	0xD000 0000 - 0xDFFF FFFF	FMC bank 6
	0xC000 0000 - 0xCFFF FFFF	FMC bank 5
	0xA000 1000 - 0xBFFF FFFF	Reserved
	0xA000 0000 - 0xA000 0FFF	FMC control register
	0x9000 0000 - 0x9FFF FFFF	FMC bank 4
	0x8000 0000 - 0x8FFF FFFF	FMC bank 3
	0x7000 0000 - 0x7FFF FFFF	FMC bank 2
	0x6000 0000 - 0x6FFF FFFF	FMC bank 1
	0x5006 0C00 - 0x5FFF FFFF	Reserved
AHB2	0x5006 0800 - 0x5006 0BFF	RNG
	0x5005 0400 - 0x5006 07FF	Reserved
	0x5005 0000 - 0x5005 03FF	DCMI
	0x5004 0000 - 0x5004 FFFF	Reserved
	0x5000 0000 - 0x5003 FFFF	USB OTG FS

Table 13. STM32F427xx and STM32F429xx register boundary addresses (continued)

Bus	Boundary address	Peripheral
	0x4008 0000- 0x4FFF FFFF	Reserved
AHB1	0x4004 0000 - 0x4007 FFFF	USB OTG HS
	0x4002 BC00- 0x4003 FFFF	Reserved
	0x4002 B000 - 0x4002 BBFF	DMA2D
	0x4002 9400 - 0x4002 AFFF	Reserved
	0x4002 9000 - 0x4002 93FF	ETHERNET MAC
	0x4002 8C00 - 0x4002 8FFF	
	0x4002 8800 - 0x4002 8BFF	
	0x4002 8400 - 0x4002 87FF	
	0x4002 8000 - 0x4002 83FF	
	0x4002 6800 - 0x4002 7FFF	Reserved
	0x4002 6400 - 0x4002 67FF	DMA2
	0x4002 6000 - 0x4002 63FF	DMA1
	0x4002 5000 - 0x4002 5FFF	Reserved
	0x4002 4000 - 0x4002 4FFF	BKPSRAM
	0x4002 3C00 - 0x4002 3FFF	Flash interface register
	0x4002 3800 - 0x4002 3BFF	RCC
	0x4002 3400 - 0x4002 37FF	Reserved
	0x4002 3000 - 0x4002 33FF	CRC
	0x4002 2C00 - 0x4002 2FFF	Reserved
	0x4002 2800 - 0x4002 2BFF	GPIOK
	0x4002 2400 - 0x4002 27FF	GPIOJ
	0x4002 2000 - 0x4002 23FF	GPIOI
	0x4002 1C00 - 0x4002 1FFF	GPIOH
	0x4002 1800 - 0x4002 1BFF	GPIOG
	0x4002 1400 - 0x4002 17FF	GPIOF
	0x4002 1000 - 0x4002 13FF	GPIOE
	0x4002 0C00 - 0x4002 0FFF	GPIOD
	0x4002 0800 - 0x4002 0BFF	GPIOC
	0x4002 0400 - 0x4002 07FF	GPIOB
	0x4002 0000 - 0x4002 03FF	GPIOA

Table 13. STM32F427xx and STM32F429xx register boundary addresses (continued)

Bus	Boundary address	Peripheral
	0x4001 6C00 - 0x4001 FFFF	Reserved
APB2	0x4001 6800 - 0x4001 6BFF	LCD-TFT
	0x4001 5C00 - 0x4001 67FF	Reserved
	0x4001 5800 - 0x4001 5BFF	SAI1
	0x4001 5400 - 0x4001 57FF	SPI6
	0x4001 5000 - 0x4001 53FF	SPI5
	0x4001 5400 - 0x4001 57FF	SPI6
	0x4001 5000 - 0x4001 53FF	SPI5
	0x4001 4C00 - 0x4001 4FFF	Reserved
	0x4001 4800 - 0x4001 4BFF	TIM11
	0x4001 4400 - 0x4001 47FF	TIM10
	0x4001 4000 - 0x4001 43FF	TIM9
	0x4001 3C00 - 0x4001 3FFF	EXTI
	0x4001 3800 - 0x4001 3BFF	SYSCFG
	0x4001 3400 - 0x4001 37FF	SPI4
	0x4001 3000 - 0x4001 33FF	SPI1
	0x4001 2C00 - 0x4001 2FFF	SDIO
	0x4001 2400 - 0x4001 2BFF	Reserved
	0x4001 2000 - 0x4001 23FF	ADC1 - ADC2 - ADC3
	0x4001 1800 - 0x4001 1FFF	Reserved
	0x4001 1400 - 0x4001 17FF	USART6
	0x4001 1000 - 0x4001 13FF	USART1
	0x4001 0800 - 0x4001 0FFF	Reserved
	0x4001 0400 - 0x4001 07FF	TIM8
0x4001 0000 - 0x4001 03FF	TIM1	

Table 13. STM32F427xx and STM32F429xx register boundary addresses (continued)

Bus	Boundary address	Peripheral
	0x4000 8000 - 0x4000 FFFF	Reserved
APB1	0x4000 7C00 - 0x4000 7FFF	UART8
	0x4000 7800 - 0x4000 7BFF	UART7
	0x4000 7400 - 0x4000 77FF	DAC
	0x4000 7000 - 0x4000 73FF	PWR
	0x4000 6C00 - 0x4000 6FFF	Reserved
	0x4000 6800 - 0x4000 6BFF	CAN2
	0x4000 6400 - 0x4000 67FF	CAN1
	0x4000 6000 - 0x4000 63FF	Reserved
	0x4000 5C00 - 0x4000 5FFF	I2C3
	0x4000 5800 - 0x4000 5BFF	I2C2
	0x4000 5400 - 0x4000 57FF	I2C1
	0x4000 5000 - 0x4000 53FF	UART5
	0x4000 4C00 - 0x4000 4FFF	UART4
	0x4000 4800 - 0x4000 4BFF	USART3
	0x4000 4400 - 0x4000 47FF	USART2
	0x4000 4000 - 0x4000 43FF	I2S3ext
	0x4000 3C00 - 0x4000 3FFF	SPI3 / I2S3
	0x4000 3800 - 0x4000 3BFF	SPI2 / I2S2
	0x4000 3400 - 0x4000 37FF	I2S2ext
	0x4000 3000 - 0x4000 33FF	IWDG
	0x4000 2C00 - 0x4000 2FFF	WWDG
	0x4000 2800 - 0x4000 2BFF	RTC & BKP Registers
	0x4000 2400 - 0x4000 27FF	Reserved
	0x4000 2000 - 0x4000 23FF	TIM14
	0x4000 1C00 - 0x4000 1FFF	TIM13
	0x4000 1800 - 0x4000 1BFF	TIM12
	0x4000 1400 - 0x4000 17FF	TIM7
	0x4000 1000 - 0x4000 13FF	TIM6
	0x4000 0C00 - 0x4000 0FFF	TIM5
	0x4000 0800 - 0x4000 0BFF	TIM4
0x4000 0400 - 0x4000 07FF	TIM3	
0x4000 0000 - 0x4000 03FF	TIM2	

6 Electrical characteristics

6.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS} .

6.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at $T_A = 25\text{ }^\circ\text{C}$ and $T_A = T_{A\text{max}}$ (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation ($\text{mean} \pm 3\sigma$).

6.1.2 Typical values

Unless otherwise specified, typical data are based on $T_A = 25\text{ }^\circ\text{C}$, $V_{DD} = 3.3\text{ V}$ (for the $1.8\text{ V} \leq V_{DD} \leq 3.6\text{ V}$ voltage range). They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated ($\text{mean} \pm 2\sigma$).

6.1.3 Typical curves

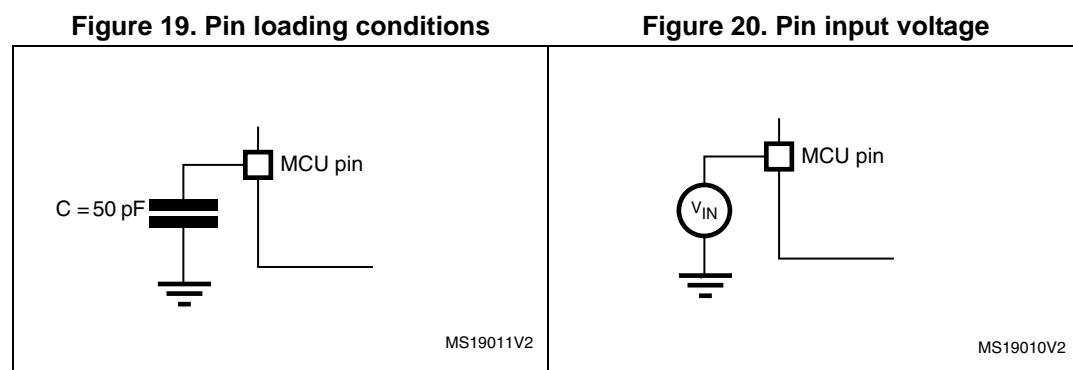
Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

6.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in [Figure 19](#).

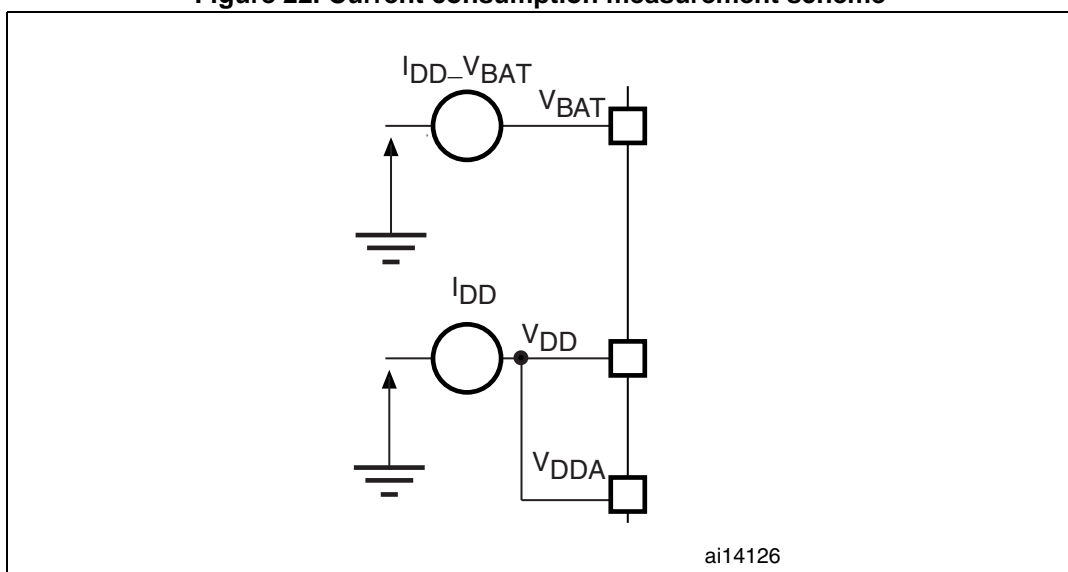
6.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in [Figure 20](#).



6.1.7 Current consumption measurement

Figure 22. Current consumption measurement scheme



6.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in [Table 14: Voltage characteristics](#), [Table 15: Current characteristics](#), and [Table 16: Thermal characteristics](#) may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Table 14. Voltage characteristics

Symbol	Ratings	Min	Max	Unit
$V_{DD}-V_{SS}$	External main supply voltage (including V_{DDA} , V_{DD} and V_{BAT}) ⁽¹⁾	-0.3	4.0	V
V_{IN}	Input voltage on FT pins ⁽²⁾	$V_{SS}-0.3$	$V_{DD}+4.0$	
	Input voltage on TTa pins	$V_{SS}-0.3$	4.0	
	Input voltage on any other pin	$V_{SS}-0.3$	4.0	
$ \Delta V_{DDx} $	Variations between different V_{DD} power pins	-	50	mV
$ V_{SSx}-V_{SS} $	Variations between all the different ground pins	-	50	
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	see Section 6.3.15: Absolute maximum ratings (electrical sensitivity)		

1. All main power (V_{DD} , V_{DDA}) and ground (V_{SS} , V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. V_{IN} maximum value must always be respected. Refer to [Table 15](#) for the values of the maximum allowed injected current.

Table 15. Current characteristics

Symbol	Ratings	Max.	Unit
ΣI_{VDD}	Total current into sum of all V_{DD_x} power lines (source) ⁽¹⁾	270	mA
ΣI_{VSS}	Total current out of sum of all V_{SS_x} ground lines (sink) ⁽¹⁾	-270	
I_{VDD}	Maximum current into each V_{DD_x} power line (source) ⁽¹⁾	100	
I_{VSS}	Maximum current out of each V_{SS_x} ground line (sink) ⁽¹⁾	-100	
I_{IO}	Output current sunk by any I/O and control pin	25	
	Output current sourced by any I/Os and control pin	-25	
ΣI_{IO}	Total output current sunk by sum of all I/O and control pins ⁽²⁾	120	
	Total output current sourced by sum of all I/Os and control pins ⁽²⁾	-120	
$I_{INJ(PIN)}^{(3)}$	Injected current on FT pins ⁽⁴⁾	-5/+0	
	Injected current on NRST and B pins ⁽⁴⁾		
	Injected current on TTa pins ⁽⁵⁾	±5	
$\Sigma I_{INJ(PIN)}^{(5)}$	Total injected current (sum of all I/O and control pins) ⁽⁶⁾	±25	

1. All main power (V_{DD} , V_{DDA}) and ground (V_{SS} , V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. This current consumption must be correctly distributed over all I/Os and control pins. The total output current must not be sunk/sourced between two consecutive power supply pins referring to high pin count LQFP packages.
3. Negative injection disturbs the analog performance of the device. See note in [Section 6.3.21: 12-bit ADC characteristics](#).
4. Positive injection is not possible on these I/Os and does not occur for input voltages lower than the specified maximum value.
5. A positive injection is induced by $V_{IN} > V_{DDA}$ while a negative injection is induced by $V_{IN} < V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to [Table 14](#) for the values of the maximum allowed input voltage.
6. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 16. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	-65 to +150	°C
T_J	Maximum junction temperature	125	°C

6.3 Operating conditions

6.3.1 General operating conditions

Table 17. General operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
f _{HCLK}	Internal AHB clock frequency	Power Scale 3 (VOS[1:0] bits in PWR_CR register = 0x01), Regulator ON, over-drive OFF	0	-	120	MHz	
		Power Scale 2 (VOS[1:0] bits in PWR_CR register = 0x10), Regulator ON	Over-drive OFF	0	-		144
			Over-drive ON		-		168
		Power Scale 1 (VOS[1:0] bits in PWR_CR register= 0x11), Regulator ON	Over-drive OFF	0	-		168
			Over-drive ON		-		180
		f _{PCLK1}	Internal APB1 clock frequency	Over-drive OFF	0		-
Over-drive ON	0			-	45		
f _{PCLK2}	Internal APB2 clock frequency	Over-drive OFF	0	-	84		
		Over-drive ON	0	-	90		

Table 17. General operating conditions (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{DD}	Standard operating voltage		1.8 ⁽¹⁾	-	3.6	V
V _{DDA} ⁽²⁾ V _{DDA} ⁽³⁾	Analog operating voltage (ADC limited to 1.2 M samples)	Must be the same potential as V _{DD} ⁽⁴⁾	1.8 ⁽¹⁾	-	2.4	
	Analog operating voltage (ADC limited to 2.4 M samples)		2.4	-	3.6	
V _{BAT}	Backup operating voltage		1.65	-	3.6	
V ₁₂	Regulator ON: 1.2 V internal voltage on V _{CAP_1} /V _{CAP_2} pins	Power Scale 3 ((VOS[1:0] bits in PWR_CR register = 0x01), 120 MHz HCLK max frequency	1.08	1.14	1.20	
		Power Scale 2 ((VOS[1:0] bits in PWR_CR register = 0x10), 144 MHz HCLK max frequency with over-drive OFF or 168 MHz with over-drive ON	1.20	1.26	1.32	
		Power Scale 1 ((VOS[1:0] bits in PWR_CR register = 0x11), 168 MHz HCLK max frequency with over-drive OFF or 180 MHz with over-drive ON	1.26	1.32	1.40	
	Regulator OFF: 1.2 V external voltage must be supplied from external regulator on V _{CAP_1} /V _{CAP_2} pins ⁽⁵⁾	Max frequency 120 MHz	1.10	1.14	1.20	
		Max frequency 144 MHz	1.20	1.26	1.32	
		Max frequency 168 MHz	1.26	1.32	1.38	
	V _{IN}	Input voltage on RST and FT pins ⁽⁶⁾	2 V ≤ V _{DD} ≤ 3.6 V	-0.3	-	5.5
V _{DD} ≤ 2 V			-0.3	-	5.2	
Input voltage on TTa pins		-0.3	-	V _{DDA} + 0.3		
	Input voltage on B pin	0	-	5.5		
P _D	Power dissipation at T _A = 85 °C for suffix 6 or T _A = 105 °C for suffix 7 ⁽⁷⁾	LQFP100	-	-	465	mW
		WLCSP143	-	-	641	
		LQFP144	-	-	500	
		LQFP176	-	-	526	
		UFBGA176	-	-	513	
		LQFP208	-	-	1053	
		TFBGA216	-	-	690	
T _A	Ambient temperature for 6 suffix version	Maximum power dissipation	-40		85	°C
		Low power dissipation ⁽⁸⁾	-40		105	
	Ambient temperature for 7 suffix version	Maximum power dissipation	-40		105	°C
		Low power dissipation ⁽⁸⁾	-40		125	
T _J	Junction temperature range	6 suffix version	-40		105	°C
		7 suffix version	-40		125	

1. V_{DD}/V_{DDA} minimum value of 1.7 V is obtained when the device operates in a reduced temperature range, with the use of an external power supply supervisor (refer to [Section 3.17.2: Internal reset OFF](#)).
2. When the ADC is used, refer to [Table 76: ADC characteristics](#).
3. If V_{REF+} pin is present, it must respect the following condition: $V_{DDA}-V_{REF+} < 1.2$ V.
4. It is recommended to power V_{DD} and V_{DDA} from the same source. A maximum difference of 300 mV between V_{DD} and V_{DDA} can be tolerated during power-up and power-down operation.
5. The over-drive mode is not supported when the external regulator is ON.
6. To sustain a voltage higher than $V_{DD}+0.3$, the internal Pull-up and Pull-Down resistors must be disabled
7. If T_A is lower, higher P_D values are allowed as long as T_J does not exceed T_{Jmax} .
8. In low power dissipation state, T_A can be extended to this range as long as T_J does not exceed T_{Jmax} .

Table 18. Limitations depending on the operating power supply range

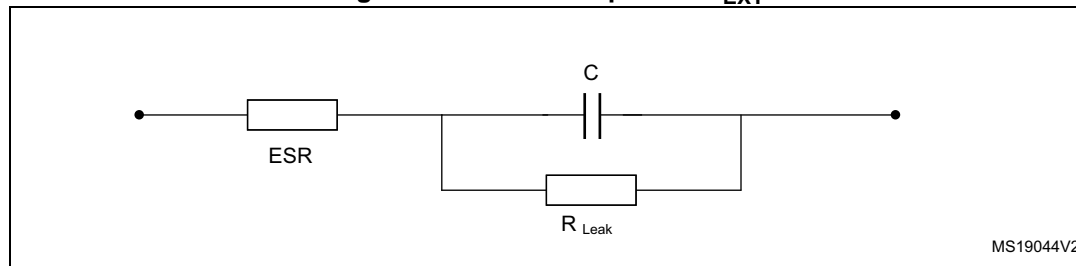
Operating power supply range	ADC operation	Maximum Flash memory access frequency with no wait states ($f_{Flashmax}$)	Maximum Flash memory access frequency with wait states ⁽¹⁾⁽²⁾	I/O operation	Possible Flash memory operations
$V_{DD} = 1.8$ to 2.1 V ⁽³⁾	Conversion time up to 1.2 Msps	20 MHz ⁽⁴⁾	168 MHz with 7 wait states	– No I/O compensation	8-bit erase and program operations only
$V_{DD} = 2.1$ to 2.4 V	Conversion time up to 1.2 Msps	22 MHz	180 MHz with 8 wait states and over-drive ON	– No I/O compensation	16-bit erase and program operations
$V_{DD} = 2.4$ to 2.7 V	Conversion time up to 2.4 Msps	24 MHz	180 MHz with 7 wait states and over-drive ON	– I/O compensation works	16-bit erase and program operations
$V_{DD} = 2.7$ to 3.6 V ⁽⁵⁾	Conversion time up to 2.4 Msps	30 MHz	180 MHz with 5 wait states and over-drive ON	– I/O compensation works	32-bit erase and program operations

1. Applicable only when the code is executed from Flash memory. When the code is executed from RAM, no wait state is required.
2. Thanks to the ART accelerator and the 128-bit Flash memory, the number of wait states given here does not impact the execution speed from Flash memory since the ART accelerator allows to achieve a performance equivalent to 0 wait state program execution.
3. V_{DD}/V_{DDA} minimum value of 1.7 V is obtained when the device operates in a reduced temperature range, with the use of an external power supply supervisor (refer to [Section 3.17.2: Internal reset OFF](#)).
4. Prefetch is not available.
5. The voltage range for USB full speed embedded PHYs can drop down to 2.7 V. However the electrical characteristics of D- and D+ pins will be degraded between 2.7 and 3 V.

6.3.2 VCAP1/VCAP2 external capacitor

Stabilization for the main regulator is achieved by connecting an external capacitor C_{EXT} to the VCAP1/VCAP2 pins. C_{EXT} is specified in [Table 19](#).

Figure 23. External capacitor C_{EXT}



1. Legend: ESR is the equivalent series resistance.

Table 19. VCAP1/VCAP2 operating conditions⁽¹⁾

Symbol	Parameter	Conditions
CEXT	Capacitance of external capacitor	2.2 μ F
ESR	ESR of external capacitor	< 2 Ω

1. When bypassing the voltage regulator, the two 2.2 μ F V_{CAP} capacitors are not required and should be replaced by two 100 nF decoupling capacitors.

6.3.3 Operating conditions at power-up / power-down (regulator ON)

Subject to general operating conditions for T_A .

Table 20. Operating conditions at power-up / power-down (regulator ON)

Symbol	Parameter	Min	Max	Unit
t_{VDD}	V_{DD} rise time rate	20	∞	μ s/V
	V_{DD} fall time rate	20	∞	

6.3.4 Operating conditions at power-up / power-down (regulator OFF)

Subject to general operating conditions for T_A .

Table 21. Operating conditions at power-up / power-down (regulator OFF)⁽¹⁾

Symbol	Parameter	Conditions	Min	Max	Unit
t_{VDD}	V_{DD} rise time rate	Power-up	20	∞	μ s/V
	V_{DD} fall time rate	Power-down	20	∞	
t_{VCAP}	V_{CAP_1} and V_{CAP_2} rise time rate	Power-up	20	∞	
	V_{CAP_1} and V_{CAP_2} fall time rate	Power-down	20	∞	

1. To reset the internal logic at power-down, a reset must be applied on pin PA0 when V_{DD} reach below 1.08 V.

6.3.5 Embedded reset and power control block characteristics

The parameters given in [Table 22](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 17](#).

Table 22. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{PVD}	Programmable voltage detector level selection	PLS[2:0]=000 (rising edge)	2.09	2.14	2.19	V
		PLS[2:0]=000 (falling edge)	1.98	2.04	2.08	V
		PLS[2:0]=001 (rising edge)	2.23	2.30	2.37	V
		PLS[2:0]=001 (falling edge)	2.13	2.19	2.25	V
		PLS[2:0]=010 (rising edge)	2.39	2.45	2.51	V
		PLS[2:0]=010 (falling edge)	2.29	2.35	2.39	V
		PLS[2:0]=011 (rising edge)	2.54	2.60	2.65	V
		PLS[2:0]=011 (falling edge)	2.44	2.51	2.56	V
		PLS[2:0]=100 (rising edge)	2.70	2.76	2.82	V
		PLS[2:0]=100 (falling edge)	2.59	2.66	2.71	V
		PLS[2:0]=101 (rising edge)	2.86	2.93	2.99	V
		PLS[2:0]=101 (falling edge)	2.65	2.84	3.02	V
		PLS[2:0]=110 (rising edge)	2.96	3.03	3.10	V
		PLS[2:0]=110 (falling edge)	2.85	2.93	2.99	V
		PLS[2:0]=111 (rising edge)	3.07	3.14	3.21	V
PLS[2:0]=111 (falling edge)	2.95	3.03	3.09	V		
$V_{PVDhyst}^{(1)}$	PVD hysteresis		-	100	-	mV
$V_{POR/PDR}$	Power-on/power-down reset threshold	Falling edge	1.60	1.68	1.76	V
		Rising edge	1.64	1.72	1.80	V
$V_{PDRhyst}^{(1)}$	PDR hysteresis		-	40	-	mV
V_{BOR1}	Brownout level 1 threshold	Falling edge	2.13	2.19	2.24	V
		Rising edge	2.23	2.29	2.33	V
V_{BOR2}	Brownout level 2 threshold	Falling edge	2.44	2.50	2.56	V
		Rising edge	2.53	2.59	2.63	V
V_{BOR3}	Brownout level 3 threshold	Falling edge	2.75	2.83	2.88	V
		Rising edge	2.85	2.92	2.97	V
$V_{BORhyst}^{(1)}$	BOR hysteresis		-	100	-	mV
$T_{RSTTEMPO}^{(1)(2)}$	POR reset temporization		0.5	1.5	3.0	ms

Table 22. Embedded reset and power control block characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_{RUSH}^{(1)}$	InRush current on voltage regulator power-on (POR or wakeup from Standby)		-	160	200	mA
$E_{RUSH}^{(1)}$	InRush energy on voltage regulator power-on (POR or wakeup from Standby)	$V_{DD} = 1.8\text{ V}$, $T_A = 105\text{ }^\circ\text{C}$, $I_{RUSH} = 171\text{ mA}$ for $31\text{ }\mu\text{s}$	-	-	5.4	μC

1. Guaranteed by design, not tested in production.
2. The reset temporization is measured from the power-on (POR reset or wakeup from V_{BAT}) to the instant when first instruction is read by the user application code.

6.3.6 Over-drive switching characteristics

When the over-drive mode switches from enabled to disabled or disabled to enabled, the system clock is stalled during the internal voltage set-up.

The over-drive switching characteristics are given in [Table 23](#). They are subject to general operating conditions for T_A .

Table 23. Over-drive switching characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Tod_swen	Over_drive switch enable time	HSI	-	45	-	μs
		HSE max for 4 MHz and min for 26 MHz	45	-	100	
		External HSE 50 MHz	-	40	-	
Tod_swdis	Over_drive switch disable time	HSI	-	20	-	
		HSE max for 4 MHz and min for 26 MHz.	20	-	80	
		External HSE 50 MHz	-	15	-	

1. Guaranteed by design, not tested in production.

6.3.7 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, ambient temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code.

The current consumption is measured as described in [Figure 22: Current consumption measurement scheme](#).

All the run-mode current consumption measurements given in this section are performed with a reduced code that gives a consumption equivalent to CoreMark code.

Typical and maximum current consumption

The MCU is placed under the following conditions:

- All I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load).
- All peripherals are disabled except if it is explicitly mentioned.
- The Flash memory access time is adjusted both to f_{HCLK} frequency and V_{DD} range (see [Table 18: Limitations depending on the operating power supply range](#)).
- Regulator ON
- The voltage scaling and over-drive mode are adjusted to f_{HCLK} frequency as follows:
 - Scale 3 for $f_{HCLK} \leq 120$ MHz
 - Scale 2 for $120 \text{ MHz} < f_{HCLK} \leq 144$ MHz
 - Scale 1 for $144 \text{ MHz} < f_{HCLK} \leq 180$ MHz. The over-drive is only ON at 180 MHz.
- The system clock is HCLK, $f_{PCLK1} = f_{HCLK}/4$, and $f_{PCLK2} = f_{HCLK}/2$.
- External clock frequency is 4 MHz and PLL is ON when f_{HCLK} is higher than 25 MHz.
- The maximum values are obtained for $V_{DD} = 3.6$ V and a maximum ambient temperature (T_A), and the typical values for $T_A = 25$ °C and $V_{DD} = 3.3$ V unless otherwise specified.

Table 24. Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator enabled except prefetch) or RAM⁽¹⁾

Symbol	Parameter	Conditions	f _{HCLK} (MHz)	Typ	Max ⁽²⁾			Unit
					T _A = 25 °C	T _A = 85 °C	T _A = 105 °C	
I _{DD}	Supply current in RUN mode	All Peripherals enabled ⁽³⁾⁽⁴⁾	180	98	104 ⁽⁵⁾	123 ⁽⁵⁾	141 ⁽⁵⁾	mA
			168	89	98 ⁽⁵⁾	116 ⁽⁵⁾	133 ⁽⁵⁾	
			150	75	84	100	115	
			144	72	81	96	112	
			120	54	58	72	85	
			90	43	45	56	66	
			60	29	30	38	45	
			30	16	20	34	46	
			25	13	16	30	43	
			16	11	13	27	39	
			8	5	9	23	36	
			4	4	8	21	34	
		2	2	7	20	33		
		All Peripherals disabled ⁽³⁾	180	44	47 ⁽⁵⁾	69 ⁽⁵⁾	87 ⁽⁵⁾	
			168	41	45 ⁽⁵⁾	66 ⁽⁵⁾	83 ⁽⁵⁾	
			150	31	39	57	73	
			144	33	37	56	72	
			120	25	29	43	56	
			90	20	21	32	41	
			60	14	15	22	28	
			30	8	8	12	26	
			25	7	7	10	24	
			16	7	6.5	9	22	
			8	3	3.4	7	21	
4	3		2.7	6	20			
2	2	2.4	6	20				

- Code and data processing running from SRAM1 using boot pins.
- Based on characterization, not tested in production.
- When analog peripheral blocks such as ADCs, DACs, HSE, LSE, HSI, or LSI are ON, an additional power consumption should be considered.
- When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.6 mA per ADC for the analog part.
- Based on characterization, tested in production.

Table 25. Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator disabled)

Symbol	Parameter	Conditions	f _{HCLK} (MHz)	Typ	Max ⁽¹⁾			Unit
					TA=25 °C	TA=85 °C	TA=105 °C	
I _{DD}	Supply current in RUN mode	All Peripherals enabled ⁽²⁾⁽³⁾	180	103	112	140	151	mA
			168	98	107	126	144	
			150	87	95	112	128	
			120	66	71	85	99	
			90	54	58	69	80	
			60	37	39	47	55	
			30	20	24	39	51	
			25	17	21	35	48	
			16	12	16	30	42	
			8	7	11	24	37	
			4	5	8	22	35	
		2	3	7	21	34		
		All Peripherals disabled ⁽³⁾	180	57	62	87	106	
			168	50	54	76	93	
			150	46	50	70	86	
			144	45	49	68	84	
			90	29	34	46	57	
			60	21	24	33	41	
			30	13	17	31	44	
			25	11	15	28	41	
			16	8	12	25	38	
			8	5	9	23	35	
4	4		7	21	34			
2	3	6.5	20	33				

1. Based on characterization, not tested in production unless otherwise specified.
2. When analog peripheral blocks such as ADCs, DACs, HSE, LSE, HSI, or LSI are ON, an additional power consumption should be considered.
3. When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.6 mA per ADC for the analog part.

Table 26. Typical and maximum current consumption in Sleep mode

Symbol	Parameter	Conditions	f _{HCLK} (MHz)	Typ	Max ⁽¹⁾			Unit
					T _A = 25 °C	T _A = 85 °C	T _A = 105 °C	
I _{DD}	Supply current in Sleep mode	All Peripherals enabled ⁽²⁾	180	78	89 ⁽³⁾	110 ⁽³⁾	130 ⁽³⁾	mA
			168	66	75 ⁽³⁾	93 ⁽³⁾	110 ⁽³⁾	
			150	56	61	80	96	
			144	54	58	78	94	
			120	40	44	59	72	
			90	32	34	46	56	
			60	22	23	31	38	
			30	10	16	30	43	
			25	9	14	28	40	
			16	5	12	25	40	
			8	3	8	22	35	
			4	3	7	21	34	
		2	2	6.5	20	33		
		All Peripherals disabled	180	21	26 ⁽³⁾	54 ⁽³⁾	76 ⁽³⁾	
			168	16	20 ⁽³⁾	41 ⁽³⁾	58 ⁽³⁾	
			150	14	17	36	52	
			144	13	16.5	35	51	
			120	10	14	28	41	
			90	8	13	26	37	
			60	6	9	17	25	
			30	5	8	22	35	
			25	3	7	21	34	
			16	3	7	21	34	
			8	2	6	20	33	
4	2		6	20	33			
2	2	6	20	33				

1. Based on characterization, not tested in production unless otherwise specified.
2. When analog peripheral blocks such as ADCs, DACs, HSE, LSE, HSI, or LSI are ON, an additional power consumption should be considered.
3. Based on characterization, tested in production.

Table 27. Typical and maximum current consumptions in Stop mode

Symbol	Parameter	Conditions	Max ⁽¹⁾				Unit
			V _{DD} = 3.6 V				
			Typ	T _A = 25 °C	T _A = 85 °C	T _A = 105 °C	
I _{DD_STOP_NM} (normal mode)	Supply current in Stop mode with voltage regulator in main regulator mode	Flash memory in Stop mode, all oscillators OFF, no independent watchdog	0.40	1.50	14.00	25.00	mA
		Flash memory in Deep power down mode, all oscillators OFF, no independent watchdog	0.35	1.50	14.00	25.00	
	Supply current in Stop mode with voltage regulator in Low Power regulator mode	Flash memory in Stop mode, all oscillators OFF, no independent watchdog	0.29	1.10	10.00	18.00	
		Flash memory in Deep power down mode, all oscillators OFF, no independent watchdog	0.23	1.10	10.00	18.00	
I _{DD_STOP_UDM} (under-drive mode)	Supply current in Stop mode with voltage regulator in main regulator and under-drive mode	Flash memory in Deep power down mode, main regulator in under-drive mode, all oscillators OFF, no independent watchdog	0.19	0.50	6.00	9.00	
	Supply current in Stop mode with voltage regulator in Low Power regulator and under-drive mode	Flash memory in Deep power down mode, Low Power regulator in under-drive mode, all oscillators OFF, no independent watchdog	0.12	0.40	4.00	7.00	

1. Data based on characterization, tested in production.

Table 28. Typical and maximum current consumptions in Standby mode

Symbol	Parameter	Conditions	Typ ⁽¹⁾			Max ⁽²⁾			Unit
			T _A = 25 °C			T _A = 25 °C	T _A = 85 °C	T _A = 105 °C	
			V _{DD} = 1.8 V	V _{DD} = 2.4 V	V _{DD} = 3.3 V	V _{DD} = 3.6 V			
I _{DD_STBY}	Supply current in Standby mode	Backup SRAM ON, low-speed oscillator (LSE) and RTC ON	2.80	3.00	3.60	7.00	19.00	36.00	µA
		Backup SRAM OFF, low-speed oscillator (LSE) and RTC ON	2.30	2.60	3.10	6.00	16.00	31.00	
		Backup SRAM ON, RTC and LSE OFF	2.30	2.50	2.90	6.00 ⁽³⁾	18.00 ⁽³⁾	35.00 ⁽³⁾	
		Backup SRAM OFF, RTC and LSE OFF	1.70	1.90	2.20	5.00 ⁽³⁾	15.00 ⁽³⁾	30.00 ⁽³⁾	

1. When the PDR is OFF (internal reset is OFF), the typical current consumption is reduced by 1.2 µA.



- 2. Based on characterization, not tested in production unless otherwise specified.
- 3. Based on characterization, tested in production.

Table 29. Typical and maximum current consumptions in V_{BAT} mode

Symbol	Parameter	Conditions ⁽¹⁾	Typ			Max ⁽²⁾		Unit
			T _A = 25 °C			T _A = 85 °C	T _A = 105 °C	
			V _{BAT} = 1.8 V	V _{BAT} = 2.4 V	V _{BAT} = 3.3 V	V _{BAT} = 3.6 V		
I _{DD_VBAT}	Backup domain supply current	Backup SRAM ON, low-speed oscillator (LSE) and RTC ON	1.28	1.40	1.62	6	11	µA
		Backup SRAM OFF, low-speed oscillator (LSE) and RTC ON	0.66	0.76	0.97	3	5	
		Backup SRAM ON, RTC and LSE OFF	0.70	0.72	0.74	5	10	
		Backup SRAM OFF, RTC and LSE OFF	0.10	0.10	0.10	2	4	

- 1. Crystal used: Abracon ABS07-120-32.768 kHz-T with a C_L of 6 pF for typical values.
- 2. Based on characterization, not tested in production.

Figure 24. Typical V_{BAT} current consumption (LSE and RTC ON/backup RAM OFF)

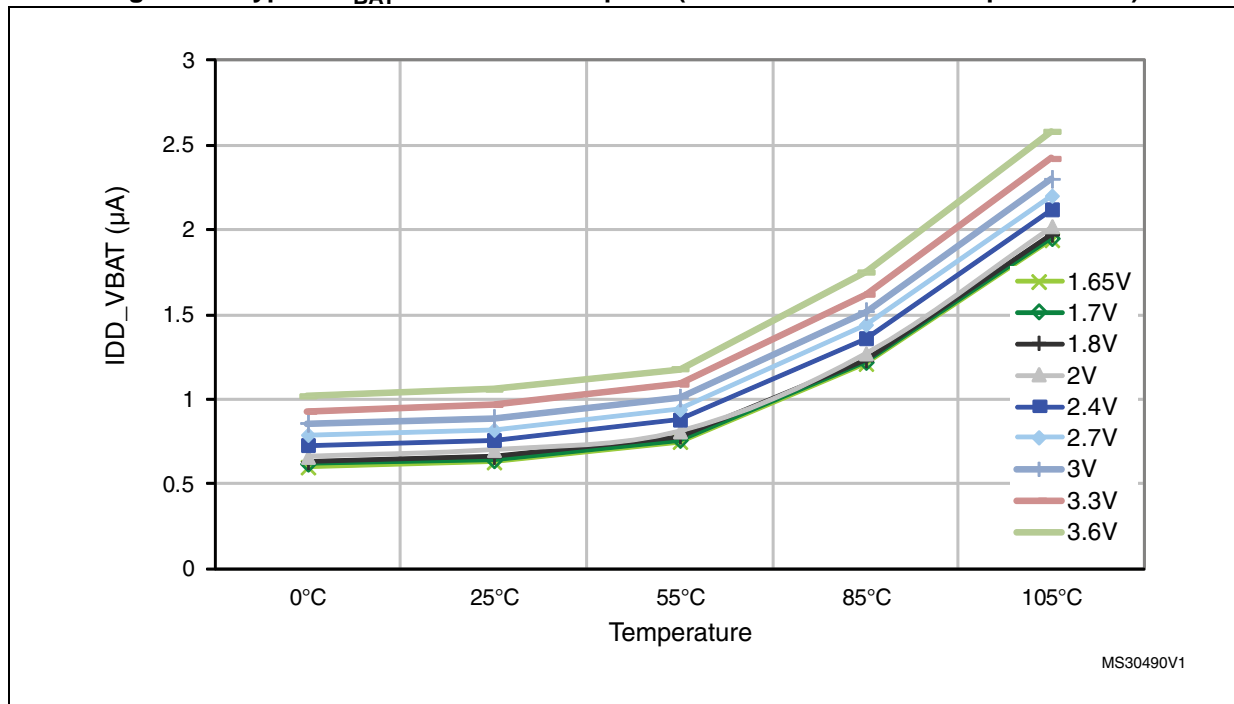
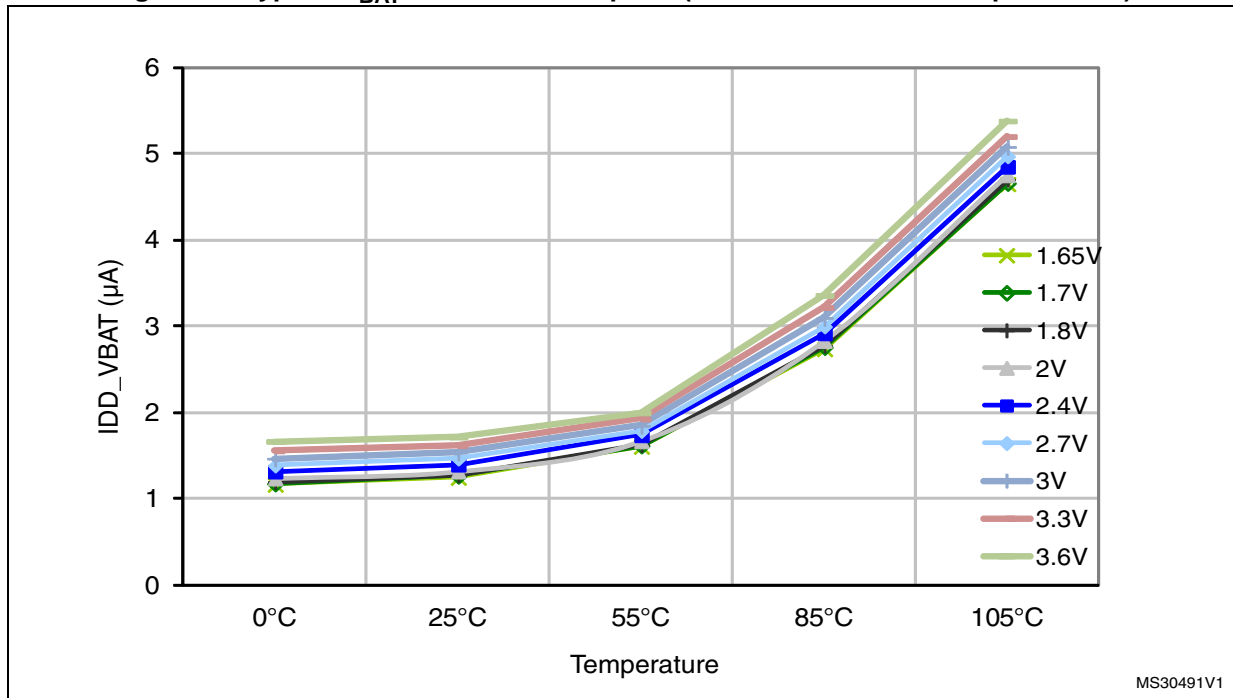


Figure 25. Typical V_{BAT} current consumption (LSE and RTC ON/backup RAM ON)



MS30491V1

Additional current consumption

The MCU is placed under the following conditions:

- All I/O pins are configured in analog mode.
- The Flash memory access time is adjusted to f_{HCLK} frequency.
- The voltage scaling is adjusted to f_{HCLK} frequency as follows:
 - Scale 3 for $f_{HCLK} \leq 120$ MHz,
 - Scale 2 for $120 \text{ MHz} < f_{HCLK} \leq 144$ MHz
 - Scale 1 for $144 \text{ MHz} < f_{HCLK} \leq 180$ MHz. The over-drive is only ON at 180 MHz.
- The system clock is HCLK, $f_{PCLK1} = f_{HCLK}/4$, and $f_{PCLK2} = f_{HCLK}/2$.
- HSE crystal clock frequency is 25 MHz.
- When the regulator is OFF, V12 is provided externally as described in [Table 17: General operating conditions](#)
- $T_A = 25^\circ\text{C}$.

Table 30. Typical current consumption in Run mode, code with data processing running from Flash memory, regulator ON (ART accelerator enabled except prefetch), $V_{DD}=1.8\text{ V}^{(1)}$

Symbol	Parameter	Conditions	f_{HCLK} (MHz)	Typ	Unit
I_{DD}	Supply current in RUN mode from V_{DD} supply	All Peripheral enabled	168	92.3	mA
			150	82.7	
			144	75.3	
			120	56.9	
			90	43.9	
			60	29.3	
			30	16.7	
		All Peripheral disabled	25	14.7	
			168	42.4	
			150	38.1	
			144	34.8	
			120	26.1	
			90	20.5	
			60	14.1	
30	8.2				
25	7.3				

1. When peripherals are enabled, the power consumption corresponding to the analog part of the peripherals (such as ADC, or DAC) is not included.

Table 31. Typical current consumption in Run mode, code with data processing running from Flash memory, regulator OFF (ART accelerator enabled except prefetch)⁽¹⁾

Symbol	Parameter	Conditions	f _{HCLK} (MHz)	VDD=3.3 V		VDD=1.8 V		Unit
				I _{DD12}	I _{DD}	I _{DD12}	I _{DD}	
I _{DD12} / I _{DD}	Supply current in RUN mode from V ₁₂ and V _{DD} supply	All Peripherals enabled	180	77.6	1.4	-	-	mA
			168	74.4	1.3	77.8	1.0	
			150	67.8	1.3	70.8	1.0	
			144	61.2	1.3	64.5	1.0	
			120	47.6	2.2	49.9	0.9	
			90	37.5	1.4	39.2	1.1	
			60	26.1	1.2	27.2	0.9	
			30	15.0	1.2	15.6	0.9	
		25	13.2	1.2	13.6	0.9		
		All Peripherals disabled	180	37.2	1.4	-	-	
			168	35.2	1.3	38.2	1.0	
			150	31.9	1.3	34.6	1.0	
			144	28.6	1.3	31.3	1.0	
			120	21.9	1.2	24.0	0.9	
			90	17.1	1.4	18.1	1.1	
			60	11.9	1.2	12.9	0.9	
30	6.6		1.2	7.2	0.9			
25	5.8	1.2	6.3	0.9				

1. When peripherals are enabled, the power consumption corresponding to the analog part of the peripherals (such as ADC, or DAC) is not included.

Table 32. Typical current consumption in Sleep mode, regulator ON, V_{DD}=1.8 V⁽¹⁾

Symbol	Parameter	Conditions	f _{HCLK} (MHz)	Typ	Unit
I _{DD}	Supply current in Sleep mode from V _{DD} supply	All Peripherals enabled	168	69.2	mA
			150	61.9	
			144	56.4	
			120	42.0	
			90	32.7	
			60	22.3	
			30	13.2	
			25	11.7	
		All Peripherals disabled	168	15.5	
			150	14.1	
			144	12.9	
			120	9.8	
			90	8.3	
			60	6.0	
			30	4.1	
			25	3.8	

1. When peripherals are enabled, the power consumption corresponding to the analog part of the peripherals (such as ADC, or DAC) is not included.

Table 33. Typical current consumption in Sleep mode, regulator OFF⁽¹⁾

Symbol	Parameter	Conditions	f _{HCLK} (MHz)	VDD=3.3 V		VDD=1.8 V		Unit
				I _{DD12}	I _{DD}	I _{DD12}	I _{DD}	
I _{DD12} /I _{DD}	Supply current in Sleep mode from V ₁₂ and V _{DD} supply	All Peripherals enabled	180	61.5	1.4	-	-	mA
			168	59.4	1.3	59.4	1.0	
			150	53.9	1.3	53.9	1.0	
			144	49.0	1.3	49.0	1.0	
			120	38.0	1.2	38.0	0.9	
			90	29.3	1.4	29.3	1.1	
			60	20.2	1.2	20.2	0.9	
			30	11.9	1.2	11.9	0.9	
		25	10.4	1.2	10.4	0.9		
		All Peripherals disabled	180	14.9	1.4	-	-	
			168	14.0	1.3	14.0	1.0	
			150	12.6	1.3	12.6	1.0	
			144	11.5	1.3	11.5	1.0	
			120	8.7	1.2	8.7	0.9	
			90	7.1	1.4	7.1	1.1	
			60	5.0	1.2	5.0	0.9	
30	3.1		1.2	3.1	0.9			
25	2.8	1.2	2.8	0.9				

1. When peripherals are enabled, the power consumption corresponding to the analog part of the peripherals (such as ADC, or DAC) is not included.

I/O system current consumption

The current consumption of the I/O system has two components: static and dynamic.

I/O static current consumption

All the I/Os used as inputs with pull-up generate current consumption when the pin is externally held low. The value of this current consumption can be simply computed by using the pull-up/pull-down resistors values given in [Table 56: I/O static characteristics](#).

For the output pins, any external pull-down or external load must also be considered to estimate the current consumption.

Additional I/O current consumption is due to I/Os configured as inputs if an intermediate voltage level is externally applied. This current consumption is caused by the input Schmitt trigger circuits used to discriminate the input value. Unless this specific configuration is required by the application, this supply current consumption can be avoided by configuring these I/Os in analog mode. This is notably the case of ADC input pins which should be configured as analog inputs.

Caution: Any floating input pin can also settle to an intermediate voltage level or switch inadvertently, as a result of external electromagnetic noise. To avoid current consumption related to floating pins, they must either be configured in analog mode, or forced internally to a definite digital value. This can be done either by using pull-up/down resistors or by configuring the pins in output mode.

I/O dynamic current consumption

In addition to the internal peripheral current consumption (see [Table 35: Peripheral current consumption](#)), the I/Os used by an application also contribute to the current consumption. When an I/O pin switches, it uses the current from the MCU supply voltage to supply the I/O pin circuitry and to charge/discharge the capacitive load (internal or external) connected to the pin:

$$I_{SW} = V_{DD} \times f_{SW} \times C$$

where

I_{SW} is the current sunk by a switching I/O to charge/discharge the capacitive load

V_{DD} is the MCU supply voltage

f_{SW} is the I/O switching frequency

C is the total capacitance seen by the I/O pin: $C = C_{INT} + C_{EXT}$

The test pin is configured in push-pull output mode and is toggled by software at a fixed frequency.

Table 34. Switching output I/O current consumption⁽¹⁾

Symbol	Parameter	Conditions	I/O toggling frequency (fsw)	Typ	Unit
I _{DDIO}	I/O switching Current	V _{DD} = 3.3 V C = C _{INT} ⁽²⁾	2 MHz	0.0	mA
			8 MHz	0.2	
			25 MHz	0.6	
			50 MHz	1.1	
			60 MHz	1.3	
			84 MHz	1.8	
			90 MHz	1.9	
		V _{DD} = 3.3 V C _{EXT} = 0 pF C = C _{INT} + C _{EXT} + C _S	2 MHz	0.1	
			8 MHz	0.4	
			25 MHz	1.23	
			50 MHz	2.43	
			60 MHz	2.93	
			84 MHz	3.86	
			90 MHz	4.07	

Table 34. Switching output I/O current consumption⁽¹⁾ (continued)

Symbol	Parameter	Conditions	I/O toggling frequency (fsw)	Typ	Unit
I _{DDIO}	I/O switching Current	$V_{DD} = 3.3\text{ V}$ $C_{EXT} = 10\text{ pF}$ $C = C_{INT} + C_{EXT} + C_S$	2 MHz	0.18	mA
			8 MHz	0.67	
			25 MHz	2.09	
			50 MHz	3.6	
			60 MHz	4.5	
			84 MHz	7.8	
			90 MHz	9.8	
		$V_{DD} = 3.3\text{ V}$ $C_{EXT} = 22\text{ pF}$ $C = C_{INT} + C_{EXT} + C_S$	2 MHz	0.26	
			8 MHz	1.01	
			25 MHz	3.14	
			50 MHz	6.39	
		$V_{DD} = 3.3\text{ V}$ $C_{EXT} = 33\text{ pF}$ $C = C_{INT} + C_{EXT} + C_S$	60 MHz	10.68	
			2 MHz	0.33	
			8 MHz	1.29	
			25 MHz	4.23	
			50 MHz	11.02	

1. C_S is the PCB board capacitance including the pad pin. C_S = 7 pF (estimated value).
2. This test is performed by cutting the LQFP176 package pin (pad removal).

On-chip peripheral current consumption

The MCU is placed under the following conditions:

- At startup, all I/O pins are in analog input configuration.
- All peripherals are disabled unless otherwise mentioned.
- I/O compensation cell enabled.
- The ART accelerator is ON.
- Scale 1 mode selected, internal digital voltage V12 = 1.32 V.
- HCLK is the system clock. f_{PCLK1} = f_{HCLK}/4, and f_{PCLK2} = f_{HCLK}/2.
 The given value is calculated by measuring the difference of current consumption
 - with all peripherals clocked off
 - with only one peripheral clocked on
 - f_{HCLK} = 180 MHz (Scale1 + over-drive ON), f_{HCLK} = 144 MHz (Scale 2), f_{HCLK} = 120 MHz (Scale 3)"
- Ambient operating temperature is 25 °C and V_{DD}=3.3 V.

Table 35. Peripheral current consumption

Peripheral		I _{DD} (Typ) ⁽¹⁾			Unit
		Scale 1	Scale 2	Scale 3	
AHB1 (up to 180 MHz)	GPIOA	2.50	2.36	2.08	μA/MHz
	GPIOB	2.56	2.36	2.08	
	GPIOC	2.44	2.29	2.00	
	GPIOD	2.50	2.36	2.08	
	GPIOE	2.44	2.29	2.00	
	GPIOF	2.44	2.29	2.00	
	GPIOG	2.39	2.22	2.00	
	GPIOH	2.33	2.15	1.92	
	GPIOI	2.39	2.22	2.00	
	GPIOJ	2.33	2.15	1.92	
	GPIOK	2.33	2.15	1.92	
	OTG_HS+ULPI	27.00	24.86	21.92	
	CRC	0.44	0.42	0.33	
	BKPSRAM	0.78	0.69	0.58	
	DMA1	25.33	23.26	20.50	
	DMA2	24.72	22.71	20.00	
DMA2D	28.50	26.32	23.33		
ETH_MAC ETH_MAC_TX ETH_MAC_RX ETH_MAC_PTP	21.56	20.07	17.75		
AHB2 (up to 180 MHz)	OTG_FS	25.67	26.67	23.58	μA/MHz
	DCMI	3.72	3.40	3.00	
	RNG	2.28	2.36	2.17	
AHB3 (up to 180 MHz)	FMC	21.39	19.79	17.50	μA/MHz
Bus matrix ⁽²⁾		14.06	13.19	11.75	μA/MHz

Table 35. Peripheral current consumption (continued)

Peripheral		I _{DD} (Typ) ⁽¹⁾			Unit
		Scale 1	Scale 2	Scale 3	
APB1 (up to 45 MHz)	TIM2	17.56	16.42	14.47	μA/MHz
	TIM3	14.22	13.36	11.80	
	TIM4	14.89	13.64	12.13	
	TIM5	17.33	16.42	14.47	
	TIM6	2.89	2.53	2.47	
	TIM7	3.11	2.81	2.47	
	TIM12	7.33	6.97	6.13	
	TIM13	4.89	4.47	4.13	
	TIM14	5.56	5.31	4.80	
	PWR	11.11	10.31	9.13	
	USART2	4.22	3.92	3.47	
	USART3	4.44	4.19	3.80	
	UART4	4.00	3.92	3.47	
	UART5	4.00	3.92	3.47	
	UART7	4.00	3.92	3.47	
	UART8	3.78	3.92	3.47	
	I2C1	4.00	3.92	3.47	
	I2C2	4.00	3.92	3.47	
	I2C3	4.00	3.92	3.47	
	SPI2 ⁽³⁾	3.11	3.08	2.80	
	SPI3 ⁽³⁾	3.56	3.36	3.13	
	I2S2	2.89	2.81	2.47	
	I2S3	3.33	3.08	2.80	
	CAN1	6.89	6.42	5.80	
	CAN2	6.67	6.14	5.47	
	DAC ⁽⁴⁾	2.89	2.25	2.13	
WWDG	0.89	0.86	0.80		

Table 35. Peripheral current consumption (continued)

Peripheral		I _{DD} (Typ) ⁽¹⁾			Unit
		Scale 1	Scale 2	Scale 3	
APB2 (up to 90 MHz)	SDIO	8.11	8.75	7.83	μA/MHz
	TIM1	17.11	15.97	14.17	
	TIM8	17.33	16.11	14.33	
	TIM9	7.22	6.67	6.00	
	TIM10	4.56	4.31	3.83	
	TIM11	4.78	4.44	4.00	
	ADC1 ⁽⁵⁾	4.67	4.31	3.83	
	ADC2 ⁽⁵⁾	4.78	4.44	4.00	
	ADC3 ⁽⁵⁾	4.56	4.17	3.67	
	SPI1	1.44	1.39	1.17	
	USART1	4.00	3.75	3.33	
	USART6	4.00	3.75	3.33	
	SPI4	1.44	1.39	1.17	
	SPI5	1.44	1.39	1.17	
	SPI6	1.44	1.39	1.17	
	SYSCFG	0.78	0.69	0.67	
	LCD_TFT	39.89	37.22	33.17	
SAI1	3.78	3.47	3.17		

1. When the I/O compensation cell is ON, I_{DD} typical value increases by 0.22 mA.
2. The BusMatrix is automatically active when at least one master is ON.
3. I2SMOD bit set in SPI_I2SCFGR register, and then the I2SE bit set to enable I2S peripheral.
4. When DAC is ON and EN1/2 bits are set in DAC_CR register, add an additional power consumption of 0.8 mA per DAC channel for the analog part.
5. When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.6 mA per ADC for the analog part.

6.3.8 Wakeup time from low-power modes

The wakeup times given in [Table 36](#) are measured starting from the wakeup event trigger up to the first instruction executed by the CPU:

- For Stop or Sleep modes: the wakeup event is WFE.
- WKUP (PA0) pin is used to wakeup from Standby, Stop and Sleep modes.

All timings are derived from tests performed under ambient temperature and V_{DD}=3.3 V.

Table 36. Low-power mode wakeup timings

Symbol	Parameter	Conditions	Typ ⁽¹⁾	Max ⁽¹⁾	Unit
$t_{WUSLEEP}^{(2)}$	Wakeup from Sleep	-	6	-	CPU clock cycle
$t_{WUSTOP}^{(2)}$	Wakeup from Stop mode with MR/LP regulator in normal mode	Main regulator is ON	13.6	-	μs
		Main regulator is ON and Flash memory in Deep power down mode	93	111	
		Low power regulator is ON	22	32	
		Low power regulator is ON and Flash memory in Deep power down mode	103	126	
$t_{WUSTOP}^{(2)}$	Wakeup from Stop mode with MR/LP regulator in Under-drive mode	Main regulator in under-drive mode (Flash memory in Deep power-down mode)	125	155	
		Low power regulator in under-drive mode (Flash memory in Deep power-down mode)	105	128	
$t_{WUSTDBY}^{(2)(3)}$	Wakeup from Standby mode		318	412	

1. Based on characterization, not tested in production.

2. The wakeup times are measured from the wakeup event to the point in which the application code reads the first

3. $t_{WUSTDBY}$ maximum value is given at $-40\text{ }^{\circ}\text{C}$.

6.3.9 External clock source characteristics

High-speed external user clock generated from an external source

In bypass mode the HSE oscillator is switched off and the input pin is a standard I/O. The external clock signal has to respect the [Table 56](#). However, the recommended clock input waveform is shown in [Figure 26](#).

The characteristics given in [Table 37](#) result from tests performed using an high-speed external clock source, and under ambient temperature and supply voltage conditions summarized in [Table 17](#).

Table 37. High-speed external user clock characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f _{HSE_ext}	External user clock source frequency ⁽¹⁾		1	-	50	MHz
V _{HSEH}	OSC_IN input pin high level voltage		0.7V _{DD}	-	V _{DD}	V
V _{HSEL}	OSC_IN input pin low level voltage		V _{SS}	-	0.3V _{DD}	
t _{w(HSE)} t _{w(HSE)}	OSC_IN high or low time ⁽¹⁾		5	-	-	ns
t _{r(HSE)} t _{f(HSE)}	OSC_IN rise or fall time ⁽¹⁾		-	-	10	
C _{in(HSE)}	OSC_IN input capacitance ⁽¹⁾		-	5	-	pF
DuCy _(HSE)	Duty cycle		45	-	55	%
I _L	OSC_IN Input leakage current	V _{SS} ≤ V _{IN} ≤ V _{DD}	-	-	±1	µA

1. Guaranteed by design, not tested in production.

Low-speed external user clock generated from an external source

In bypass mode the LSE oscillator is switched off and the input pin is a standard I/O. The external clock signal has to respect the [Table 56](#). However, the recommended clock input waveform is shown in [Figure 27](#).

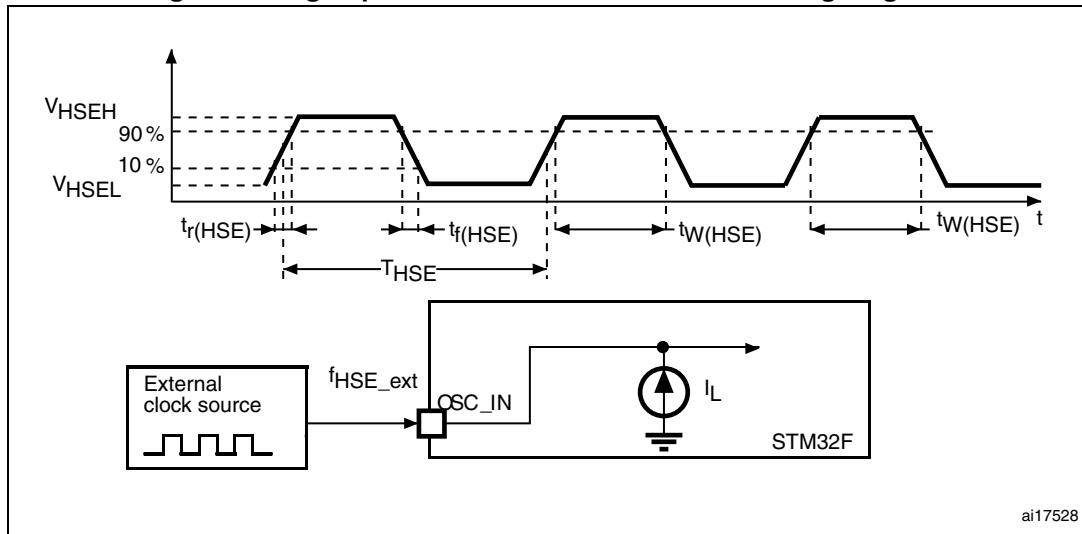
The characteristics given in [Table 38](#) result from tests performed using an low-speed external clock source, and under ambient temperature and supply voltage conditions summarized in [Table 17](#).

Table 38. Low-speed external user clock characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f _{LSE_ext}	User External clock source frequency ⁽¹⁾		-	32.768	1000	kHz
V _{LSEH}	OSC32_IN input pin high level voltage		0.7V _{DD}	-	V _{DD}	V
V _{LSEL}	OSC32_IN input pin low level voltage		V _{SS}	-	0.3V _{DD}	
t _{w(LSE)} t _{f(LSE)}	OSC32_IN high or low time ⁽¹⁾		450	-	-	ns
t _{r(LSE)} t _{f(LSE)}	OSC32_IN rise or fall time ⁽¹⁾		-	-	50	
C _{in(LSE)}	OSC32_IN input capacitance ⁽¹⁾		-	5	-	pF
DuCy _(LSE)	Duty cycle		30	-	70	%
I _L	OSC32_IN Input leakage current	V _{SS} ≤ V _{IN} ≤ V _{DD}	-	-	±1	µA

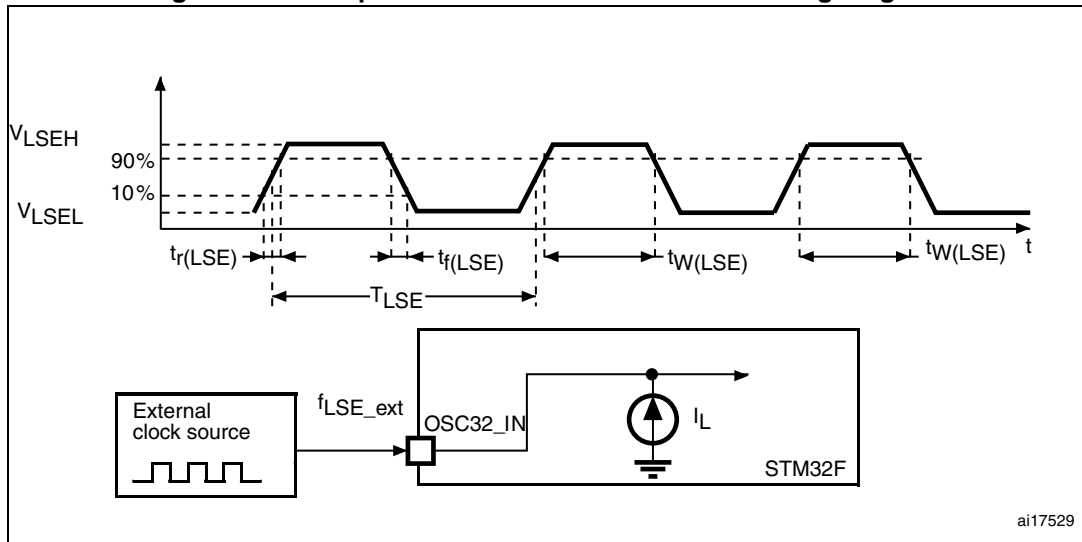
1. Guaranteed by design, not tested in production.

Figure 26. High-speed external clock source AC timing diagram



ai17528

Figure 27. Low-speed external clock source AC timing diagram



ai17529

High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 4 to 26 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in [Table 39](#). In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 39. HSE 4-26 MHz oscillator characteristics (1)

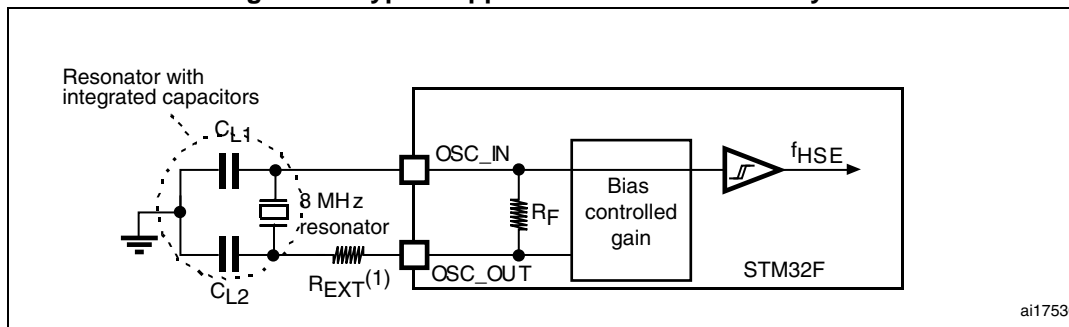
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{OSC_IN}	Oscillator frequency		4	-	26	MHz
R_F	Feedback resistor		-	200	-	k Ω
I_{DD}	HSE current consumption	$V_{DD}=3.3\text{ V}$, ESR= 30 Ω , $C_L=5\text{ pF}@25\text{ MHz}$	-	450	-	μA
		$V_{DD}=3.3\text{ V}$, ESR= 30 Ω , $C_L=10\text{ pF}@25\text{ MHz}$	-	530	-	
$G_{m_crit_max}$	Maximum critical crystal g_m	Startup	-	-	1	mA/V
$t_{SU(HSE)}^{(2)}$	Startup time	V_{DD} is stabilized	-	2	-	ms

1. Guaranteed by design, not tested in production.
2. $t_{SU(HSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is based on characterization and not tested in production. It is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

For C_{L1} and C_{L2} , it is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see [Figure 28](#)). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2} . PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2} .

Note: For information on selecting the crystal, refer to the application note AN2867 “Oscillator design guide for ST microcontrollers” available from the ST website www.st.com.

Figure 28. Typical application with an 8 MHz crystal



1. R_{EXT} value depends on the crystal characteristics.

Low-speed external clock generated from a crystal/ceramic resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in [Table 40](#). In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

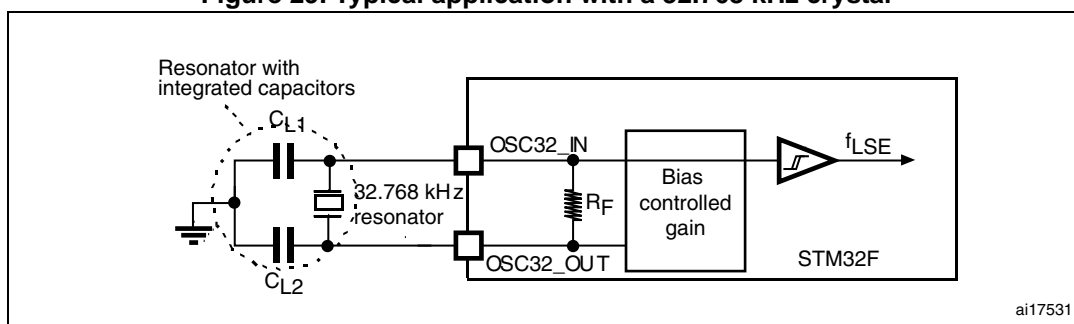
Table 40. LSE oscillator characteristics ($f_{LSE} = 32.768 \text{ kHz}$) ⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
R_F	Feedback resistor		-	18.4	-	M Ω
I_{DD}	LSE current consumption		-	-	1	μA
$G_{m_crit_max}$	Maximum critical crystal g_m	Startup	-	-	0.56	$\mu\text{A/V}$
$t_{SU(LSE)}$ ⁽²⁾	startup time	V_{DD} is stabilized	-	2	-	s

1. Guaranteed by design, not tested in production.
2. $t_{SU(LSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is based on characterization and not tested in production. It is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

Note: For information on selecting the crystal, refer to the application note AN2867 “Oscillator design guide for ST microcontrollers” available from the ST website www.st.com.

Figure 29. Typical application with a 32.768 kHz crystal



6.3.10 Internal clock source characteristics

The parameters given in [Table 41](#) and [Table 42](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 17](#).

High-speed internal (HSI) RC oscillator

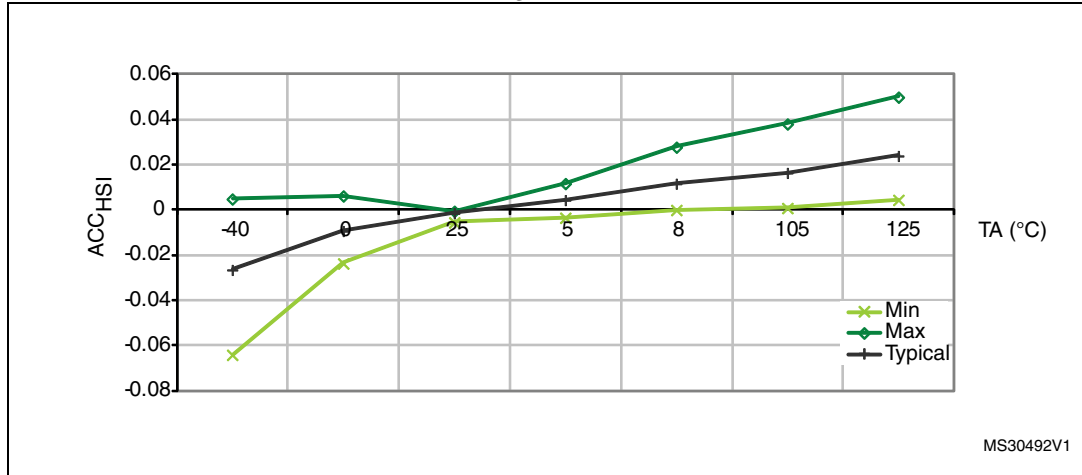
Table 41. HSI oscillator characteristics ⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
f_{HSI}	Frequency		-	16	-	MHz	
ACC_{HSI}	Accuracy of the HSI oscillator	User-trimmed with the RCC_CR register ⁽²⁾	-	-	1	%	
		Factory-calibrated	$T_A = -40 \text{ to } 105 \text{ }^\circ\text{C}$ ⁽³⁾	-8	-	4.5	%
			$T_A = -10 \text{ to } 85 \text{ }^\circ\text{C}$ ⁽³⁾	-4	-	4	%
		$T_A = 25 \text{ }^\circ\text{C}$	-1	-	1	%	
$t_{su(HSI)}$ ⁽²⁾	HSI oscillator startup time		-	2.2	4	μs	
$I_{DD(HSI)}$ ⁽²⁾	HSI oscillator power consumption		-	60	80	μA	

1. $V_{DD} = 3.3 \text{ V}$, $T_A = -40 \text{ to } 105 \text{ }^\circ\text{C}$ unless otherwise specified.

- 2. Guaranteed by design, not tested in production
- 3. Based on characterization, not tested in production.

Figure 30. ACC_{HSI} versus temperature



- 1. Based on characterisation results, not tested in production.

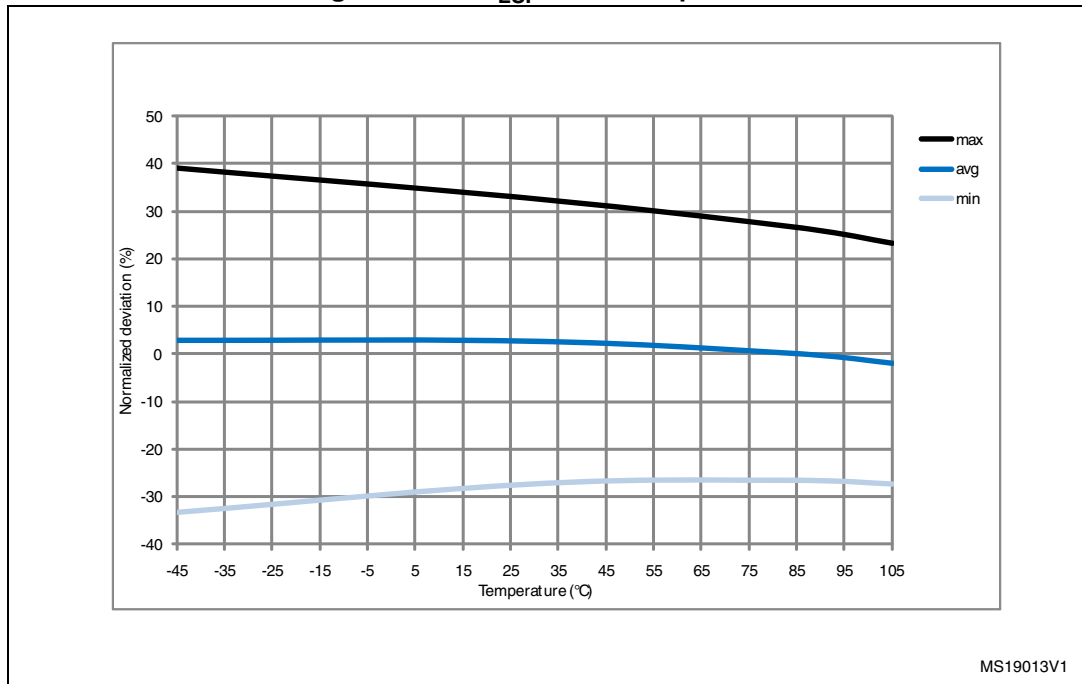
Low-speed internal (LSI) RC oscillator

Table 42. LSI oscillator characteristics ⁽¹⁾

Symbol	Parameter	Min	Typ	Max	Unit
f _{LSI} ⁽²⁾	Frequency	17	32	47	kHz
t _{su(LSI)} ⁽³⁾	LSI oscillator startup time	-	15	40	µs
I _{DD(LSI)} ⁽³⁾	LSI oscillator power consumption	-	0.4	0.6	µA

- 1. V_{DD} = 3 V, T_A = -40 to 105 °C unless otherwise specified.
- 2. Based on characterization, not tested in production.
- 3. Guaranteed by design, not tested in production.

Figure 31. ACC_{LSI} versus temperature



6.3.11 PLL characteristics

The parameters given in [Table 43](#) and [Table 44](#) are derived from tests performed under temperature and V_{DD} supply voltage conditions summarized in [Table 17](#).

Table 43. Main PLL characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f _{PLL_IN}	PLL input clock ⁽¹⁾		0.95 ⁽²⁾	1	2.10	MHz
f _{PLL_OUT}	PLL multiplier output clock		24	-	180	MHz
f _{PLL48_OUT}	48 MHz PLL multiplier output clock		-	48	75	MHz
f _{VCO_OUT}	PLL VCO output		192	-	432	MHz
t _{LOCK}	PLL lock time	VCO freq = 192 MHz	75	-	200	μs
		VCO freq = 432 MHz	100	-	300	

Table 43. Main PLL characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
Jitter ⁽³⁾	Cycle-to-cycle jitter	System clock 120 MHz	RMS	-	25	-	ps
			peak to peak	-	±150	-	
	Period Jitter		RMS	-	15	-	
			peak to peak	-	±200	-	
	Main clock output (MCO) for RMI Ethernet	Cycle to cycle at 50 MHz on 1000 samples	-	32	-		
	Main clock output (MCO) for MII Ethernet	Cycle to cycle at 25 MHz on 1000 samples	-	40	-		
	Bit Time CAN jitter	Cycle to cycle at 1 MHz on 1000 samples	-	330	-		
I _{DD(PLL)} ⁽⁴⁾	PLL power consumption on VDD	VCO freq = 192 MHz VCO freq = 432 MHz	0.15 0.45	-	0.40 0.75	mA	
I _{DDA(PLL)} ⁽⁴⁾	PLL power consumption on VDDA	VCO freq = 192 MHz VCO freq = 432 MHz	0.30 0.55	-	0.40 0.85	mA	

1. Take care of using the appropriate division factor M to obtain the specified PLL input clock values. The M factor is shared between PLL and PLLI2S.
2. Guaranteed by design, not tested in production.
3. The use of 2 PLLs in parallel could degraded the Jitter up to +30%.
4. Based on characterization, not tested in production.

Table 44. PLLI2S (audio PLL) characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
f _{PLLI2S_IN}	PLLI2S input clock ⁽¹⁾		0.95 ⁽²⁾	1	2.10	MHz	
f _{PLLI2S_OUT}	PLLI2S multiplier output clock		-	-	216	MHz	
f _{VCO_OUT}	PLLI2S VCO output		192	-	432	MHz	
t _{LOCK}	PLLI2S lock time	VCO freq = 192 MHz	75	-	200	µs	
		VCO freq = 432 MHz	100	-	300		
Jitter ⁽³⁾	Master I2S clock jitter	Cycle to cycle at 12.288 MHz on 48KHz period, N=432, R=5	RMS	-	90	-	ps
			peak to peak	-	±280	-	
		Average frequency of 12.288 MHz N = 432, R = 5 on 1000 samples	-	90	-	ps	
	WS I2S clock jitter	Cycle to cycle at 48 KHz on 1000 samples	-	400	-	ps	

Table 44. PLLI2S (audio PLL) characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_{DD(PLLI2S)}^{(4)}$	PLLI2S power consumption on V_{DD}	VCO freq = 192 MHz VCO freq = 432 MHz	0.15 0.45	-	0.40 0.75	mA
$I_{DDA(PLLI2S)}^{(4)}$	PLLI2S power consumption on V_{DDA}	VCO freq = 192 MHz VCO freq = 432 MHz	0.30 0.55	-	0.40 0.85	mA

1. Take care of using the appropriate division factor M to have the specified PLL input clock values.
2. Guaranteed by design, not tested in production.
3. Value given with main PLL running.
4. Based on characterization, not tested in production.

Table 45. PLLISAI (audio and LCD-TFT PLL) characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{PLLSAI_IN}	PLLSAI input clock ⁽¹⁾		0.95 ⁽²⁾	1	2.10	MHz
f_{PLLSAI_OUT}	PLLSAI multiplier output clock		-	-	216	MHz
f_{VCO_OUT}	PLLSAI VCO output		192	-	432	MHz
t_{LOCK}	PLLSAI lock time	VCO freq = 192 MHz	75	-	200	µs
		VCO freq = 432 MHz	100	-	300	
Jitter ⁽³⁾	Main SAI clock jitter	Cycle to cycle at 12.288 MHz on 48KHz period, N=432, R=5	RMS	-	90	-
			peak to peak	-	±280	-
		Average frequency of 12.288 MHz N = 432, R = 5 on 1000 samples		-	90	-
	FS clock jitter	Cycle to cycle at 48 KHz on 1000 samples	-	400	-	ps
$I_{DD(PLLSAI)}^{(4)}$	PLLSAI power consumption on V_{DD}	VCO freq = 192 MHz VCO freq = 432 MHz	0.15 0.45	-	0.40 0.75	mA
$I_{DDA(PLLSAI)}^{(4)}$	PLLSAI power consumption on V_{DDA}	VCO freq = 192 MHz VCO freq = 432 MHz	0.30 0.55	-	0.40 0.85	mA

1. Take care of using the appropriate division factor M to have the specified PLL input clock values.
2. Guaranteed by design, not tested in production.
3. Value given with main PLL running.
4. Based on characterization, not tested in production.

6.3.12 PLL spread spectrum clock generation (SSCG) characteristics

The spread spectrum clock generation (SSCG) feature allows to reduce electromagnetic interferences (see [Table 52: EMI characteristics](#)). It is available only on the main PLL.

Table 46. SSCG parameters constraint

Symbol	Parameter	Min	Typ	Max ⁽¹⁾	Unit
f_{Mod}	Modulation frequency	-	-	10	KHz
md	Peak modulation depth	0.25	-	2	%
MODEPER * INCSTEP		-	-	$2^{15}-1$	-

1. Guaranteed by design, not tested in production.

Equation 1

The frequency modulation period (MODEPER) is given by the equation below:

$$\text{MODEPER} = \text{round}[f_{\text{PLL_IN}} / (4 \times f_{\text{Mod}})]$$

$f_{\text{PLL_IN}}$ and f_{Mod} must be expressed in Hz.

As an example:

If $f_{\text{PLL_IN}} = 1 \text{ MHz}$, and $f_{\text{MOD}} = 1 \text{ kHz}$, the modulation depth (MODEPER) is given by equation 1:

$$\text{MODEPER} = \text{round}[10^6 / (4 \times 10^3)] = 250$$

Equation 2

Equation 2 allows to calculate the increment step (INCSTEP):

$$\text{INCSTEP} = \text{round}[(2^{15} - 1) \times \text{md} \times \text{PLL}_N / (100 \times 5 \times \text{MODEPER})]$$

$f_{\text{VCO_OUT}}$ must be expressed in MHz.

With a modulation depth (md) = $\pm 2 \%$ (4 % peak to peak), and $\text{PLL}_N = 240$ (in MHz):

$$\text{INCSTEP} = \text{round}[(2^{15} - 1) \times 2 \times 240 / (100 \times 5 \times 250)] = 126 \text{md}(\text{quantitized})\%$$

An amplitude quantization error may be generated because the linear modulation profile is obtained by taking the quantized values (rounded to the nearest integer) of MODPER and INCSTEP. As a result, the achieved modulation depth is quantized. The percentage quantized modulation depth is given by the following formula:

$$\text{md}_{\text{quantized}}\% = (\text{MODEPER} \times \text{INCSTEP} \times 100 \times 5) / ((2^{15} - 1) \times \text{PLL}_N)$$

As a result:

$$\text{md}_{\text{quantized}}\% = (250 \times 126 \times 100 \times 5) / ((2^{15} - 1) \times 240) = 2.002\%(\text{peak})$$

Figure 32 and Figure 33 show the main PLL output clock waveforms in center spread and down spread modes, where:

- F0 is f_{PLL_OUT} nominal.
- T_{mode} is the modulation period.
- md is the modulation depth.

Figure 32. PLL output clock waveforms in center spread mode

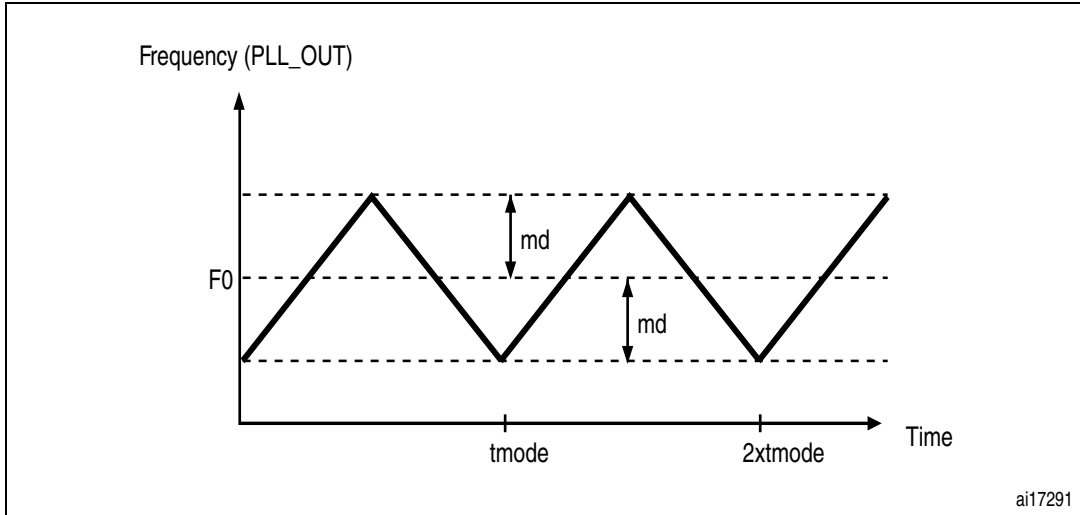
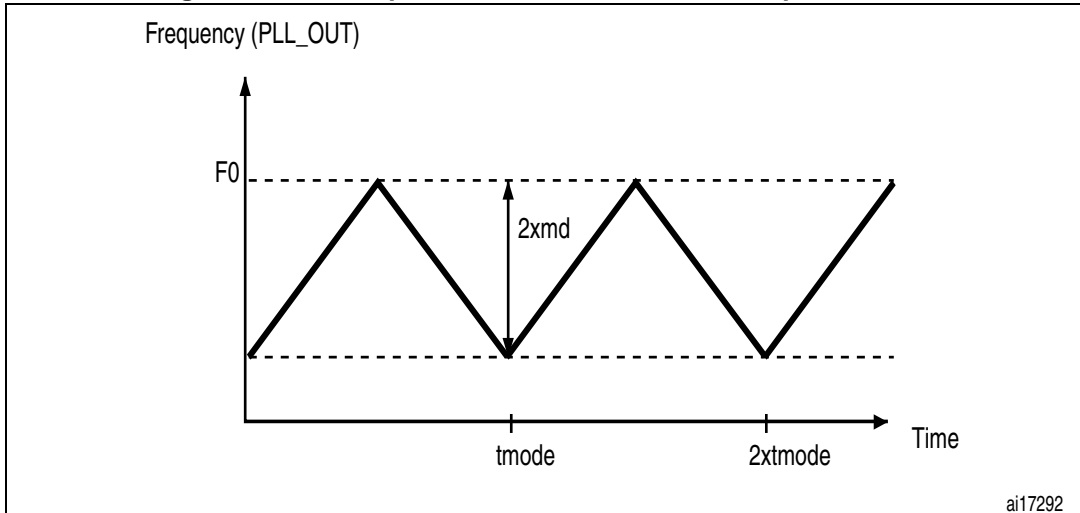


Figure 33. PLL output clock waveforms in down spread mode



6.3.13 Memory characteristics

Flash memory

The characteristics are given at $T_A = -40$ to 105 °C unless otherwise specified.

The devices are shipped to customers with the Flash memory erased.

Table 47. Flash memory characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{DD}	Supply current	Write / Erase 8-bit mode, $V_{DD} = 1.8$ V	-	5	-	mA
		Write / Erase 16-bit mode, $V_{DD} = 2.1$ V	-	8	-	
		Write / Erase 32-bit mode, $V_{DD} = 3.3$ V	-	12	-	

Table 48. Flash memory programming

Symbol	Parameter	Conditions	Min ⁽¹⁾	Typ	Max ⁽¹⁾	Unit
t_{prog}	Word programming time	Program/erase parallelism (PSIZE) = x 8/16/32	-	16	100 ⁽²⁾	μ s
$t_{ERASE16KB}$	Sector (16 KB) erase time	Program/erase parallelism (PSIZE) = x 8	-	400	800	ms
		Program/erase parallelism (PSIZE) = x 16	-	300	600	
		Program/erase parallelism (PSIZE) = x 32	-	250	500	
$t_{ERASE64KB}$	Sector (64 KB) erase time	Program/erase parallelism (PSIZE) = x 8	-	1200	2400	ms
		Program/erase parallelism (PSIZE) = x 16	-	700	1400	
		Program/erase parallelism (PSIZE) = x 32	-	550	1100	
$t_{ERASE128KB}$	Sector (128 KB) erase time	Program/erase parallelism (PSIZE) = x 8	-	2	4	s
		Program/erase parallelism (PSIZE) = x 16	-	1.3	2.6	
		Program/erase parallelism (PSIZE) = x 32	-	1	2	
t_{ME}	Mass erase time	Program/erase parallelism (PSIZE) = x 8	-	16	32	s
		Program/erase parallelism (PSIZE) = x 16	-	11	22	
		Program/erase parallelism (PSIZE) = x 32	-	8	16	

Table 48. Flash memory programming (continued)

Symbol	Parameter	Conditions	Min ⁽¹⁾	Typ	Max ⁽¹⁾	Unit
t _{BE}	Bank erase time	Program/erase parallelism (PSIZE) = x 8	-	16	32	s
		Program/erase parallelism (PSIZE) = x 16	-	11	22	
		Program/erase parallelism (PSIZE) = x 32	-	8	16	
V _{prog}	Programming voltage	32-bit program operation	2.7	-	3.6	V
		16-bit program operation	2.1	-	3.6	V
		8-bit program operation	1.8	-	3.6	V

1. Based on characterization, not tested in production.
2. The maximum programming time is measured after 100K erase operations.

Table 49. Flash memory programming with V_{PP}

Symbol	Parameter	Conditions	Min ⁽¹⁾	Typ	Max ⁽¹⁾	Unit
t _{prog}	Double word programming	T _A = 0 to +40 °C V _{DD} = 3.3 V V _{PP} = 8.5 V	-	16	100 ⁽²⁾	μs
t _{ERASE16KB}	Sector (16 KB) erase time		-	230	-	ms
t _{ERASE64KB}	Sector (64 KB) erase time		-	490	-	
t _{ERASE128KB}	Sector (128 KB) erase time		-	875	-	
t _{ME}	Mass erase time		-	6.9	-	s
t _{BE}	Bank erase time		-	6.9	-	s
V _{prog}	Programming voltage		2.7	-	3.6	V
V _{PP}	V _{PP} voltage range		7	-	9	V
I _{PP}	Minimum current sunk on the V _{PP} pin		10	-	-	mA
t _{VPP} ⁽³⁾	Cumulative time during which V _{PP} is applied		-	-	1	hour

1. Guaranteed by design, not tested in production.
2. The maximum programming time is measured after 100K erase operations.
3. V_{PP} should only be connected during programming/erasing.

Table 50. Flash memory endurance and data retention

Symbol	Parameter	Conditions	Value	Unit
			Min ⁽¹⁾	
N _{END}	Endurance	T _A = -40 to +85 °C (6 suffix versions) T _A = -40 to +105 °C (7 suffix versions)	10	kcycles
t _{RET}	Data retention	1 kcycle ⁽²⁾ at T _A = 85 °C	30	Years
		1 kcycle ⁽²⁾ at T _A = 105 °C	10	
		10 kcycles ⁽²⁾ at T _A = 55 °C	20	

1. Based on characterization, not tested in production.
2. Cycling performed over the whole temperature range.

6.3.14 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports), the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB**: A burst of fast transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in [Table 51](#). They are based on the EMS levels and classes defined in application note AN1709.

Table 51. EMS characteristics

Symbol	Parameter	Conditions	Level/Class
V _{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V _{DD} = 3.3 V, LQFP176, T _A = +25 °C, f _{HCLK} = 168 MHz, conforms to IEC 61000-4-2	2B
V _{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V _{DD} and V _{SS} pins to induce a functional disturbance	V _{DD} = 3.3 V, LQFP176, T _A = +25 °C, f _{HCLK} = 168 MHz, conforms to IEC 61000-4-2	4A

When the application is exposed to a noisy environment, it is recommended to avoid pin exposition to disturbances. The pins showing a middle range robustness are: PA0, PA1, PA2, PH2, PH3, PH4, PH5, PA3, PA4, PA5, PA6, PA7, PC4, and PC5.

As a consequence, it is recommended to add a serial resistor (1 kΩ) located as close as possible to the MCU to the pins exposed to noise (connected to tracks longer than 50 mm on PCB).

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (control registers...)

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application, executing EEMBC[?] code, is running. This emission test is compliant with SAE IEC61967-2 standard which specifies the test board and the pin loading.

Table 52. EMI characteristics

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. [f _{HSE} /f _{CPU}]	Max vs. [f _{HSE} /f _{CPU}]	Unit
				25/168 MHz	25/180 MHz	
S _{EMI}	Peak level	V _{DD} = 3.3 V, T _A = 25 °C, LQFP176 package, conforming to SAE J1752/3 EEMBC, ART ON, all peripheral clocks enabled, clock dithering disabled.	0.1 to 30 MHz	16	19	dBμV
			30 to 130 MHz	23	23	
			130 MHz to 1GHz	25	22	
			SAE EMI Level	4	4	-
		V _{DD} = 3.3 V, T _A = 25 °C, LQFP176 package, conforming to SAE J1752/3 EEMBC, ART ON, all peripheral clocks enabled, clock dithering enabled	0.1 to 30 MHz	17	16	dBμV
			30 to 130 MHz	8	10	
			130 MHz to 1GHz	11	16	
			SAE EMI level	3.5	3.5	-

6.3.15 Absolute maximum ratings (electrical sensitivity)

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the JESD22-A114/C101 standard.

Table 53. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Class	Maximum value ⁽¹⁾	Unit
V _{ESD(HBM)}	Electrostatic discharge voltage (human body model)	T _A = +25 °C conforming to JESD22-A114	2	2000	V
V _{ESD(CDM)}	Electrostatic discharge voltage (charge device model)	T _A = +25 °C conforming to JESD22-C101	II	500	

1. Based on characterization results, not tested in production.

Static latchup

Two complementary static tests are required on six parts to assess the latchup performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD 78A IC latchup standard.

Table 54. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	T _A = +105 °C conforming to JESD78A	II level A

6.3.16 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard, 3 V-capable I/O pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (>5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of – 5 μA/+0 μA range), or other functional failure (for example reset, oscillator frequency deviation).

Negative induced leakage current is caused by negative injection and positive induced leakage current by positive injection.

The test results are given in [Table 55](#).

Table 55. I/O current injection susceptibility⁽¹⁾

Symbol	Description	Functional susceptibility		Unit
		Negative injection	Positive injection	
I _{INJ}	Injected current on B pin	-0	NA	mA
	Injected current on NRST pin	-0	NA	
	Injected current on PH1, PC0, PC1, PC2, PC3, PA0, PA1, PA2, PH2, PH3, PH4, PH5, PA3, PA6, PA7, PC4, PC5, PB0	-0	NA	
	Injected current on TTa pins: PA4 and PA5	-0	+5	
	Injected current on any other FT pin	-5	NA	
	Injected current on any other pin	-5	+5	

1. NA = not applicable.

Note: It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.

6.3.17 I/O port characteristics

General input/output characteristics

Unless otherwise specified, the parameters given in [Table 56](#) are derived from tests performed under the conditions summarized in [Table 17](#). All I/Os are CMOS and TTL compliant.

Table 56. I/O static characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{IL}	Input low level voltage	TTL compliant	-	-	0.8	V
V _{IH}	Input high level voltage	2.7 V ≤ V _{DD} ≤ 3.6 V	2.0	-	-	
V _{IL} ⁽¹⁾	Input low level voltage	CMOS compliant	-	-	0.3V _{DD}	
V _{IH} ⁽¹⁾	Input high level voltage	1.8 V ≤ V _{DD} ≤ 3.6 V	0.7V _{DD}	-	-	
V _{hys}	I/O Schmitt trigger voltage hysteresis ⁽²⁾		-	200	-	mV
	IO FT Schmitt trigger voltage hysteresis ⁽²⁾		5% V _{DD} ⁽³⁾	-	-	
I _{Ikg}	I/O input leakage current ⁽⁴⁾	V _{SS} ≤ V _{IN} ≤ V _{DD}	-	-	±1	μA
	I/O FT input leakage current ⁽⁵⁾	V _{IN} = 5 V	-	-	3	

Table 56. I/O static characteristics (continued)

Symbol	Parameter		Conditions	Min	Typ	Max	Unit
R _{PU}	Weak pull-up equivalent resistor ⁽⁶⁾	All pins except for PA10 and PB12	V _{IN} = V _{SS}	30	40	50	kΩ
		PA10 and PB12		8	11	15	
R _{PD}	Weak pull-down equivalent resistor ⁽⁷⁾	All pins except for PA10 and PB12	V _{IN} = V _{DD}	30	40	50	
		PA10 and PB12		8	11	15	
C _{I/O} ⁽⁸⁾	I/O pin capacitance				5		pF

1. Tested in production.
2. Hysteresis voltage between Schmitt trigger switching levels. Based on characterization, not tested in production.
3. With a minimum of 100 mV.
4. Leakage could be higher than the maximum value, if negative current is injected on adjacent pins, Refer to [Table 55: I/O current injection susceptibility](#)
5. To sustain a voltage higher than VDD +0.3 V, the internal pull-up/pull-down resistors must be disabled. Leakage could be higher than the maximum value, if negative current is injected on adjacent pins. Refer to [Table 55: I/O current injection susceptibility](#)
6. Pull-up resistors are designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is minimum (~10% order).
7. Pull-down resistors are designed with a true resistance in series with a switchable NMOS. This NMOS contribution to the series resistance is minimum (~10% order).
8. Voltage hysteresis between Schmitt trigger switching levels. Based on characterization, not tested in production.

Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to ±8 mA, and sink or source up to ±20 mA (with a relaxed V_{OL}/V_{OH}) except PC13, PC14, PC15 and PI8 which can sink or source up to ±3mA. When using the PC13 to PC15 and PI8 GPIOs in output mode, the speed should not exceed 2 MHz with a maximum load of 30 pF.

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in [Section 6.2](#). In particular:

- The sum of the currents sourced by all the I/Os on V_{DD}, plus the maximum Run consumption of the MCU sourced on V_{DD}, cannot exceed the absolute maximum rating ΣI_{VDD} (see [Table 15](#)).
- The sum of the currents sunk by all the I/Os on V_{SS} plus the maximum Run consumption of the MCU sunk on V_{SS} cannot exceed the absolute maximum rating ΣI_{VSS} (see [Table 15](#)).

Output voltage levels

Unless otherwise specified, the parameters given in [Table 57](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 17](#). All I/Os are CMOS and TTL compliant.

Table 57. Output voltage characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{OL}^{(2)}$	Output low level voltage for an I/O pin	CMOS port ⁽³⁾ $I_{IO} = +8 \text{ mA}$ $2.7 \text{ V} < V_{DD} < 3.6 \text{ V}$	-	0.4	V
$V_{OH}^{(4)}$	Output high level voltage for an I/O pin		$V_{DD}-0.4$	-	
$V_{OL}^{(2)}$	Output low level voltage for an I/O pin	TTL port ⁽³⁾ $I_{IO} = +8 \text{ mA}$ $2.7 \text{ V} < V_{DD} < 3.6 \text{ V}$	-	0.4	V
$V_{OH}^{(4)}$	Output high level voltage for an I/O pin		2.4	-	
$V_{OL}^{(2)(5)}$	Output low level voltage for an I/O pin	$I_{IO} = +20 \text{ mA}$ $2.7 \text{ V} < V_{DD} < 3.6 \text{ V}$	-	1.3	V
$V_{OH}^{(4)(5)}$	Output high level voltage for an I/O pin		$V_{DD}-1.3$	-	
$V_{OL}^{(2)(5)}$	Output low level voltage for an I/O pin	$I_{IO} = +6 \text{ mA}$ $2 \text{ V} < V_{DD} < 2.7 \text{ V}$	-	0.4	V
$V_{OH}^{(4)(5)}$	Output high level voltage for an I/O pin		$V_{DD}-0.4$	-	

1. PC13, PC14, PC15 and PI8 are supplied through the power switch. Since the switch only sinks a limited amount of current (3 mA), the use of GPIOs PC13 to PC15 and PI8 in output mode is limited: the speed should not exceed 2 MHz with a maximum load of 30 pF and these I/Os must not be used as a current source (e.g. to drive an LED).
2. The I_{IO} current sunk by the device must always respect the absolute maximum rating specified in [Table 15](#) and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VSS} .
3. TTL and CMOS outputs are compatible with JEDEC standards JESD36 and JESD52.
4. The I_{IO} current sourced by the device must always respect the absolute maximum rating specified in [Table 15](#) and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VDD} .
5. Based on characterization data, not tested in production.

Input/output AC characteristics

The definition and values of input/output AC characteristics are given in [Figure 34](#) and [Table 58](#), respectively.

Unless otherwise specified, the parameters given in [Table 58](#) are derived from tests performed under the ambient temperature and V_{DD} supply voltage conditions summarized in [Table 17](#).

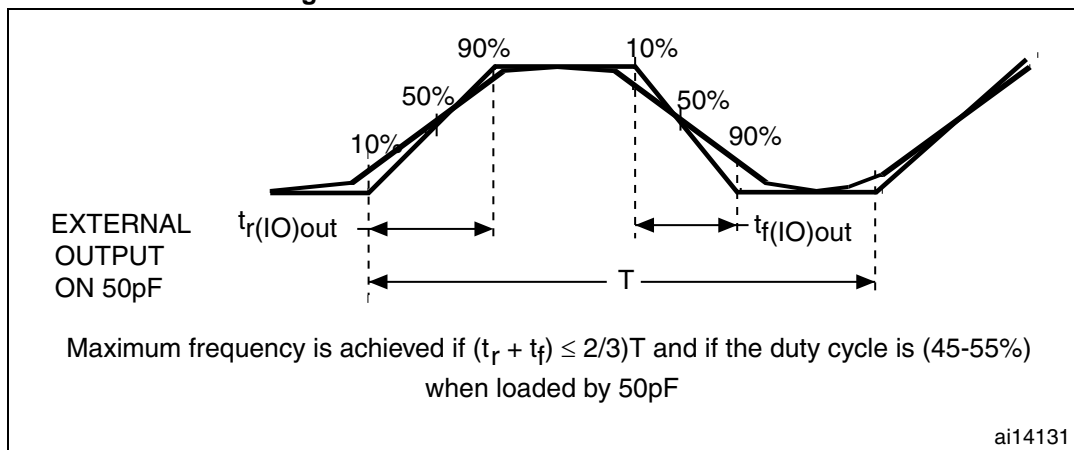
Table 58. I/O AC characteristics⁽¹⁾⁽²⁾

OSPEEDRy [1:0] bit value ⁽¹⁾	Symbol	Parameter	Conditions	Min	Typ	Max	Unit
00	f _{max(IO)out}	Maximum frequency ⁽³⁾	C _L = 50 pF, V _{DD} > 2.70 V	-	-	4	MHz
			C _L = 50 pF, V _{DD} > 1.8 V	-	-	2	
			C _L = 10 pF, V _{DD} > 2.70 V	-	-	8	
			C _L = 10 pF, V _{DD} > 1.8 V	-	-	4	
	t _{f(IO)out} / t _{r(IO)out}	Output high to low level fall time and output low to high level rise time	C _L = 50 pF, V _{DD} = 1.8 V to 3.6 V	-	-	100	ns
01	f _{max(IO)out}	Maximum frequency ⁽³⁾	C _L = 50 pF, V _{DD} > 2.70 V	-	-	25	MHz
			C _L = 50 pF, V _{DD} > 1.8 V	-	-	12.5	
			C _L = 10 pF, V _{DD} > 2.70 V	-	-	50 ⁽⁴⁾	
			C _L = 10 pF, V _{DD} > 1.8 V	-	-	20	
	t _{f(IO)out} / t _{r(IO)out}	Output high to low level fall time and output low to high level rise time	C _L = 50 pF, V _{DD} > 2.7 V	-	-	10	ns
			C _L = 50 pF, V _{DD} > 1.8 V	-	-	20	
			C _L = 10 pF, V _{DD} > 2.70 V	-	-	6	
			C _L = 10 pF, V _{DD} > 1.8 V	-	-	10	
10	f _{max(IO)out}	Maximum frequency ⁽³⁾	C _L = 40 pF, V _{DD} > 2.70 V	-	-	50 ⁽⁴⁾	MHz
			C _L = 40 pF, V _{DD} > 1.8 V	-	-	25	
			C _L = 10 pF, V _{DD} > 2.70 V	-	-	100 ⁽⁴⁾	
			C _L = 10 pF, V _{DD} > 1.8 V	-	-	50 ⁽⁴⁾	
	t _{f(IO)out} / t _{r(IO)out}	Output high to low level fall time and output low to high level rise time	C _L = 40 pF, V _{DD} > 2.70 V	-	-	6	ns
			C _L = 40 pF, V _{DD} > 1.8 V	-	-	10	
			C _L = 10 pF, V _{DD} > 2.70 V	-	-	4	
			C _L = 10 pF, V _{DD} > 1.8 V	-	-	6	
11	F _{max(IO)out}	Maximum frequency ⁽³⁾	C _L = 30 pF, V _{DD} > 2.70 V	-	-	100 ⁽⁴⁾	MHz
			C _L = 30 pF, V _{DD} > 1.8 V	-	-	50 ⁽⁴⁾	
			C _L = 10 pF, V _{DD} > 2.70 V	-	-	180 ⁽⁴⁾	
			C _L = 10 pF, V _{DD} > 1.8 V	-	-	100 ⁽⁴⁾	
	t _{f(IO)out} / t _{r(IO)out}	Output high to low level fall time and output low to high level rise time	C _L = 30 pF, V _{DD} > 2.70 V	-	-	4	ns
			C _L = 30 pF, V _{DD} > 1.8 V	-	-	6	
			C _L = 10 pF, V _{DD} > 2.70 V	-	-	2.5	
			C _L = 10 pF, V _{DD} > 1.8 V	-	-	4	
-	t _{EXTIpw}	Pulse width of external signals detected by the EXTI controller		10	-	-	ns

1. Based on characterization data, not tested in production.

- The I/O speed is configured using the OSPEEDRy[1:0] bits. Refer to the STM32F4xx reference manual for a description of the GPIOx_SPEEDR GPIO port output speed register.
- The maximum frequency is defined in [Figure 34](#).
- For maximum frequencies above 50 MHz, the compensation cell should be used.

Figure 34. I/O AC characteristics definition



6.3.18 NRST pin characteristics

The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor, R_{PU} (see [Table 56](#)).

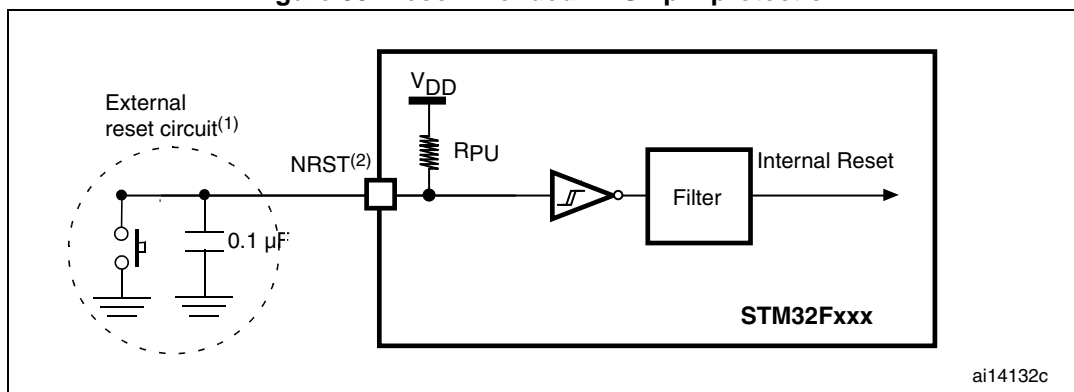
Unless otherwise specified, the parameters given in [Table 59](#) are derived from tests performed under the ambient temperature and V_{DD} supply voltage conditions summarized in [Table 17](#).

Table 59. NRST pin characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{IL(NRST)}^{(1)}$	NRST Input low level voltage	TTL ports $2.7V \leq V_{DD} \leq 3.6V$	-	-	0.8	V
$V_{IH(NRST)}^{(1)}$	NRST Input high level voltage		2	-	-	
$V_{IL(NRST)}^{(1)}$	NRST Input low level voltage	CMOS ports $1.8V \leq V_{DD} \leq 3.6V$	-	-	0.3VDD	
$V_{IH(NRST)}^{(1)}$	NRST Input high level voltage		0.7VDD	-	-	
$V_{hys(NRST)}$	NRST Schmitt trigger voltage hysteresis		-	200	-	mV
R_{PU}	Weak pull-up equivalent resistor ⁽²⁾	$V_{IN} = V_{SS}$	30	40	50	kΩ
$V_{F(NRST)}^{(1)}$	NRST Input filtered pulse		-	-	100	ns
$V_{NF(NRST)}^{(1)}$	NRST Input not filtered pulse	$V_{DD} > 2.7 V$	300	-	-	ns
T_{NRST_OUT}	Generated reset pulse duration	Internal Reset source	20	-	-	μs

- Guaranteed by design, not tested in production.
- The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance must be minimum (~10% order).

Figure 35. Recommended NRST pin protection



1. The reset network protects the device against parasitic resets.
2. The user must ensure that the level on the NRST pin can go below the $V_{IL(NRST)}$ max level specified in [Table 59](#). Otherwise the reset is not taken into account by the device.

6.3.19 TIM timer characteristics

The parameters given in [Table 60](#) are guaranteed by design.

Refer to [Section 6.3.17: I/O port characteristics](#) for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

Table 60. TIMx characteristics⁽¹⁾⁽²⁾

Symbol	Parameter	Conditions ⁽³⁾	Min	Max	Unit
$t_{res(TIM)}$	Timer resolution time	AHB/APBx prescaler=1 or 2 or 4, $f_{TIMxCLK} = 180\text{ MHz}$	1	-	$t_{TIMxCLK}$
		AHB/APBx prescaler>4, $f_{TIMxCLK} = 90\text{ MHz}$	1	-	$t_{TIMxCLK}$
f_{EXT}	Timer external clock frequency on CH1 to CH4	$f_{TIMxCLK} = 180\text{ MHz}$	0	$f_{TIMxCLK}/2$	MHZ
Res_{TIM}	Timer resolution		-	16/32	bit
t_{MAX_COUNT}	Maximum possible count with 32-bit counter		-	65536×65536	$t_{TIMxCLK}$

1. TIMx is used as a general term to refer to the TIM1 to TIM12 timers.
2. Guaranteed by design, not tested in production.
3. The maximum timer frequency on APB1 or APB2 is up to 180 MHz, by setting the TIMPRE bit in the RCC_DCKCFGR register, if APBx prescaler is 1 or 2 or 4, then $TIMxCLK = HCKL$, otherwise $TIMxCLK = 4x PCLKx$.

6.3.20 Communications interfaces

I²C interface characteristics

The I²C interface meets the requirements of the standard I²C communication protocol with the following restrictions: the I/O pins SDA and SCL are mapped to are not “true” open-drain. When configured as open-drain, the PMOS connected between the I/O pin and V_{DD} is disabled, but is still present.

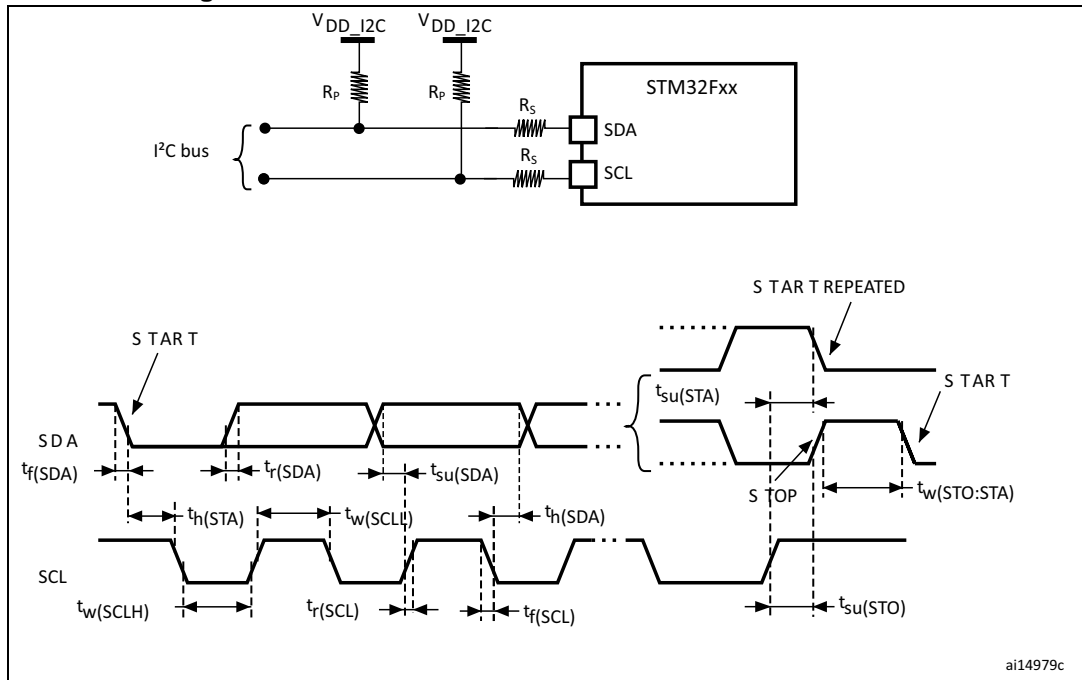
The I²C characteristics are described in [Table 61](#). Refer also to [Section 6.3.17: I/O port characteristics](#) for more details on the input/output alternate function characteristics (SDA and SCL).

Table 61. I²C characteristics

Symbol	Parameter	Standard mode I ² C ⁽¹⁾		Fast mode I ² C ⁽¹⁾⁽²⁾		Unit
		Min	Max	Min	Max	
t _{w(SCLL)}	SCL clock low time	4.7	-	1.3	-	μs
t _{w(SCLH)}	SCL clock high time	4.0	-	0.6	-	
t _{su(SDA)}	SDA setup time	250	-	100	-	ns
t _{h(SDA)}	SDA data hold time	0 ⁽³⁾	-	0	900 ⁽⁴⁾	
t _{r(SDA)} t _{r(SCL)}	SDA and SCL rise time	-	1000	-	300	
t _{f(SDA)} t _{f(SCL)}	SDA and SCL fall time	-	300	-	300	
t _{h(STA)}	Start condition hold time	4.0	-	0.6	-	μs
t _{su(STA)}	Repeated Start condition setup time	4.7	-	0.6	-	
t _{su(STO)}	Stop condition setup time	4.0	-	0.6	-	μs
t _{w(STO:STA)}	Stop to Start condition time (bus free)	4.7	-	1.3	-	μs
C _b	Capacitive load for each bus line	-	400	-	400	pF

1. Guaranteed by design, not tested in production.
2. f_{PCLK1} must be at least 2 MHz to achieve standard mode I²C frequencies. It must be at least 4 MHz to achieve fast mode I²C frequencies, and a multiple of 10 MHz to reach the 400 kHz maximum I²C fast mode clock.
3. The device must internally provide a hold time of at least 300 ns for the SDA signal in order to bridge the undefined region of the falling edge of SCL.
4. The maximum data hold time has only to be met if the interface does not stretch the low period of SCL signal.

Figure 36. I²C bus AC waveforms and measurement circuit



1. R_S = series protection resistor.
2. R_P = external pull-up resistor.
3. V_{DD_I2C} is the I2C bus power supply.

Table 62. SCL frequency ($f_{PCLK1} = 42\text{ MHz}, V_{DD} = V_{DD_I2C} = 3.3\text{ V}$)⁽¹⁾⁽²⁾

f_{SCL} (kHz)	I2C_CCR value
	$R_P = 4.7\text{ k}\Omega$
400	0x8019
300	0x8021
200	0x8032
100	0x0096
50	0x012C
20	0x02EE

1. R_P = External pull-up resistance, f_{SCL} = I²C speed,
2. For speeds around 200 kHz, the tolerance on the achieved speed is of $\pm 5\%$. For other speed ranges, the tolerance on the achieved speed $\pm 2\%$. These variations depend on the accuracy of the external components used to design the application.

SPI interface characteristics

Unless otherwise specified, the parameters given in [Table 63](#) for the SPI interface are derived from tests performed under the ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in [Table 17](#), with the following configuration:

- Output speed is set to $OSPEEDRy[1:0] = 10$
- Capacitive load $C = 30 \text{ pF}$
- Measurement points are done at CMOS levels: $0.5V_{DD}$

Refer to [Section 6.3.17: I/O port characteristics](#) for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO for SPI).

Table 63. SPI dynamic characteristics⁽¹⁾

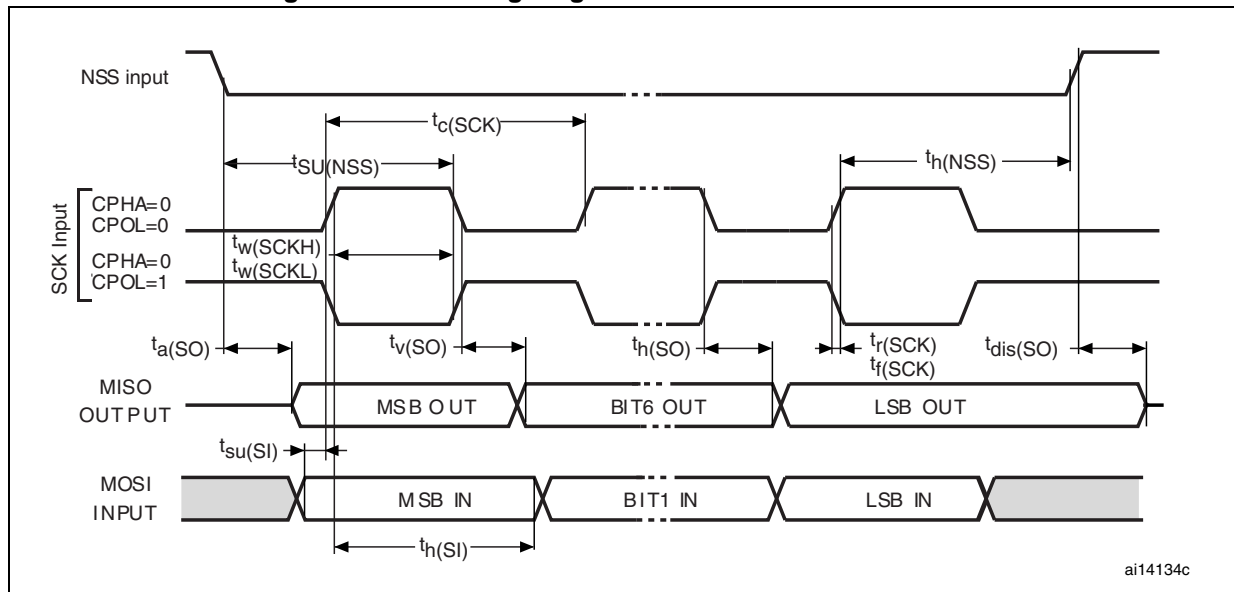
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{SCK}	SPI clock frequency	Master mode, SPI1/4/5/6, 2.7 V < V_{DD} < 3.6 V	-	-	45	MHz
		Slave mode, SPI1/4/5/6, 2.7 V < V_{DD} < 3.6 V			45	
$1/t_{c(SCK)}$		Master mode, SPI1/2/3/4/5/6, 1.8 V < V_{DD} < 3.6 V	-	-	22.5	
		Slave mode, SPI1/2/3/4/5/6, 1.8 V < V_{DD} < 3.6 V			22.5	
Duty(SCK)	Duty cycle of SPI clock frequency	Slave mode	30	50	70	%
$t_{w(SCKH)}$	SCK high and low time	Master mode, SPI presc = 2, 2.7 V < V_{DD} < 3.6 V	$T_{PCLK} - 0.5$	T_{PCLK}	$T_{PCLK} + 0.5$	ns
$t_{w(SCKL)}$		Master mode, SPI presc = 2, 1.8 V < V_{DD} < 3.6 V	$T_{PCLK} - 2$	T_{PCLK}	$T_{PCLK} + 2$	ns
$t_{su(NSS)}$	NSS setup time	Slave mode, SPI presc = 2	$4T_{PCLK}$	-	-	ns
$t_{h(NSS)}$	NSS hold time	Slave mode, SPI presc = 2	$2T_{PCLK}$	-	-	ns
$t_{su(MI)}$	Data input setup time	Master mode	3	-	-	ns
$t_{su(SI)}$		Slave mode	0	-	-	ns
$t_{h(MI)}$	Data input hold time	Master mode	0.5	-	-	ns
$t_{h(SI)}$		Slave mode	2	-	-	ns
$t_{a(SO)}^{(2)}$	Data output access time	Slave mode, SPI presc = 2	0	-	$4T_{PCLK}$	ns
$t_{dis(SO)}^{(3)}$	Data output disable time	Slave mode, SPI1/4/5/6, 2.7 V < V_{DD} < 3.6 V	0	-	8.5	ns
		Slave mode, SPI1/2/3/4/5/6 and 1.8 V < V_{DD} < 3.6 V	0	-	16.5	ns

Table 63. SPI dynamic characteristics⁽¹⁾ (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{v(SO)}$ $t_{h(SO)}$	Data output valid/hold time	Slave mode (after enable edge), SPI1/4/5/6 and $2.7V < V_{DD} < 3.6V$	-	11	13	ns
		Slave mode (after enable edge), SPI2/3, $2.7V < V_{DD} < 3.6V$	-	14	15	ns
		Slave mode (after enable edge), SPI1/4/5/6, $1.8V < V_{DD} < 3.6V$	-	15.5	19	ns
		Slave mode (after enable edge), SPI2/3, $1.8V < V_{DD} < 3.6V$	-	15.5	17.5	ns
$t_{v(MO)}$	Data output valid time	Master mode (after enable edge), SPI1/4/5/6, $2.7V < V_{DD} < 3.6V$	-	-	2.5	ns
		Master mode (after enable edge), SPI1/2/3/4/5/6, $1.8V < V_{DD} < 3.6V$	-	-	4.5	ns
$t_{h(MO)}$	Data output hold time	Master mode (after enable edge)	0	-	-	ns

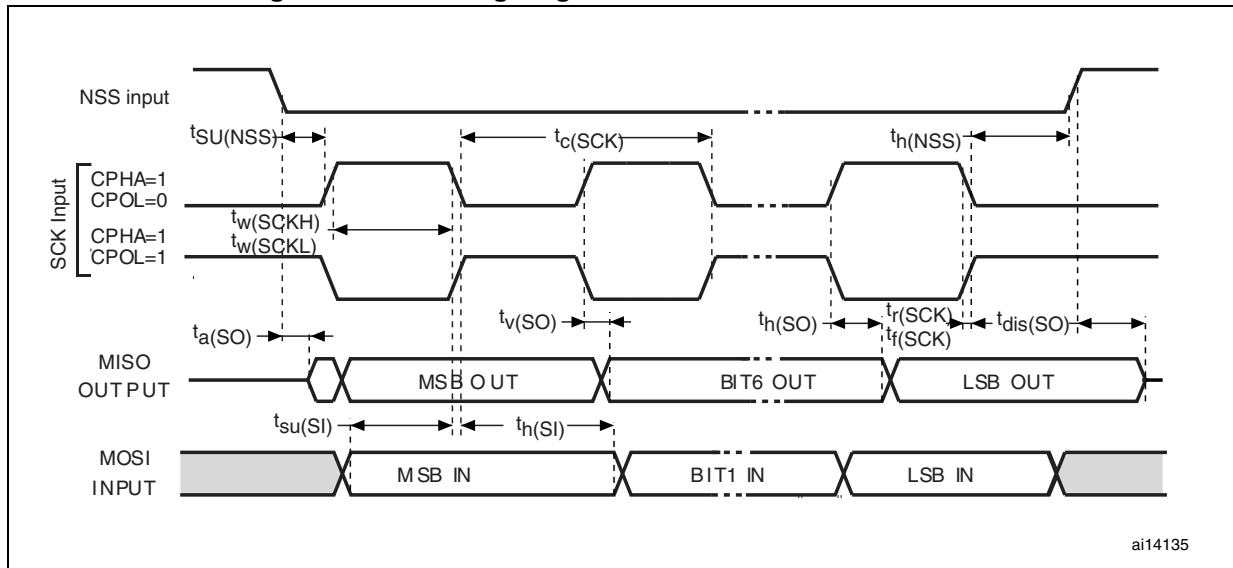
1. Data based on characterization results, not tested in production.
2. The minimum value of this timing corresponds to the minimum time to drive the output, and the maximum value to maximum time to validate the data.
3. The minimum value of this timing corresponds to the minimum time to invalidate the output and the maximum value to the maximum time to put the data in Hi-Z.

Figure 37. SPI timing diagram - slave mode and CPHA = 0



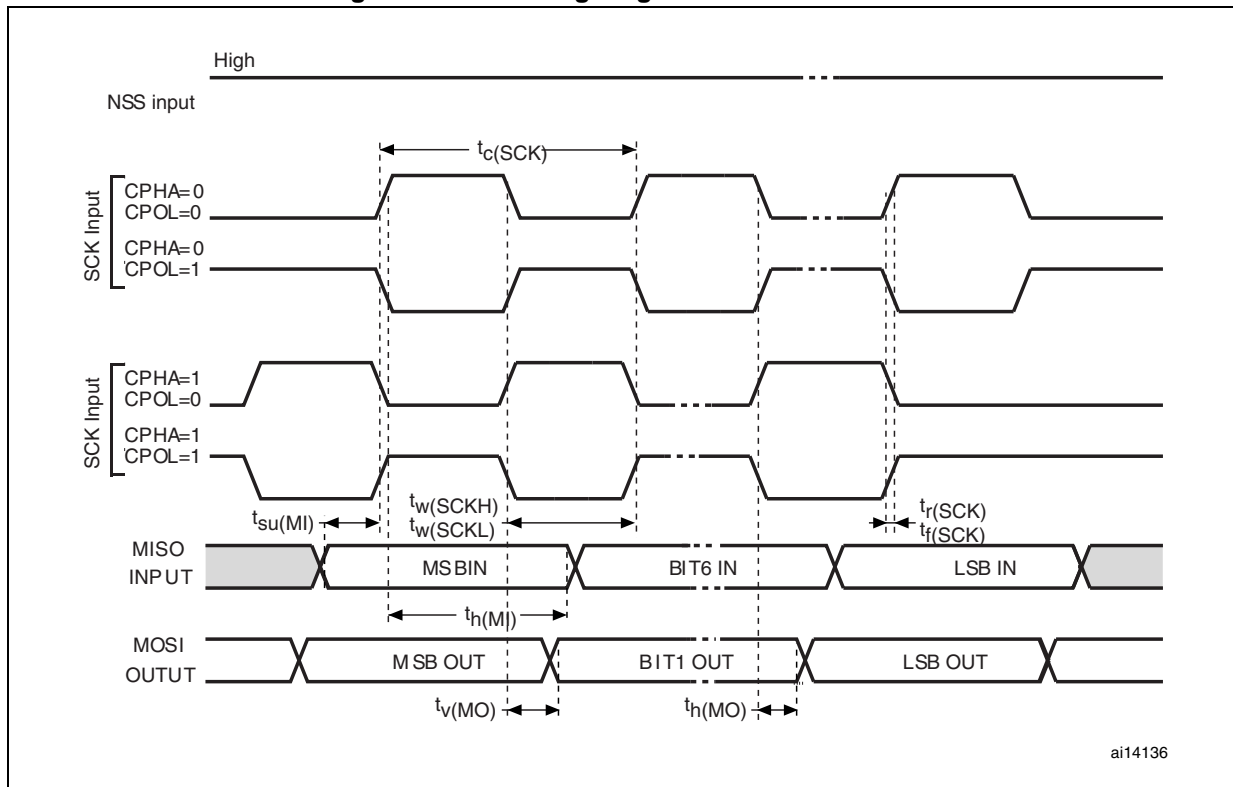
ai14134c

Figure 38. SPI timing diagram - slave mode and CPHA = 1⁽¹⁾



ai14135

Figure 39. SPI timing diagram - master mode⁽¹⁾



ai14136

I²S interface characteristics

Unless otherwise specified, the parameters given in [Table 64](#) for the I²S interface are derived from tests performed under the ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in [Table 17](#), with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: $0.5V_{DD}$

Refer to [Section 6.3.17: I/O port characteristics](#) for more details on the input/output alternate function characteristics (CK, SD, WS).

Table 64. I²S dynamic characteristics⁽¹⁾

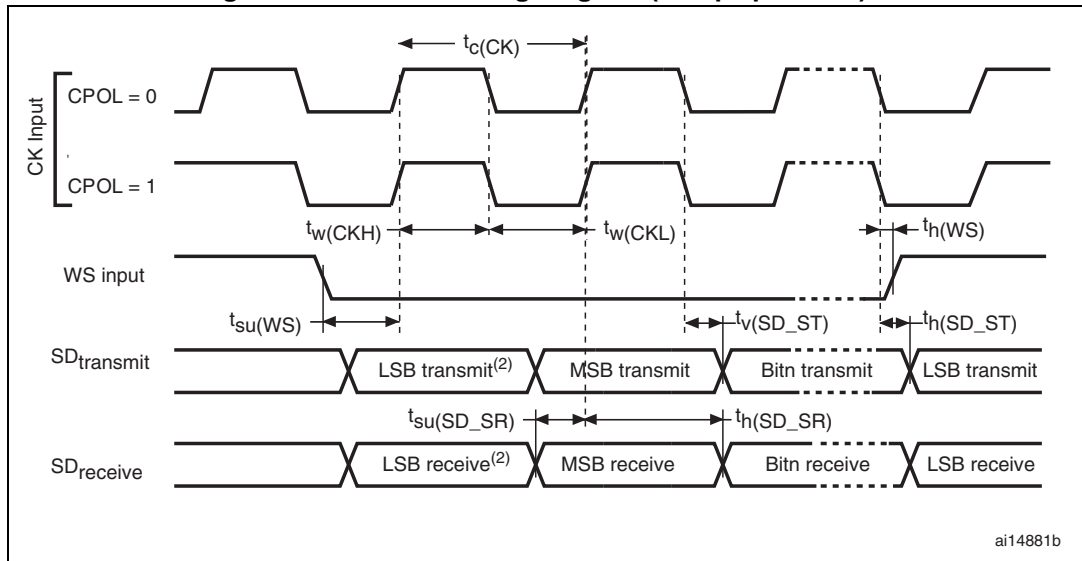
Symbol	Parameter	Conditions	Min	Max	Unit
f_{MCK}	I2S Main clock output	-	256x8K	256x F_S ⁽²⁾	MHz
f_{CK}	I2S clock frequency	Master data: 32 bits	-	64x F_S	MHz
		Slave data: 32 bits	-	64x F_S	
D_{CK}	I2S clock frequency duty cycle	Slave receiver	30	70	%
$t_{v(WS)}$	WS valid time	Master mode	0	6	ns
$t_{h(WS)}$	WS hold time	Master mode	0	-	
$t_{su(WS)}$	WS setup time	Slave mode	1	-	
$t_{h(WS)}$	WS hold time	Slave mode	0	-	
$t_{su(SD_MR)}$	Data input setup time	Master receiver	7.5	-	
$t_{su(SD_SR)}$		Slave receiver	2	-	
$t_{h(SD_MR)}$	Data input hold time	Master receiver	0	-	
$t_{h(SD_SR)}$		Slave receiver	0	-	
$t_{v(SD_ST)}$	Data output valid time	Slave transmitter (after enable edge)	-	27	
$t_{h(SD_ST)}$		Master transmitter (after enable edge)	-	20	
$t_{v(SD_MT)}$			Master transmitter (after enable edge)	-	
$t_{h(SD_MT)}$	Data output hold time	Master transmitter (after enable edge)	2.5	-	

1. Data based on characterization results, not tested in production.
2. The maximum value of 256x F_S is 45 MHz (APB1 maximum frequency).

Note: Refer to the I2S section of RM0090 reference manual for more details on the sampling frequency (F_S).

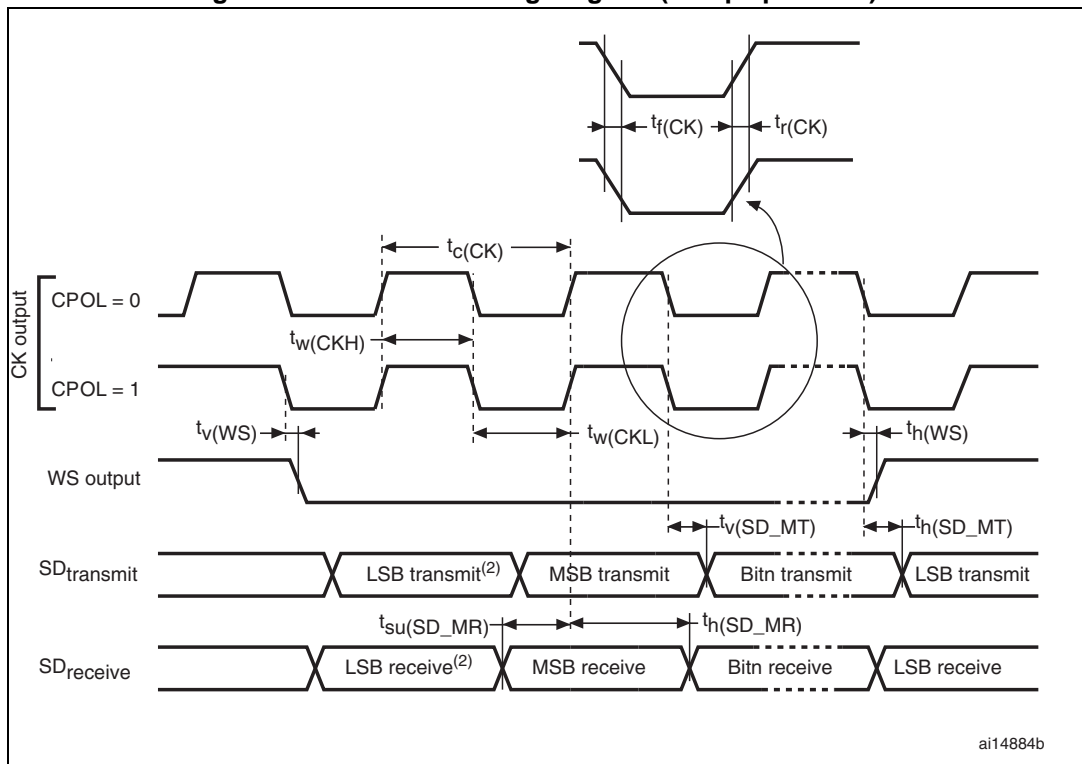
f_{MCK} , f_{CK} , and D_{CK} values reflect only the digital peripheral behavior. The values of these parameters might be slightly impacted by the source clock precision. D_{CK} depends mainly on the value of ODD bit. The digital contribution leads to a minimum value of $(I2SDIV/(2*I2SDIV+ODD))$ and a maximum value of $(I2SDIV+ODD)/(2*I2SDIV+ODD)$. F_S maximum value is supported for each mode/condition.

Figure 40. I²S slave timing diagram (Philips protocol)⁽¹⁾



1. .LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

Figure 41. I²S master timing diagram (Philips protocol)⁽¹⁾



1. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

SAI characteristics

Unless otherwise specified, the parameters given in [Table 65](#) for SAI are derived from tests performed under the ambient temperature, f_{PCLKx} frequency and VDD supply voltage conditions summarized in [Table 17](#), with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load C=30 pF
- Measurement points are performed at CMOS levels: 0.5V_{DD}

Refer to [Section 6.3.17: I/O port characteristics](#) for more details on the input/output alternate function characteristics (SCK,SD,WS).

Table 65. SAI characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Max	Unit
f _{MCKL}	SAI Main clock output	-	256 x 8K	256xFs ⁽²⁾	MHz
F _{SCK}	SAI clock frequency	Master data: 32 bits	-	64xFs	MHz
		Slave data: 32 bits	-	64xFs	
D _{SCK}	SAI clock frequency duty cycle	Slave receiver	30	70	%
t _{v(FS)}	FS valid time	Master mode	8	22	ns
t _{su(FS)}	FS setup time	Slave mode	2	-	
t _{h(FS)}	FS hold time	Master mode	8	-	
		Slave mode	0	-	
t _{su(SD_MR)}	Data input setup time	Master receiver	5	-	
t _{su(SD_SR)}		Slave receiver	3	-	
t _{h(SD_MR)}	Data input hold time	Master receiver	0	-	
t _{h(SD_SR)}		Slave receiver	0	-	
t _{v(SD_ST)}	Data output valid time	Slave transmitter (after enable edge)	-	22	
t _{h(SD_ST)}		Master transmitter (after enable edge)	-	20	
t _{v(SD_MT)}	Data output hold time	Master transmitter (after enable edge)	8	-	
t _{h(SD_MT)}					

1. Data based on characterization results, not tested in production.
2. 256xFs maximum corresponds to 45 MHz (APB2 xaximum frequency)

Figure 42. SAI master timing waveforms

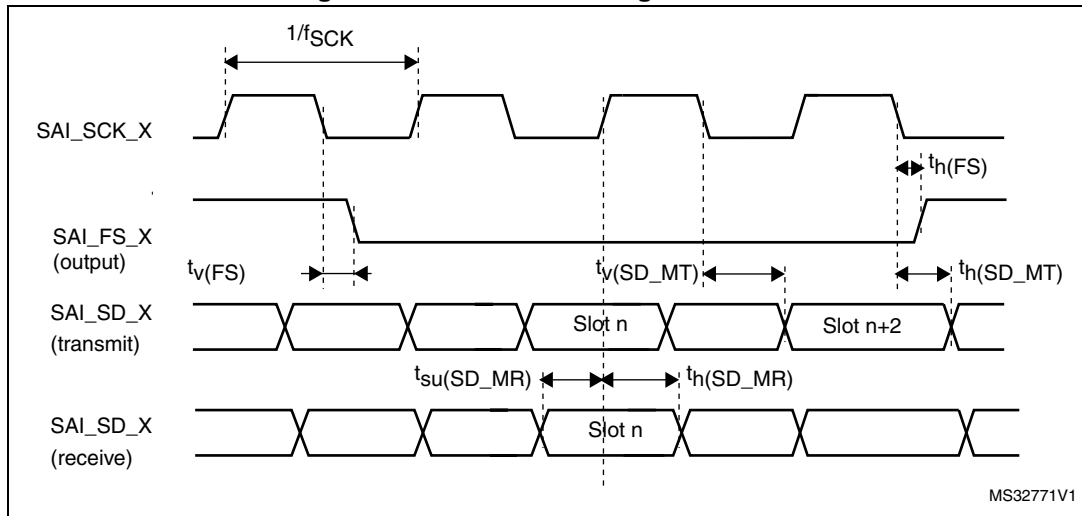
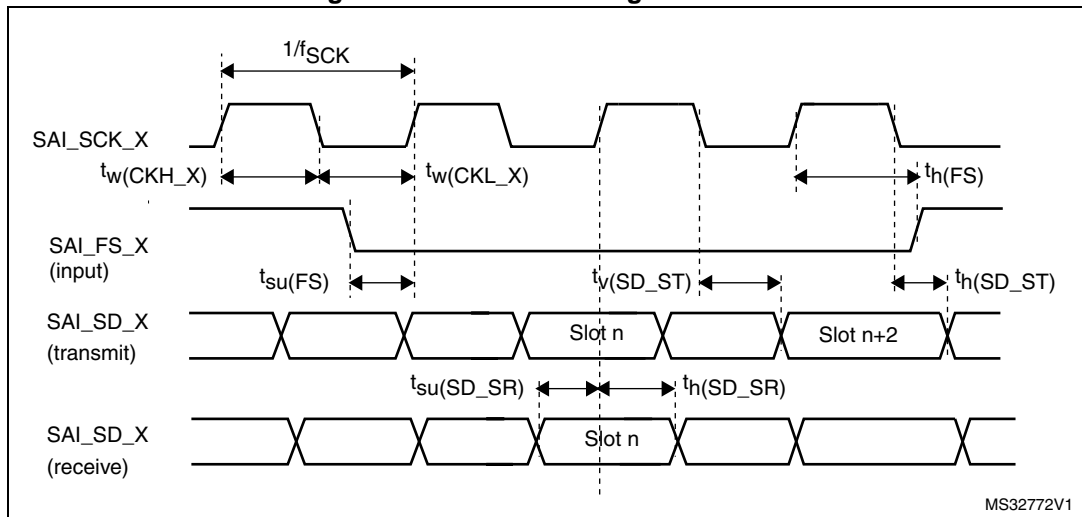


Figure 43. SAI slave timing waveforms



USB OTG full speed (FS) characteristics

This interface is present in both the USB OTG HS and USB OTG FS controllers.

Table 66. USB OTG FS startup time

Symbol	Parameter	Max	Unit
$t_{STARTUP}^{(1)}$	USB OTG FS transceiver startup time	1	μs

1. Guaranteed by design, not tested in production.

Table 67. USB OTG FS DC electrical characteristics

Symbol	Parameter	Conditions	Min. ⁽¹⁾	Typ.	Max. ⁽¹⁾	Unit	
Input levels	V_{DD}	USB OTG FS operating voltage	3.0 ⁽²⁾	-	3.6	V	
	$V_{DI}^{(3)}$	Differential input sensitivity	I(USB_FS_DP/DM, USB_HS_DP/DM)	0.2	-	-	V
	$V_{CM}^{(3)}$	Differential common mode range	Includes V_{DI} range	0.8	-	2.5	
	$V_{SE}^{(3)}$	Single ended receiver threshold		1.3	-	2.0	
Output levels	V_{OL}	Static output level low	R_L of 1.5 k Ω to 3.6 V ⁽⁴⁾	-	-	0.3	V
	V_{OH}	Static output level high	R_L of 15 k Ω to $V_{SS}^{(4)}$	2.8	-	3.6	
R_{PD}	PA11, PA12, PB14, PB15 (USB_FS_DP/DM, USB_HS_DP/DM)	$V_{IN} = V_{DD}$	17	21	24	k Ω	
	PA9, PB13 (OTG_FS_VBUS, OTG_HS_VBUS)		0.65	1.1	2.0		
R_{PU}	PA12, PB15 (USB_FS_DP, USB_HS_DP)	$V_{IN} = V_{SS}$	1.5	1.8	2.1		
	PA9, PB13 (OTG_FS_VBUS, OTG_HS_VBUS)	$V_{IN} = V_{SS}$	0.25	0.37	0.55		

1. All the voltages are measured from the local ground potential.
2. The USB OTG FS functionality is ensured down to 2.7 V but not the full USB full speed electrical characteristics which are degraded in the 2.7-to-3.0 V V_{DD} voltage range.
3. Guaranteed by design, not tested in production.
4. R_L is the load connected on the USB OTG FS drivers.

Note: When VBUS sensing feature is enabled, PA9 and PB13 should be left at their default state (floating input), not as alternate function. A typical 200 μA current consumption of the embedded sensing block (current to voltage conversion to determine the different sessions) can be observed on PA9 and PB13 when the feature is enabled.

Figure 44. USB OTG FS timings: definition of data signal rise and fall time

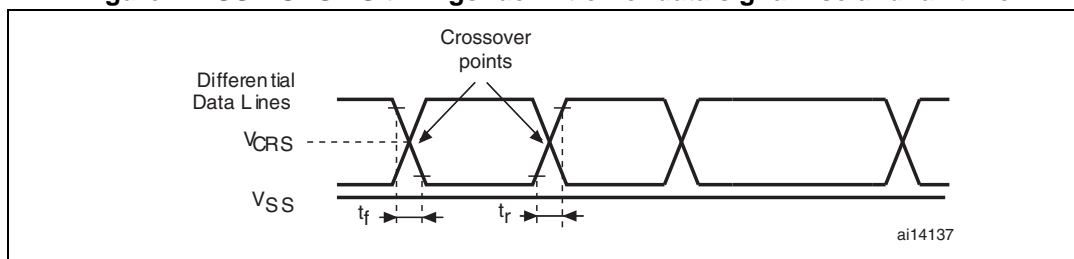


Table 68. USB OTG FS electrical characteristics⁽¹⁾

Driver characteristics					
Symbol	Parameter	Conditions	Min	Max	Unit
t_r	Rise time ⁽²⁾	$C_L = 50 \text{ pF}$	4	20	ns
t_f	Fall time ⁽²⁾	$C_L = 50 \text{ pF}$	4	20	ns
t_{rfm}	Rise/ fall time matching	t_r/t_f	90	110	%
V_{CRS}	Output signal crossover voltage		1.3	2.0	V

1. Guaranteed by design, not tested in production.
2. Measured from 10% to 90% of the data signal. For more detailed informations, please refer to USB Specification - Chapter 7 (version 2.0).

USB HS characteristics

Unless otherwise specified, the parameters given in [Table 71](#) for ULPI are derived from tests performed under the ambient temperature, f_{HCLK} frequency summarized in [Table 70](#) and V_{DD} supply voltage conditions summarized in [Table 69](#), with the following configuration:

- Output speed is set to $OSPEEDRy[1:0] = 10$
- Capacitive load $C = 30 \text{ pF}$
- Measurement points are done at CMOS levels: $0.5V_{DD}$.

Refer to [Section 6.3.17: I/O port characteristics](#) for more details on the input/output characteristics.

Table 69. USB HS DC electrical characteristics

Symbol	Parameter	Min. ⁽¹⁾	Max. ⁽¹⁾	Unit
Input level V_{DD}	USB OTG HS operating voltage	2.7	3.6	V

1. All the voltages are measured from the local ground potential.

Table 70. USB HS clock timing parameters⁽¹⁾

Parameter	Symbol	Min	Nominal	Max	Unit
f_{HCLK} value to guarantee proper operation of USB HS interface		30			MHz
Frequency (first transition) 8-bit $\pm 10\%$	F_{START_8BIT}	54	60	66	MHz
Frequency (steady state) $\pm 500 \text{ ppm}$	F_{STEADY}	59.97	60	60.03	MHz
Duty cycle (first transition) 8-bit $\pm 10\%$	D_{START_8BIT}	40	50	60	%

Table 70. USB HS clock timing parameters⁽¹⁾ (continued)

Parameter	Symbol	Min	Nominal	Max	Unit
Duty cycle (steady state) ±500 ppm	D _{STEADY}	49.975	50	50.025	%
Time to reach the steady state frequency and duty cycle after the first transition	T _{STEADY}	-	-	1.4	ms
Clock startup time after the de-assertion of SuspendM	Peripheral	T _{START_DEV}	-	-	5.6
	Host	T _{START_HOST}	-	-	-
PHY preparation time after the first transition of the input clock	T _{PREP}	-	-	-	µs

1. Guaranteed by design, not tested in production.

Figure 45. ULPI timing diagram

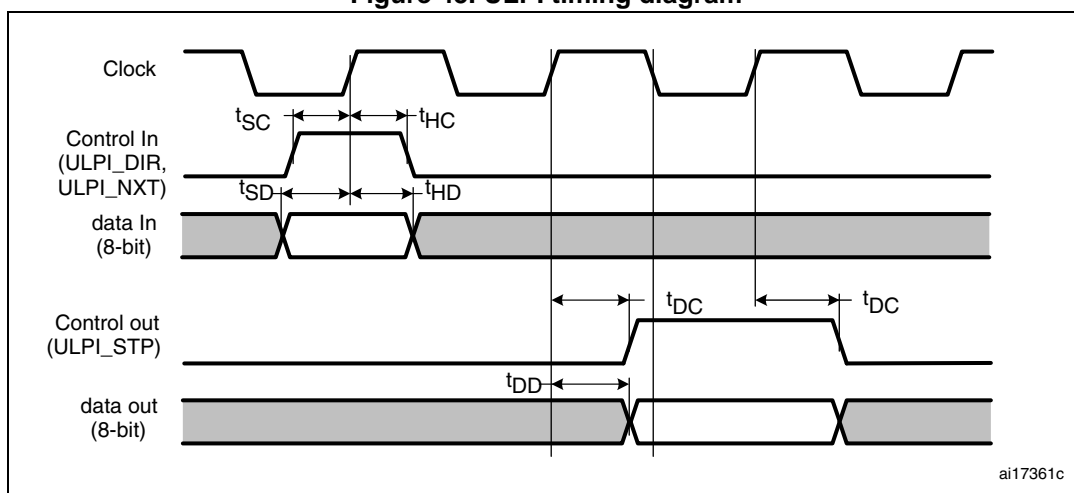


Table 71. Dynamic characteristics: USB ULPI⁽¹⁾

Symbol	Parameter	Min.	Typ.	Max.	Unit
T _{SC}	Control in (ULPI_DIR, ULPI_NXT) setup time	-	-	1.5	ns
T _{HC}	Control in (ULPI_DIR, ULPI_NXT) hold time	0.5	-	-	
T _{SD}	Data in setup time	-	-	1.5	
T _{HD}	Data in hold time	0	-	-	
T _{DC}	Control output delay	-	10	11	
T _{DD}	Data output delay	-	12	15	

1. Data based on characterization results, not tested in production.

Ethernet characteristics

Unless otherwise specified, the parameters given in [Table 73](#), [Table 74](#) and [Table 75](#) for SMI, RMII and MII are derived from tests performed under the ambient temperature, f_{HCLK} frequency summarized in [Table 17](#) and V_{DD} supply voltage conditions summarized in [Table 72](#), with the following configuration:

- Output speed is set to $OSPEEDRy[1:0] = 10$
- Capacitive load $C = 30 \text{ pF}$
- Measurement points are done at CMOS levels: $0.5V_{DD}$.

Refer to [Section 6.3.17: I/O port characteristics](#) for more details on the input/output characteristics.

Table 72. Ethernet DC electrical characteristics

Symbol		Parameter	Min. ⁽¹⁾	Max. ⁽¹⁾	Unit
Input level	V_{DD}	Ethernet operating voltage	2.7	3.6	V

1. All the voltages are measured from the local ground potential.

[Table 73](#) gives the list of Ethernet MAC signals for the SMI (station management interface) and [Figure 46](#) shows the corresponding timing diagram.

Figure 46. Ethernet SMI timing diagram

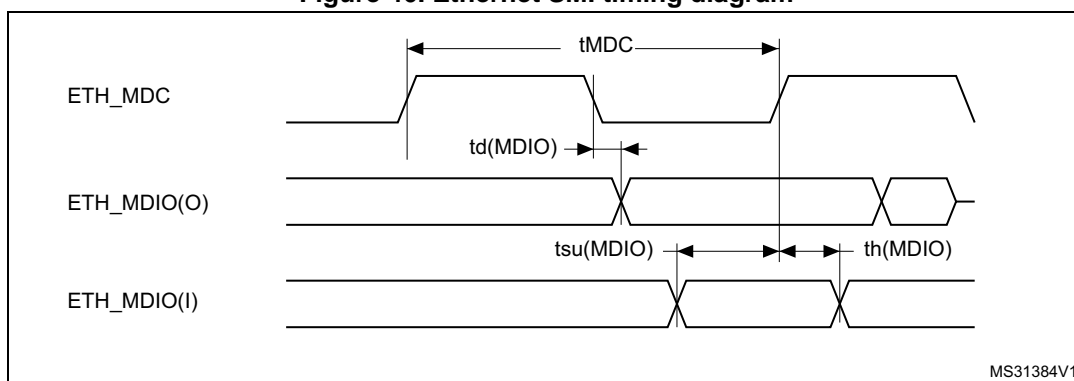


Table 73. Dynamics characteristics: Ethernet MAC signals for SMI⁽¹⁾

Symbol	Parameter	Min	Typ	Max	Unit
t_{MDC}	MDC cycle time(2.38 MHz)	411	420	425	ns
$T_d(MDIO)$	Write data valid time	6	10	13	
$t_{su}(MDIO)$	Read data setup time	12	-	-	
$t_h(MDIO)$	Read data hold time	0	-	-	

1. Data based on characterization results, not tested in production.

[Table 74](#) gives the list of Ethernet MAC signals for the RMII and [Figure 47](#) shows the corresponding timing diagram.

Figure 47. Ethernet RMII timing diagram

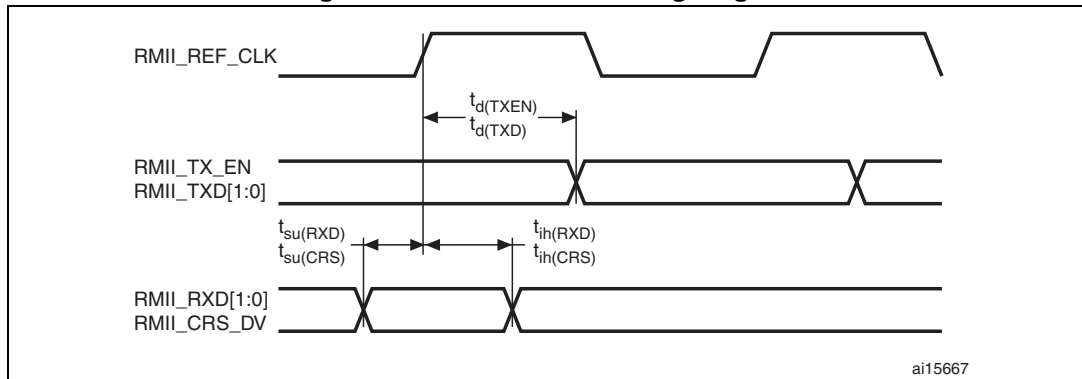


Table 74. Dynamics characteristics: Ethernet MAC signals for RMII⁽¹⁾

Symbol	Parameter	Min	Typ	Max	Unit
$t_{su}(RXD)$	Receive data setup time	1.5	-	-	ns
$t_h(RXD)$	Receive data hold time	0	-	-	
$t_{su}(CRS)$	Carrier sense setup time	1	-	-	
$t_h(CRS)$	Carrier sense hold time	1	-	-	
$t_d(TXEN)$	Transmit enable valid delay time	0	10.5	12	
$t_d(TXD)$	Transmit data valid delay time	0	11	12.5	

1. Data based on characterization results, not tested in production.

Table 75 gives the list of Ethernet MAC signals for MII and Figure 47 shows the corresponding timing diagram.

Figure 48. Ethernet MII timing diagram

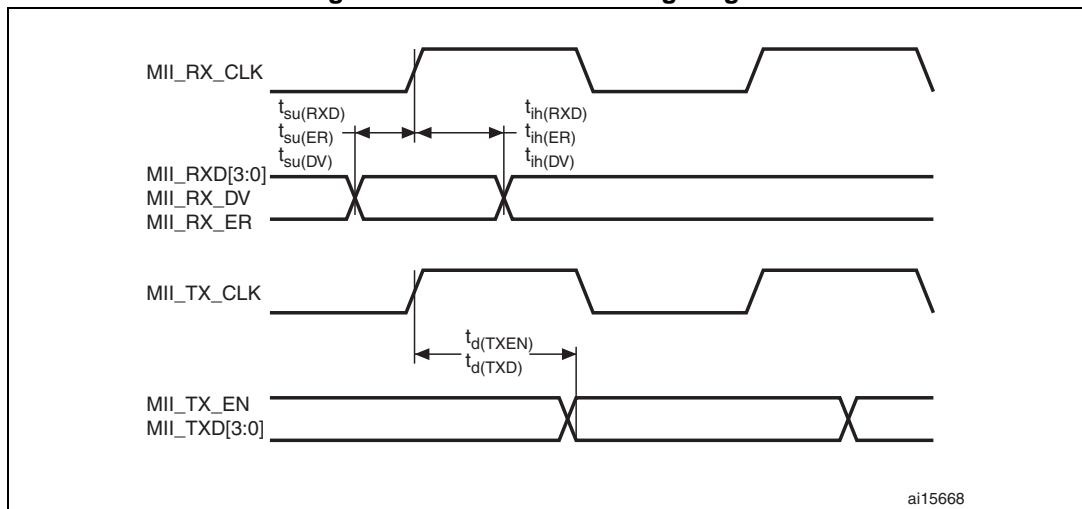


Table 75. Dynamics characteristics: Ethernet MAC signals for MII⁽¹⁾

Symbol	Parameter	Min	Typ	Max	Unit
$t_{su}(RXD)$	Receive data setup time	9		-	ns
$t_{ih}(RXD)$	Receive data hold time	10		-	
$t_{su}(DV)$	Data valid setup time	9		-	
$t_{ih}(DV)$	Data valid hold time	8		-	
$t_{su}(ER)$	Error setup time	6		-	
$t_{ih}(ER)$	Error hold time	8		-	
$t_d(TXEN)$	Transmit enable valid delay time	0	10	14	
$t_d(TXD)$	Transmit data valid delay time	0	10	15	

1. Data based on characterization results, not tested in production.

CAN (controller area network) interface

Refer to [Section 6.3.17: I/O port characteristics](#) for more details on the input/output alternate function characteristics (CANx_TX and CANx_RX).

6.3.21 12-bit ADC characteristics

Unless otherwise specified, the parameters given in [Table 76](#) are derived from tests performed under the ambient temperature, f_{PCLK2} frequency and V_{DDA} supply voltage conditions summarized in [Table 17](#).

Table 76. ADC characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DDA}	Power supply	$V_{DDA} - V_{REF+} < 1.2\text{ V}$	1.8 ⁽¹⁾	-	3.6	V
V_{REF+}	Positive reference voltage		1.8 ⁽¹⁾	-	V_{DDA}	V
f_{ADC}	ADC clock frequency	$V_{DDA} = 1.8^{(1)}\text{ to }2.4\text{ V}$	0.6	15	18	MHz
		$V_{DDA} = 2.4\text{ to }3.6\text{ V}$	0.6	30	36	MHz
$f_{TRIG}^{(2)}$	External trigger frequency	$f_{ADC} = 30\text{ MHz}$, 12-bit resolution	-	-	1764	kHz
			-	-	17	$1/f_{ADC}$
V_{AIN}	Conversion voltage range ⁽³⁾		0 (V_{SSA} or V_{REF-} tied to ground)	-	V_{REF+}	V
$R_{AIN}^{(2)}$	External input impedance	See Equation 1 for details	-	-	50	k Ω
$R_{ADC}^{(2)(4)}$	Sampling switch resistance		-	-	6	k Ω
$C_{ADC}^{(2)}$	Internal sample and hold capacitor		-	4	7	pF
$t_{lat}^{(2)}$	Injection trigger conversion latency	$f_{ADC} = 30\text{ MHz}$	-	-	0.100	μs
			-	-	3 ⁽⁵⁾	$1/f_{ADC}$

Table 76. ADC characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{latr}^{(2)}$	Regular trigger conversion latency	$f_{ADC} = 30$ MHz	-	-	0.067	μ s
			-	-	$2^{(5)}$	$1/f_{ADC}$
$t_S^{(2)}$	Sampling time	$f_{ADC} = 30$ MHz	0.100	-	16	μ s
			3	-	480	$1/f_{ADC}$
$t_{STAB}^{(2)}$	Power-up time		-	2	3	μ s
$t_{CONV}^{(2)}$	Total conversion time (including sampling time)	$f_{ADC} = 30$ MHz 12-bit resolution	0.50	-	16.40	μ s
		$f_{ADC} = 30$ MHz 10-bit resolution	0.43	-	16.34	μ s
		$f_{ADC} = 30$ MHz 8-bit resolution	0.37	-	16.27	μ s
		$f_{ADC} = 30$ MHz 6-bit resolution	0.30	-	16.20	μ s
		9 to 492 (t_S for sampling + n-bit resolution for successive approximation)				
$f_S^{(2)}$	Sampling rate ($f_{ADC} = 30$ MHz, and $t_S = 3$ ADC cycles)	12-bit resolution Single ADC	-	-	2	Msp/s
		12-bit resolution Interleave Dual ADC mode	-	-	3.75	Msp/s
		12-bit resolution Interleave Triple ADC mode	-	-	6	Msp/s
$I_{VREF+}^{(2)}$	ADC V_{REF} DC current consumption in conversion mode		-	300	500	μ A
$I_{VDDA}^{(2)}$	ADC V_{DDA} DC current consumption in conversion mode		-	1.6	1.8	mA

- V_{DDA} minimum value of 1.7 V is obtained when the device operates in reduced temperature range, with the use of an external power supply supervisor (refer to [Section 3.17.2: Internal reset OFF](#)).
- Based on characterization, not tested in production.
- V_{REF+} is internally connected to V_{DDA} and V_{REF-} is internally connected to V_{SSA} .
- R_{ADC} maximum value is given for $V_{DD}=1.8$ V, and minimum value for $V_{DD}=3.3$ V.
- For external triggers, a delay of $1/f_{PCLK2}$ must be added to the latency specified in [Table 76](#).

Equation 1: R_{AIN} max formula

$$R_{AIN} = \frac{(k - 0.5)}{f_{ADC} \times C_{ADC} \times \ln(2^{N+2})} - R_{ADC}$$

The formula above (*Equation 1*) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. N = 12 (from 12-bit resolution) and k is the number of sampling periods defined in the ADC_SMPR1 register.

Table 77. ADC static accuracy at $f_{ADC} = 18\text{ MHz}^{(1)}$

Symbol	Parameter	Test conditions	Typ	Max ⁽²⁾	Unit
ET	Total unadjusted error	$f_{ADC} = 18\text{ MHz}$ $V_{DDA} = 1.8\text{ to }3.6\text{ V}$ $V_{REF} = 1.8\text{ to }3.6\text{ V}$ $V_{DDA} - V_{REF} < 1.2\text{ V}$	±3	±4	LSB
EO	Offset error		±2	±3	
EG	Gain error		±1	±3	
ED	Differential linearity error		±1	±2	
EL	Integral linearity error		±2	±3	

1. Better performance could be achieved in restricted V_{DD} , frequency and temperature ranges.
2. Based on characterization, not tested in production.

Table 78. ADC static accuracy at $f_{ADC} = 30\text{ MHz}^{(1)}$

Symbol	Parameter	Test conditions	Typ	Max ⁽²⁾	Unit
ET	Total unadjusted error	$f_{ADC} = 30\text{ MHz}$, $R_{AIN} < 10\text{ k}\Omega$, $V_{DDA} = 2.4\text{ to }3.6\text{ V}$, $V_{REF} = 1.8\text{ to }3.6\text{ V}$, $V_{DDA} - V_{REF} < 1.2\text{ V}$	±2	±5	LSB
EO	Offset error		±1.5	±2.5	
EG	Gain error		±1.5	±3	
ED	Differential linearity error		±1	±2	
EL	Integral linearity error		±1.5	±3	

1. Better performance could be achieved in restricted V_{DD} , frequency and temperature ranges.
2. Based on characterization, not tested in production.

Table 79. ADC static accuracy at $f_{ADC} = 36\text{ MHz}^{(1)}$

Symbol	Parameter	Test conditions	Typ	Max ⁽²⁾	Unit
ET	Total unadjusted error	$f_{ADC} = 36\text{ MHz}$, $V_{DDA} = 2.4\text{ to }3.6\text{ V}$, $V_{REF} = 1.8\text{ to }3.6\text{ V}$ $V_{DDA} - V_{REF} < 1.2\text{ V}$	±4	±7	LSB
EO	Offset error		±2	±3	
EG	Gain error		±3	±6	
ED	Differential linearity error		±2	±3	
EL	Integral linearity error		±3	±6	

1. Better performance could be achieved in restricted V_{DD} , frequency and temperature ranges.
2. Based on characterization, not tested in production.

Table 80. ADC dynamic accuracy at $f_{ADC} = 18$ MHz - limited test conditions⁽¹⁾

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
ENOB	Effective number of bits	$f_{ADC} = 18$ MHz $V_{DDA} = V_{REF+} = 1.8$ V Input Frequency = 20 KHz Temperature = 25 °C	10.3	10.4	-	bits
SINAD	Signal-to-noise and distortion ratio		64	64.2	-	dB
SNR	Signal-to-noise ratio		64	65	-	
THD	Total harmonic distortion		-67	-72	-	

1. Data based on characterization results, not tested in production.

Table 81. ADC dynamic accuracy at $f_{ADC} = 36$ MHz - limited test conditions⁽¹⁾

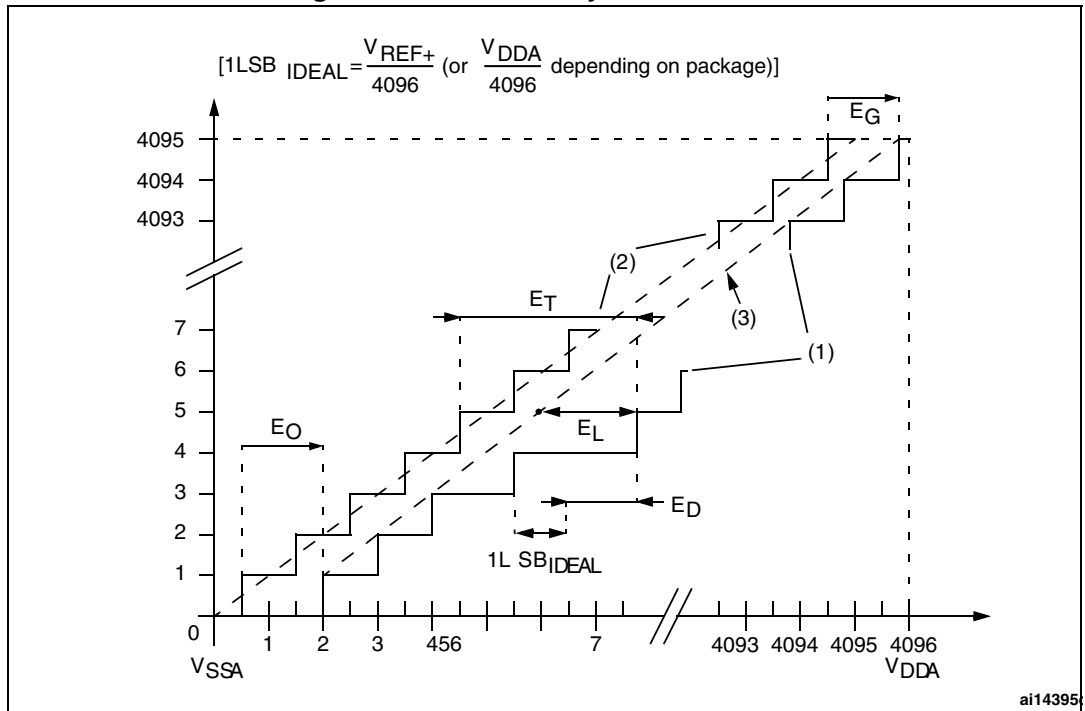
Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
ENOB	Effective number of bits	$f_{ADC} = 36$ MHz $V_{DDA} = V_{REF+} = 3.3$ V Input Frequency = 20 KHz Temperature = 25 °C	10.6	10.8	-	bits
SINAD	Signal-to noise and distortion ratio		66	67	-	dB
SNR	Signal-to noise ratio		64	68	-	
THD	Total harmonic distortion		-70	-72	-	

1. Data based on characterization results, not tested in production.

Note: ADC accuracy vs. negative injection current: injecting a negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.

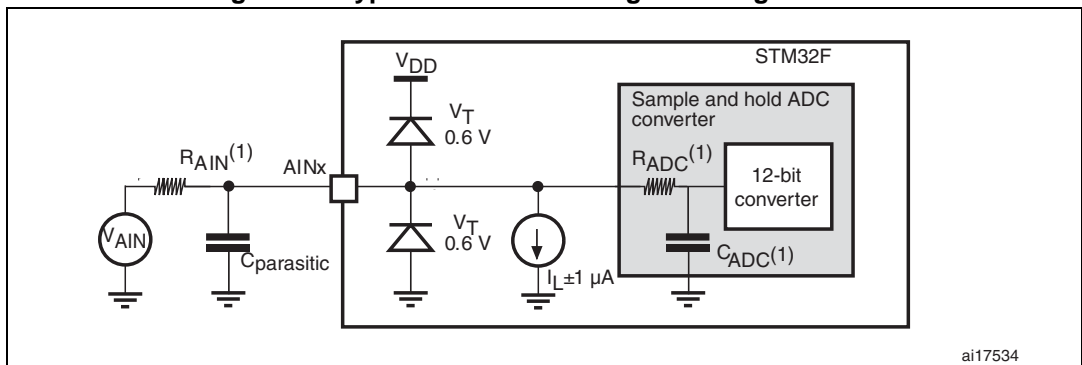
Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in [Section 6.3.17](#) does not affect the ADC accuracy.

Figure 49. ADC accuracy characteristics



1. See also [Table 78](#).
2. Example of an actual transfer curve.
3. Ideal transfer curve.
4. End point correlation line.
5. E_T = Total Unadjusted Error: maximum deviation between the actual and the ideal transfer curves.
 E_O = Offset Error: deviation between the first actual transition and the first ideal one.
 E_G = Gain Error: deviation between the last ideal transition and the last actual one.
 E_D = Differential Linearity Error: maximum deviation between actual steps and the ideal one.
 E_L = Integral Linearity Error: maximum deviation between any actual transition and the end point correlation line.

Figure 50. Typical connection diagram using the ADC

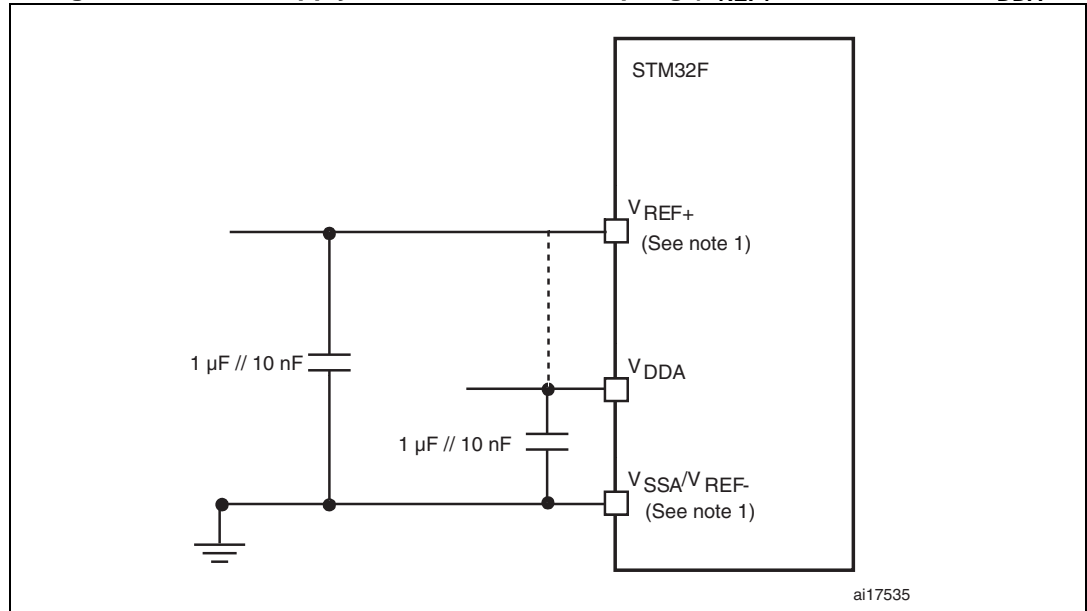


1. Refer to [Table 76](#) for the values of R_{AIN} , R_{ADC} and C_{ADC} .
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 5 pF). A high $C_{parasitic}$ value downgrades conversion accuracy. To remedy this, f_{ADC} should be reduced.

General PCB design guidelines

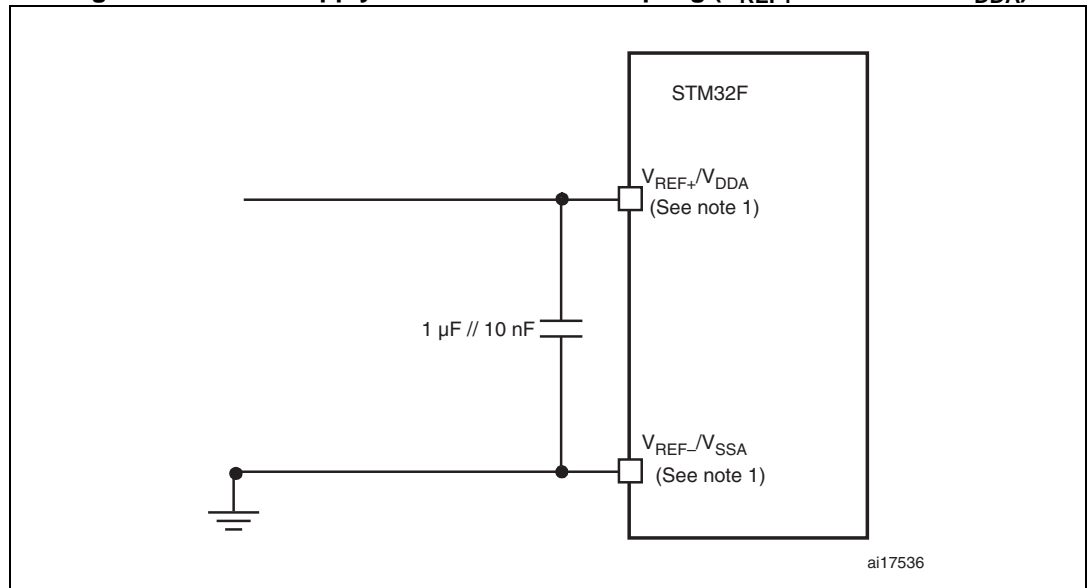
Power supply decoupling should be performed as shown in *Figure 51* or *Figure 52*, depending on whether V_{REF+} is connected to V_{DDA} or not. The 10 nF capacitors should be ceramic (good quality). They should be placed as close as possible to the chip.

Figure 51. Power supply and reference decoupling (V_{REF+} not connected to V_{DDA})



1. V_{REF+} and V_{REF-} inputs are both available on UFBGA176. V_{REF+} is also available on LQFP100, LQFP144, and LQFP176. When V_{REF+} and V_{REF-} are not available, they are internally connected to V_{DDA} and V_{SSA} .

Figure 52. Power supply and reference decoupling (V_{REF+} connected to V_{DDA})



1. V_{REF+} and V_{REF-} inputs are both available on UFBGA176. V_{REF+} is also available on LQFP100, LQFP144, and LQFP176. When V_{REF+} and V_{REF-} are not available, they are internally connected to V_{DDA} and V_{SSA} .

6.3.22 Temperature sensor characteristics

Table 82. Temperature sensor characteristics

Symbol	Parameter	Min	Typ	Max	Unit
$T_L^{(1)}$	V_{SENSE} linearity with temperature	-	± 1	± 2	$^{\circ}C$
Avg_Slope ⁽¹⁾	Average slope	-	2.5		mV/ $^{\circ}C$
$V_{25}^{(1)}$	Voltage at 25 $^{\circ}C$	-	0.76		V
$t_{START}^{(2)}$	Startup time	-	6	10	μs
$T_{S_temp}^{(3)(2)}$	ADC sampling time when reading the temperature (1 $^{\circ}C$ accuracy)	10	-	-	μs

1. Based on characterization, not tested in production.
2. Guaranteed by design, not tested in production.
3. Shortest sampling time can be determined in the application by multiple iterations.

Table 83. Temperature sensor calibration values

Symbol	Parameter	Memory address
TS_CAL1	TS ADC raw data acquired at temperature of 30 $^{\circ}C$, $V_{DDA} = 3.3 V$	0x1FFF 7A2C - 0x1FFF 7A2D
TS_CAL2	TS ADC raw data acquired at temperature of 110 $^{\circ}C$, $V_{DDA} = 3.3 V$	0x1FFF 7A2E - 0x1FFF 7A2F

6.3.23 V_{BAT} monitoring characteristics

Table 84. V_{BAT} monitoring characteristics

Symbol	Parameter	Min	Typ	Max	Unit
R	Resistor bridge for V_{BAT}	-	50	-	K Ω
Q	Ratio on V_{BAT} measurement	-	4	-	
$Er^{(1)}$	Error on Q	-1	-	+1	%
$T_{S_vbat}^{(2)(2)}$	ADC sampling time when reading the V_{BAT} 1 mV accuracy	5	-	-	μs

1. Guaranteed by design, not tested in production.
2. Shortest sampling time can be determined in the application by multiple iterations.

6.3.24 Embedded reference voltage

The parameters given in [Table 85](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 17](#).

Table 85. Embedded internal reference voltage

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{REFINT}	Internal reference voltage	$-40^{\circ}C < T_A < +105^{\circ}C$	1.18	1.21	1.24	V
$T_{S_vrefint}^{(1)}$	ADC sampling time when reading the internal reference voltage		10	-	-	μs

Table 85. Embedded internal reference voltage (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{RERINT_s}^{(2)}$	Internal reference voltage spread over the temperature range	$V_{DD} = 3V \pm 10mV$	-	3	5	mV
$T_{Ccoeff}^{(2)}$	Temperature coefficient		-	30	50	ppm/°C
$t_{START}^{(2)}$	Startup time		-	6	10	µs

1. Shortest sampling time can be determined in the application by multiple iterations.
2. Guaranteed by design, not tested in production

Table 86. Internal reference voltage calibration values

Symbol	Parameter	Memory address
V_{REFIN_CAL}	Raw data acquired at temperature of 30 °C $V_{DDA} = 3.3 V$	0x1FFF 7A2A - 0x1FFF 7A2B

6.3.25 DAC electrical characteristics

Table 87. DAC characteristics

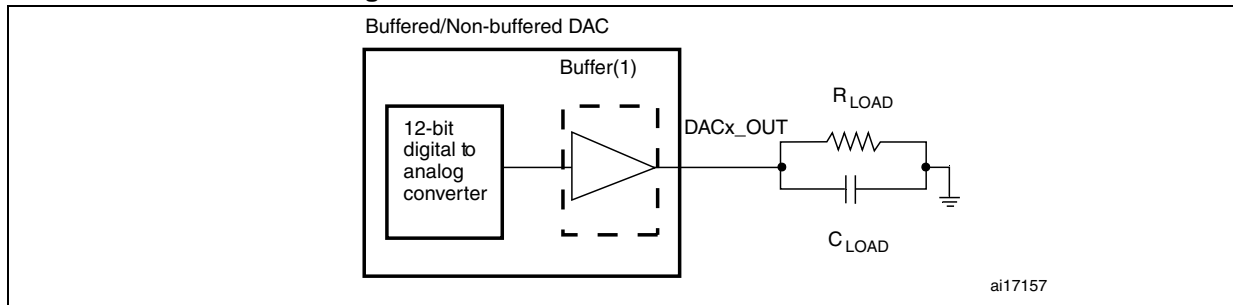
Symbol	Parameter	Min	Typ	Max	Unit	Comments
V_{DDA}	Analog supply voltage	1.8 ⁽¹⁾	-	3.6	V	
V_{REF+}	Reference supply voltage	1.8 ⁽¹⁾	-	3.6	V	$V_{REF+} \leq V_{DDA}$
V_{SSA}	Ground	0	-	0	V	
$R_{LOAD}^{(2)}$	Resistive load with buffer ON	5	-	-	kΩ	
$R_O^{(2)}$	Impedance output with buffer OFF	-	-	15	kΩ	When the buffer is OFF, the Minimum resistive load between DAC_OUT and V_{SS} to have a 1% accuracy is 1.5 MΩ
$C_{LOAD}^{(2)}$	Capacitive load	-	-	50	pF	Maximum capacitive load at DAC_OUT pin (when the buffer is ON).
$DAC_OUT_{min}^{(2)}$	Lower DAC_OUT voltage with buffer ON	0.2	-	-	V	It gives the maximum output excursion of the DAC. It corresponds to 12-bit input code (0x0E0) to (0xF1C) at $V_{REF+} = 3.6 V$ and (0x1C7) to (0xE38) at $V_{REF+} = 1.8 V$
$DAC_OUT_{max}^{(2)}$	Higher DAC_OUT voltage with buffer ON	-	-	$V_{DDA} - 0.2$	V	
$DAC_OUT_{min}^{(2)}$	Lower DAC_OUT voltage with buffer OFF	-	0.5	-	mV	It gives the maximum output excursion of the DAC.
$DAC_OUT_{max}^{(2)}$	Higher DAC_OUT voltage with buffer OFF	-	-	$V_{REF+} - 1LSB$	V	
$I_{VREF+}^{(4)}$	DAC DC V_{REF} current consumption in quiescent mode (Standby mode)	-	170	240	µA	With no load, worst code (0x800) at $V_{REF+} = 3.6 V$ in terms of DC consumption on the inputs
		-	50	75		With no load, worst code (0xF1C) at $V_{REF+} = 3.6 V$ in terms of DC consumption on the inputs

Table 87. DAC characteristics (continued)

Symbol	Parameter	Min	Typ	Max	Unit	Comments
$I_{DDA}^{(4)}$	DAC DC VDDA current consumption in quiescent mode ⁽³⁾	-	280	380	μA	With no load, middle code (0x800) on the inputs
		-	475	625	μA	With no load, worst code (0xF1C) at $V_{REF+} = 3.6\text{ V}$ in terms of DC consumption on the inputs
DNL ⁽⁴⁾	Differential non linearity Difference between two consecutive code-1LSB)	-	-	± 0.5	LSB	Given for the DAC in 10-bit configuration.
		-	-	± 2	LSB	Given for the DAC in 12-bit configuration.
INL ⁽⁴⁾	Integral non linearity (difference between measured value at Code i and the value at Code i on a line drawn between Code 0 and last Code 1023)	-	-	± 1	LSB	Given for the DAC in 10-bit configuration.
		-	-	± 4	LSB	Given for the DAC in 12-bit configuration.
Offset ⁽⁴⁾	Offset error (difference between measured value at Code (0x800) and the ideal value = $V_{REF+}/2$)	-	-	± 10	mV	Given for the DAC in 12-bit configuration
		-	-	± 3	LSB	Given for the DAC in 10-bit at $V_{REF+} = 3.6\text{ V}$
		-	-	± 12	LSB	Given for the DAC in 12-bit at $V_{REF+} = 3.6\text{ V}$
Gain error ⁽⁴⁾	Gain error	-	-	± 0.5	%	Given for the DAC in 12-bit configuration
$t_{SETTLING}^{(4)}$	Settling time (full scale: for a 10-bit input code transition between the lowest and the highest input codes when DAC_OUT reaches final value $\pm 4\text{LSB}$)	-	3	6	μs	$C_{LOAD} \leq 50\text{ pF}$, $R_{LOAD} \geq 5\text{ k}\Omega$
THD ⁽⁴⁾	Total Harmonic Distortion Buffer ON	-	-	-	dB	$C_{LOAD} \leq 50\text{ pF}$, $R_{LOAD} \geq 5\text{ k}\Omega$
Update rate ⁽²⁾	Max frequency for a correct DAC_OUT change when small variation in the input code (from code i to i+1LSB)	-	-	1	MS/s	$C_{LOAD} \leq 50\text{ pF}$, $R_{LOAD} \geq 5\text{ k}\Omega$
$t_{WAKEUP}^{(4)}$	Wakeup time from off state (Setting the ENx bit in the DAC Control register)	-	6.5	10	μs	$C_{LOAD} \leq 50\text{ pF}$, $R_{LOAD} \geq 5\text{ k}\Omega$ input code between lowest and highest possible ones.
PSRR ⁺ (2)	Power supply rejection ratio (to V_{DDA}) (static DC measurement)	-	-67	-40	dB	No R_{LOAD} , $C_{LOAD} = 50\text{ pF}$

- V_{DDA} minimum value of 1.7 V is obtained when the device operates in reduced temperature range, with the use of an external power supply supervisor (refer to [Section 3.17.2: Internal reset OFF](#)).
- Guaranteed by design, not tested in production.
- The quiescent mode corresponds to a state where the DAC maintains a stable output level to ensure that no dynamic consumption occurs.
- Guaranteed by characterization, not tested in production.

Figure 53. 12-bit buffered /non-buffered DAC



1. The DAC integrates an output buffer that can be used to reduce the output impedance and to drive external loads directly without the use of an external operational amplifier. The buffer can be bypassed by configuring the BOFFx bit in the DAC_CR register.

6.3.26 FMC characteristics

Unless otherwise specified, the parameters given in [Table 88](#) to [Table 103](#) for the FMC interface are derived from tests performed under the ambient temperature, f_{HCLK} frequency and V_{DD} supply voltage conditions summarized in [Table 17](#), with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10
- Measurement points are done at CMOS levels: $0.5V_{DD}$

Refer to [Section 6.3.17: I/O port characteristics](#) for more details on the input/output characteristics.

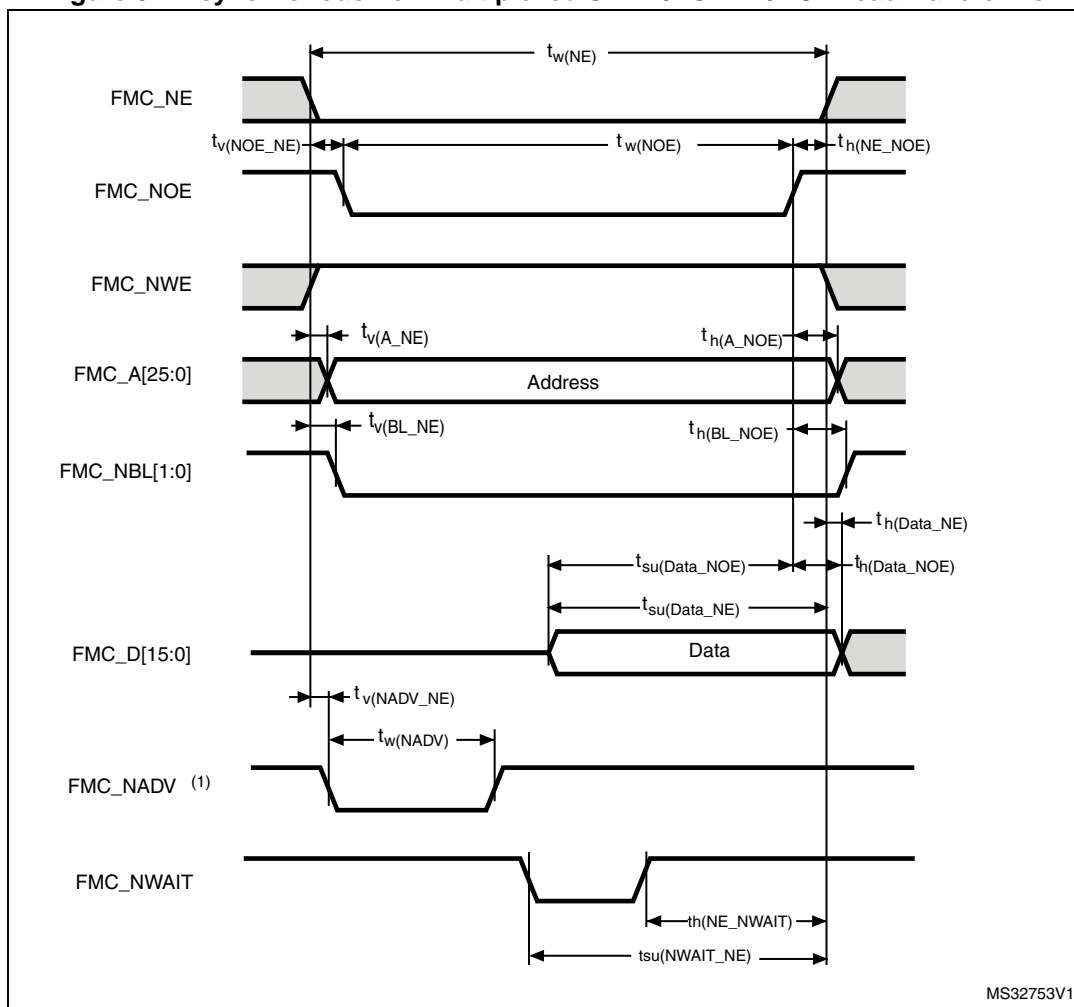
Asynchronous waveforms and timings

[Figure 54](#) through [Figure 57](#) represent asynchronous waveforms and [Table 88](#) through [Table 95](#) provide the corresponding timings. The results shown in these tables are obtained with the following FMC configuration:

- AddressSetupTime = 0x1
- AddressHoldTime = 0x1
- DataSetupTime = 0x1 (except for asynchronous NWAIT mode , DataSetupTime = 0x5)
- BusTurnAroundDuration = 0x0

In all timing tables, the T_{HCLK} is the HCLK clock period.

Figure 54. Asynchronous non-multiplexed SRAM/PSRAM/NOR read waveforms



MS32753V1

1. Mode 2/B, C and D only. In Mode 1, FMC_NADV is not used.

Table 88. Asynchronous non-multiplexed SRAM/PSRAM/NOR - read timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$t_w(NE)$	FMC_NE low time	$2T_{HCLK} - 0.5$	$2T_{HCLK} + 0.5$	ns
$t_{v(NOE_NE)}$	FMC_NEx low to FMC_NOE low	0	1	ns
$t_w(NOE)$	FMC_NOE low time	$2T_{HCLK}$	$2T_{HCLK} + 0.5$	ns
$t_h(NE_NOE)$	FMC_NOE high to FMC_NE high hold time	0	-	ns
$t_{v(A_NE)}$	FMC_NEx low to FMC_A valid	-	2	ns
$t_h(A_NOE)$	Address hold time after FMC_NOE high	0	-	ns
$t_{v(BL_NE)}$	FMC_NEx low to FMC_BL valid	-	2	ns
$t_h(BL_NOE)$	FMC_BL hold time after FMC_NOE high	0	-	ns
$t_{su(Data_NE)}$	Data to FMC_NEx high setup time	$T_{HCLK} + 2.5$	-	ns
$t_{su(Data_NOE)}$	Data to FMC_NOEx high setup time	$T_{HCLK} + 2$	-	ns

Table 88. Asynchronous non-multiplexed SRAM/PSRAM/NOR - read timings⁽¹⁾⁽²⁾ (continued)

Symbol	Parameter	Min	Max	Unit
$t_{h(Data_NOE)}$	Data hold time after FMC_NOE high	0	-	ns
$t_{h(Data_NE)}$	Data hold time after FMC_NEx high	0	-	ns
$t_{v(NADV_NE)}$	FMC_NEx low to FMC_NADV low	-	0	ns
$t_{w(NADV)}$	FMC_NADV low time	-	$T_{HCLK} + 1$	ns

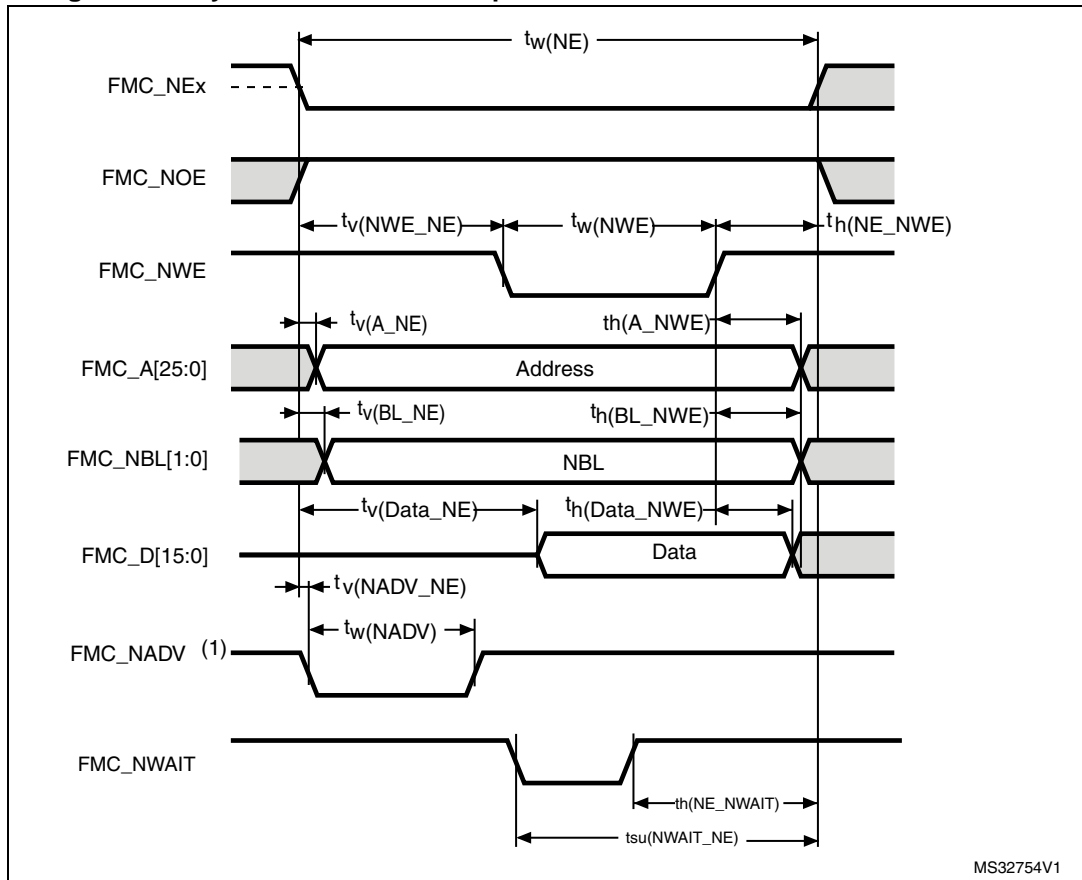
1. $C_L = 30$ pF.
2. Based on characterization, not tested in production.

Table 89. Asynchronous non-multiplexed SRAM/PSRAM/NOR read - NWAIT timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$7T_{HCLK} + 0.5$	$7T_{HCLK} + 1$	ns
$t_{w(NOE)}$	FMC_NWE low time	$5T_{HCLK} - 1.5$	$5T_{HCLK} + 2$	
$t_{su(NWAIT_NE)}$	FMC_NWAIT valid before FMC_NEx high	$5T_{HCLK} + 1.5$	-	
$t_{h(NE_NWAIT)}$	FMC_NEx hold time after FMC_NWAIT invalid	$4T_{HCLK} + 1$	-	

1. $C_L = 30$ pF.
2. Based on characterization, not tested in production.

Figure 55. Asynchronous non-multiplexed SRAM/PSRAM/NOR write waveforms



MS32754V1

1. Mode 2/B, C and D only. In Mode 1, FMC_NADV is not used.

Table 90. Asynchronous non-multiplexed SRAM/PSRAM/NOR write timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$3T_{HCLK}$	$3T_{HCLK}+1$	ns
$t_{v(NWE_NE)}$	FMC_NEx low to FMC_NWE low	$T_{HCLK}-0.5$	$T_{HCLK}+0.5$	ns
$t_{w(NWE)}$	FMC_NWE low time	T_{HCLK}	$T_{HCLK}+0.5$	ns
$t_{h(NE_NWE)}$	FMC_NWE high to FMC_NE high hold time	$T_{HCLK}+1.5$	-	ns
$t_{v(A_NE)}$	FMC_NEx low to FMC_A valid	-	0	ns
$t_{h(A_NWE)}$	Address hold time after FMC_NWE high	$T_{HCLK}+0.5$	-	ns
$t_{v(BL_NE)}$	FMC_NEx low to FMC_NBL valid	-	1.5	ns
$t_{h(BL_NWE)}$	FMC_NBL hold time after FMC_NWE high	$T_{HCLK}+0.5$	-	ns
$t_{v(Data_NE)}$	Data to FMC_NEx low to Data valid	-	$T_{HCLK}+2$	ns
$t_{h(Data_NWE)}$	Data hold time after FMC_NWE high	$T_{HCLK}+0.5$	-	ns
$t_{v(NADV_NE)}$	FMC_NEx low to FMC_NADV low	-	0.5	ns
$t_{w(NADV)}$	FMC_NADV low time	-	$T_{HCLK}+0.5$	ns

1. $C_L = 30$ pF.

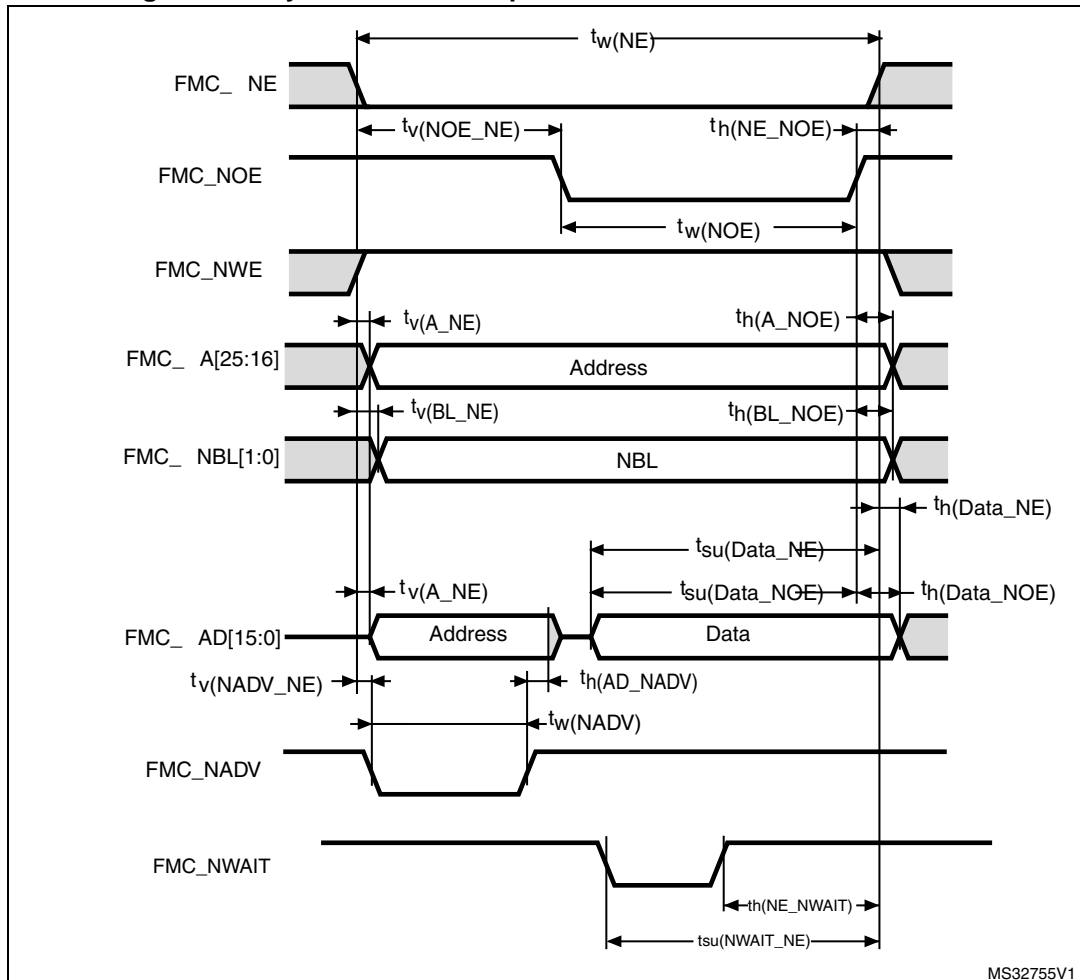
2. Based on characterization, not tested in production.

Table 91. Asynchronous non-multiplexed SRAM/PSRAM/NOR write - NWAIT timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$8T_{HCLK}+1$	$8T_{HCLK}+2$	ns
$t_{w(NWE)}$	FMC_NWE low time	$6T_{HCLK}-1$	$6T_{HCLK}+2$	ns
$t_{su(NWAIT_NE)}$	FMC_NWAIT valid before FMC_NEx high	$6T_{HCLK}+1.5$	-	ns
$t_{h(NE_NWAIT)}$	FMC_NEx hold time after FMC_NWAIT invalid	$4T_{HCLK}+1$		ns

1. $C_L = 30$ pF.
2. Based on characterization, not tested in production.

Figure 56. Asynchronous multiplexed PSRAM/NOR read waveforms



MS32755V1

Table 92. Asynchronous multiplexed PSRAM/NOR read timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$3T_{HCLK}-1$	$3T_{HCLK}+0.5$	ns
$t_{v(NOE_NE)}$	FMC_NEx low to FMC_NOE low	$2T_{HCLK}-0.5$	$2T_{HCLK}$	ns
$t_{tw(NOE)}$	FMC_NOE low time	$T_{HCLK}-1$	$T_{HCLK}+1$	ns
$t_{h(NE_NOE)}$	FMC_NOE high to FMC_NE high hold time	1	-	ns
$t_{v(A_NE)}$	FMC_NEx low to FMC_A valid	-	2	ns
$t_{v(NADV_NE)}$	FMC_NEx low to FMC_NADV low	0	2	ns
$t_{w(NADV)}$	FMC_NADV low time	$T_{HCLK}-0.5$	$T_{HCLK}+0.5$	ns
$t_{h(AD_NADV)}$	FMC_AD(address) valid hold time after FMC_NADV high	0	-	ns
$t_{h(A_NOE)}$	Address hold time after FMC_NOE high	$T_{HCLK}-0.5$	-	ns
$t_{h(BL_NOE)}$	FMC_BL time after FMC_NOE high	0	-	ns
$t_{v(BL_NE)}$	FMC_NEx low to FMC_BL valid	-	2	ns
$t_{su(Data_NE)}$	Data to FMC_NEx high setup time	$T_{HCLK}+1.5$	-	ns
$t_{su(Data_NOE)}$	Data to FMC_NOE high setup time	$T_{HCLK}+1$	-	ns
$t_{h(Data_NE)}$	Data hold time after FMC_NEx high	0	-	ns
$t_{h(Data_NOE)}$	Data hold time after FMC_NOE high	0	-	ns

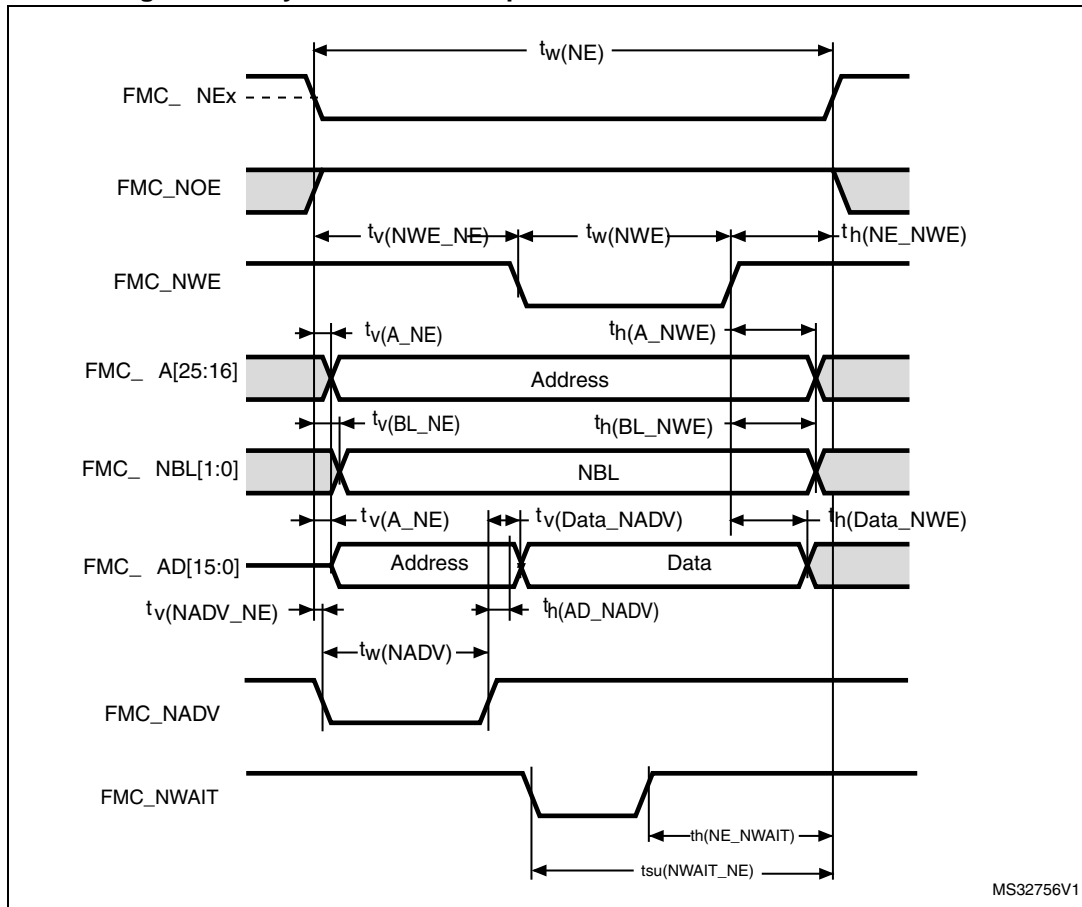
1. $C_L = 30$ pF.
2. Based on characterization, not tested in production.

Table 93. Asynchronous multiplexed PSRAM/NOR read-NWAIT timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$8T_{HCLK}+0.5$	$8T_{HCLK}+2$	ns
$t_{w(NOE)}$	FMC_NWE low time	$5T_{HCLK}-1$	$5T_{HCLK}+1.5$	ns
$t_{su(NWAIT_NE)}$	FMC_NWAIT valid before FMC_NEx high	$5T_{HCLK}+1.5$	-	ns
$t_{h(NE_NWAIT)}$	FMC_NEx hold time after FMC_NWAIT invalid	$4T_{HCLK}+1$	-	ns

1. $C_L = 30$ pF.
2. Based on characterization, not tested in production.

Figure 57. Asynchronous multiplexed PSRAM/NOR write waveforms



MS32756V1

Table 94. Asynchronous multiplexed PSRAM/NOR write timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$4T_{HCLK}$	$4T_{HCLK}+0.5$	ns
$t_{v(NWE_NE)}$	FMC_NEx low to FMC_NWE low	$T_{HCLK}-1$	$T_{HCLK}+0.5$	ns
$t_{w(NWE)}$	FMC_NWE low time	$2T_{HCLK}$	$2T_{HCLK}+0.5$	ns
$t_{h(NE_NWE)}$	FMC_NWE high to FMC_NE high hold time	T_{HCLK}	-	ns
$t_{v(A_NE)}$	FMC_NEx low to FMC_A valid	-	0	ns
$t_{v(NADV_NE)}$	FMC_NEx low to FMC_NADV low	0.5	1	ns
$t_{w(NADV)}$	FMC_NADV low time	$T_{HCLK}-0.5$	$T_{HCLK}+0.5$	ns
$t_{h(AD_NADV)}$	FMC_AD(address) valid hold time after FMC_NADV high	$T_{HCLK}-2$	-	ns
$t_{h(A_NWE)}$	Address hold time after FMC_NWE high	T_{HCLK}	-	ns
$t_{h(BL_NWE)}$	FMC_BL hold time after FMC_NWE high	$T_{HCLK}-2$	-	ns
$t_{v(BL_NE)}$	FMC_NEx low to FMC_BL valid	-	2	ns

Table 94. Asynchronous multiplexed PSRAM/NOR write timings⁽¹⁾⁽²⁾ (continued)

Symbol	Parameter	Min	Max	Unit
$t_{v(Data_NADV)}$	FMC_NADV high to Data valid	-	$T_{HCLK} + 1.5$	ns
$t_{h(Data_NWE)}$	Data hold time after FMC_NWE high	$T_{HCLK} + 0.5$	-	ns

1. $C_L = 30$ pF.
2. Based on characterization, not tested in production.

Table 95. Asynchronous multiplexed PSRAM/NOR write-NWAIT timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$9T_{HCLK}$	$9T_{HCLK} + 0.5$	ns
$t_{w(NWE)}$	FMC_NWE low time	$7T_{HCLK}$	$7T_{HCLK} + 2$	ns
$t_{su(NWAIT_NE)}$	FMC_NWAIT valid before FMC_NEx high	$6T_{HCLK} + 1.5$	-	ns
$t_{h(NE_NWAIT)}$	FMC_NEx hold time after FMC_NWAIT invalid	$4T_{HCLK} - 1$	-	ns

1. $C_L = 30$ pF.
2. Based on characterization, not tested in production.

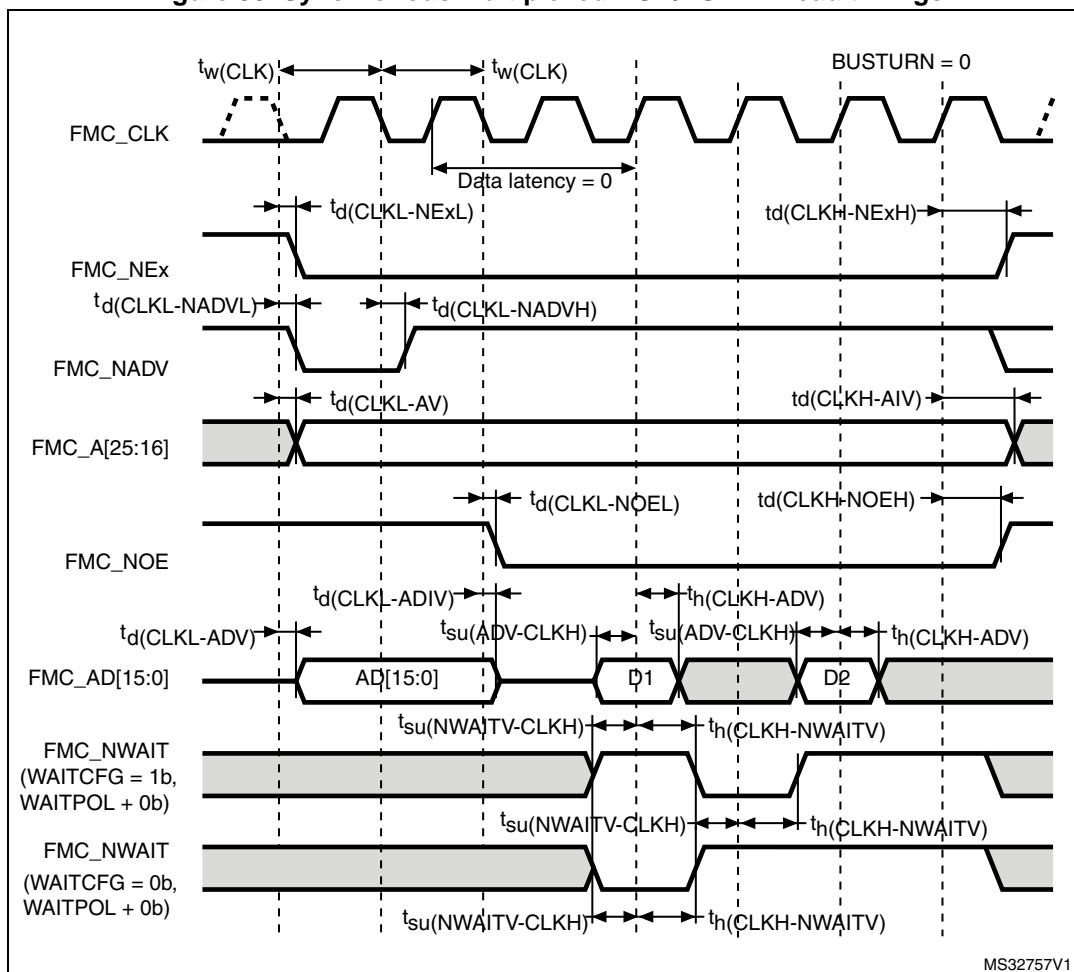
Synchronous waveforms and timings

[Figure 58](#) through [Figure 61](#) represent synchronous waveforms and [Table 96](#) through [Table 99](#) provide the corresponding timings. The results shown in these tables are obtained with the following FMC configuration:

- BurstAccessMode = FMC_BurstAccessMode_Enable;
- MemoryType = FMC_MemoryType_CRAM;
- WriteBurst = FMC_WriteBurst_Enable;
- CLKDivision = 1; (0 is not supported, see the STM32F4xx reference manual : RM0090)
- DataLatency = 1 for NOR Flash; DataLatency = 0 for PSRAM

In all timing tables, the T_{HCLK} is the HCLK clock period (with maximum FMC_CLK = 90 MHz).

Figure 58. Synchronous multiplexed NOR/PSRAM read timings



MS32757V1

Table 96. Synchronous multiplexed NOR/PSRAM read timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$t_{w(CLK)}$	FMC_CLK period	$2T_{HCLK}-1$	-	ns
$t_{d(CLKL-NExL)}$	FMC_CLK low to FMC_NEx low (x=0..2)	-	0	ns
$t_{d(CLKH-NExH)}$	FMC_CLK high to FMC_NEx high (x=0..2)	T_{HCLK}	-	ns
$t_{d(CLKL-NADVL)}$	FMC_CLK low to FMC_NADV low	-	0	ns
$t_{d(CLKL-NADVH)}$	FMC_CLK low to FMC_NADV high	0	-	ns
$t_{d(CLKL-AV)}$	FMC_CLK low to FMC_Ax valid (x=16...25)	-	0	ns
$t_{d(CLKH-AIV)}$	FMC_CLK high to FMC_Ax invalid (x=16...25)	0	-	ns
$t_{d(CLKL-NOEL)}$	FMC_CLK low to FMC_NOE low	-	$T_{HCLK}+0.5$	ns
$t_{d(CLKH-NOEH)}$	FMC_CLK high to FMC_NOE high	$T_{HCLK}-0.5$	-	ns
$t_{d(CLKL-ADV)}$	FMC_CLK low to FMC_AD[15:0] valid	-	0.5	ns
$t_{d(CLKL-ADIV)}$	FMC_CLK low to FMC_AD[15:0] invalid	0	-	ns

Table 96. Synchronous multiplexed NOR/PSRAM read timings⁽¹⁾⁽²⁾ (continued)

Symbol	Parameter	Min	Max	Unit
$t_{su(ADV-CLKH)}$	FMC_A/D[15:0] valid data before FMC_CLK high	5	-	ns
$t_h(CLKH-ADV)$	FMC_A/D[15:0] valid data after FMC_CLK high	0	-	ns
$t_{su(NWAIT-CLKH)}$	FMC_NWAIT valid before FMC_CLK high	4	-	ns
$t_h(CLKH-NWAIT)$	FMC_NWAIT valid after FMC_CLK high	0	-	ns

1. $C_L = 30$ pF.
2. Based on characterization, not tested in production.

Figure 59. Synchronous multiplexed PSRAM write timings

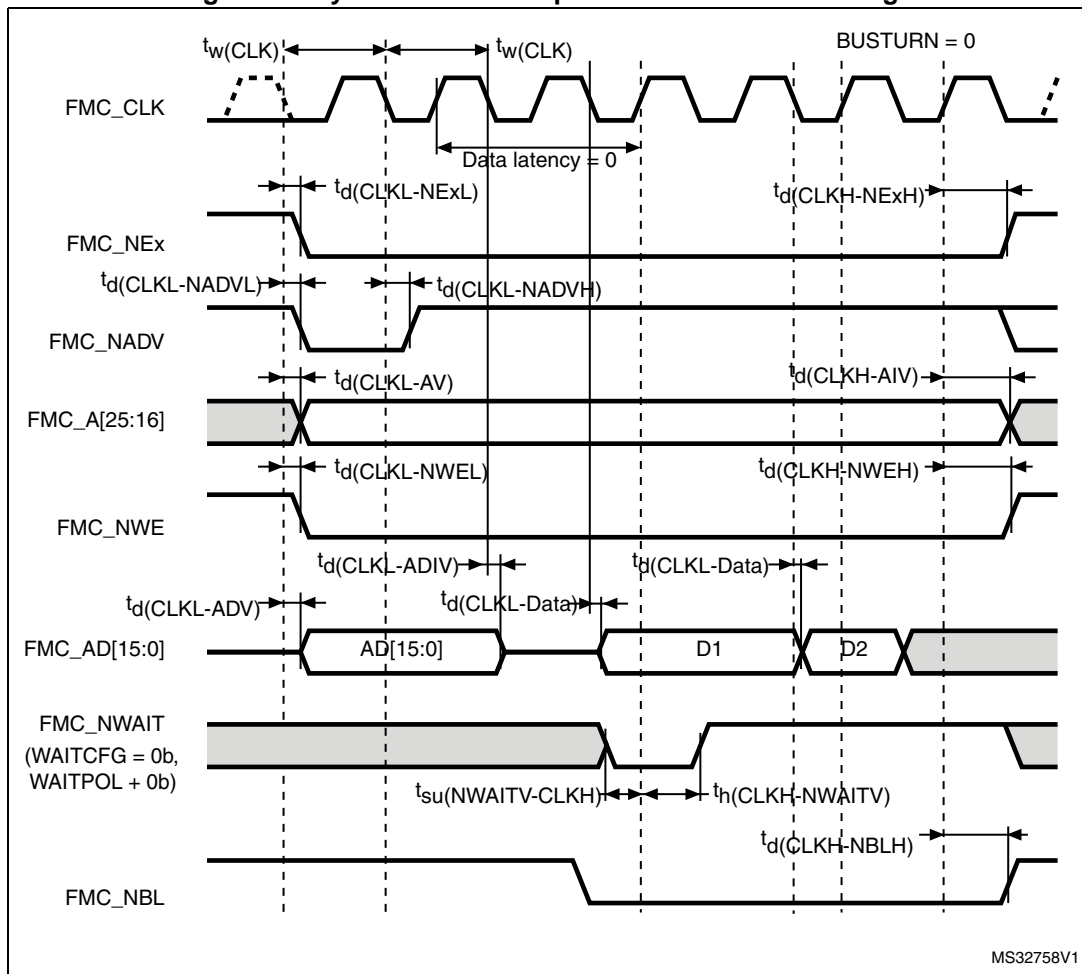


Table 97. Synchronous multiplexed PSRAM write timings⁽¹⁾⁽²⁾

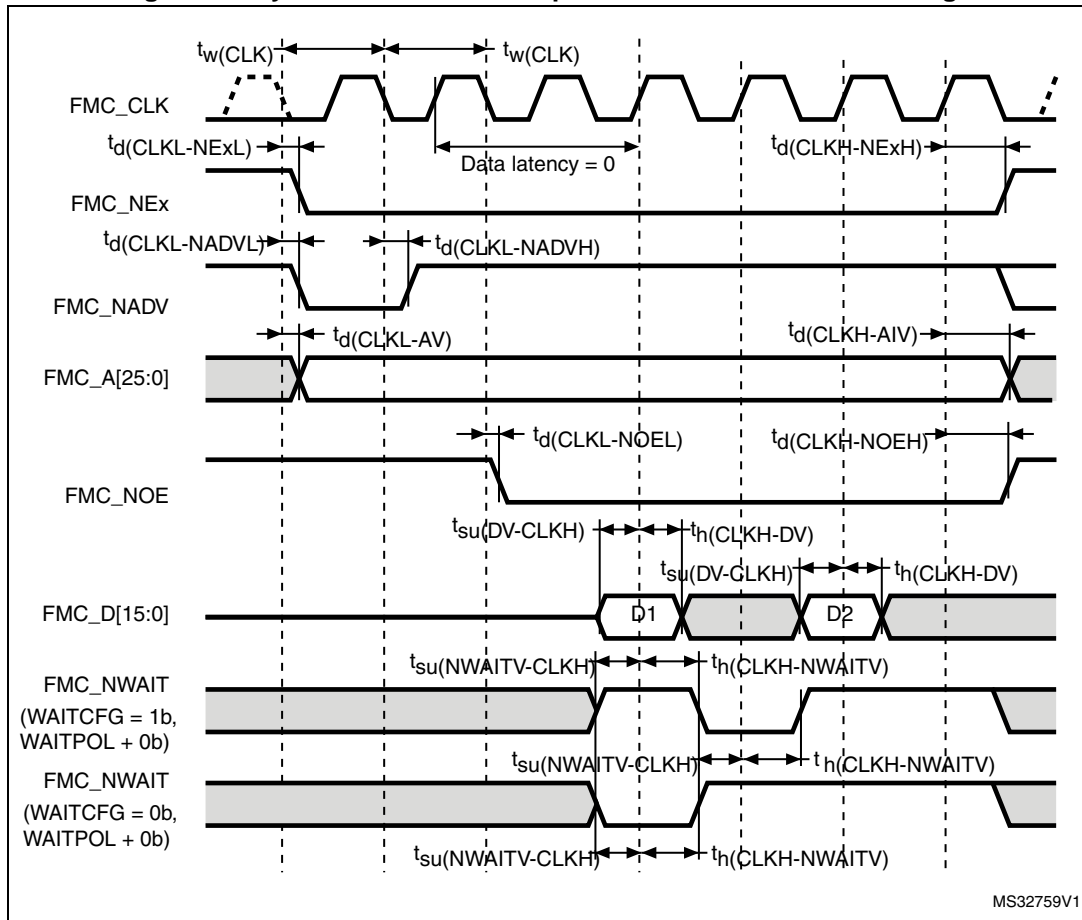
Symbol	Parameter	Min	Max	Unit
$t_w(CLK)$	FMC_CLK period, VDD range= 2.7 to 3.6 V	$2T_{HCLK}-1$	-	ns
$t_d(CLKL-NExL)$	FMC_CLK low to FMC_NEx low (x=0..2)	-	1.5	ns
$t_d(CLKH-NExH)$	FMC_CLK high to FMC_NEx high (x= 0..2)	T_{HCLK}	-	ns

Table 97. Synchronous multiplexed PSRAM write timings⁽¹⁾⁽²⁾ (continued)

Symbol	Parameter	Min	Max	Unit
$t_{d(CLKL-NADVL)}$	FMC_CLK low to FMC_NADV low	-	0	ns
$t_{d(CLKL-NADVH)}$	FMC_CLK low to FMC_NADV high	0	-	ns
$t_{d(CLKL-AV)}$	FMC_CLK low to FMC_Ax valid (x=16...25)	-	0	ns
$t_{d(CLKH-AIV)}$	FMC_CLK high to FMC_Ax invalid (x=16...25)	T_{HCLK}	-	ns
$t_{d(CLKL-NWEL)}$	FMC_CLK low to FMC_NWE low	-	0	ns
$t_{d(CLKH-NWEH)}$	FMC_CLK high to FMC_NWE high	$T_{HCLK}-0.5$	-	ns
$t_{d(CLKL-ADV)}$	FMC_CLK low to FMC_AD[15:0] valid	-	3	ns
$t_{d(CLKL-ADIV)}$	FMC_CLK low to FMC_AD[15:0] invalid	0	-	ns
$t_{d(CLKL-DATA)}$	FMC_A/D[15:0] valid data after FMC_CLK low	-	3	ns
$t_{d(CLKL-NBLL)}$	FMC_CLK low to FMC_NBL low	0	-	ns
$t_{d(CLKH-NBLH)}$	FMC_CLK high to FMC_NBL high	$T_{HCLK}-0.5$	-	ns
$t_{su(NWAIT-CLKH)}$	FMC_NWAIT valid before FMC_CLK high	4	-	ns
$t_h(CLKH-NWAIT)$	FMC_NWAIT valid after FMC_CLK high	0	-	ns

1. $C_L = 30$ pF.
2. Based on characterization, not tested in production.

Figure 60. Synchronous non-multiplexed NOR/PSRAM read timings



MS32759V1

Table 98. Synchronous non-multiplexed NOR/PSRAM read timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$t_w(\text{CLK})$	FMC_CLK period	$2T_{\text{HCLK}}-1$	-	ns
$t_{\text{d}}(\text{CLKL-NExL})$	FMC_CLK low to FMC_NEx low (x=0..2)	-	0.5	ns
$t_{\text{d}}(\text{CLKH-NExH})$	FMC_CLK high to FMC_NEx high (x=0...2)	T_{HCLK}	-	ns
$t_{\text{d}}(\text{CLKL-NADV})$	FMC_CLK low to FMC_NADV low	-	0	ns
$t_{\text{d}}(\text{CLKL-NADVH})$	FMC_CLK low to FMC_NADV high	0	-	ns
$t_{\text{d}}(\text{CLKL-AV})$	FMC_CLK low to FMC_Ax valid (x=16...25)	-	0	ns
$t_{\text{d}}(\text{CLKH-AIV})$	FMC_CLK high to FMC_Ax invalid (x=16...25)	$T_{\text{HCLK}}-0.5$	-	ns
$t_{\text{d}}(\text{CLKL-NOEL})$	FMC_CLK low to FMC_NOE low	-	$T_{\text{HCLK}}+2$	ns
$t_{\text{d}}(\text{CLKH-NOEH})$	FMC_CLK high to FMC_NOE high	$T_{\text{HCLK}}-0.5$	-	ns
$t_{\text{su}}(\text{DV-CLKH})$	FMC_D[15:0] valid data before FMC_CLK high	5	-	ns

Table 98. Synchronous non-multiplexed NOR/PSRAM read timings⁽¹⁾⁽²⁾ (continued)

Symbol	Parameter	Min	Max	Unit
$t_{h(CLKH-DV)}$	FMC_D[15:0] valid data after FMC_CLK high	0	-	ns
$t_{(NWAIT-CLKH)}$	FMC_NWAIT valid before FMC_CLK high	4		
$t_{h(CLKH-NWAIT)}$	FMC_NWAIT valid after FMC_CLK high	0		

1. $C_L = 30$ pF.
2. Based on characterization, not tested in production.

Figure 61. Synchronous non-multiplexed PSRAM write timings

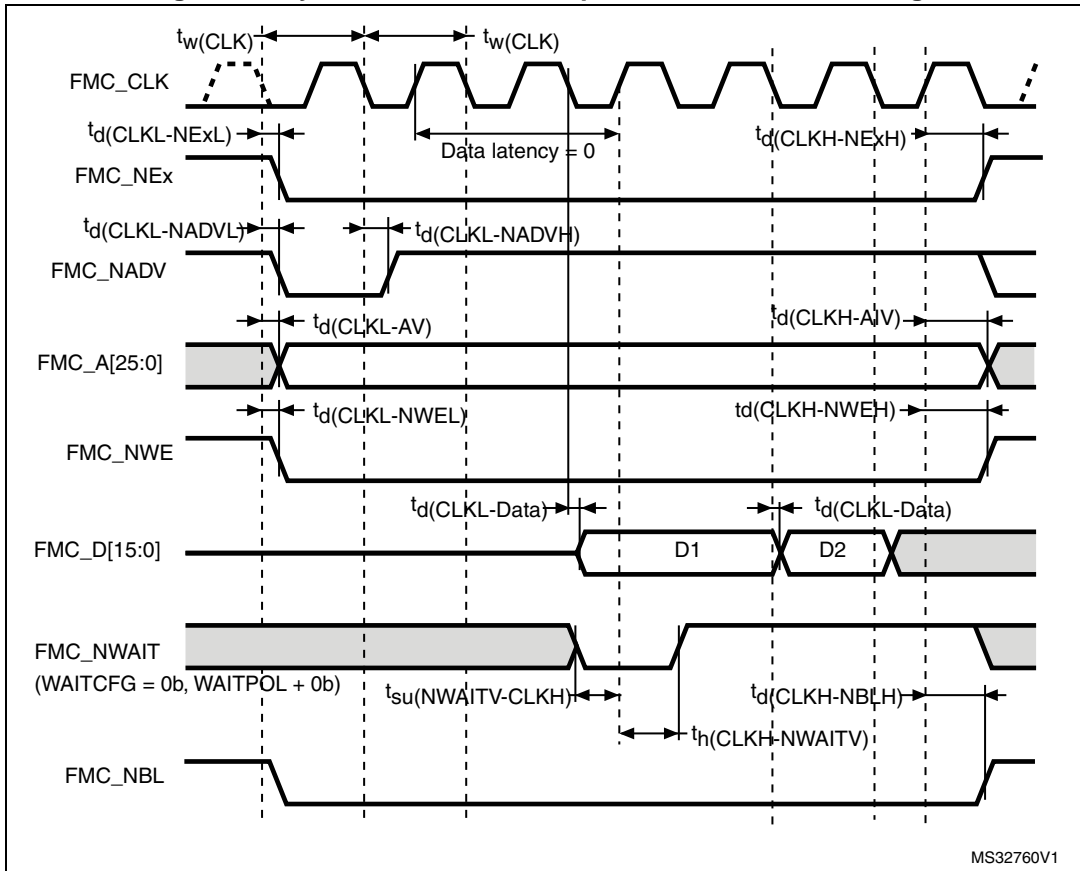


Table 99. Synchronous non-multiplexed PSRAM write timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$t_{(CLK)}$	FMC_CLK period	$2T_{HCLK}-1$	-	ns
$t_{d(CLKL-NExL)}$	FMC_CLK low to FMC_NEx low (x=0..2)	-	0.5	ns
$t_{(CLKH-NExH)}$	FMC_CLK high to FMC_NEx high (x= 0..2)	T_{HCLK}	-	ns
$t_{d(CLKL-NADV)}$	FMC_CLK low to FMC_NADV low	-	0	ns
$t_{d(CLKL-NADVH)}$	FMC_CLK low to FMC_NADV high	0	-	ns
$t_{d(CLKL-AV)}$	FMC_CLK low to FMC_Ax valid (x=16...25)	-	0	ns

Table 99. Synchronous non-multiplexed PSRAM write timings⁽¹⁾⁽²⁾ (continued)

Symbol	Parameter	Min	Max	Unit
$t_{d(\text{CLKH-AIV})}$	FMC_CLK high to FMC_Ax invalid (x=16...25)	0	-	ns
$t_{d(\text{CLKL-NWEL})}$	FMC_CLK low to FMC_NWE low	-	0	ns
$t_{d(\text{CLKH-NWEH})}$	FMC_CLK high to FMC_NWE high	$T_{\text{HCLK}}-0.5$	-	ns
$t_{d(\text{CLKL-Data})}$	FMC_D[15:0] valid data after FMC_CLK low	-	2.5	ns
$t_{d(\text{CLKL-NBLL})}$	FMC_CLK low to FMC_NBL low	0	-	ns
$t_{d(\text{CLKH-NBLH})}$	FMC_CLK high to FMC_NBL high	$T_{\text{HCLK}}-0.5$	-	ns
$t_{\text{su}(\text{NWAIT-CLKH})}$	FMC_NWAIT valid before FMC_CLK high	4		
$t_{\text{h}(\text{CLKH-NWAIT})}$	FMC_NWAIT valid after FMC_CLK high	0		

1. $C_L = 30$ pF.
2. Based on characterization, not tested in production.

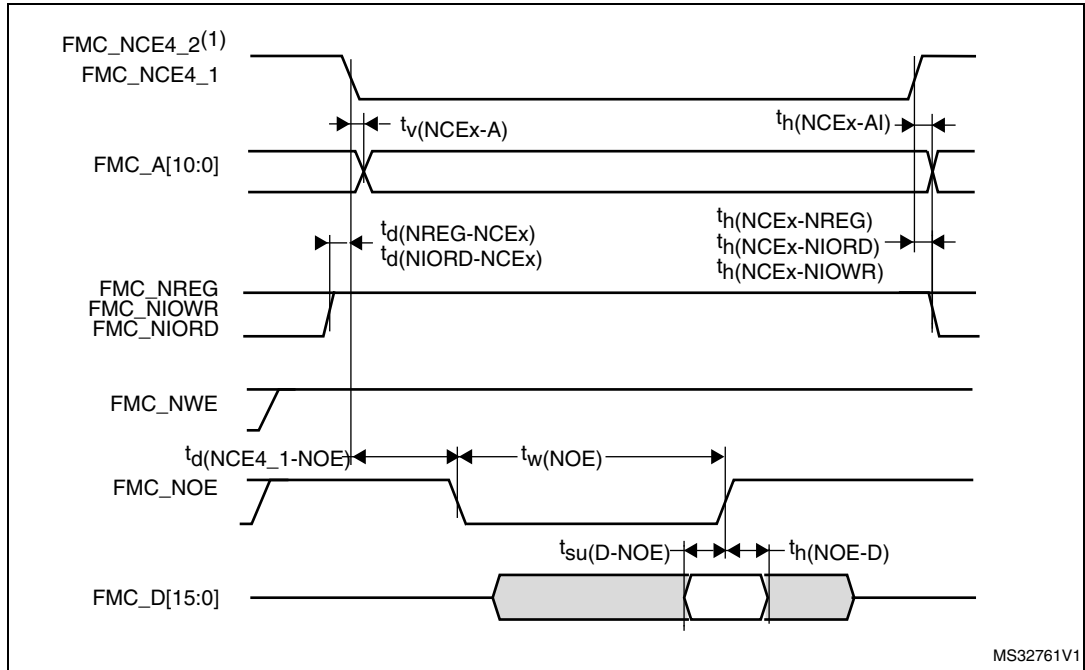
PC Card/CompactFlash controller waveforms and timings

[Figure 62](#) through [Figure 67](#) represent synchronous waveforms, and [Table 100](#) and [Table 101](#) provide the corresponding timings. The results shown in this table are obtained with the following FMC configuration:

- COM.FMC_SetupTime = 0x04;
- COM.FMC_WaitSetupTime = 0x07;
- COM.FMC_HoldSetupTime = 0x04;
- COM.FMC_HiZSetupTime = 0x00;
- ATT.FMC_SetupTime = 0x04;
- ATT.FMC_WaitSetupTime = 0x07;
- ATT.FMC_HoldSetupTime = 0x04;
- ATT.FMC_HiZSetupTime = 0x00;
- IO.FMC_SetupTime = 0x04;
- IO.FMC_WaitSetupTime = 0x07;
- IO.FMC_HoldSetupTime = 0x04;
- IO.FMC_HiZSetupTime = 0x00;
- TCLRSetupTime = 0;
- TARSetupTime = 0.

In all timing tables, the T_{HCLK} is the HCLK clock period.

Figure 62. PC Card/CompactFlash controller waveforms for common memory read access



1. FMC_NCE4_2 remains high (inactive during 8-bit access).

Figure 63. PC Card/CompactFlash controller waveforms for common memory write access

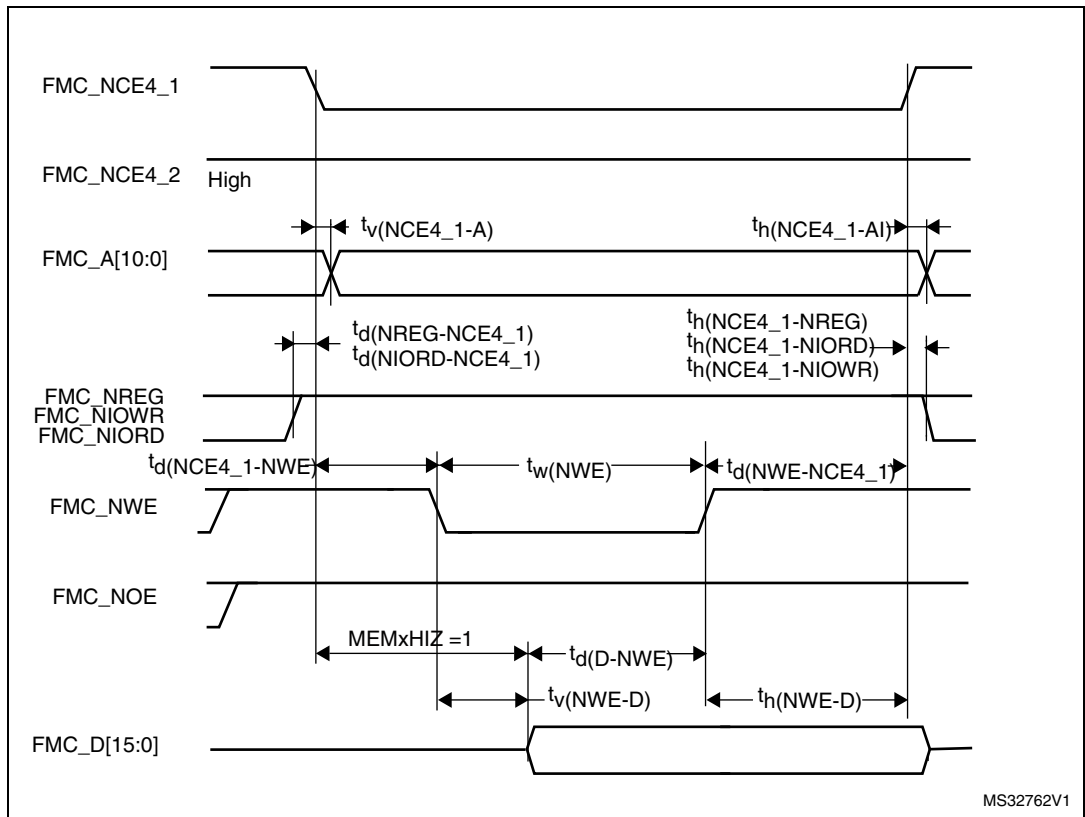
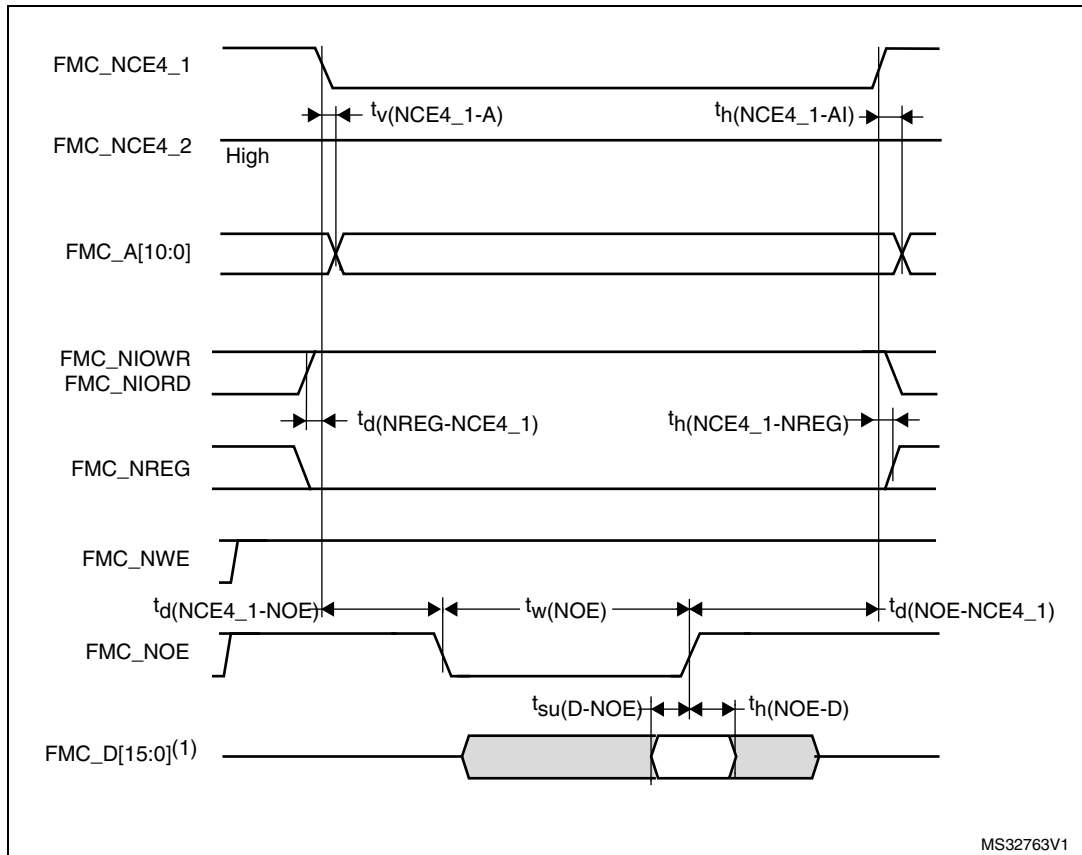
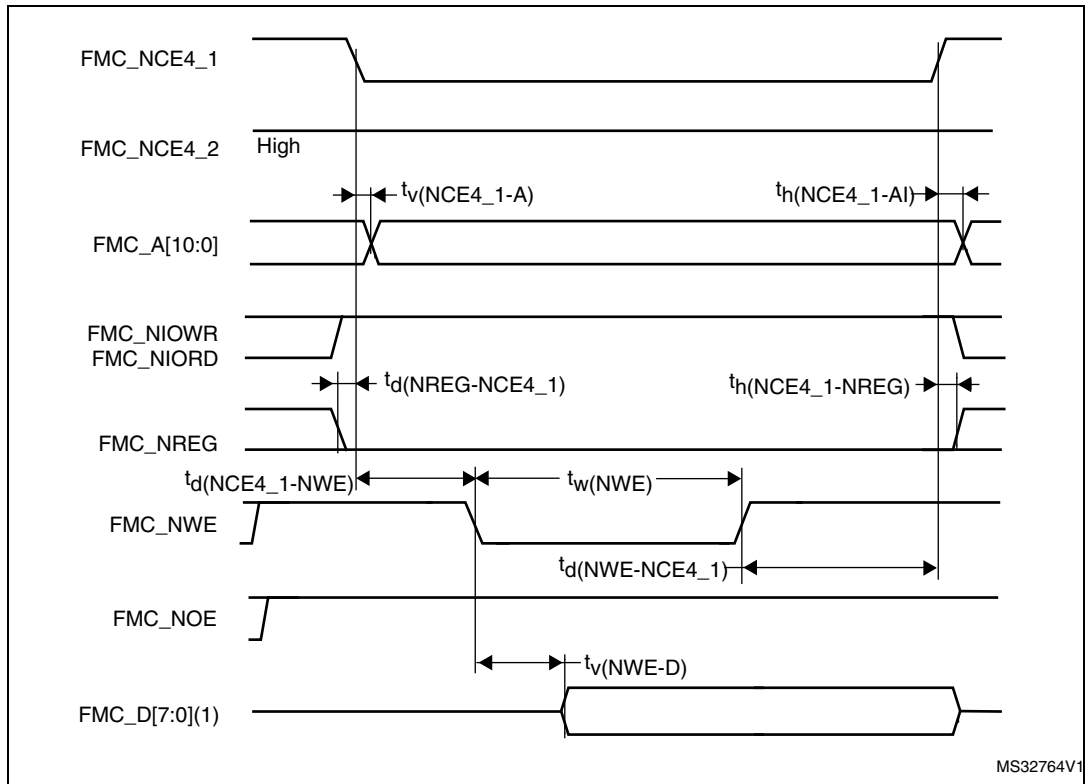


Figure 64. PC Card/CompactFlash controller waveforms for attribute memory read access



1. Only data bits 0...7 are read (bits 8...15 are disregarded).

Figure 65. PC Card/CompactFlash controller waveforms for attribute memory write access



1. Only data bits 0..7 are driven (bits 8..15 remains Hi-Z).

Figure 66. PC Card/CompactFlash controller waveforms for I/O space read access

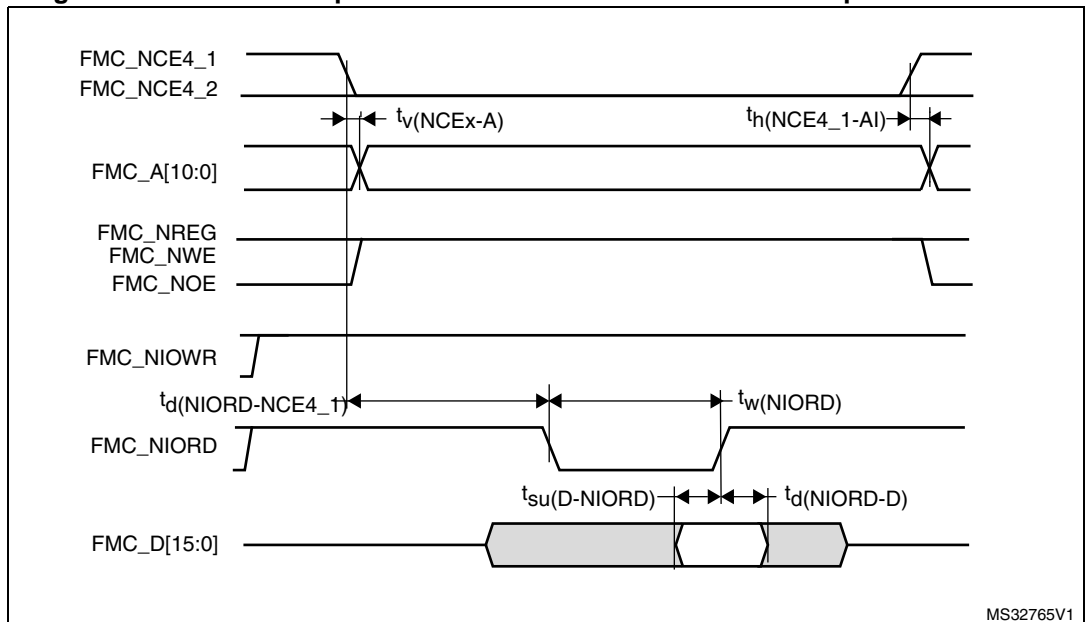


Figure 67. PC Card/CompactFlash controller waveforms for I/O space write access

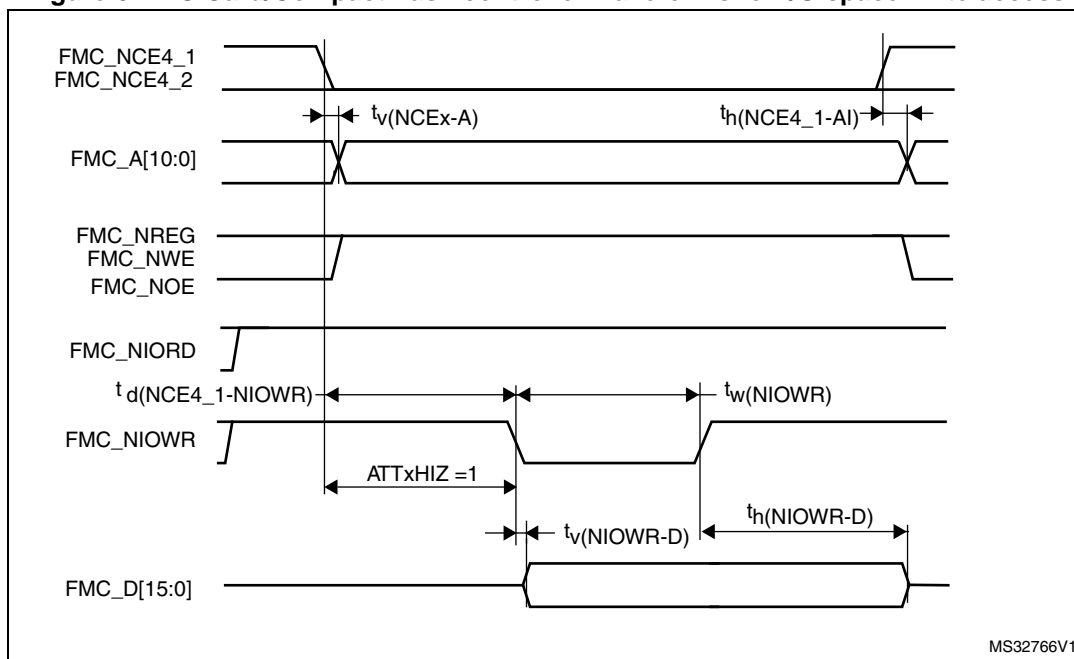


Table 100. Switching characteristics for PC Card/CF read and write cycles in attribute/common space⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$t_{v(NCEx-A)}$	FMC_Ncex low to FMC_Ay valid	-	0	ns
$t_{h(NCEx-AI)}$	FMC_NCEx high to FMC_Ax invalid	0	-	ns
$t_{d(NREG-NCEx)}$	FMC_NCEx low to FMC_NREG valid	-	1	ns
$t_{h(NCEx-NREG)}$	FMC_NCEx high to FMC_NREG invalid	$T_{HCLK}-2$	-	ns
$t_{d(NCEx-NWE)}$	FMC_NCEx low to FMC_NWE low	-	$5T_{HCLK}$	ns
$t_w(NWE)$	FMC_NWE low width	$8T_{HCLK}-0.5$	$8T_{HCLK}+0.5$	ns
$t_{d(NWE-NCEx)}$	FMC_NWE high to FMC_NCEx high	$5T_{HCLK}+1$	-	ns
$t_{v(NWE-D)}$	FMC_NWE low to FMC_D[15:0] valid	-	0	ns
$t_{h(NWE-D)}$	FMC_NWE high to FMC_D[15:0] invalid	$9T_{HCLK}-0.5$	-	ns
$t_{d(D-NWE)}$	FMC_D[15:0] valid before FMC_NWE high	$13T_{HCLK}-3$	-	ns
$t_{d(NCEx-NOE)}$	FMC_NCEx low to FMC_NOE low	-	$5T_{HCLK}$	ns
$t_w(NOE)$	FMC_NOE low width	$8T_{HCLK}-0.5$	$8T_{HCLK}+0.5$	ns
$t_{d(NOE-NCEx)}$	FMC_NOE high to FMC_NCEx high	$5T_{HCLK}-1$	-	ns
$t_{su(D-NOE)}$	FMC_D[15:0] valid data before FMC_NOE high	$1T_{HCLK}$	-	ns
$t_{h(NOE-D)}$	FMC_NOE high to FMC_D[15:0] invalid	0	-	ns

1. $C_L = 30$ pF.
2. Based on characterization, not tested in production.

Table 101. Switching characteristics for PC Card/CF read and write cycles in I/O space⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
tw(NIOWR)	FMC_NIOWR low width	$8T_{HCLK}-0.5$	-	ns
tv(NIOWR-D)	FMC_NIOWR low to FMC_D[15:0] valid	-	0	ns
th(NIOWR-D)	FMC_NIOWR high to FMC_D[15:0] invalid	$9T_{HCLK}-2$	-	ns
td(NCE4_1-NIOWR)	FMC_NCE4_1 low to FMC_NIOWR valid	-	$5T_{HCLK}$	ns
th(NCEx-NIOWR)	FMC_NCEx high to FMC_NIOWR invalid	$5T_{HCLK}$	-	ns
td(NIORD-NCEx)	FMC_NCEx low to FMC_NIORD valid	-	$5T_{HCLK}$	ns
th(NCEx-NIORD)	FMC_NCEx high to FMC_NIORD) valid	$6T_{HCLK}+2$	-	ns
tw(NIORD)	FMC_NIORD low width	$8T_{HCLK}-0.5$	$8T_{HCLK}+0.5$	ns
tsu(D-NIORD)	FMC_D[15:0] valid before FMC_NIORD high	$1T_{HCLK}$	-	ns
td(NIORD-D)	FMC_D[15:0] valid after FMC_NIORD high	0	-	ns

1. $C_L = 30$ pF.

2. Based on characterization, not tested in production.

NAND controller waveforms and timings

[Figure 68](#) through [Figure 71](#) represent synchronous waveforms, and [Table 102](#) and [Table 103](#) provide the corresponding timings. The results shown in this table are obtained with the following FMC configuration:

- COM.FMC_SetupTime = 0x01;
- COM.FMC_WaitSetupTime = 0x03;
- COM.FMC_HoldSetupTime = 0x02;
- COM.FMC_HiZSetupTime = 0x01;
- ATT.FMC_SetupTime = 0x01;
- ATT.FMC_WaitSetupTime = 0x03;
- ATT.FMC_HoldSetupTime = 0x02;
- ATT.FMC_HiZSetupTime = 0x01;
- Bank = FMC_Bank_NAND;
- MemoryDataWidth = FMC_MemoryDataWidth_16b;
- ECC = FMC_ECC_Enable;
- ECCPageSize = FMC_ECCPageSize_512Bytes;
- TCLRSetupTime = 0;
- TARSetupTime = 0.

In all timing tables, the T_{HCLK} is the HCLK clock period.

Figure 68. NAND controller waveforms for read access

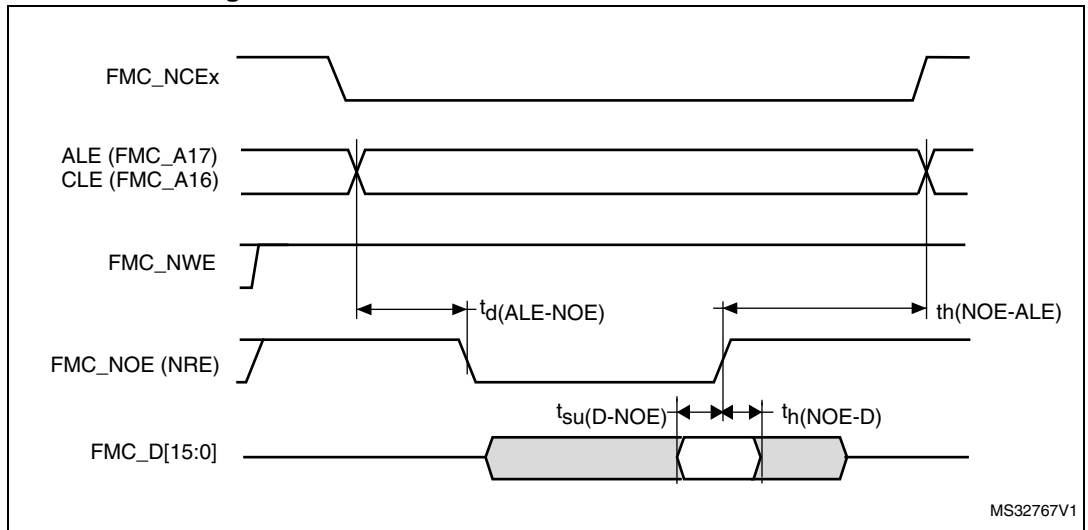


Figure 69. NAND controller waveforms for write access

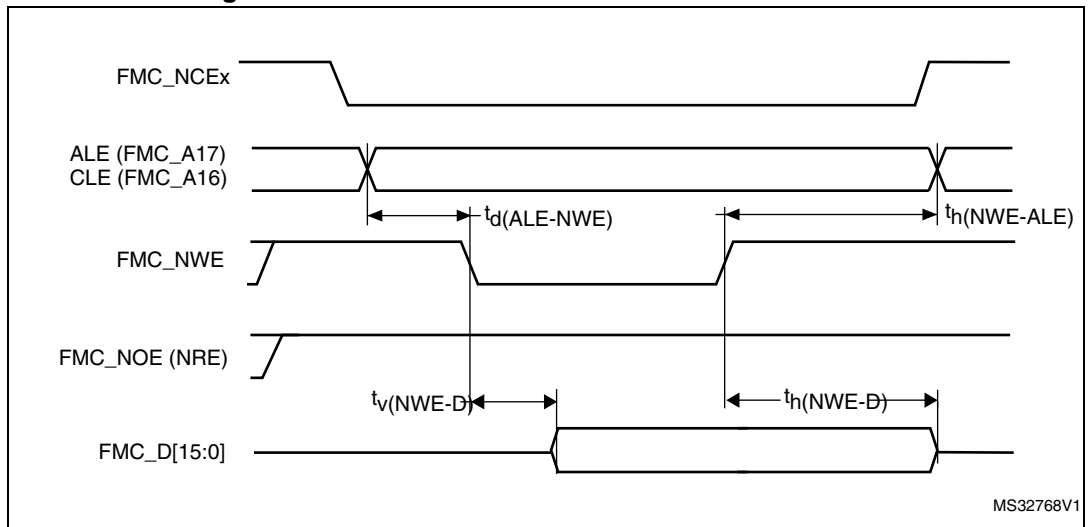
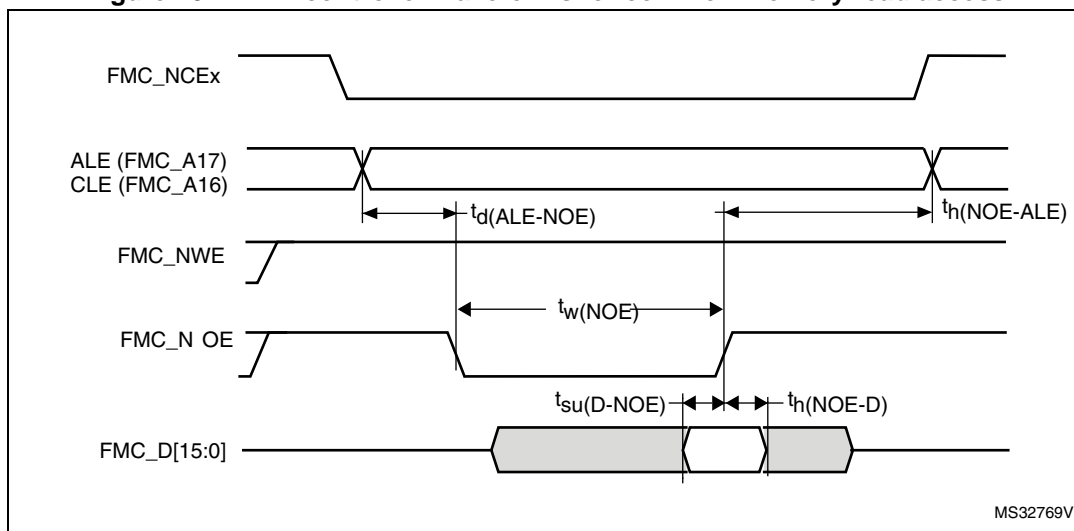
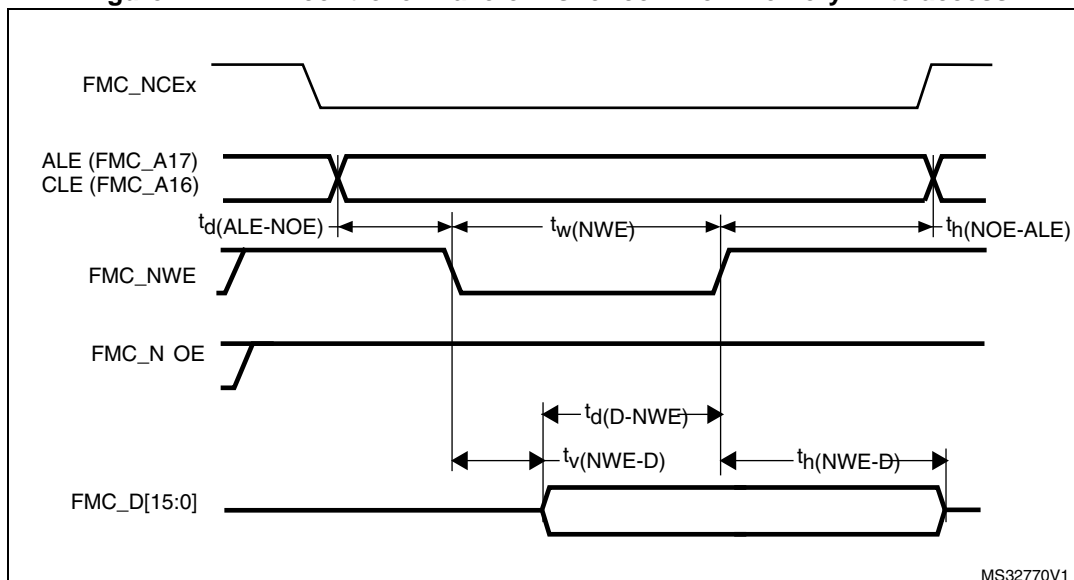


Figure 70. NAND controller waveforms for common memory read access



MS32769V1

Figure 71. NAND controller waveforms for common memory write access



MS32770V1

Table 102. Switching characteristics for NAND Flash read cycles⁽¹⁾

Symbol	Parameter	Min	Max	Unit
$t_w(\text{NOE})$	FMC_NOE low width	$4T_{\text{HCLK}}-0.5$	$4T_{\text{HCLK}}+0.5$	ns
$t_{su}(\text{D-NOE})$	FMC_D[15-0] valid data before FMC_NOE high	9	-	ns
$t_h(\text{NOE-D})$	FMC_D[15-0] valid data after FMC_NOE high	0	-	ns
$t_d(\text{ALE-NOE})$	FMC_ALE valid before FMC_NOE low	-	$3T_{\text{HCLK}}-0.5$	ns
$t_h(\text{NOE-ALE})$	FMC_NWE high to FMC_ALE invalid	$3T_{\text{HCLK}}-2$	-	ns

1. $C_L = 30 \text{ pF}$.

Table 103. Switching characteristics for NAND Flash write cycles⁽¹⁾

Symbol	Parameter	Min	Max	Unit
$t_{w(NWE)}$	FMC_NWE low width	$4T_{HCLK}$	$4T_{HCLK}+1$	ns
$t_{v(NWE-D)}$	FMC_NWE low to FMC_D[15-0] valid	0	-	ns
$t_{h(NWE-D)}$	FMC_NWE high to FMC_D[15-0] invalid	$3T_{HCLK}-1$	-	ns
$t_{d(D-NWE)}$	FMC_D[15-0] valid before FMC_NWE high	$5T_{HCLK}-3$	-	ns
$t_{d(ALE-NWE)}$	FMC_ALE valid before FMC_NWE low	-	$3T_{HCLK}-0.5$	ns
$t_{h(NWE-ALE)}$	FMC_NWE high to FMC_ALE invalid	$3T_{HCLK}-1$	-	ns

1. $C_L = 30$ pF.

SDRAM waveforms and timings

In all timing tables, T_{HCLK} is the HCLK clock period (with maximum FMC_CLK = 90 MHz frequency), and V_{DD} ranges from 2.7 to 3.6 V.

Figure 72. SDRAM read access waveforms

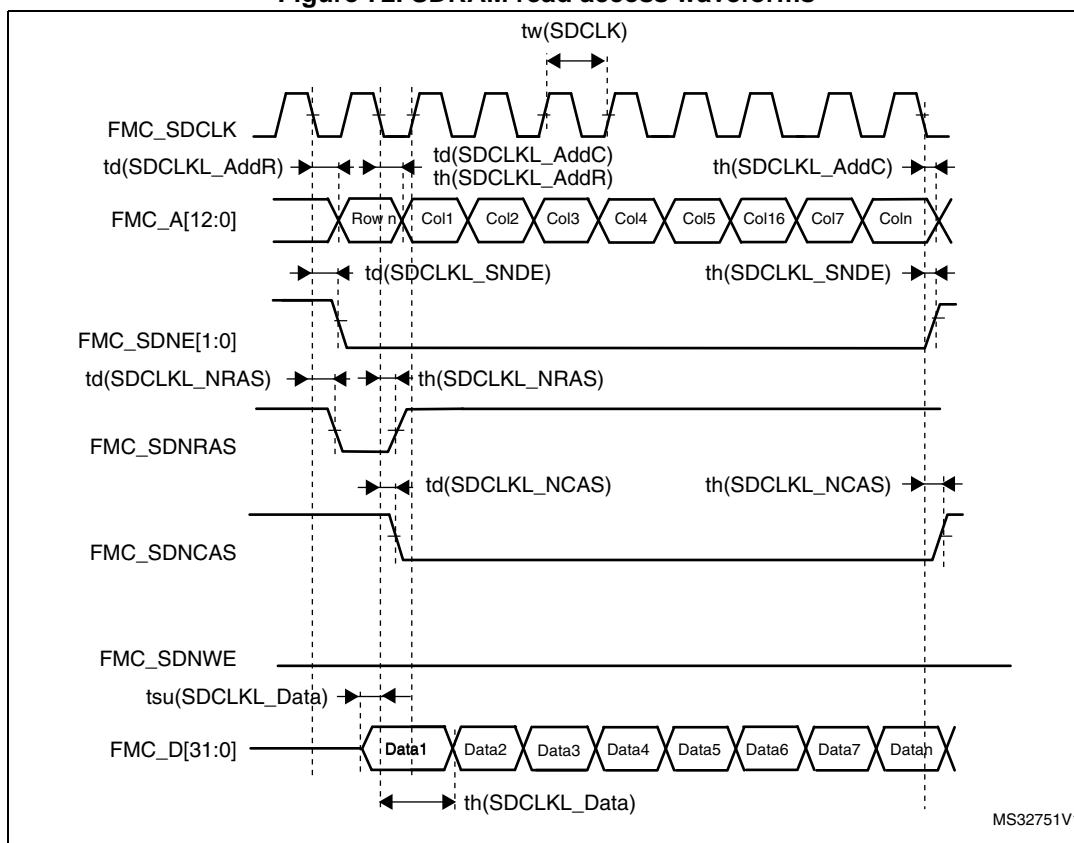
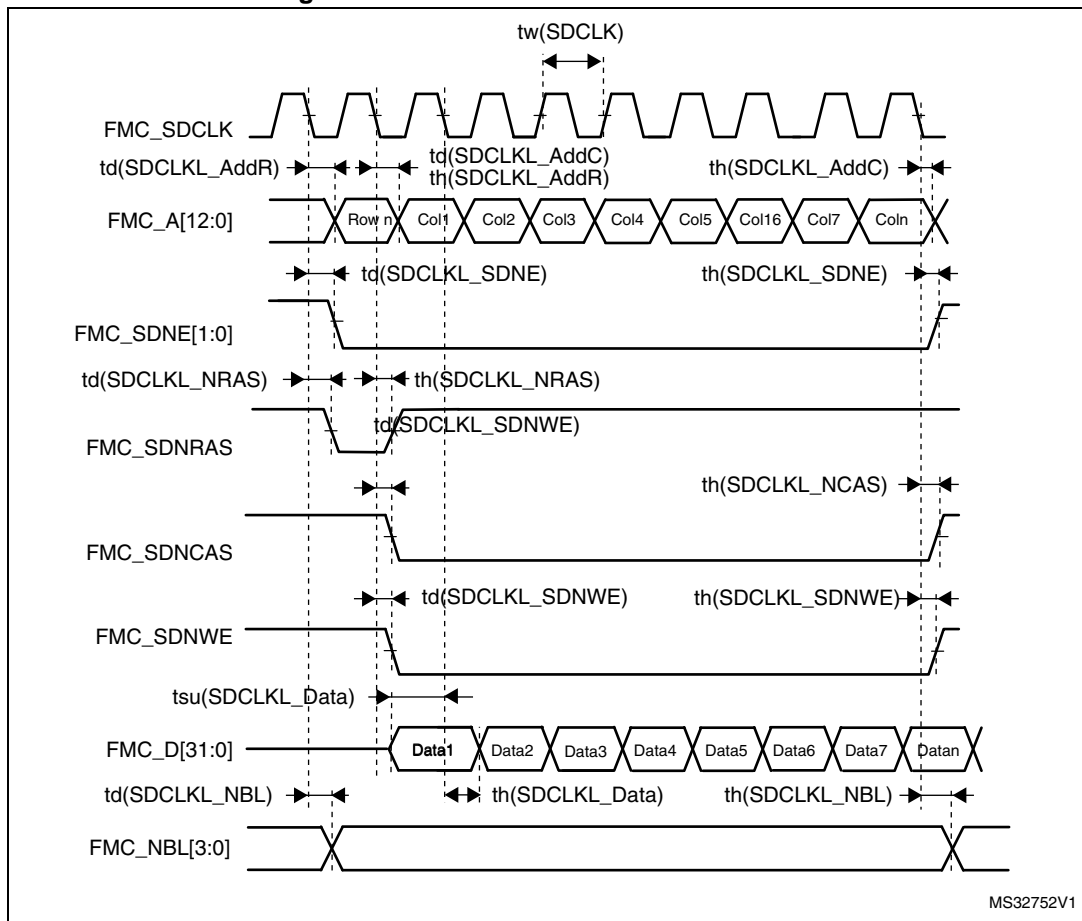


Table 104. SDRAM read timings⁽¹⁾

Symbol	Parameter	Min	Max	Unit
$t_w(\text{SDCLK})$	FMC_SDCLK period	$2T_{\text{HCLK}}-0.5$	$2T_{\text{HCLK}}+0.5$	ns
$t_{\text{su}}(\text{SDCLKH_Data})$	Data input setup time	2	-	
$t_{\text{h}}(\text{SDCLK H_Data})$	Data input hold time	0	-	
$t_{\text{d}}(\text{SDCLKL_Add})$	Address valid time	-	1.5	
$t_{\text{d}}(\text{SDCLKL- SDNE})$	Chip select valid time	-	0.5	
$t_{\text{h}}(\text{SDCLKL- SDNE})$	Chip select hold time	0	-	
$t_{\text{d}}(\text{SDCLKL-SDNRAS})$	SDNRAS valid time	-	0.5	
$t_{\text{h}}(\text{SDCLKL-SDNRAS})$	SDNRAS hold time	0	-	
$t_{\text{d}}(\text{SDCLKL-SDNCAS})$	SDNCAS valid time	-	0.5	
$t_{\text{h}}(\text{SDCLKL-SDNCAS})$	SDNCAS hold time	0	-	

1. CL = 30 pF on data and address lines. CL=15pF on FMC_SDCLK.

Figure 73. SDRAM write access waveforms



MS32752V1

Table 105. SDRAM write timings⁽¹⁾

Symbol	Parameter	Min	Max	Unit
$t_{w(SDCLK)}$	FMC_SDCLK period	$2T_{HCLK}-0.5$	$2T_{HCLK}+0.5$	ns
$t_{d(SDCLKL_Data)}$	Data output valid time	-	2.5	
$t_{h(SDCLKL_Data)}$	Data output hold time	3.5	-	
$t_{d(SDCLKL_Add)}$	Address valid time	-	1.5	
$t_{d(SDCLKL-SDNWE)}$	SDNWE valid time	-	1	
$t_{h(SDCLKL-SDNWE)}$	SDNWE hold time	0	-	
$t_{d(SDCLKL-SDNE)}$	Chip select valid time	-	0.5	
$t_{h(SDCLKL-SDNE)}$	Chip select hold time	0	-	
$t_{d(SDCLKL-SDNRAS)}$	SDNRAS valid time	-	2	
$t_{h(SDCLKL-SDNRAS)}$	SDNRAS hold time	0	-	
$t_{d(SDCLKL-SDNCAS)}$	SDNCAS valid time	-	0.5	
$t_{h(SDCLKL-SDNCAS)}$	SDNCAS hold time	0	-	

1. CL = 30 pF on data and address lines. CL=15pF on FMC_SDCLK.

6.3.27 Camera interface (DCMI) timing specifications

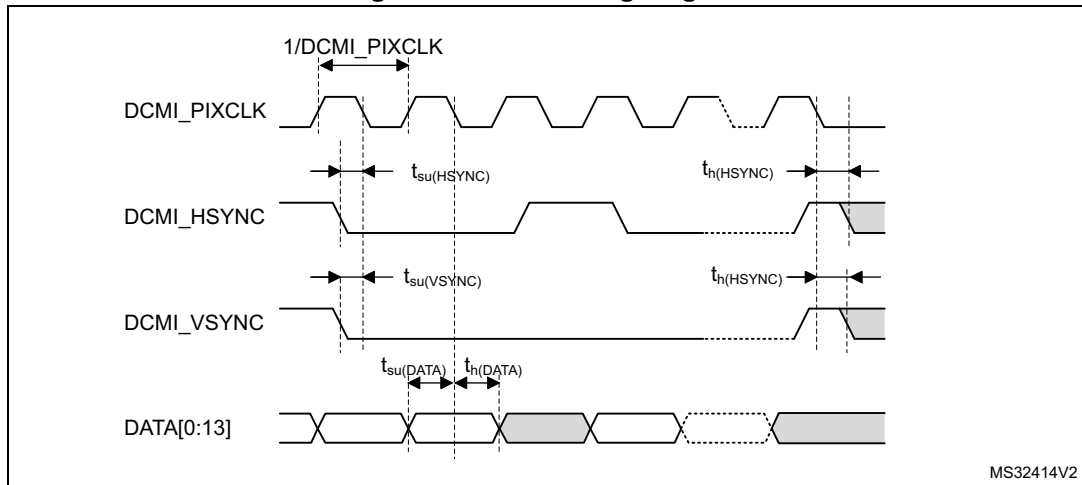
Unless otherwise specified, the parameters given in [Table 106](#) for DCMI are derived from tests performed under the ambient temperature, f_{HCLK} frequency and V_{DD} supply voltage summarized in [Table 17](#), with the following configuration:

- DCMI_PIXCLK polarity: falling
- DCMI_VSYNC and DCMI_HSYNC polarity: high
- Data formats: 14 bits

Table 106. DCMI characteristics

Symbol	Parameter	Min	Max	Unit
	Frequency ratio DCMI_PIXCLK/ f_{HCLK}	-	0.4	
DCMI_PIXCLK	Pixel clock input	-	54	MHz
D_{Pixel}	Pixel clock input duty cycle	30	70	%
$t_{su(DATA)}$	Data input setup time	2	-	ns
$t_{h(DATA)}$	Data input hold time	2.5	-	
$t_{su(HSYNC)}$ $t_{su(VSYNC)}$	DCMI_HSYNC/DCMI_VSYNC input setup time	0.5	-	
$t_{h(HSYNC)}$ $t_{h(VSYNC)}$	DCMI_HSYNC/DCMI_VSYNC input hold time	1	-	

Figure 74. DCMI timing diagram



MS32414V2

6.3.28 LCD-TFT controller (LTDC) characteristics

Unless otherwise specified, the parameters given in [Table 107](#) for LCD-TFT are derived from tests performed under the ambient temperature, f_{HCLK} frequency and VDD supply voltage summarized in [Table 17](#), with the following configuration:

- LCD_CLK polarity: high
- LCD_DE polarity : low
- LCD_VSYNC and LCD_HSYNC polarity: high
- Pixel formats: 24 bits

Table 107. LTDC characteristics

Symbol	Parameter	Min	Max	Unit
f_{CLK}	LTDC clock output frequency	-	42	MHz
D_{CLK}	LTDC clock output duty cycle	45	55	%
$t_w(CLKH)$ $t_w(CLKL)$	Clock High time, low time	$tw(CLK)/2-0.5$	$tw(CLK)/2+0.5$	ns
$t_v(DATA)$	Data output valid time	-	3.5	
$t_h(DATA)$	Data output hold time	1.5	-	
$t_v(HSYNC)$	HSYNC/VSYNC/DE output valid time	-	2.5	
$t_v(VSYNC)$		-		
$t_v(DE)$		-		
$t_h(HSYNC)$	HSYNC/VSYNC/DE output hold time	2	-	
$t_h(VSYNC)$				
$t_h(DE)$				

Figure 75. LCD-TFT horizontal timing diagram

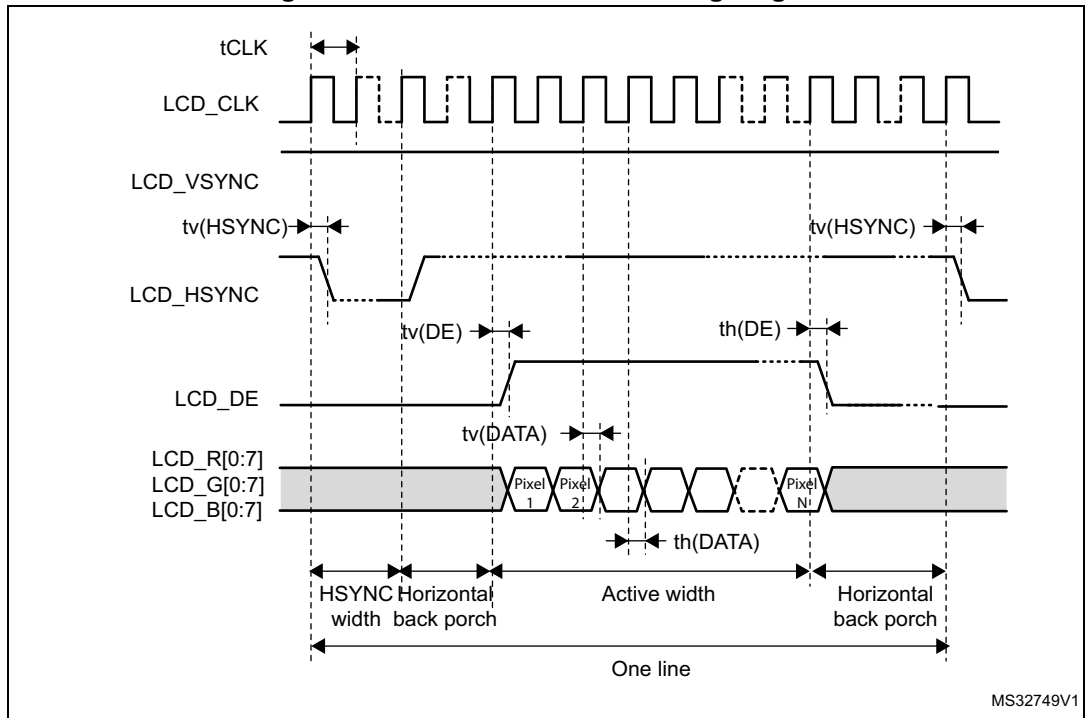
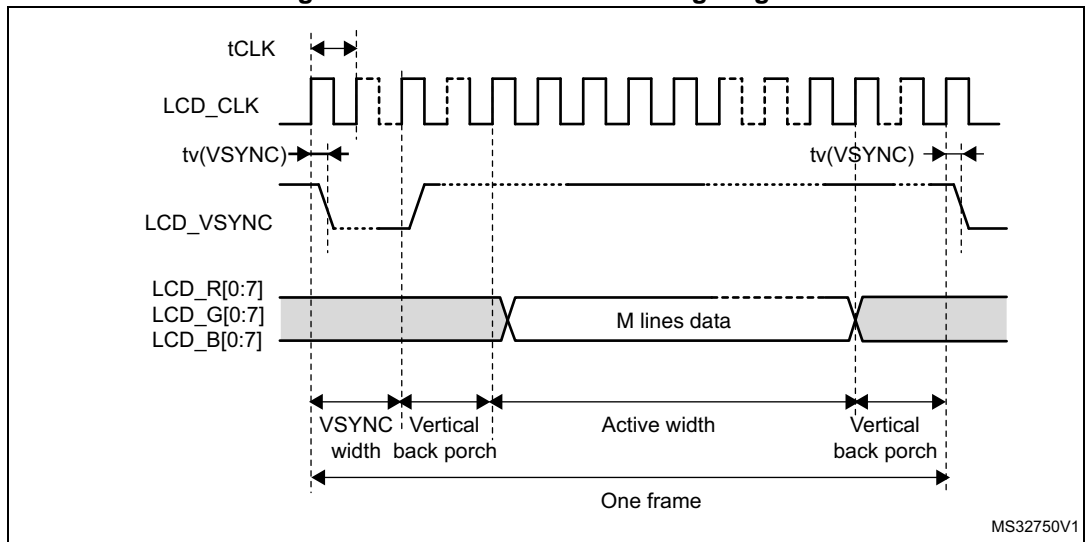


Figure 76. LCD-TFT vertical timing diagram



6.3.29 SD/SDIO MMC card host interface (SDIO) characteristics

Unless otherwise specified, the parameters given in [Table 108](#) for the SDIO/MMC interface are derived from tests performed under the ambient temperature, f_{PCLK2} frequency and V_{DD} supply voltage conditions summarized in [Table 17](#), with the following configuration:

- Output speed is set to $OSPEEDRy[1:0] = 10$
- Capacitive load $C = 30\text{ pF}$
- Measurement points are done at CMOS levels: $0.5V_{DD}$

Refer to [Section 6.3.17: I/O port characteristics](#) for more details on the input/output characteristics.

Figure 77. SDIO high-speed mode

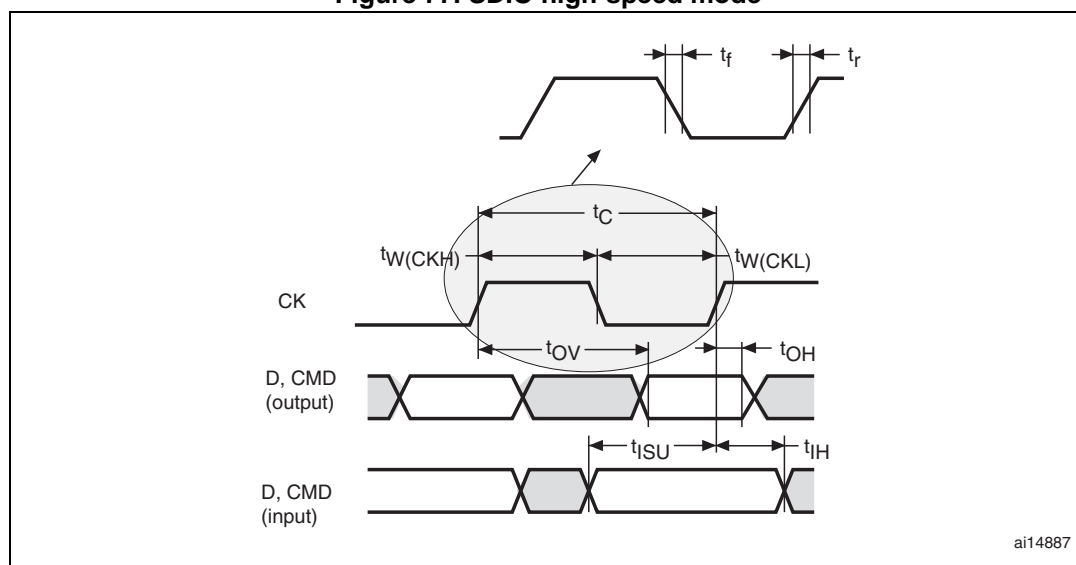


Figure 78. SD default mode

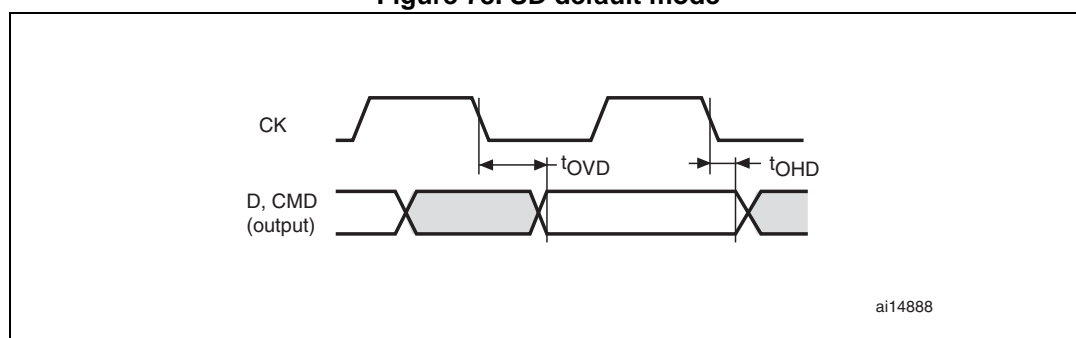


Table 108. Dynamic characteristics: SD / MMC characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{PP}	Clock frequency in data transfer mode		0		48	MHz
-	SDIO_CK/fPCLK2 frequency ratio		-	-	8/3	-
$t_{W(CKL)}$	Clock low time	$f_{pp} = 48\text{MHz}$	8.5	9	-	ns
$t_{W(CKH)}$	Clock high time	$f_{pp} = 48\text{MHz}$	8.3	10	-	

Table 108. Dynamic characteristics: SD / MMC characteristics⁽¹⁾ (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
CMD, D inputs (referenced to CK) in MMC and SD HS mode						
t _{ISU}	Input setup time HS	f _{pp} =48MHz	3.5	-	-	ns
t _{IH}	Input hold time HS	f _{pp} =48MHz	0	-	-	
CMD, D outputs (referenced to CK) in MMC and SD HS mode						
t _{OV}	Output valid time HS	f _{pp} =48MHz	-	4.5	7	ns
t _{OH}	Output hold time HS	f _{pp} =48MHz	3	-	-	
CMD, D inputs (referenced to CK) in SD default mode						
t _{ISUD}	Input setup time SD	f _{pp} =24MHz	1.5	-	-	ns
t _{IHD}	Input hold time SD	f _{pp} =24MHz	0.5	-	-	
CMD, D outputs (referenced to CK) in SD default mode						
t _{OVD}	Output valid default time SD	f _{pp} =24MHz	-	4.5	6.5	ns
t _{OHD}	Output hold default time SD	f _{pp} =24MHz	3.5	-	-	

1. Data based on characterization results, not tested in production.

6.3.30 RTC characteristics

Table 109. RTC characteristics

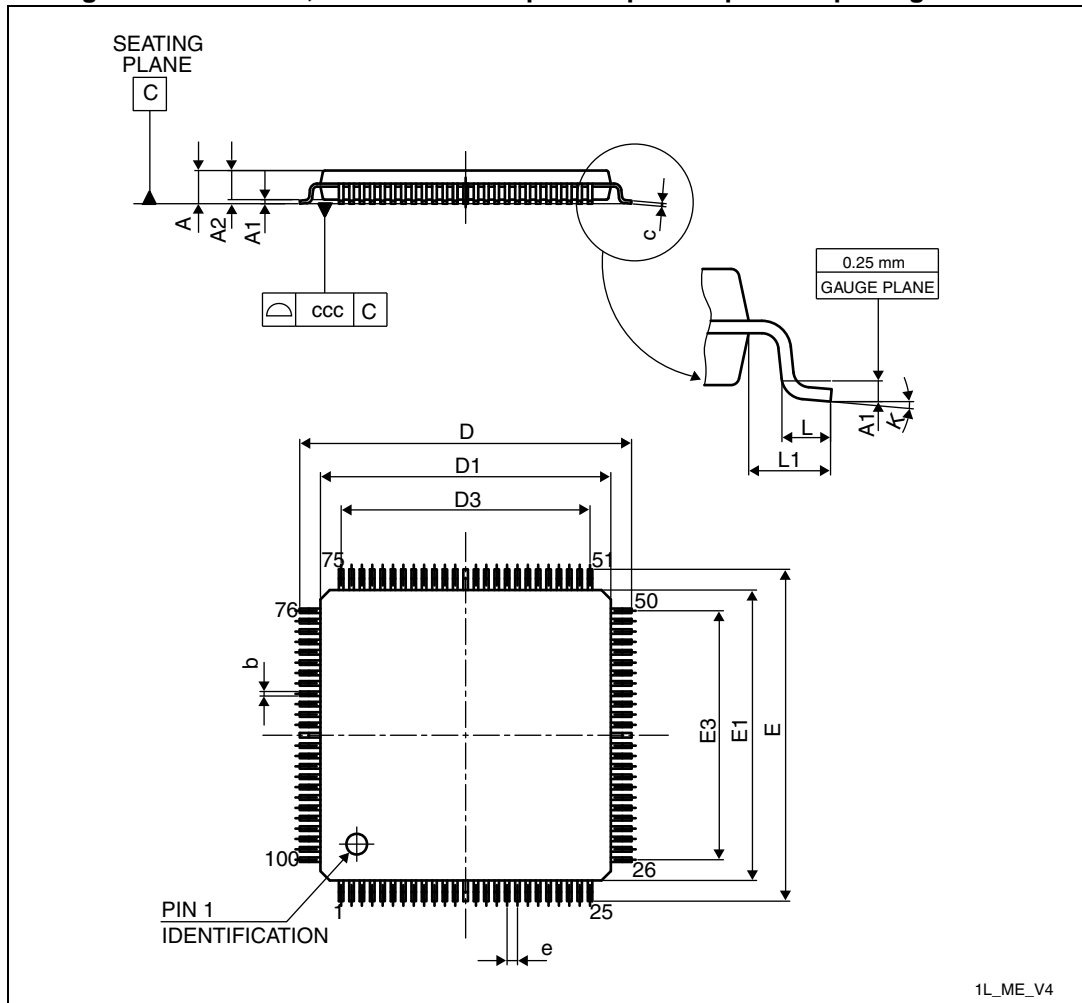
Symbol	Parameter	Conditions	Min	Max
-	f _{PCLK1} /RTCCLK frequency ratio	Any read/write operation from/to an RTC register	4	-

7 Package characteristics

7.1 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

Figure 79. LQFP100, 14 x 14 mm 100-pin low-profile quad flat package outline



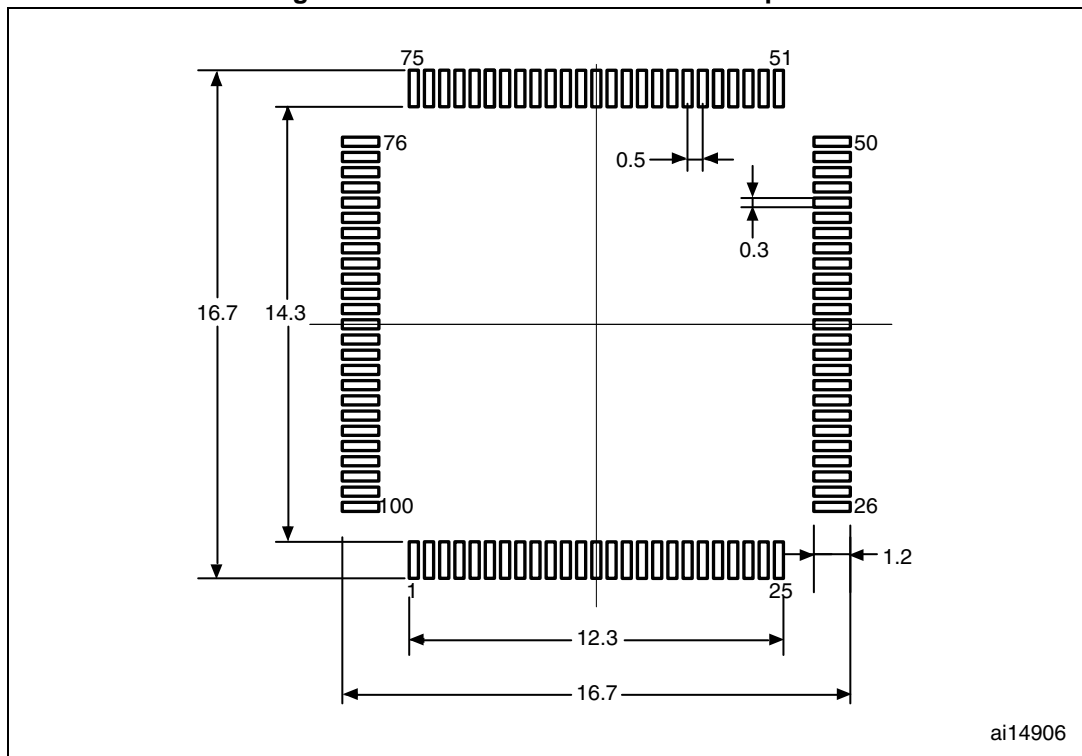
1. Drawing is not to scale.

Table 110. LQPF100, 14 x 14 mm 100-pin low-profile quad flat package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	15.800	16.000	16.200	0.6220	0.6299	0.6378
D1	13.800	14.000	14.200	0.5433	0.5512	0.5591
D3	-	12.000	-	-	0.4724	-
E	15.800	16.000	16.200	0.6220	0.6299	0.6378
E1	13.800	14.000	14.200	0.5433	0.5512	0.5591
E3	-	12.000	-	-	0.4724	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	3.5°	7°	0°	3.5°	7°
ccc	-	-	0.080	-	-	0.0031

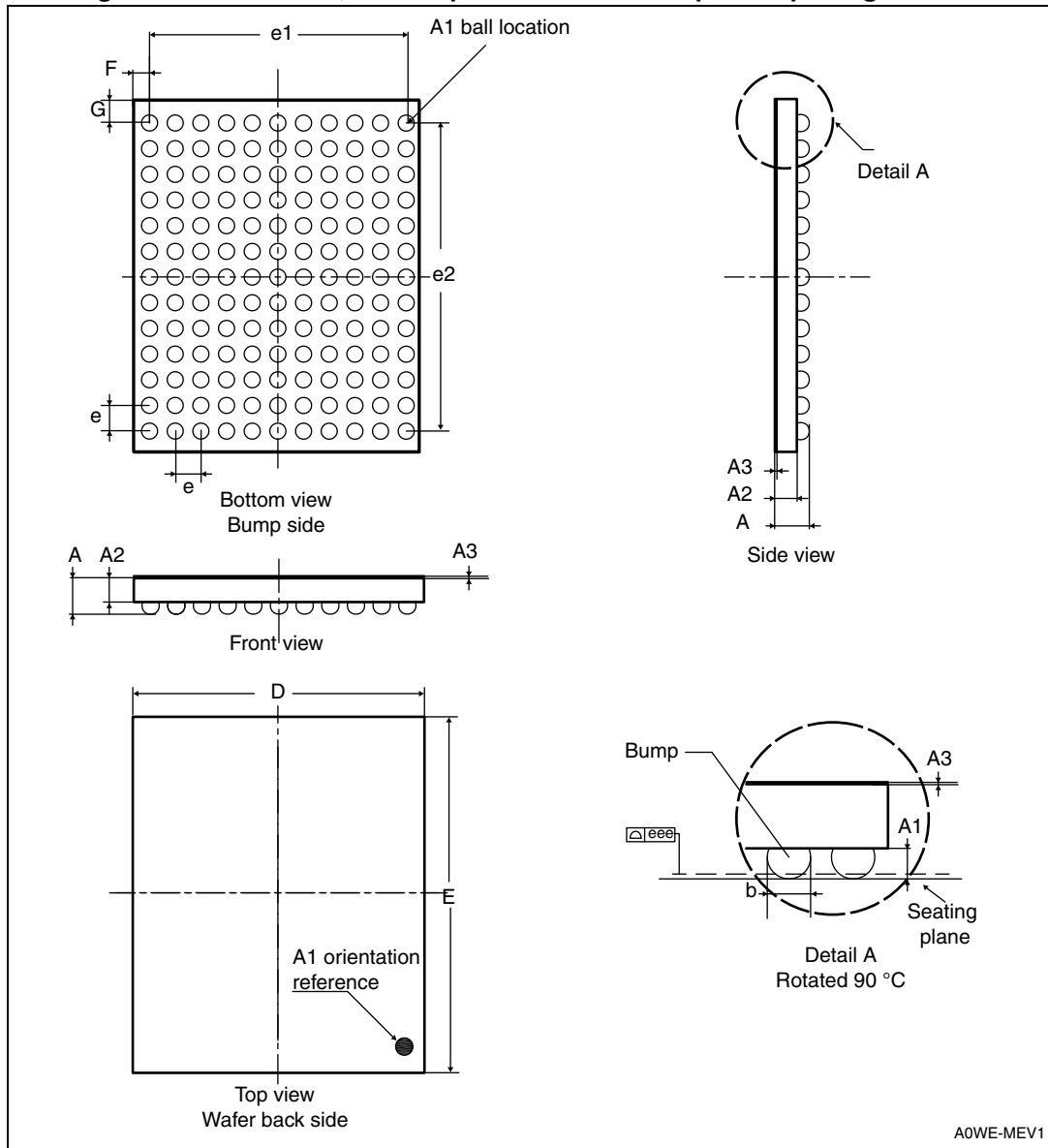
1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 80. LQPF100 recommended footprint



1. Dimensions are expressed in millimeters.

Figure 81. WLCSP143, 0.4 mm pitch wafer level chip scale package outline



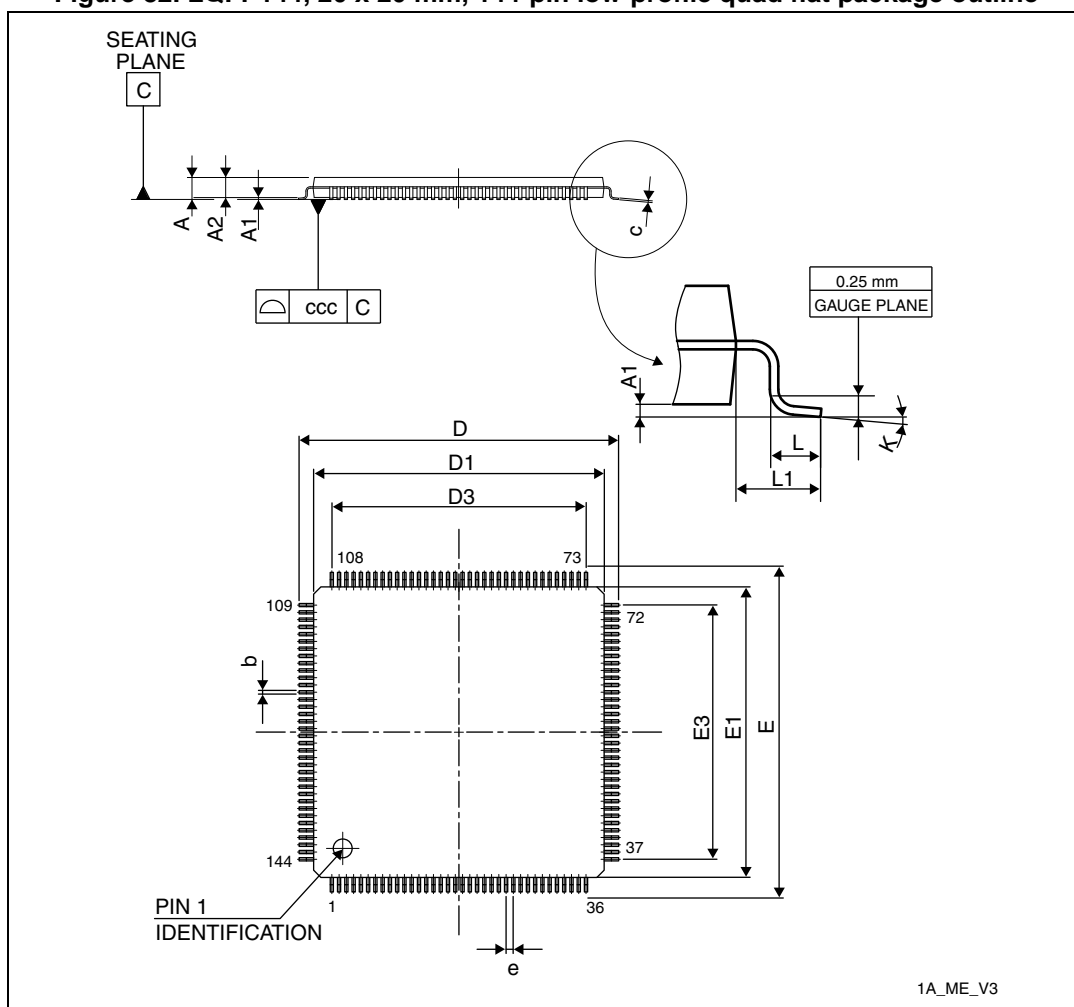
1. Drawing is not to scale.

Table 111. WLCSP143, 0.4 mm pitch wafer level chip scale package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	0.525	0.555	0.585	0.0207	0.0219	0.0230
A1	-	0.175	-	-	0.0069	-
A2	-	0.380	-	-	0.0150	-
A3	0.220	0.025	0.280	0.0087	0.0010	0.0110
b	-	0.250°	-	-	0.250°	-
D	4.486	4.521	4.556	0.1766	0.1780	0.1794
E	5.512	5.547	5.582	0.2170	0.2184	0.2198
e	-	0.400	-	-	0.0157	-
e1	-	4.000	-	-	0.1575	-
e2	-	4.800	-	-	0.1890	-
F	-	0.261	-	-	0.0103	-
G	-	0.374	-	-	0.0147	-
eee	-	0.050	-	-	0.0020	-

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 82. LQFP144, 20 x 20 mm, 144-pin low-profile quad flat package outline



1A_ME_V3

1. Drawing is not to scale.

Table 112. LQFP144, 20 x 20 mm, 144-pin low-profile quad flat package mechanical data

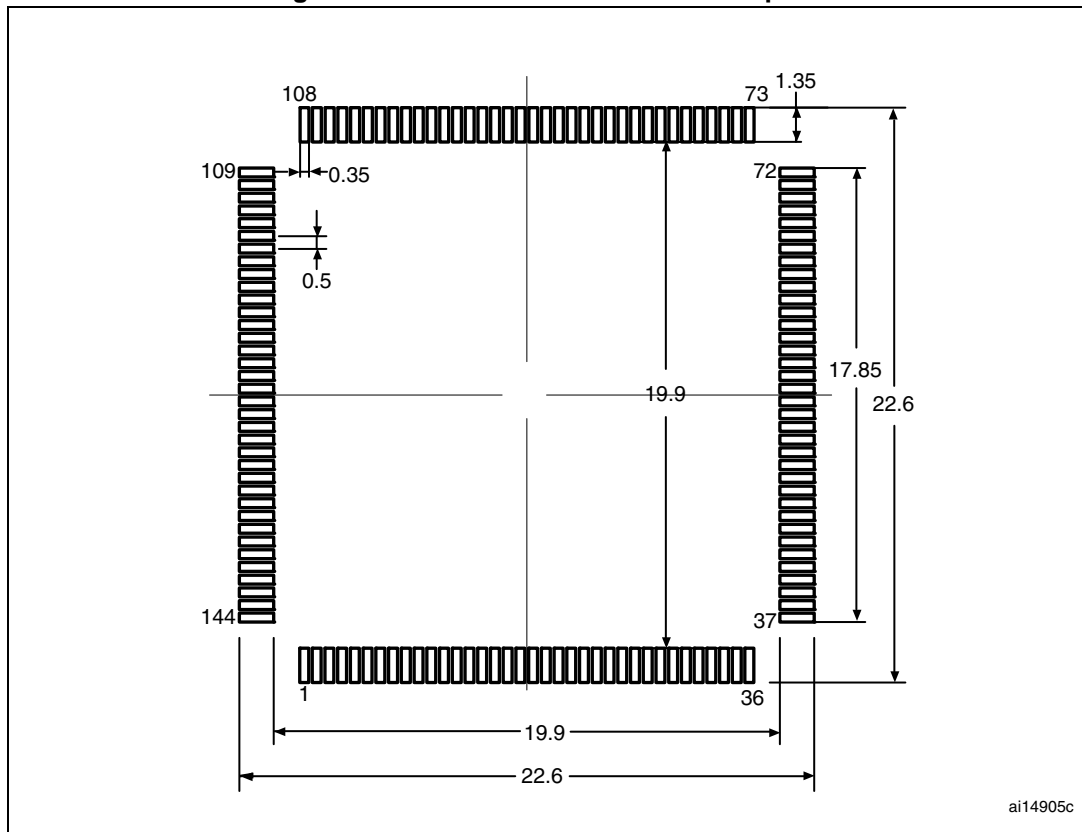
Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	21.800	22.000	22.200	0.8583	0.8661	0.874
D1	19.800	20.000	20.200	0.7795	0.7874	0.7953
D3	-	17.500	-	-	0.689	-

Table 112. LQFP144, 20 x 20 mm, 144-pin low-profile quad flat package mechanical data (continued)

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
E	21.800	22.000	22.200	0.8583	0.8661	0.8740
E1	19.800	20.000	20.200	0.7795	0.7874	0.7953
E3	-	17.500	-	-	0.6890	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	3.5°	7°	0°	3.5°	7°
ccc	-	-	0.080	-	-	0.0031

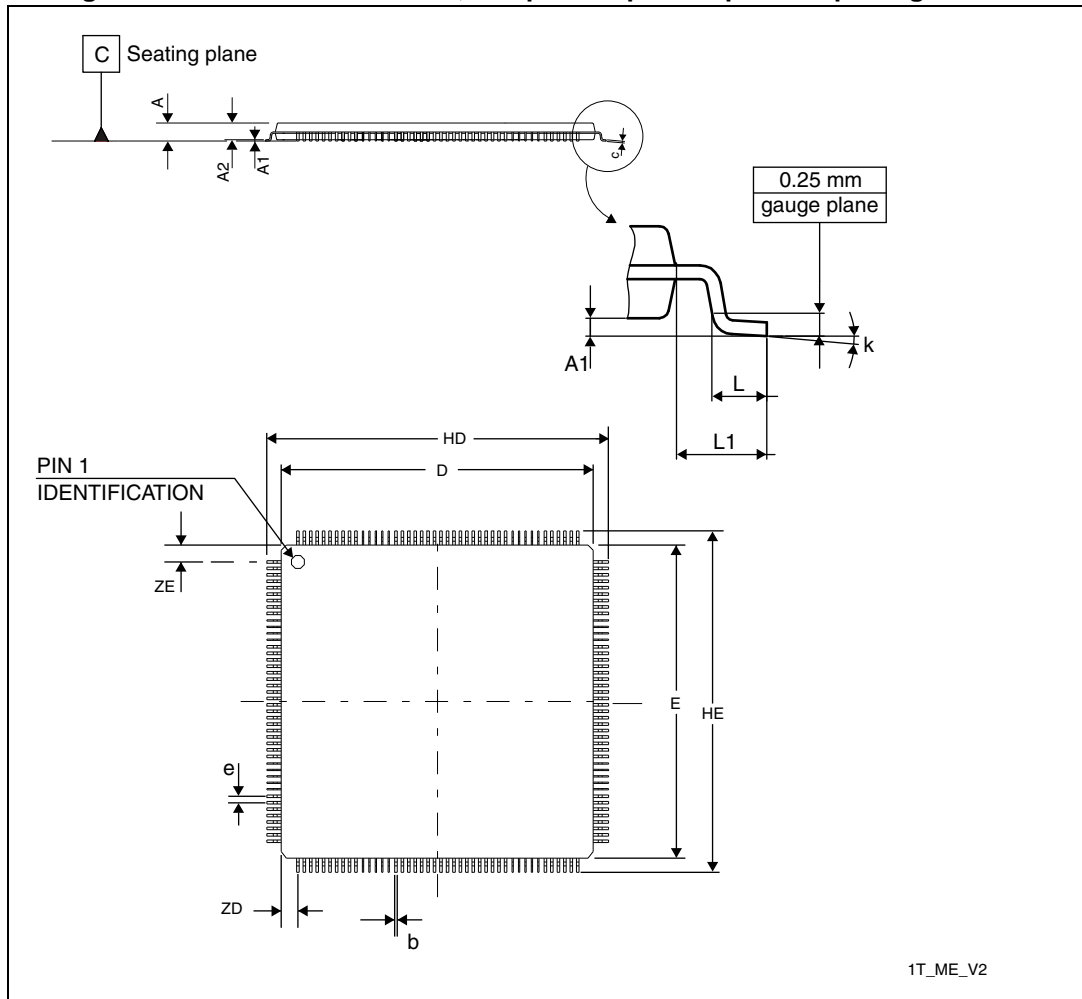
1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 83. LQFP144 recommended footprint



1. Dimensions are expressed in millimeters.

Figure 84. LQFP176 24 x 24 mm, 176-pin low-profile quad flat package outline



1. Drawing is not to scale.

Table 113. LQFP176, 24 x 24 mm, 176-pin low-profile quad flat package mechanical data

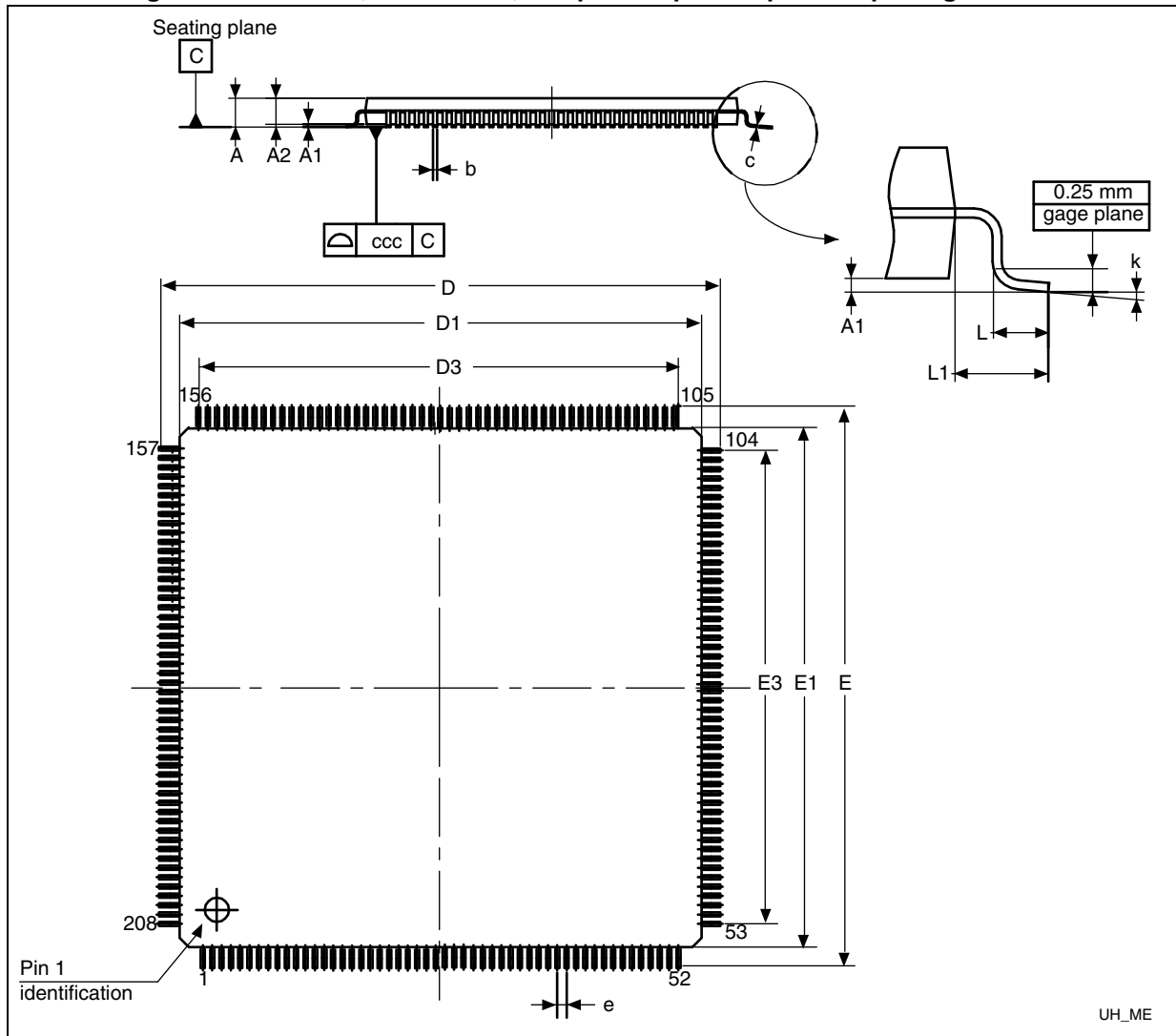
Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	-	1.450	0.0531	-	0.0060
b	0.170	-	0.270	0.0067	-	0.0106
C	0.090	-	0.200	0.0035	-	0.0079
D	23.900	-	24.100	0.9409	-	0.9488
E	23.900	-	24.100	0.9409	-	0.9488
e	-	0.500	-	-	0.0197	-
HD	25.900	-	26.100	1.0200	-	1.0276

**Table 113. LQFP176, 24 x 24 mm, 176-pin low-profile quad flat package
mechanical data (continued)**

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
HE	25.900	-	26.100	1.0200	-	1.0276
L	0.450	-	0.750	0.0177	-	0.0295
L1	-	1.000	-	-	0.0394	-
ZD	-	1.250	-	-	0.0492	-
ZE	-	1.250	-	-	0.0492	-
ccc	-	-	0.080	-	-	0.0031
k	0 °	-	7 °	0 °	-	7 °

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 86. LQFP208, 28 x 28 mm, 208-pin low-profile quad flat package outline



1. Drawing is not to scale.

Table 114. LQFP208, 28 x 28 mm, 208-pin low-profile quad flat package mechanical data

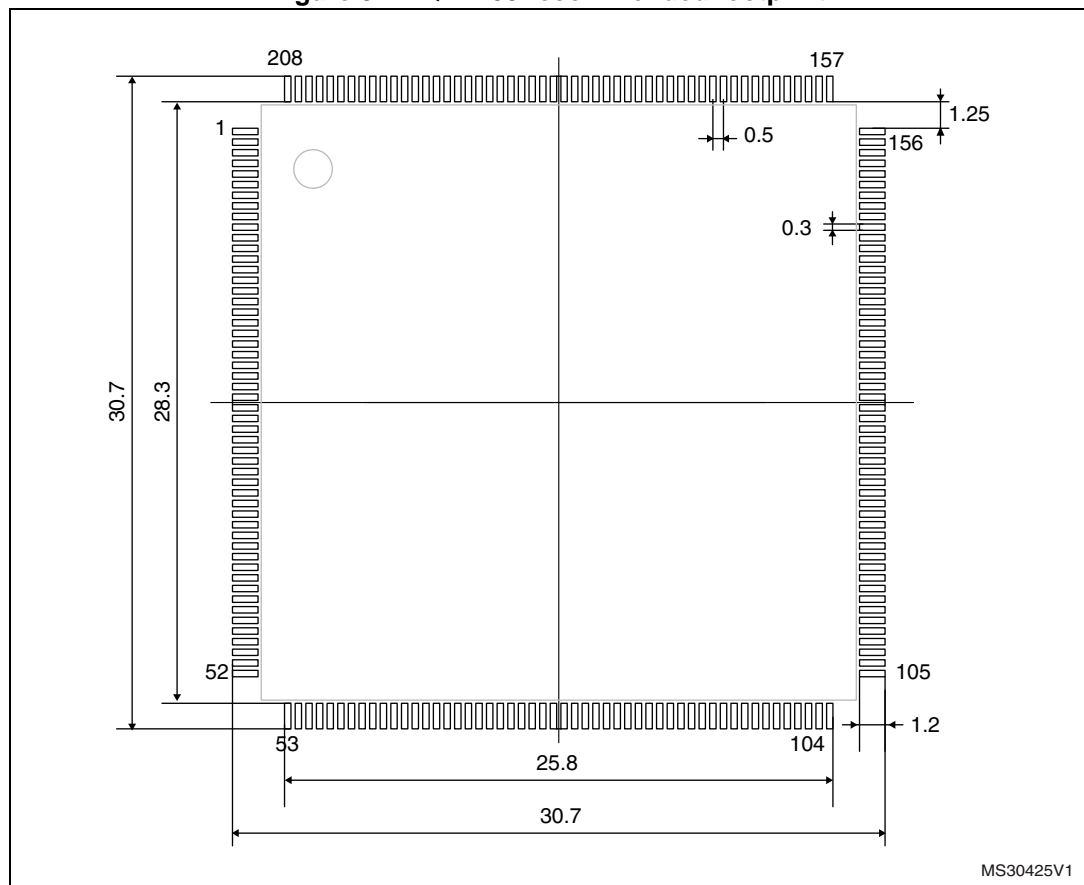
Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	--	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	29.800	30.000	30.200	1.1732	1.1811	1.1890
D1	27.800	28.000	28.200	1.0945	1.1024	1.1102

Table 114. LQFP208, 28 x 28 mm, 208-pin low-profile quad flat package mechanical data (continued)

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
D3	-	25.500	-	-	1.0039	-
E	29.800	30.000	30.200	1.1732	1.1811	1.1890
E1	27.800	28.000	28.200	1.0945	1.1024	1.1102
E3	-	25.500	-	-	1.0039	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	3.5°	7.0°	0°	3.5°	7.0°
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

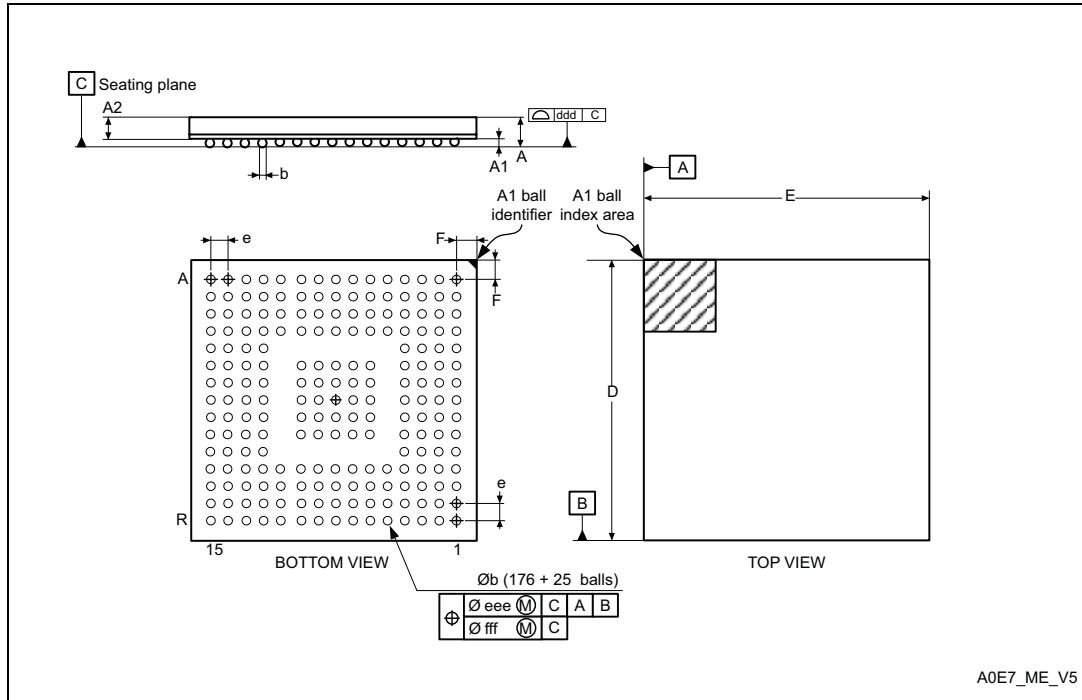
Figure 87. LQFP208 recommended footprint



MS30425V1

1. Dimensions are expressed in millimeters.

Figure 88. UFBGA176+25 - ultra thin fine pitch ball grid array 10 × 10 × 0.6 mm, package outline



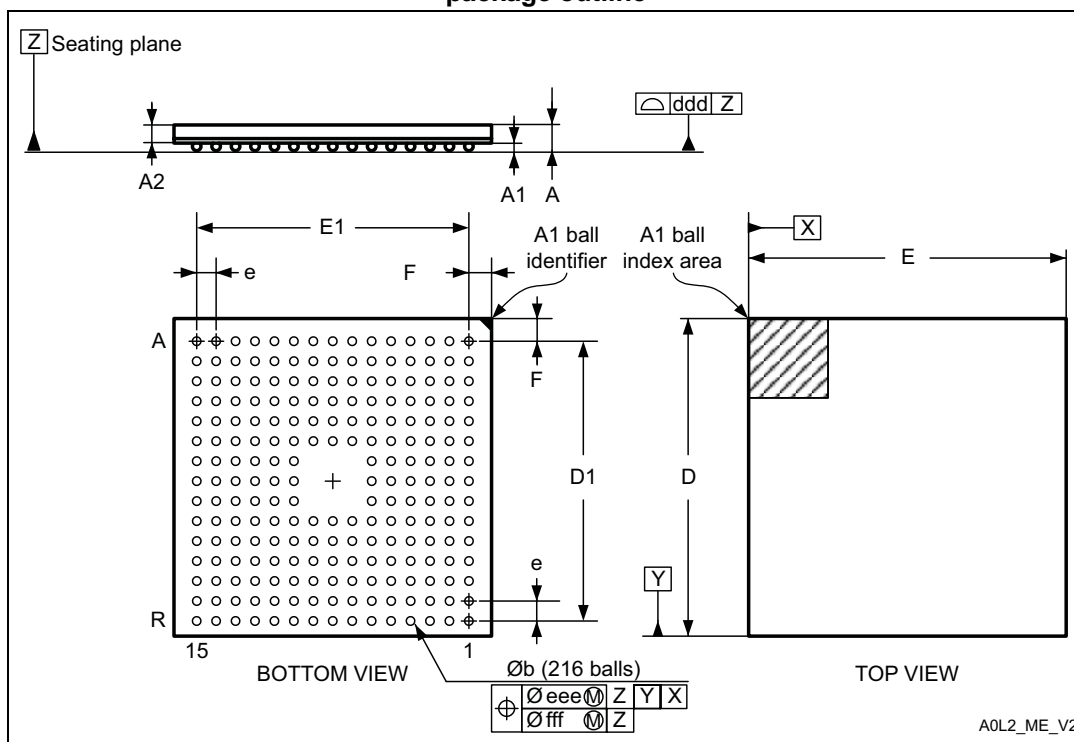
1. Drawing is not to scale.

Table 115. UFBGA176+25 - ultra thin fine pitch ball grid array 10 × 10 × 0.6 mm mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	0.460	0.530	0.600	0.0181	0.0209	0.0236
A1	0.050	0.080	0.110	0.002	0.0031	0.0043
A2	0.400	0.450	0.500	0.0157	0.0177	0.0197
b	0.230	0.280	0.330	0.0091	0.0110	0.0130
D	9.950	10.000	10.050	0.3917	0.3937	0.3957
E	9.950	10.000	10.050	0.3917	0.3937	0.3957
e	-	0.650	-	-	0.0256	-
F	0.400	0.450	0.500	0.0157	0.0177	0.0197
ddd	-	-	0.080	-	-	0.0031
eee	-	-	0.150	-	-	0.0059
fff	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 89. TFBGA216 - thin fine pitch ball grid array 13 × 13 × 0.8mm, package outline



1. Drawing is not to scale.

Table 116. TFBGA216 - thin fine pitch ball grid array 13 × 13 × 0.8mm package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.100	-	-	0.0433
A1	0.150	-	-	0.0059	-	-
A2	-	0.760	-	-	0.0299	-
A4	-	0.210	-	-	0.0083	-
b	0.350	0.400	0.450	0.0138	0.0157	0.0177
D	12.850	13.000	13.150	0.5118	0.5118	0.5177
D1	-	11.200	-	-	0.4409	-
E	12.850	13.000	13.150	0.5118	0.5118	0.5177
E1	-	11.200	-	-	0.4409	-
e	-	0.800	-	-	0.0315	-
F	-	0.900	-	-	0.0354	-
ddd	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

7.2 Thermal characteristics

The maximum chip-junction temperature, $T_J \text{ max}$, in degrees Celsius, may be calculated using the following equation:

$$T_J \text{ max} = T_A \text{ max} + (P_D \text{ max} \times \Theta_{JA})$$

Where:

- $T_A \text{ max}$ is the maximum ambient temperature in °C,
- Θ_{JA} is the package junction-to-ambient thermal resistance, in °C/W,
- $P_D \text{ max}$ is the sum of $P_{INT} \text{ max}$ and $P_{I/O} \text{ max}$ ($P_D \text{ max} = P_{INT} \text{ max} + P_{I/O} \text{ max}$),
- $P_{INT} \text{ max}$ is the product of I_{DD} and V_{DD} , expressed in Watts. This is the maximum chip internal power.

$P_{I/O} \text{ max}$ represents the maximum power dissipation on output pins where:

$$P_{I/O} \text{ max} = \Sigma (V_{OL} \times I_{OL}) + \Sigma ((V_{DD} - V_{OH}) \times I_{OH}),$$

taking into account the actual V_{OL} / I_{OL} and V_{OH} / I_{OH} of the I/Os at low and high level in the application.

Table 117. Package thermal characteristics

Symbol	Parameter	Value	Unit
Θ_{JA}	Thermal resistance junction-ambient LQFP100 - 14 × 14 mm / 0.5 mm pitch	43	°C/W
	Thermal resistance junction-ambient WLCSP143	31.2	
	Thermal resistance junction-ambient LQFP144 - 20 × 20 mm / 0.5 mm pitch	40	
	Thermal resistance junction-ambient LQFP176 - 24 × 24 mm / 0.5 mm pitch	38	
	Thermal resistance junction-ambient LQFP208 - 28 × 28 mm / 0.5 mm pitch	19	
	Thermal resistance junction-ambient UFBGA176 - 10× 10 mm / 0.5 mm pitch	39	
	Thermal resistance junction-ambient TFBGA216 - 13 × 13 mm / 0.8 mm pitch	29	

Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org.

8 Part numbering

Table 118. Ordering information scheme

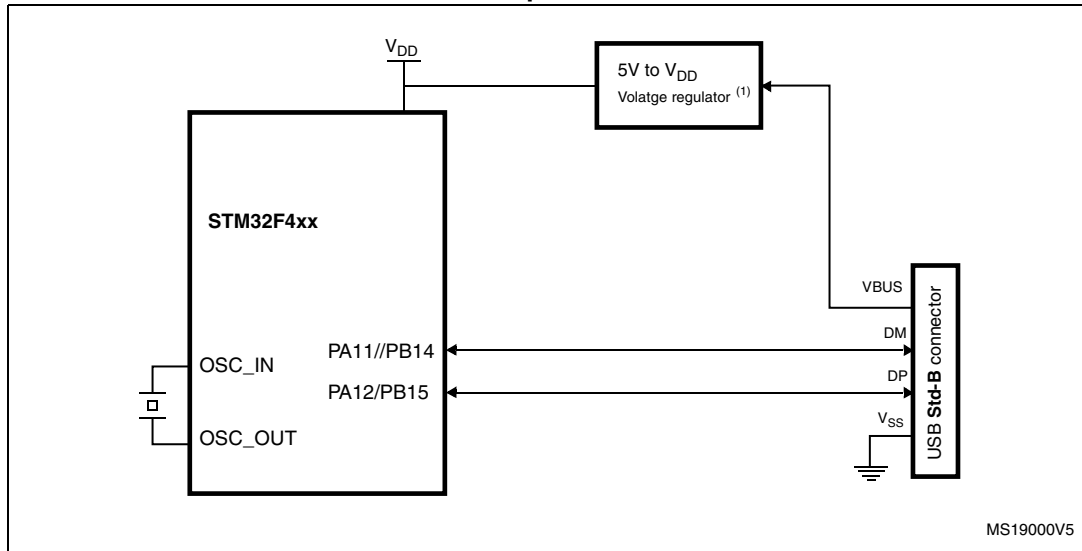
Example:	STM32	F	429	V	I	T	6	xxx
Device family								
STM32 = ARM-based 32-bit microcontroller								
Product type								
F = general-purpose								
Device subfamily								
427= STM32F427xx, USB OTG FS/HS, camera interface, Ethernet,								
429= STM32F429xx, USB OTG FS/HS, camera interface, Ethernet, LCD-TFT								
Pin count								
V = 100 pins								
Z = 144 pins								
I = 176 pins								
B = 208 pins								
N = 216 pins								
Flash memory size								
G = 1024 Kbytes of Flash memory								
I = 2048 Kbytes of Flash memory								
Package								
T = LQFP								
H = BGA								
Y = WLCSP								
Temperature range								
6 = Industrial temperature range, -40 to 85 °C.								
7 = Industrial temperature range, -40 to 105 °C.								
Options								
xxx = programmed parts								
TR = tape and reel								

For a list of available options (speed, package, etc.) or for further information on any aspect of this device, please contact your nearest ST sales office.

Appendix A Application block diagrams

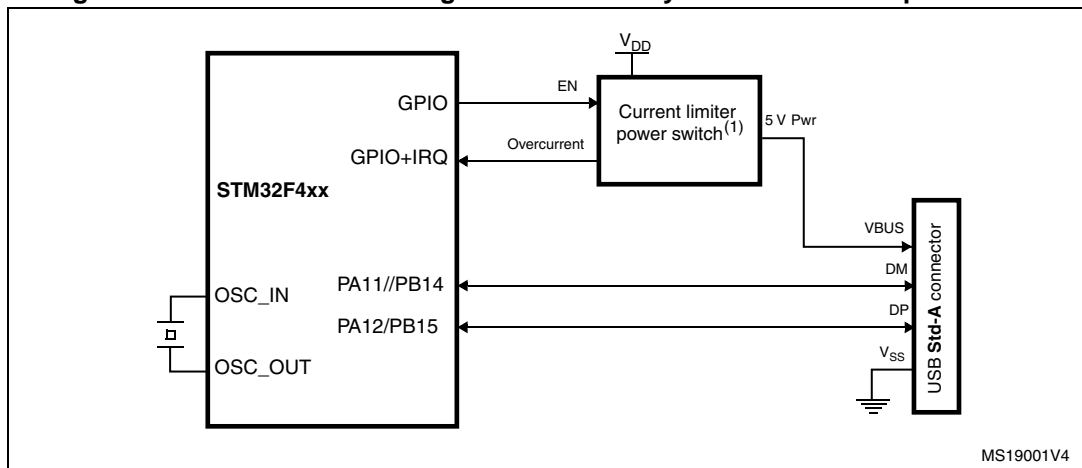
A.1 USB OTG full speed (FS) interface solutions

Figure 90. USB controller configured as peripheral-only and used in Full speed mode



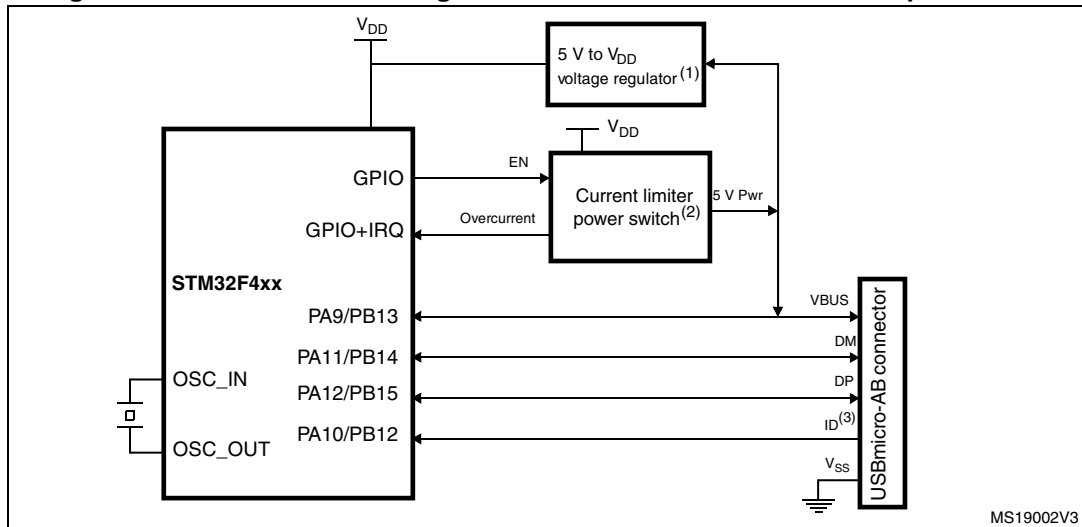
1. External voltage regulator only needed when building a V_{BUS} powered device.
2. The same application can be developed using the OTG HS in FS mode to achieve enhanced performance thanks to the large Rx/Tx FIFO and to a dedicated DMA controller.

Figure 91. USB controller configured as host-only and used in full speed mode



1. The current limiter is required only if the application has to support a V_{BUS} powered device. A basic power switch can be used if 5 V are available on the application board.
2. The same application can be developed using the OTG HS in FS mode to achieve enhanced performance thanks to the large Rx/Tx FIFO and to a dedicated DMA controller.

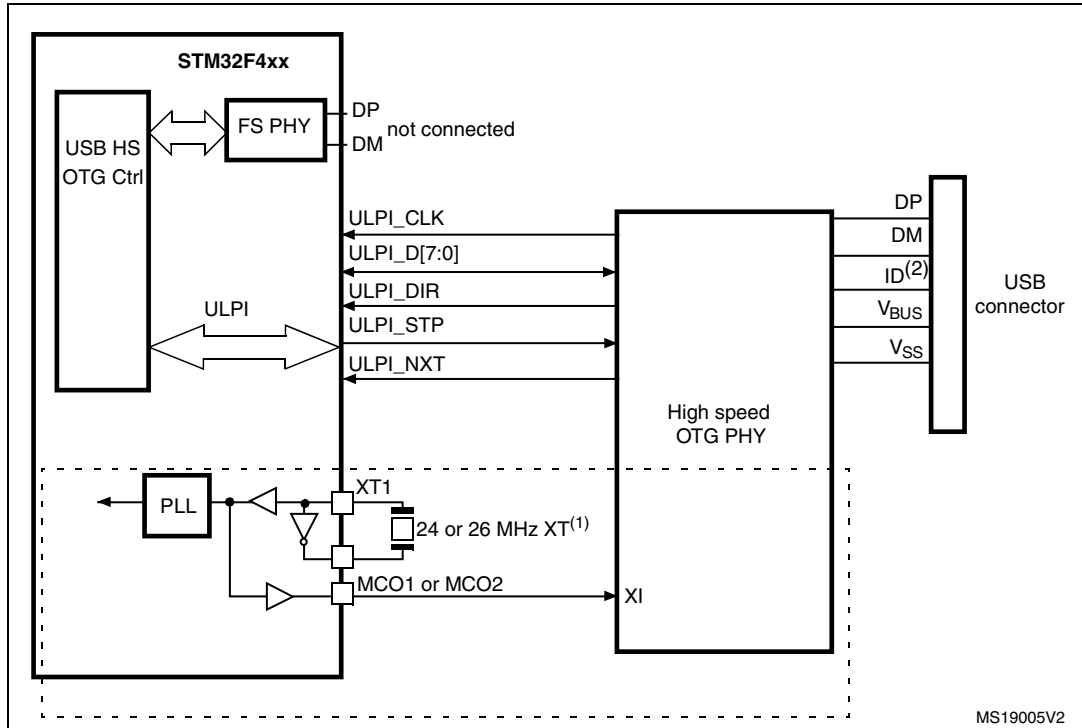
Figure 92. USB controller configured in dual mode and used in full speed mode



1. External voltage regulator only needed when building a V_{BUS} powered device.
2. The current limiter is required only if the application has to support a V_{BUS} powered device. A basic power switch can be used if 5 V are available on the application board.
3. The ID pin is required in dual role only.
4. The same application can be developed using the OTG HS in FS mode to achieve enhanced performance thanks to the large Rx/Tx FIFO and to a dedicated DMA controller.

A.2 USB OTG high speed (HS) interface solutions

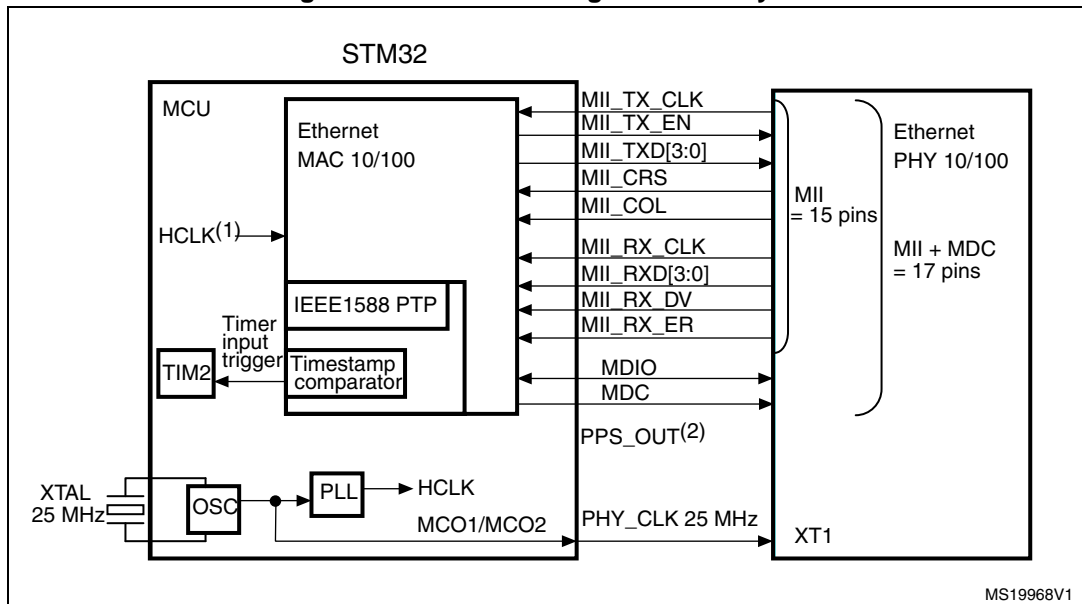
Figure 93. USB controller configured as peripheral, host, or dual-mode and used in high speed mode



1. It is possible to use MCO1 or MCO2 to save a crystal. It is however not mandatory to clock the STM32F42x with a 24 or 26 MHz crystal when using USB HS. The above figure only shows an example of a possible connection.
2. The ID pin is required in dual role only.

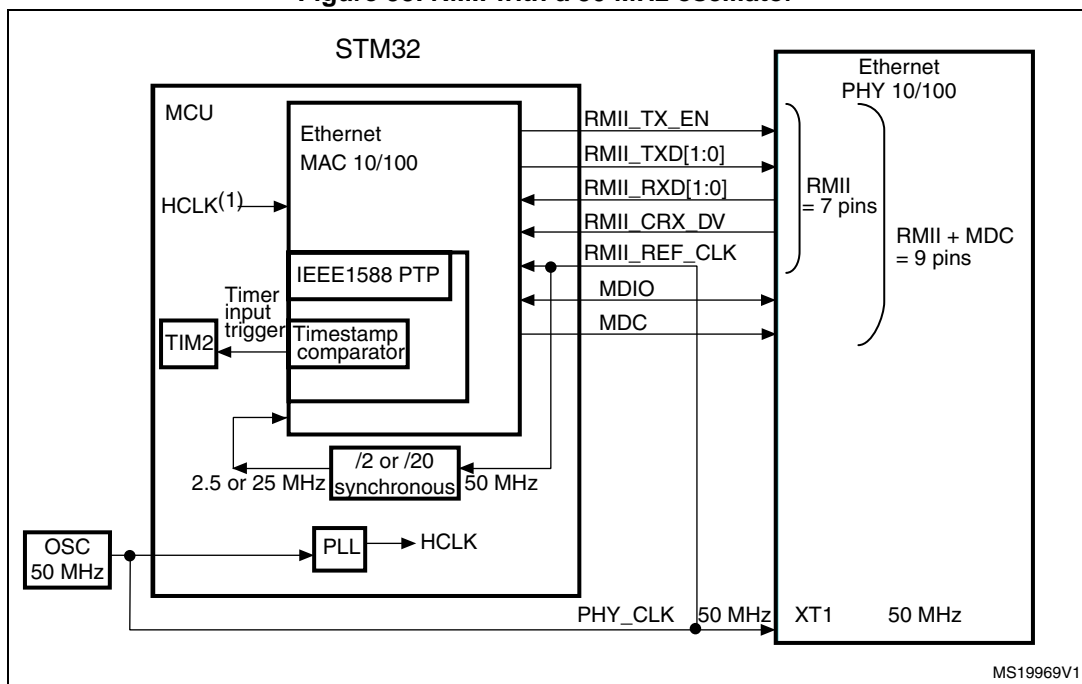
A.3 Ethernet interface solutions

Figure 94. MII mode using a 25 MHz crystal



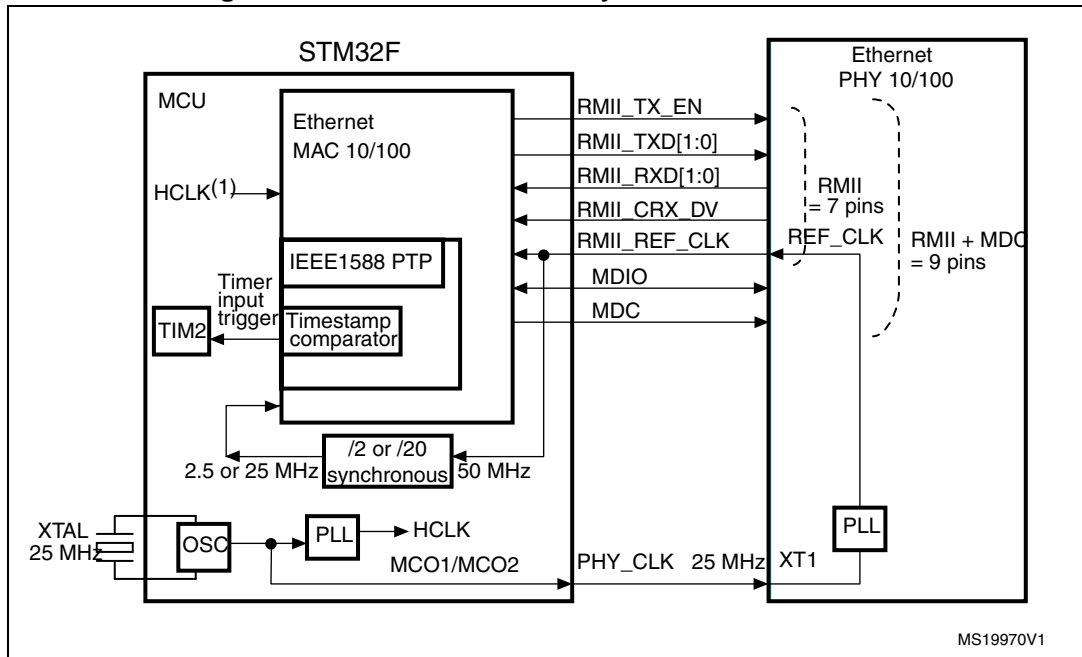
1. f_{HCLK} must be greater than 25 MHz.
2. Pulse per second when using IEEE1588 PTP optional signal.

Figure 95. RMI with a 50 MHz oscillator



1. f_{HCLK} must be greater than 25 MHz.

Figure 96. RMI with a 25 MHz crystal and PHY with PLL



1. f_{HCLK} must be greater than 25 MHz.
2. The 25 MHz (PHY_CLK) must be derived directly from the HSE oscillator, before the PLL block.

9 Revision history

Table 119. Document revision history

Date	Revision	Changes
19-Mar-2013	1	Initial release.
10-Sep-2013	2	<p>Added STM32F429xx part numbers and related informations. STM32F427xx part numbers: Replaced FSMC by FMC added Chrom-ART Accelerator and SAI interface. Increased core, timer, GPIOs, SPI maximum frequencies Updated Figure 4: STM32F427xx and STM32F429xx block diagram. Updated Figure 5: STM32F427xx and STM32F429xx Multi-AHB matrix. Removed note in Section : Standby mode. Updated Figure 14: STM32F42x LQFP176 pinout. Updated Table 10: STM32F427xx and STM32F429xx pin and ball definitions and Table 12: STM32F427xx and STM32F429xx alternate function mapping.. Modified Figure 18: Memory map. Updated Table 17: General operating conditions, Table 18: Limitations depending on the operating power supply range. Removed note 1 in Table 22: Embedded reset and power control block characteristics. Added Table 23: Over-drive switching characteristics. Updated Section : Typical and maximum current consumption, Table 34: Switching output I/O current consumption, Table 35: Peripheral current consumption and Section : On-chip peripheral current consumption. Updated Table 36: Low-power mode wakeup timings. Modified Section : High-speed external user clock generated from an external source, Section : Low-speed external user clock generated from an external source, and Section 6.3.10: Internal clock source characteristics. Updated Table 43: Main PLL characteristics and Table 45: PLLISAI (audio and LCD-TFT PLL) characteristics. Updated Table 52: EMI characteristics. Updated Table 57: Output voltage characteristics and Table 58: I/O AC characteristics. Updated Table 60: TIMx characteristics, Table 61: I2C characteristics, Table 63: SPI dynamic characteristics, Section : SAI characteristics. Updated Table 104: SDRAM read timings and Table 105: SDRAM write timings.</p>

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